



US009461065B1

(12) **United States Patent**
Haigh

(10) **Patent No.:** **US 9,461,065 B1**
(45) **Date of Patent:** **Oct. 4, 2016**

(54) **STANDARD CELL LIBRARY WITH
DFM-OPTIMIZED M0 CUTS AND V0
ADJACENCIES**

(71) Applicant: **PDF Solutions, Inc.**, San Jose, CA
(US)

(72) Inventor: **Jonathan Haigh**, Pittsburgh, PA (US)

(73) Assignee: **PDF Solutions, Inc.**, San Jose, CA
(US)

(*) Notice: Subject to any disclaimer, the term of this
patent is extended or adjusted under 35
U.S.C. 154(b) by 0 days.

(21) Appl. No.: **15/131,020**

(22) Filed: **Apr. 17, 2016**

Related U.S. Application Data

(63) Continuation-in-part of application No. 15/067,252,
filed on Mar. 11, 2016.

(51) **Int. Cl.**
H01L 27/118 (2006.01)
G06F 17/50 (2006.01)
H01L 23/528 (2006.01)
H01L 27/02 (2006.01)
H01L 23/522 (2006.01)

(52) **U.S. Cl.**
CPC **H01L 27/11807** (2013.01); **G06F 17/5068**
(2013.01); **H01L 23/528** (2013.01); **H01L**
23/5226 (2013.01); **H01L 27/0207** (2013.01);
H01L 2027/11837 (2013.01); **H01L**
2027/11883 (2013.01)

(58) **Field of Classification Search**
CPC G06F 17/5068; H01L 23/528; H01L
23/5226; H01L 27/0207; H01L 2027/11883;
H01L 2027/11837; H01L 27/11807
See application file for complete search history.

(56) **References Cited**

U.S. PATENT DOCUMENTS

7,487,474 B2 * 2/2009 Ciplickas G06F 17/5045
716/112
7,919,792 B2 * 4/2011 Law H01L 27/0207
257/202
8,726,217 B2 * 5/2014 Gullette G06F 17/5081
716/126
9,202,820 B1 * 12/2015 Haigh H01L 27/11807
2016/0111421 A1 * 4/2016 Rodder H01L 27/0886
257/401

OTHER PUBLICATIONS

V. Timoshkov, et al., "Imaging challenges in 20nm and 14nm logic
nodes: hot spots performance in Metal1 layer," 29th European Mask
and Lithography Conference, Jun. 30, 2013.
P. Mishra, et al., "FinFET Circuit Design," Springer
Science+Business Media, LLC, 2011.
A. B. Kahng, "Lithography-Induced Limits to Scaling of Design
Quality," Proc. SPIE 9053, Design-Process-Technology Co-optimi-
zation for Manufacturability VIII, Mar. 28, 2014.
C. Piguet, "Microelectronics for Systems on Chips," Lecture notes
for Chapter 1, Part 1, 2014.
C. Piguet, "Microelectronics for Systems on Chips," Lecture notes
for Chapter 1, Part 2, 2014.
C. Piguet, "Microelectronics for Systems on Chips," Lecture notes
for Chapter 2, Part 1, 2014.
C. Piguet, "Microelectronics for Systems on Chips," Lecture notes
for Chapter 2, Part 2, 2014.
J. Baker, "CMOS: circuit design, layout, and simulation (3rd ed.),"
John Wiley & Sons, 2010.

(Continued)

Primary Examiner — Naum B Levin

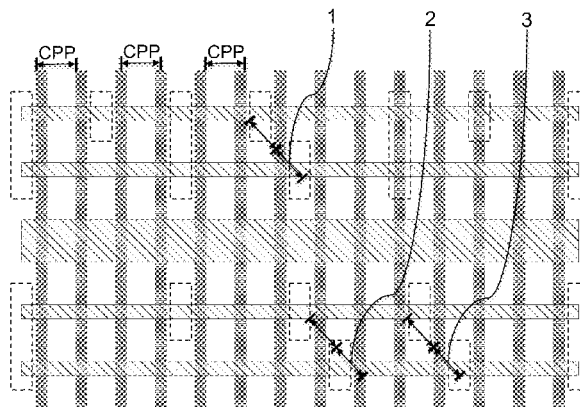
(74) *Attorney, Agent, or Firm* — David Garrod

(57) **ABSTRACT**

A library of a DFM-improved standard logic cells that avoid
pattern-degrading configurations in the M0 and/or V0
layer(s) is disclosed, along with wafers, chips and systems
constructed from such cells.

25 Claims, 372 Drawing Sheets

sdffqx1_alt



(56)

References Cited

OTHER PUBLICATIONS

J. Wright, "Standard Cell Libraries for use in Mixed Signal Circuits," EE Times, Nov. 7, 2000.
 E. N. Shauly, "CMOS Leakage and Power Reduction in Transistors and Circuits: Process and Layout Considerations," Journal of Low Power Electronics and Applications, Jan. 27, 2012.
 K. Vaidyanathan, et al., "Design implications of extremely restricted patterning," Journal of Micro/Nanolithography, MEMS, and MOEMS, Oct. 3, 2014.
 R. Aitken, "Physical design and FinFETs," Keynote address, Proceedings of the 2014 on International symposium on physical design, Mar. 30, 2014.
 T.-J. K. Liu, "Bulk CMOS Scaling to the End of the Roadmap," Symposium on VLSI Circuits Short Course, Jun. 13, 2012.
 A. J. Al-Khalili, "ASIC Design," Lecture notes from Concordia University course, date unknown.
 J. Warnock, "Circuit and PD Challenges at the 14nm Technology Node," Advanced Technologies and Design for Manufacturability, ISPD 2013, Mar. 24, 2013.
 J. Sulistyo, "Development of CMOS Standard Cell Library," VTVT Group, Virginia Information Systems Center, Oct. 31, 2014.

No author, no title, slides from Concordia VLSI Design Lab, pp. 1-90, date unknown.
 A. Biddle, "Design Solutions for 20nm and Beyond," White Paper, Synopsys, pp. 1-10, Jun. 2012.
 P. De Bisschop, et al., "Joint-Optimization of Layout and Litho for SRAM and Logic towards the 20 nm node, using 193i," Proc. SPIE 7973, Optical Microlithography, Mar. 23, 2011.
 B. Yu, "Design for Manufacturability: From Ad Hoc Solution to Extreme Regular Design," VLSI Circuits and Systems Letter, Oct. 18, 2015.
 R. S. Ghaida, et al., "Single-Mask Double-Patterning Lithography for Reduced Cost and Improved Overlay Control," IEEE Transactions on Semiconductor Manufacturing, pp. 93-103, Feb. 2011.
 A. B. Kahng, "Futures at the IC Design-Manufacturing Interface," UCSD VLSI CAD Laboratory, date unknown.
 Guc, "The Challenge and Experience Sharing on 16nm Chip Implementation," 2014.
 M. Smayling, "Gridded Design Rules: 1-D Approach Enables Scaling of CMOS Logic," Nanochip Technology Journal, pp. 33-37, 2008.
 M. P. Sole, "Layout Regularity for Design and Manufacturability," Ph.D. Thesis, Universitat Politecnica de Catalunya, Jul. 8, 2012.

* cited by examiner

sdffqx1_alt

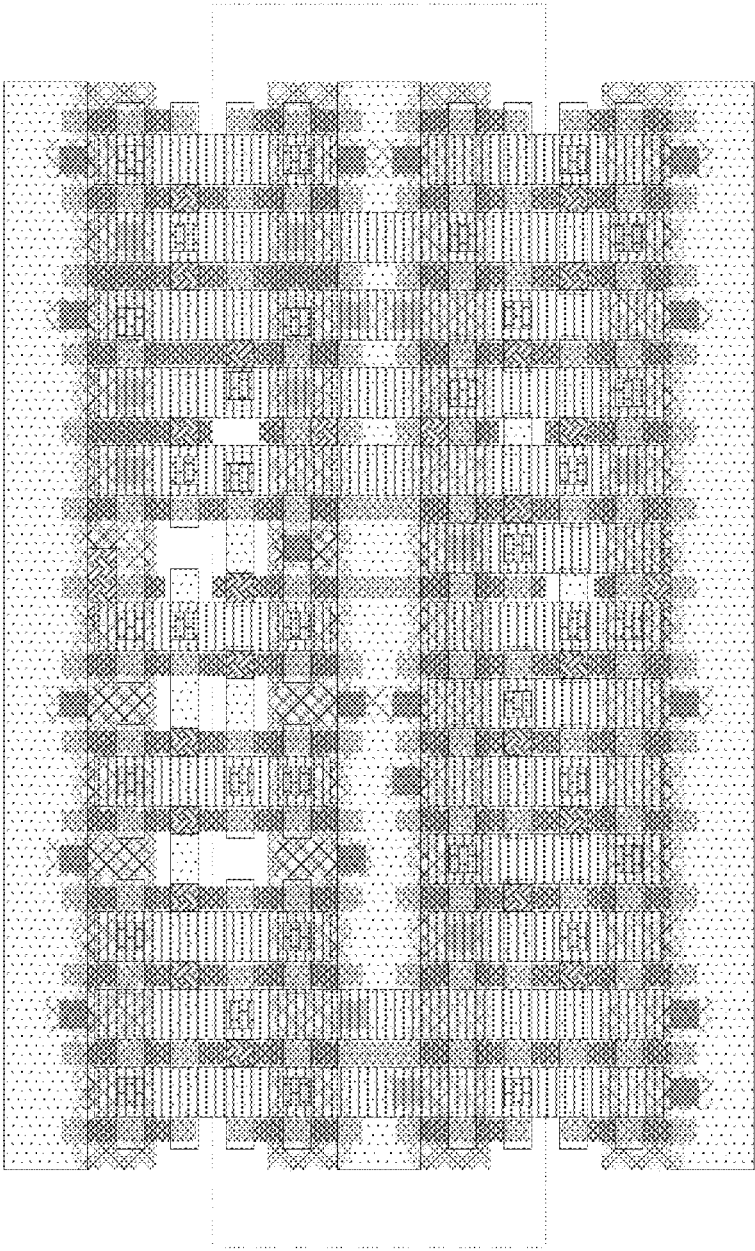


FIG. 1A

sdffqx1_alt

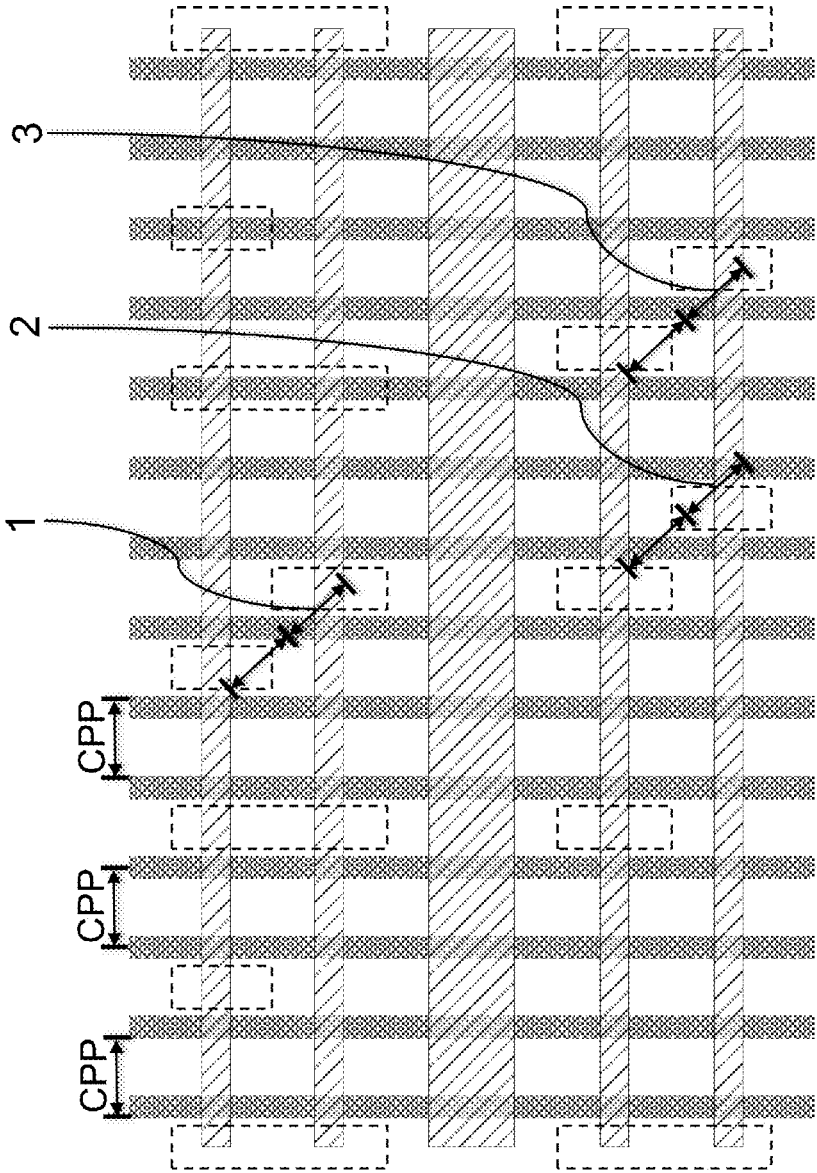


FIG. 1B

sdffqx1_alt

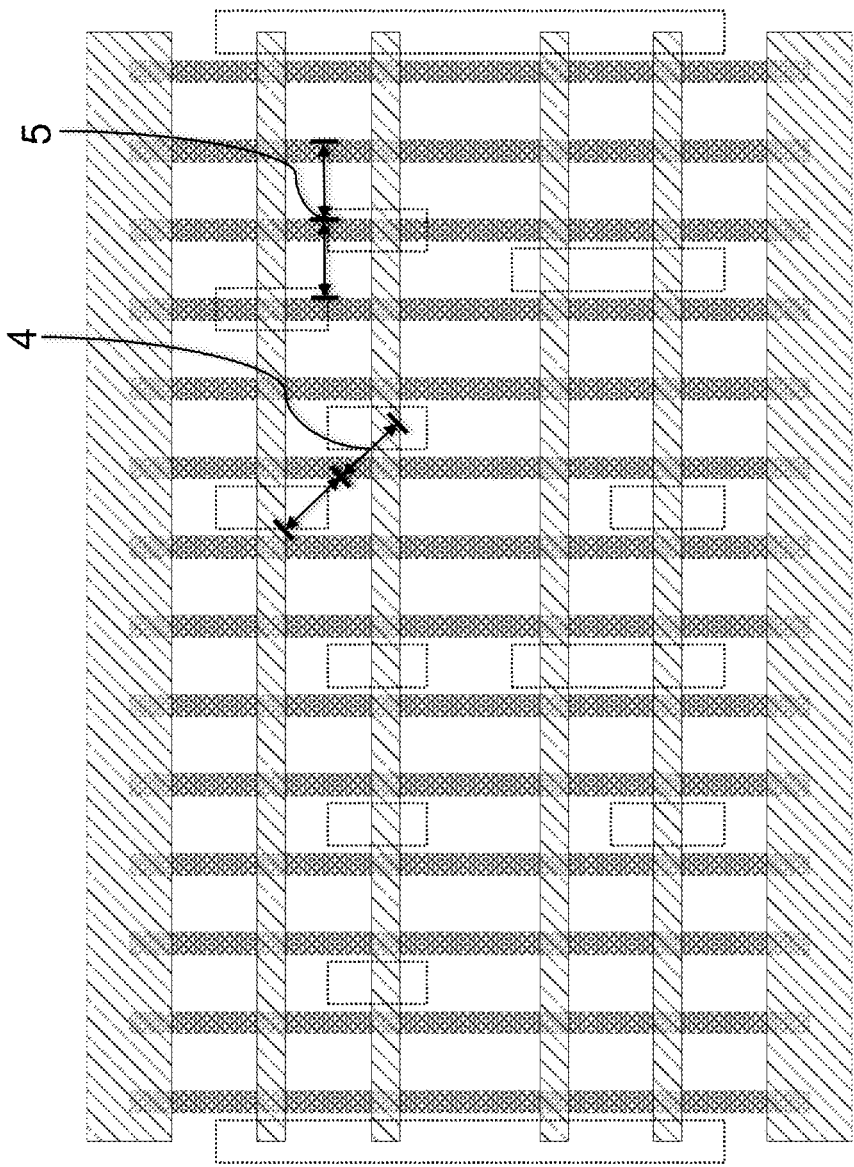


FIG. 1C

sdffqx1_alt

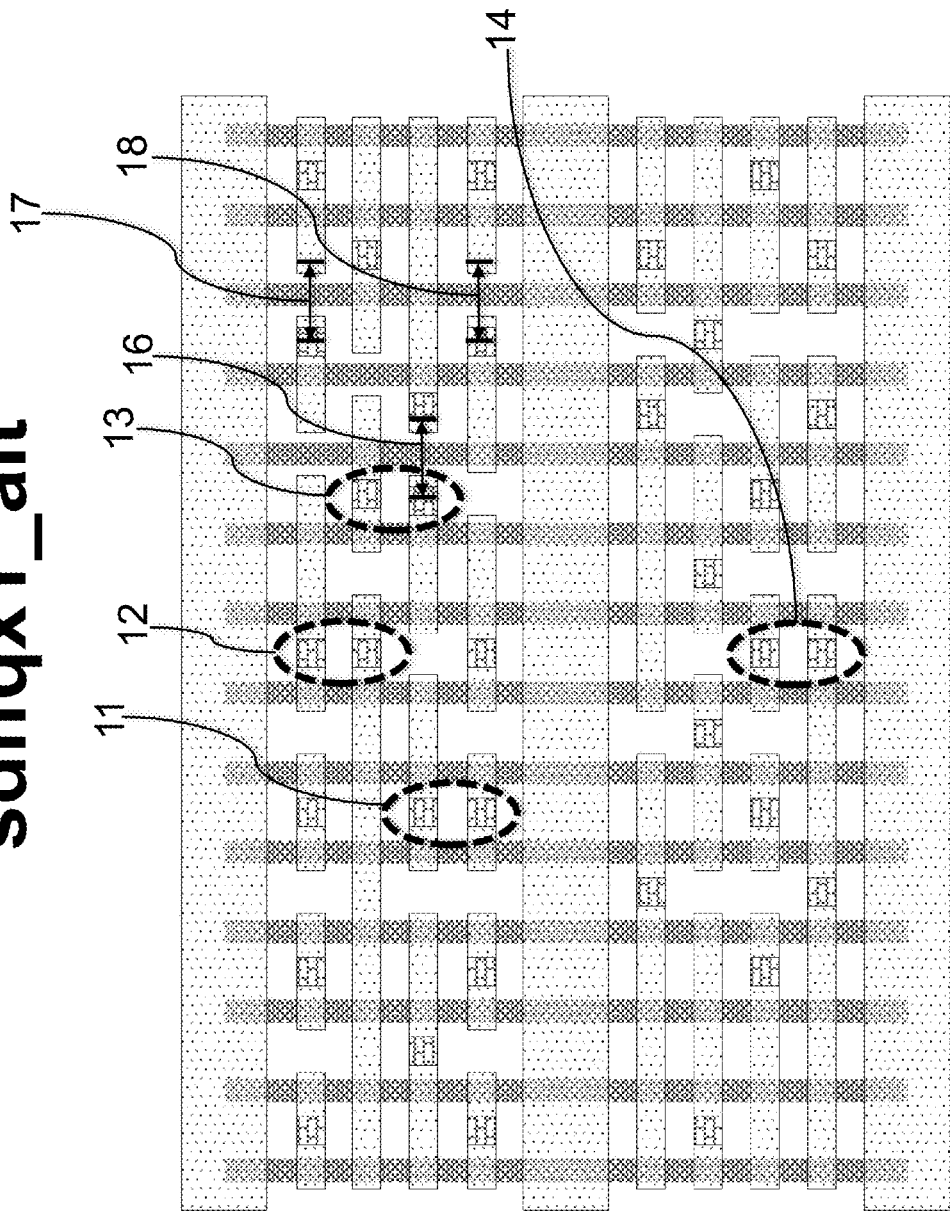


FIG. 1D

mux2x1_alt

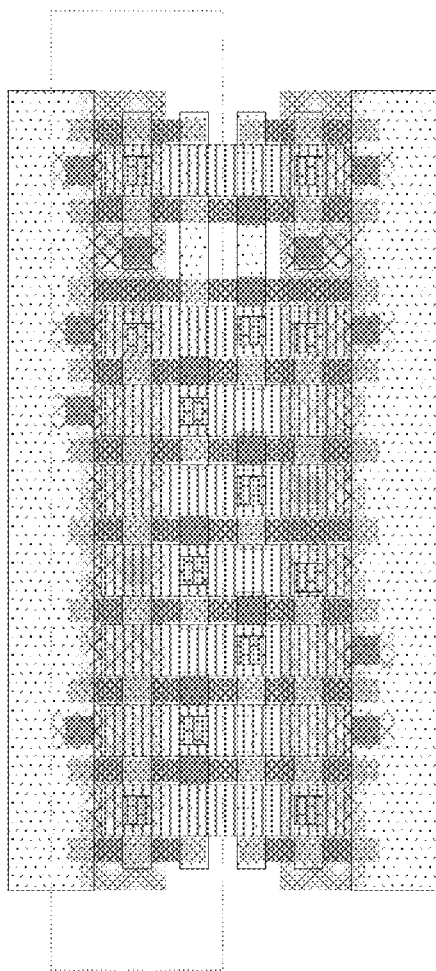


FIG. 2A

mux2x1_alt

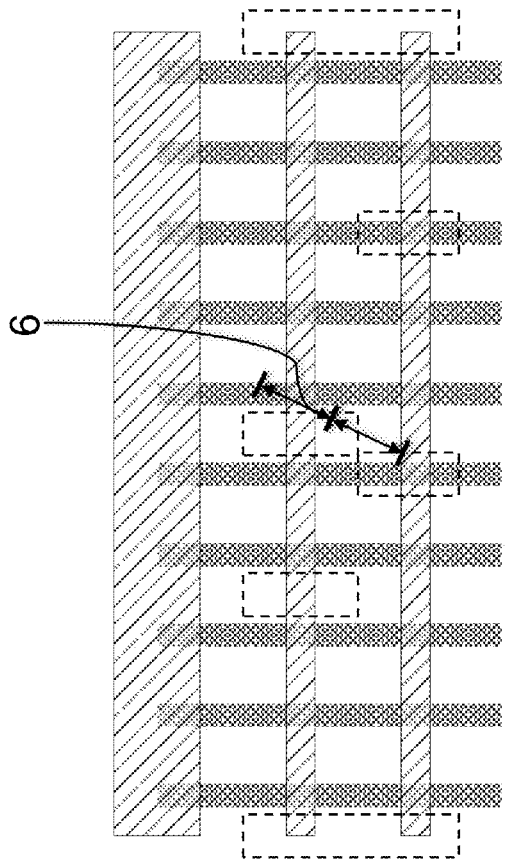


FIG. 2B

mux2x1_alt

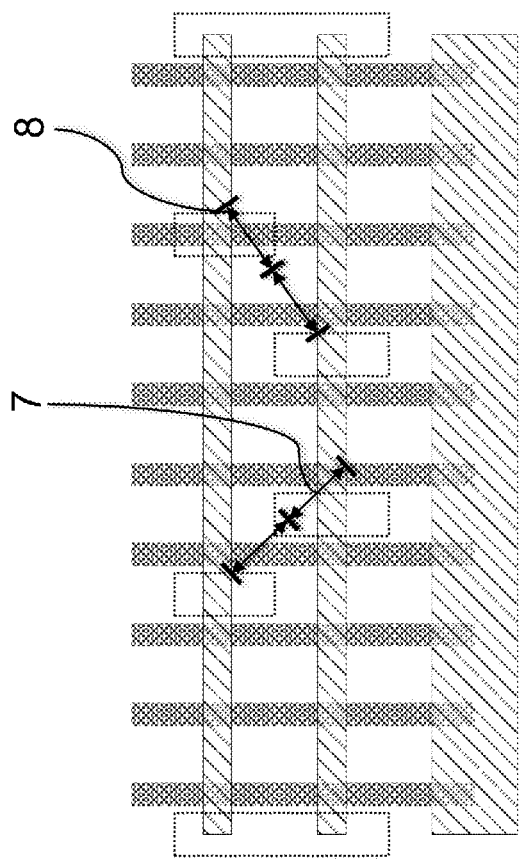


FIG. 2C

mux2x1_alt

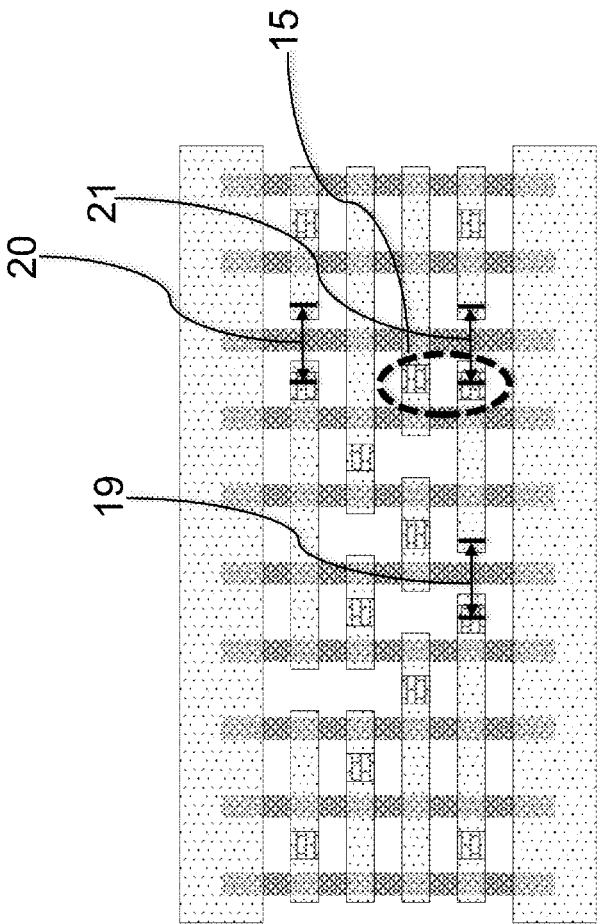


FIG. 2D

an2x1

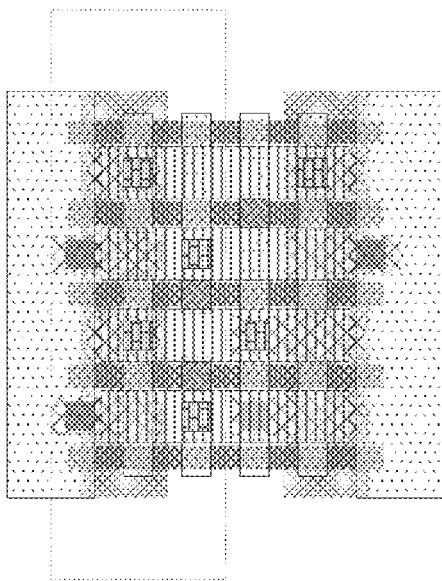


FIG. 3A

an2x1

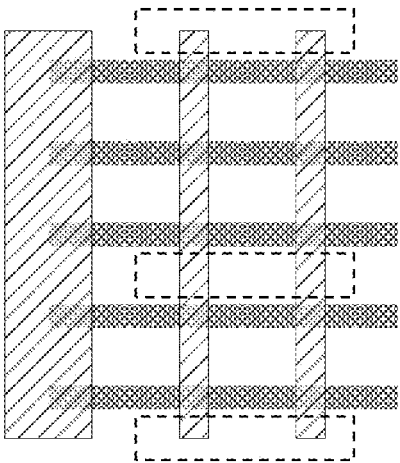


FIG. 3B

an2x1

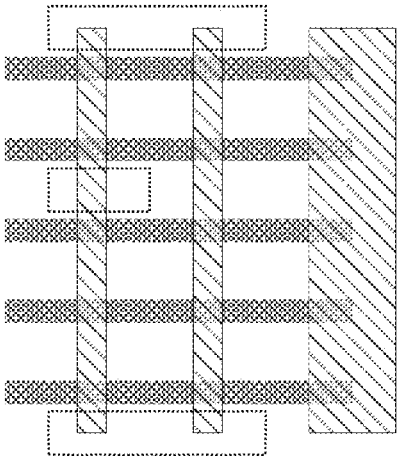


FIG. 3C

an2x1

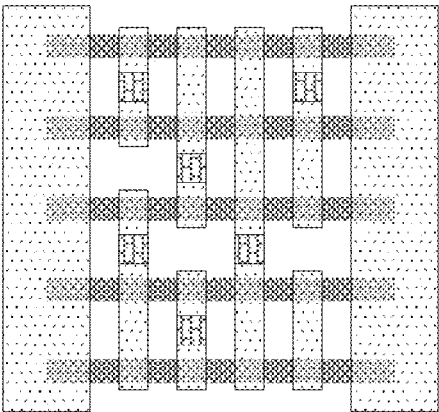


FIG. 3D

an2x2

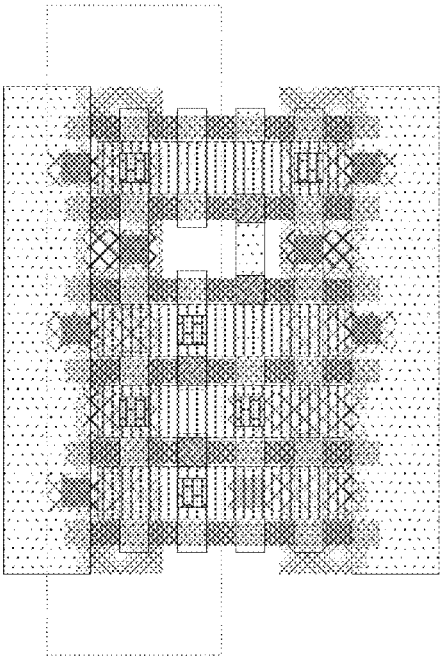


FIG. 4A

an2x2

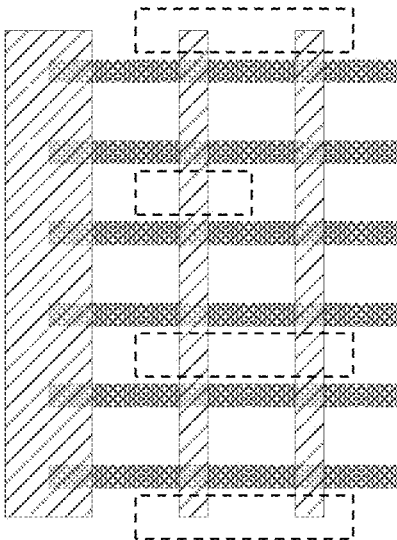


FIG. 4B

an2x2

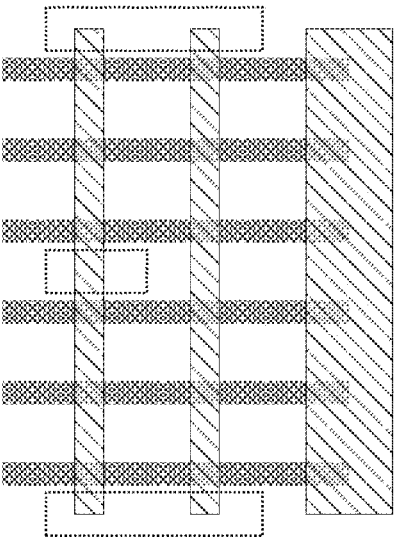


FIG. 4C

an2x2

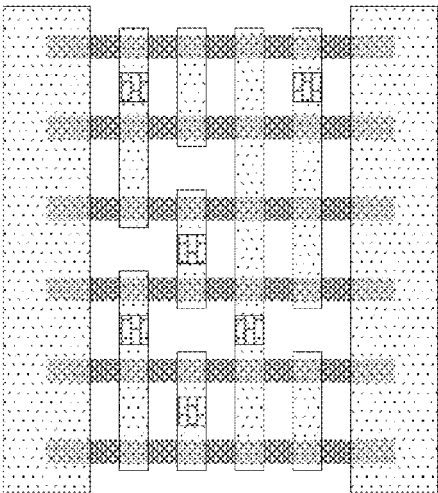


FIG. 4D

an3x1

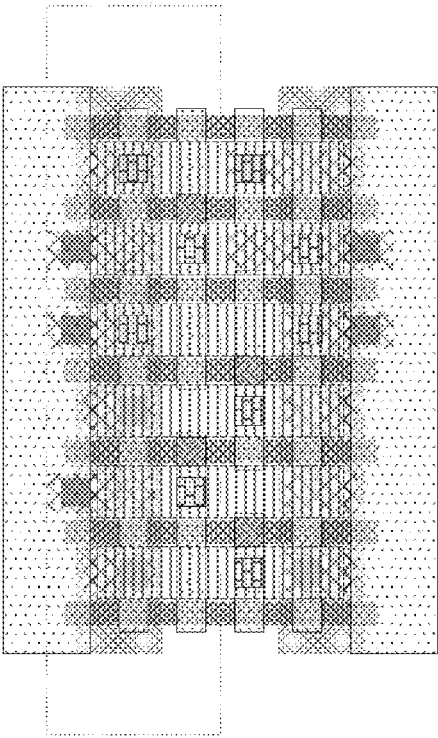


FIG. 5A

an3x1

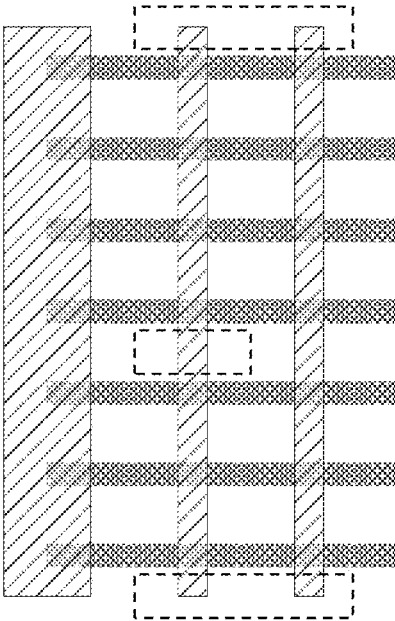


FIG. 5B

an3x1

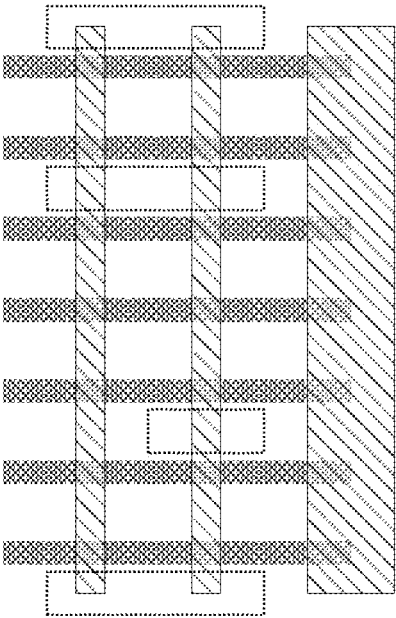


FIG. 5C

an3x1

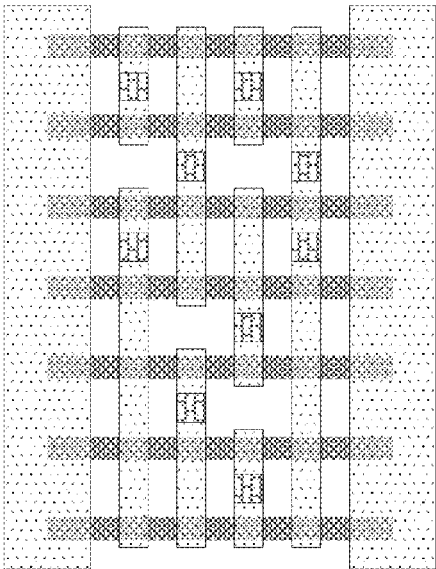


FIG. 5D

an3x2

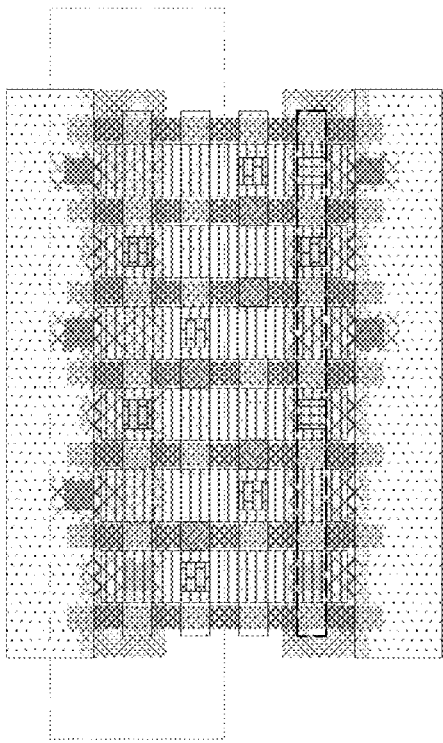


FIG. 6A

an3x2

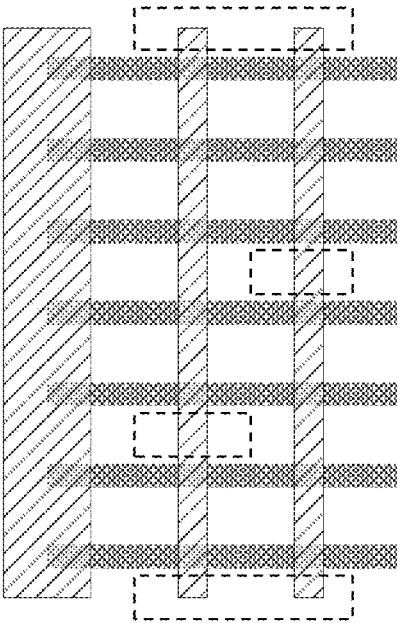


FIG. 6B

an3x2

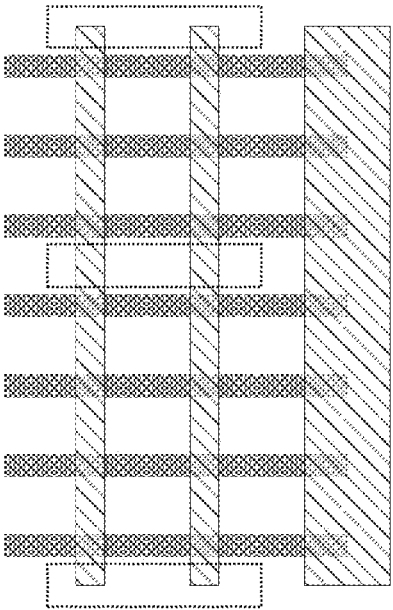


FIG. 6C

an3x2

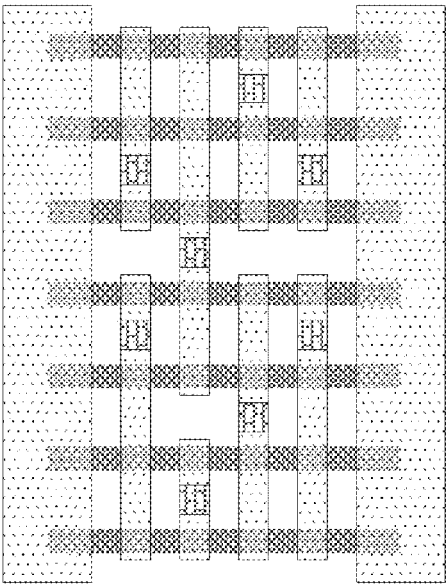


FIG. 6D

an4x1

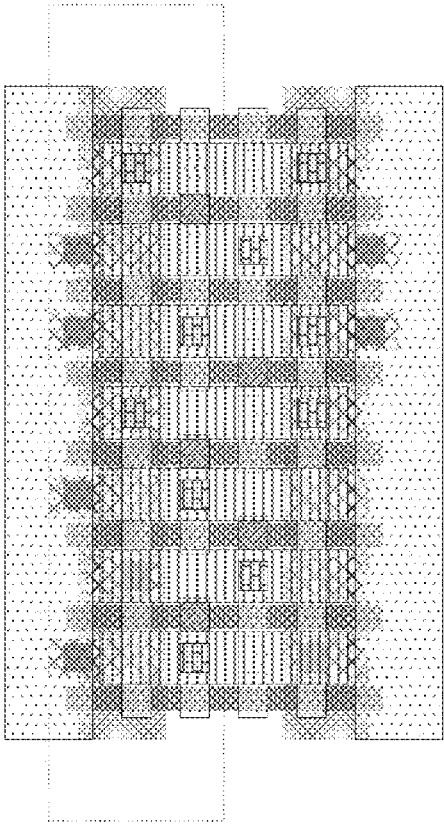


FIG. 7A

an4x1

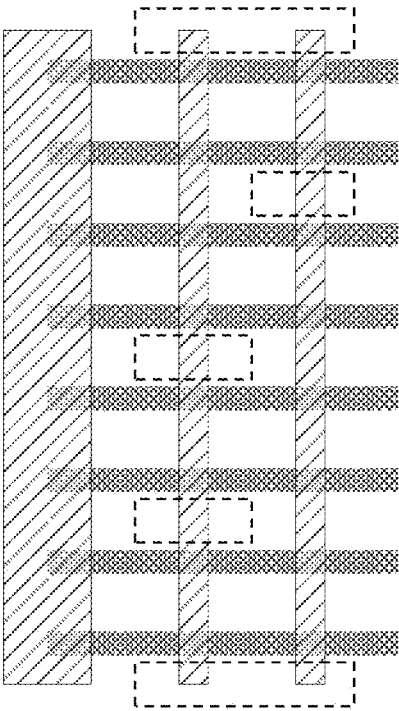


FIG. 7B

an4x1

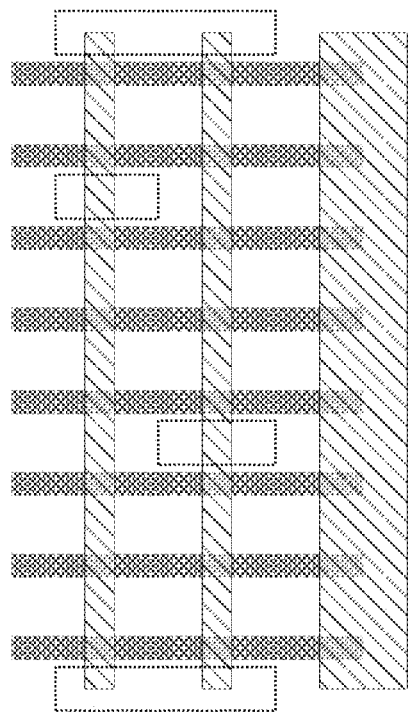


FIG. 7C

an4x1

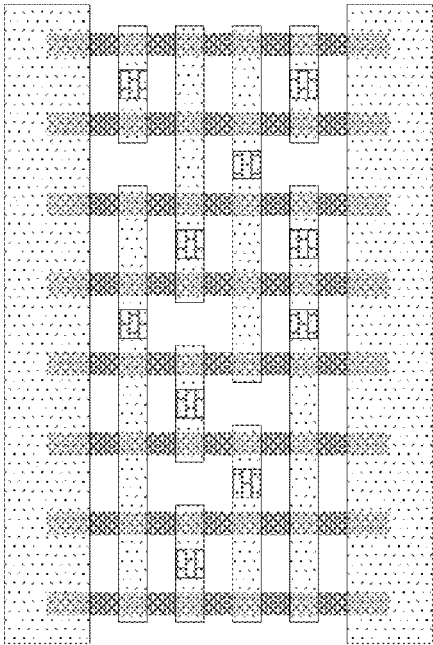


FIG. 7D

an4x2

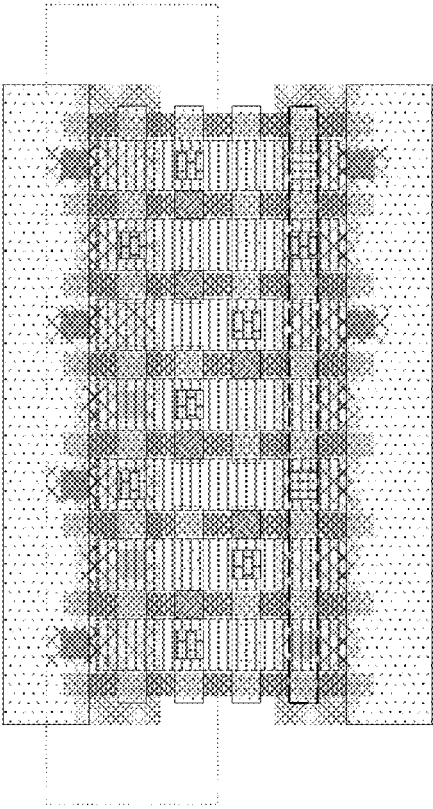


FIG. 8A

an4x2

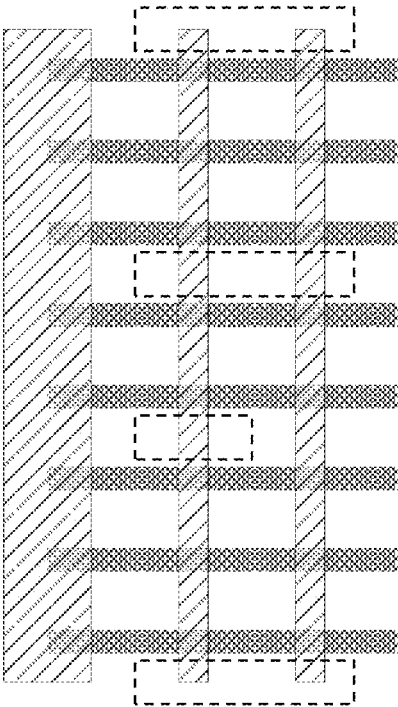


FIG. 8B

an4x2

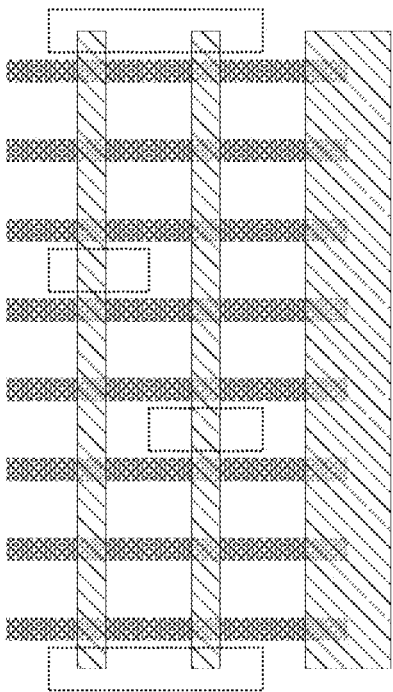


FIG. 8C

an4x2

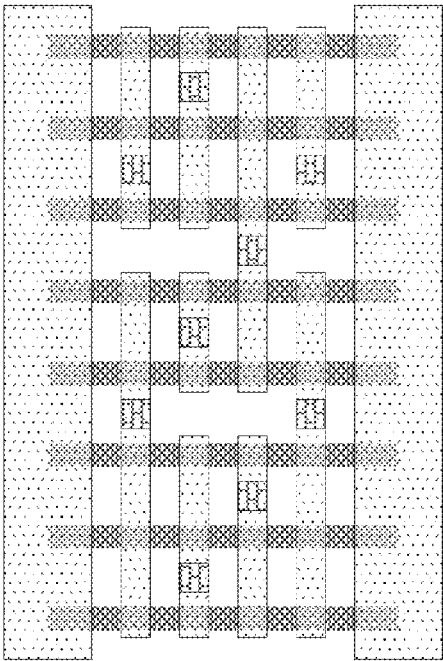


FIG. 8D

ao21x1

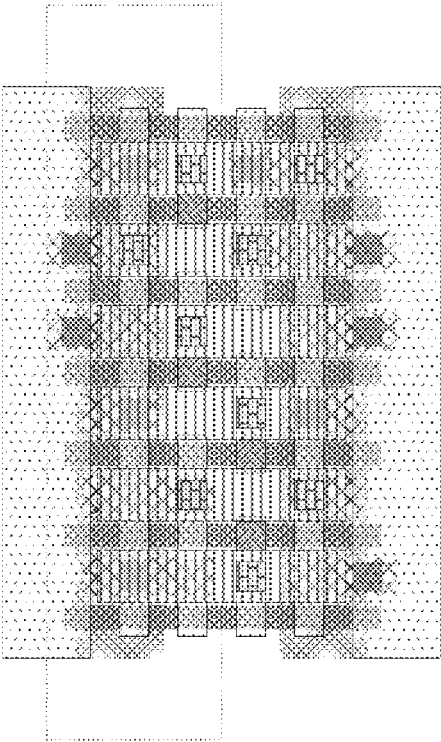


FIG. 9A

ao21x1

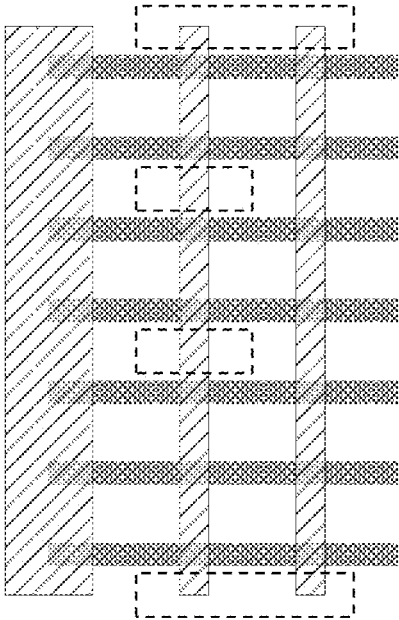


FIG. 9B

ao21x1

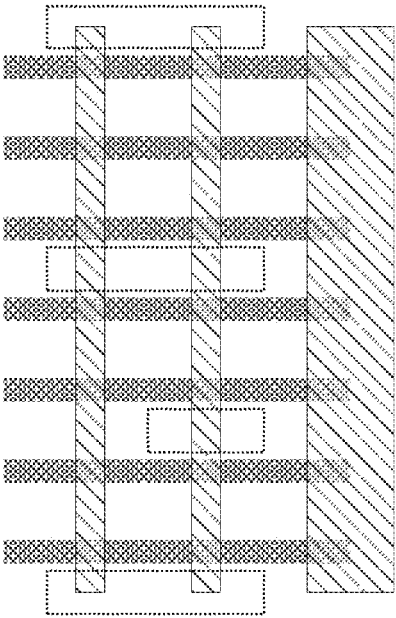


FIG. 9C

ao21x1

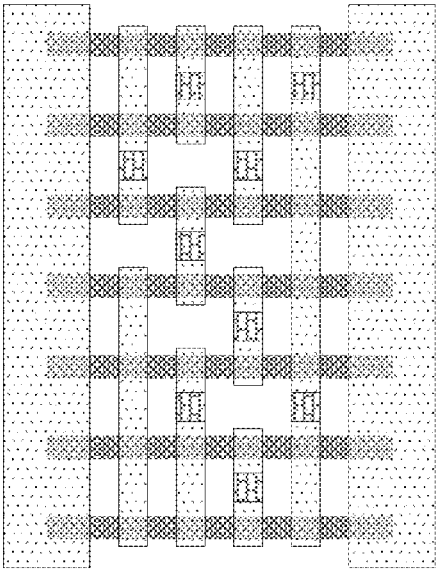


FIG. 9D

ao31x1

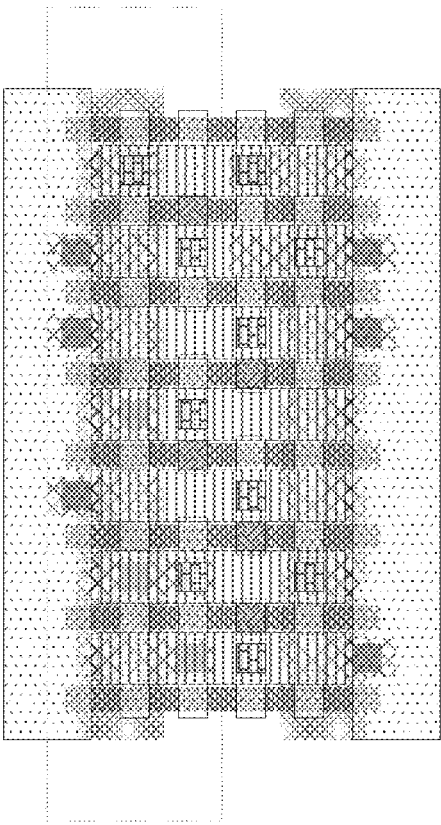


FIG. 10A

ao31x1

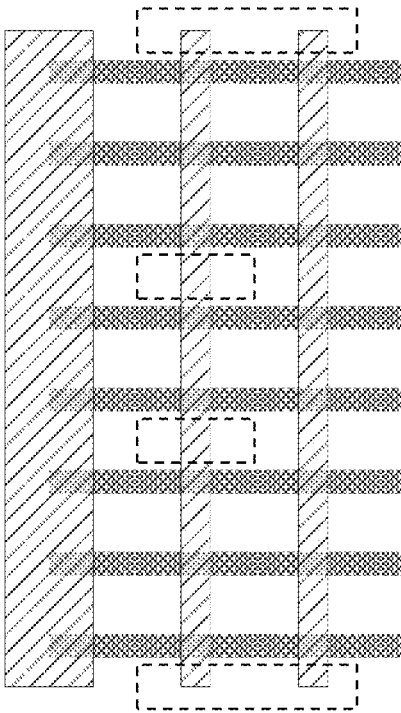


FIG. 10B

ao31x1

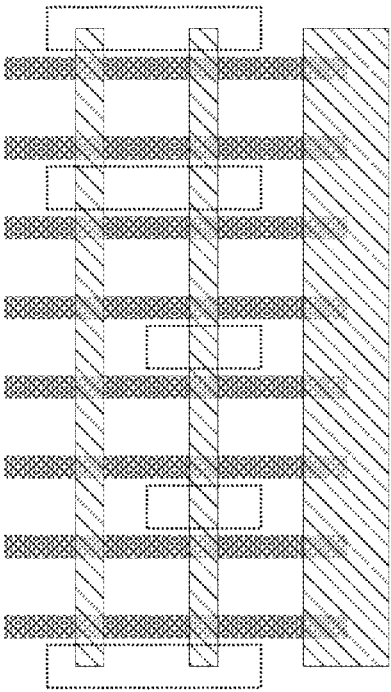


FIG. 10C

ao31x1

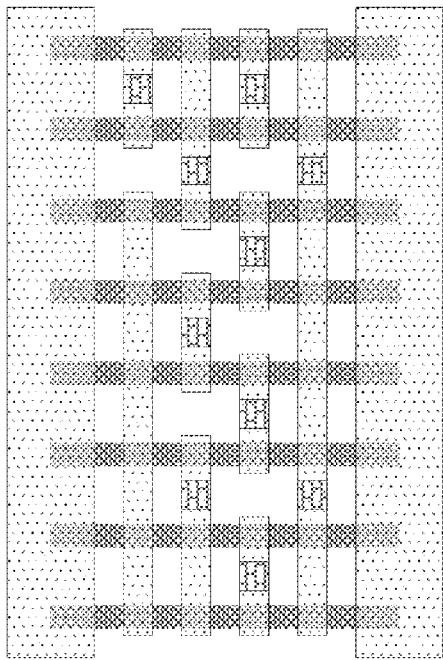


FIG. 10D

ao211x1

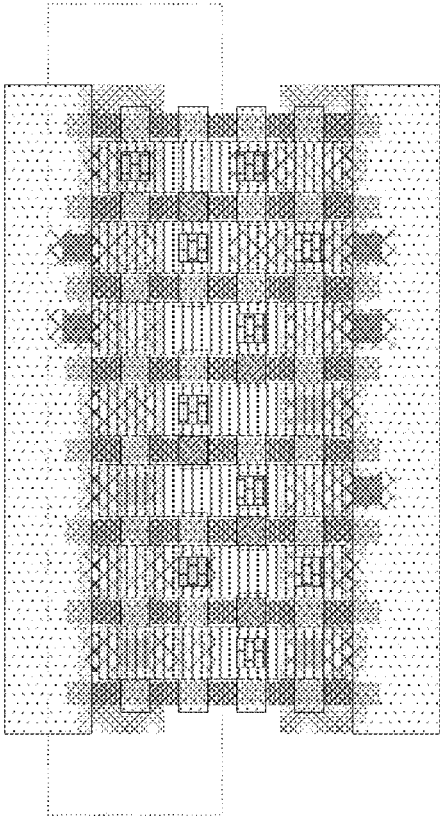


FIG. 11A

ao211x1

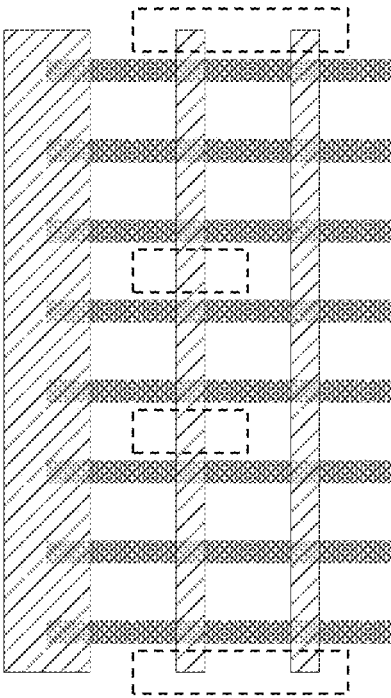


FIG. 11B

ao211x1

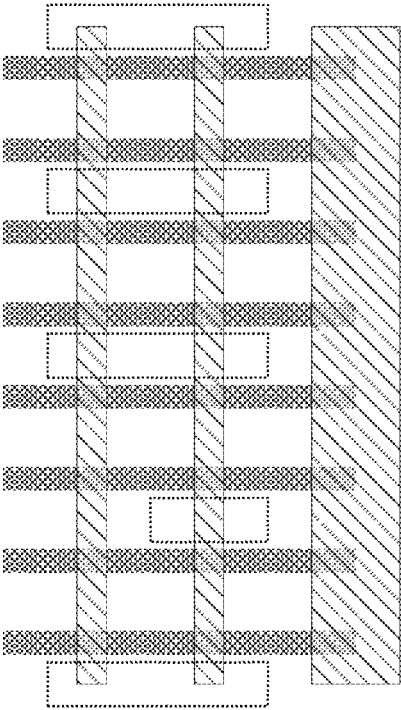


FIG. 11C

ao211x1

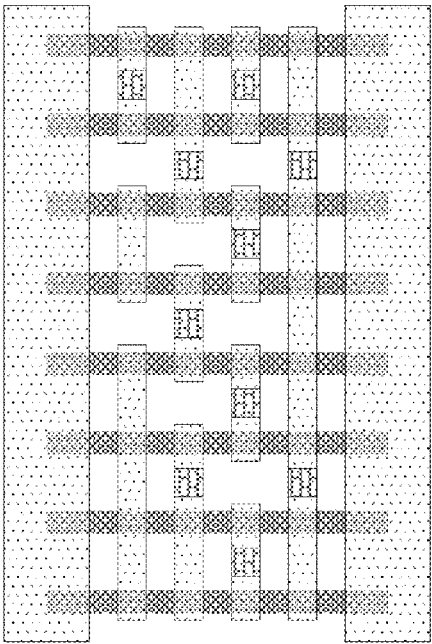


FIG. 11D

aoi21x1

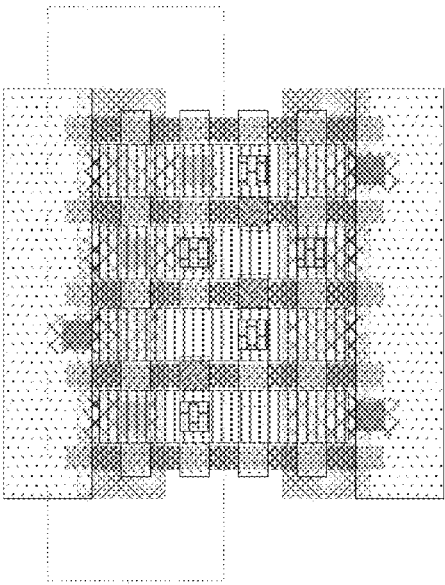


FIG. 12A

aoi21x1

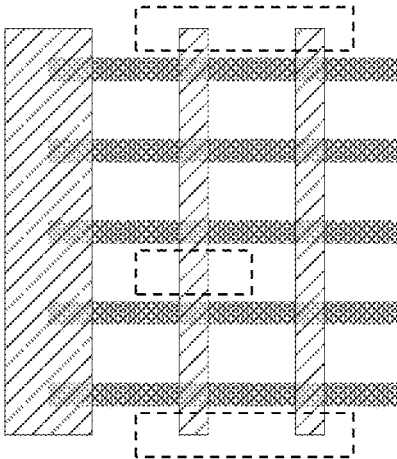


FIG. 12B

aoi21x1

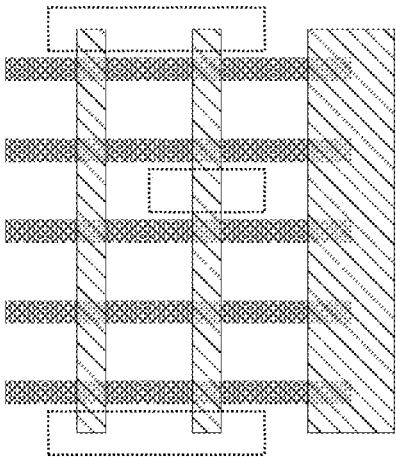


FIG. 12C

aoi21x1

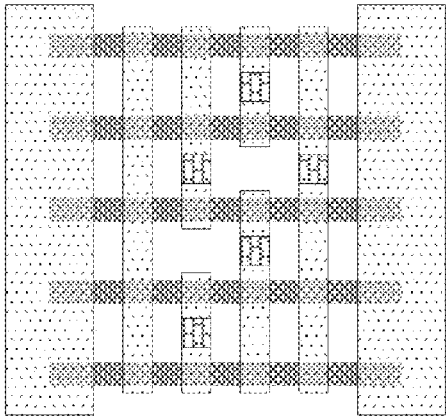


FIG. 12D

aoi21x2

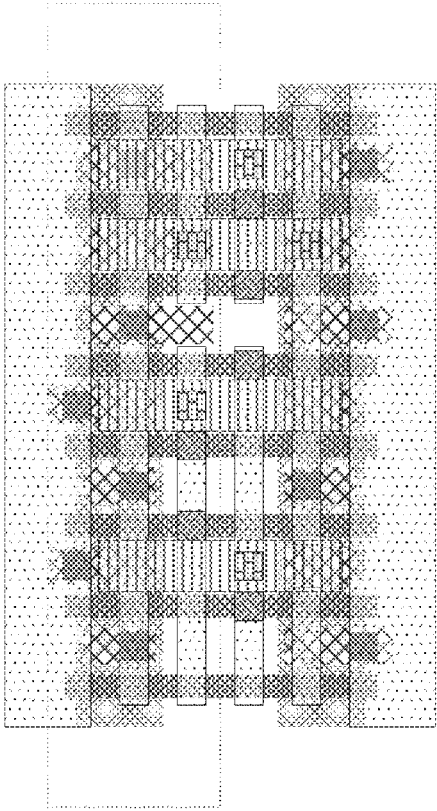


FIG. 13A

aoi21x2

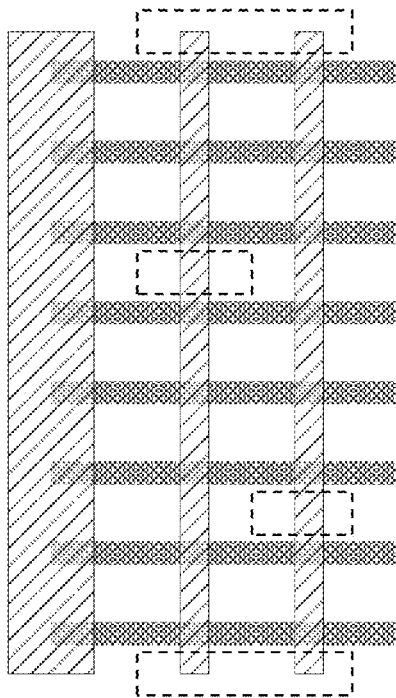


FIG. 13B

aoi21x2

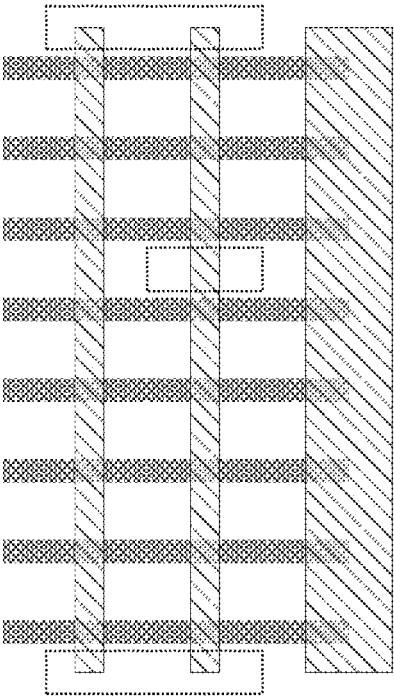


FIG. 13C

aoi21x2

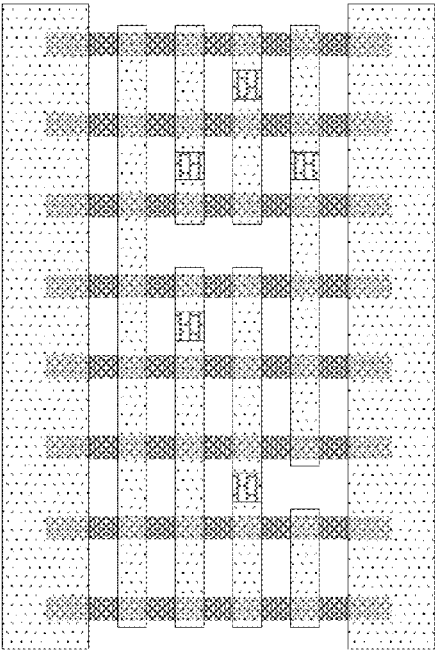


FIG. 13D

aoi22x1

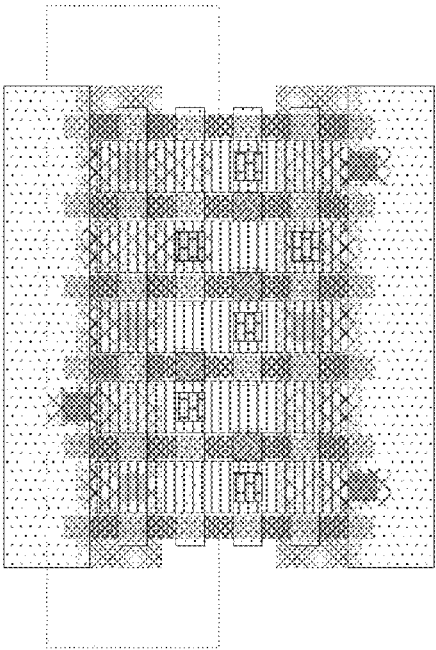


FIG. 14A

aoi22x1

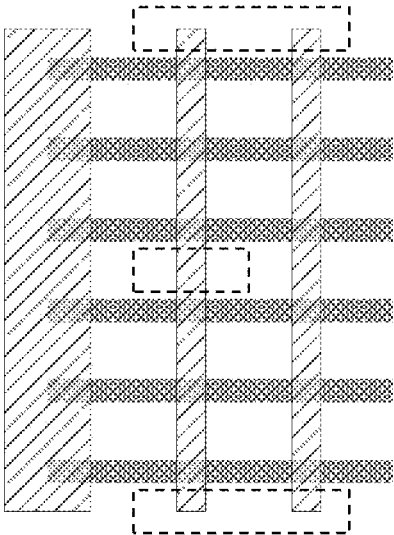


FIG. 14B

aoi22x1

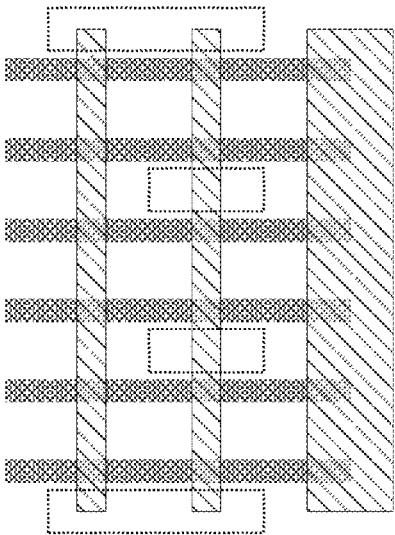


FIG. 14C

aoi22x1

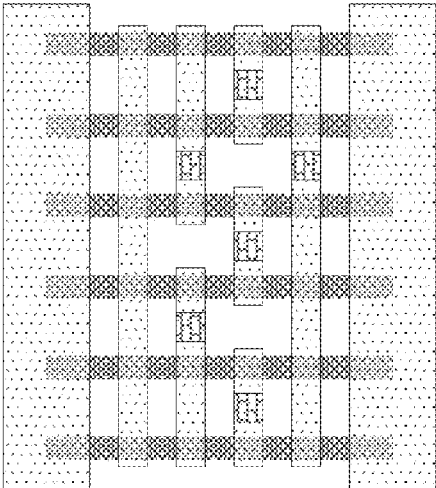


FIG. 14D

aoi22x2

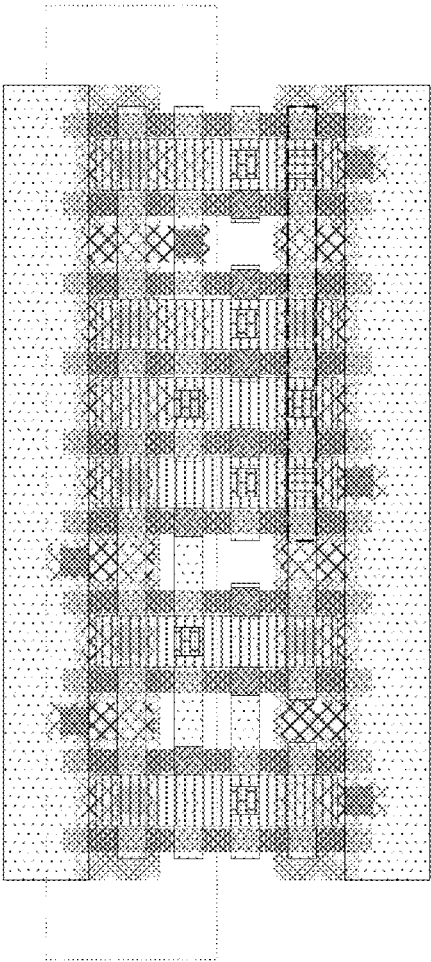


FIG. 15A

aoi22x2

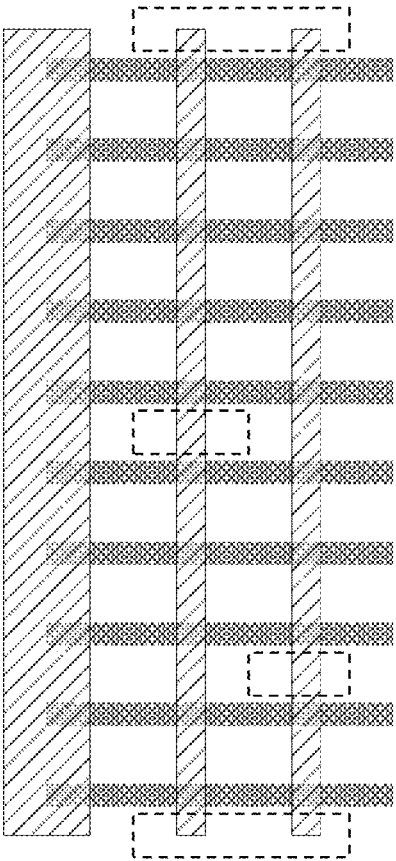


FIG. 15B

aoi22x2

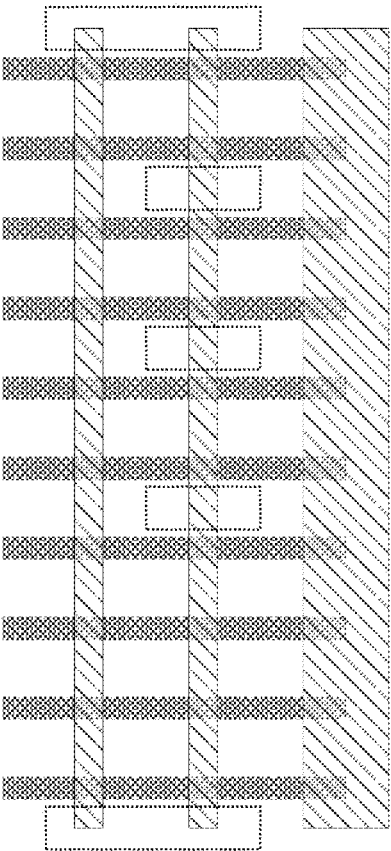


FIG. 15C

aoi22x2

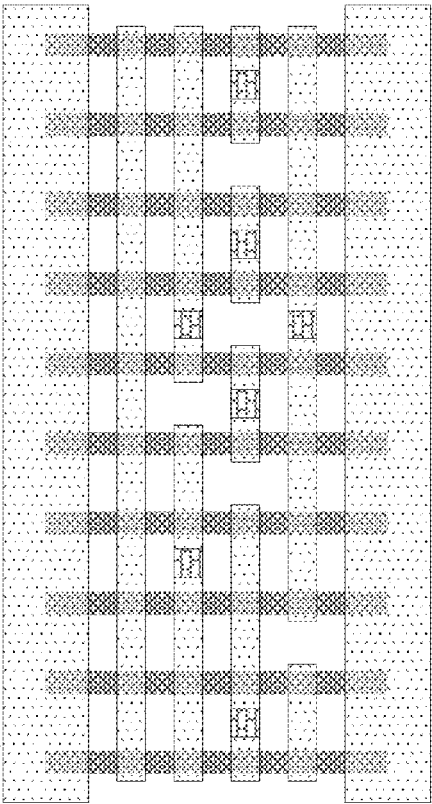


FIG. 15D

aoi31x1

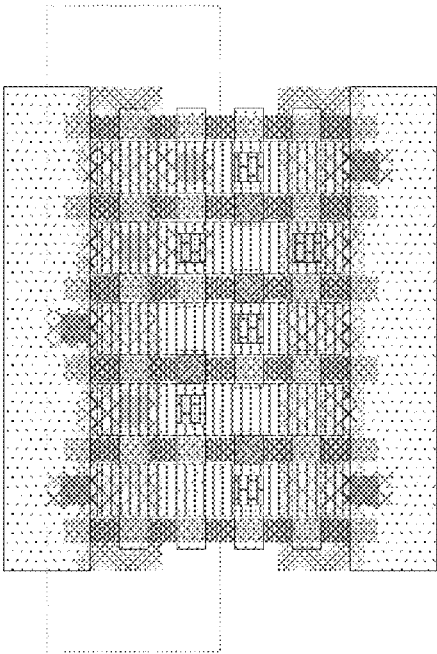


FIG. 16A

aoi31x1

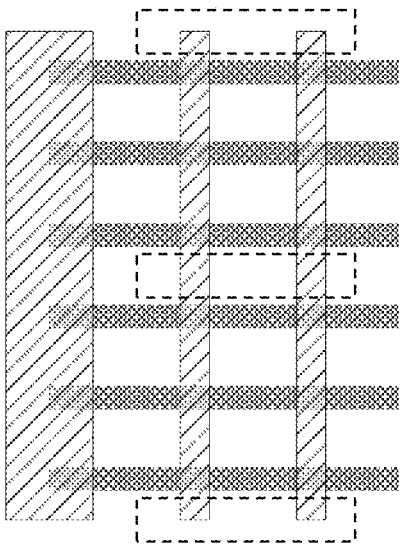


FIG. 16B

aoi31x1

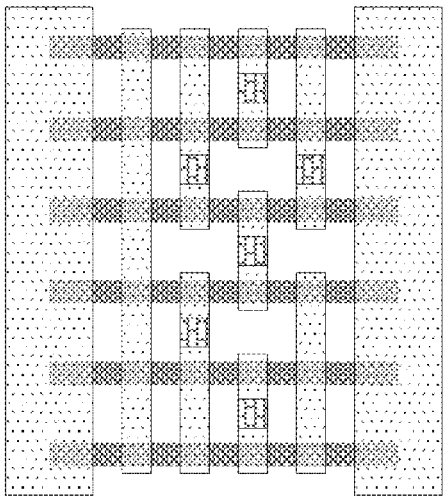


FIG. 16D

aoi31x2

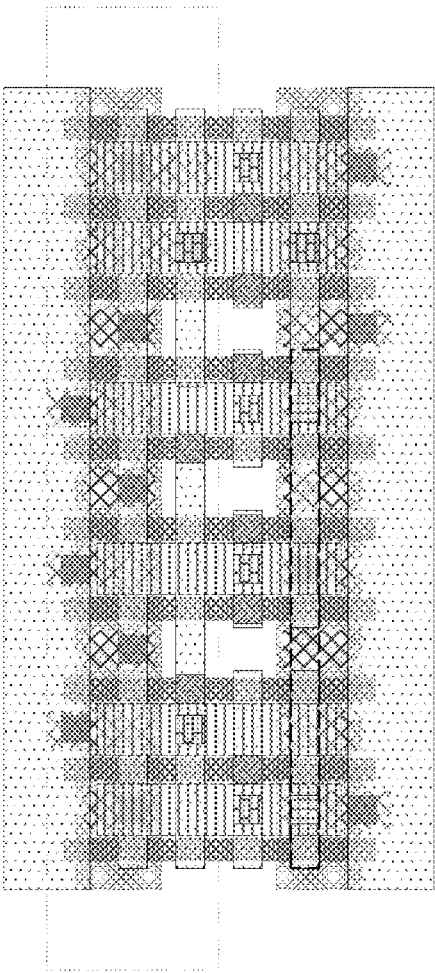


FIG. 17A

aoi31x2

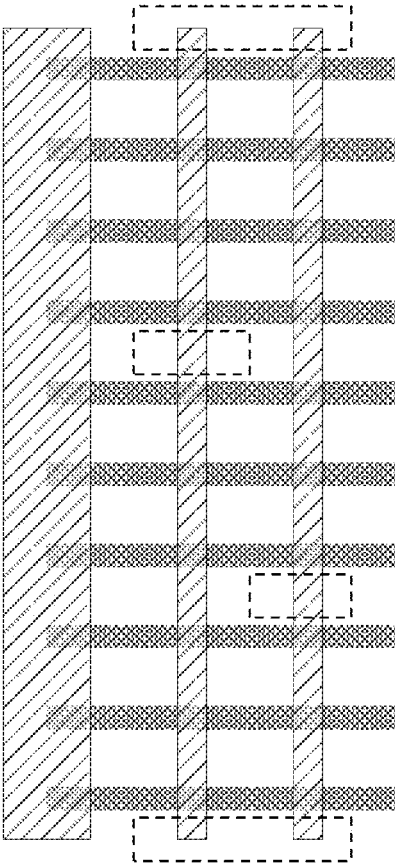


FIG. 17B

aoi31x2

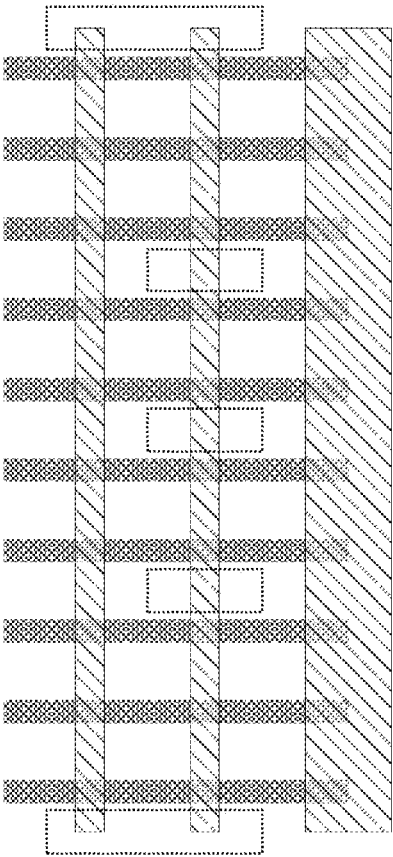


FIG. 17C

aoi31x2

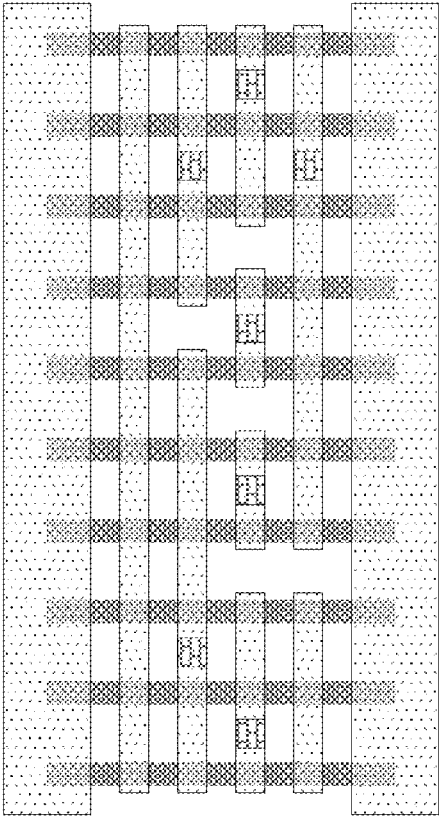


FIG. 17D

aoi211x1

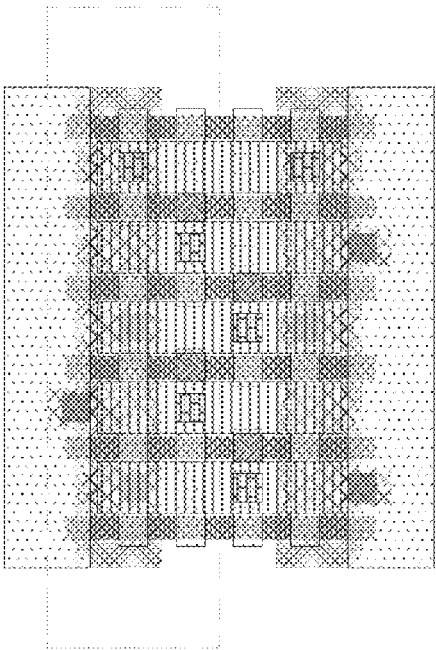


FIG. 18A

aoi211x1

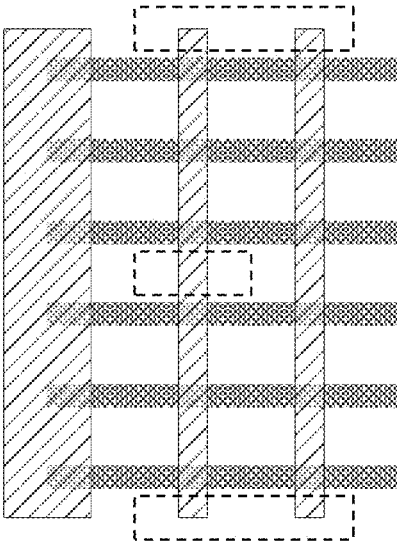


FIG. 18B

aoi211x1

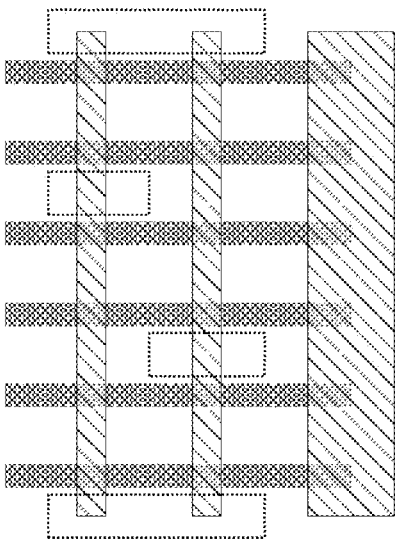


FIG. 18C

aoi211x1

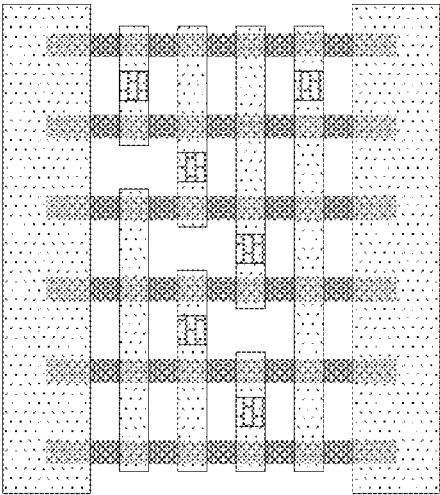


FIG. 18D

aoi222x1

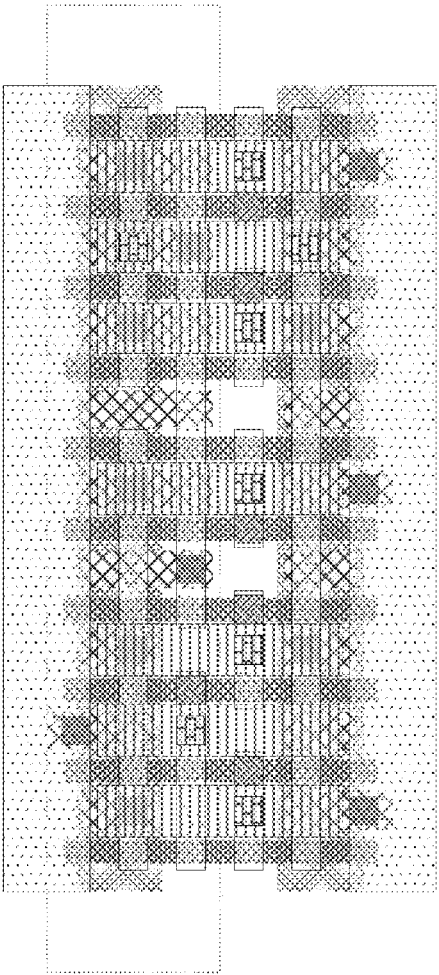


FIG. 19A

aoi222x1

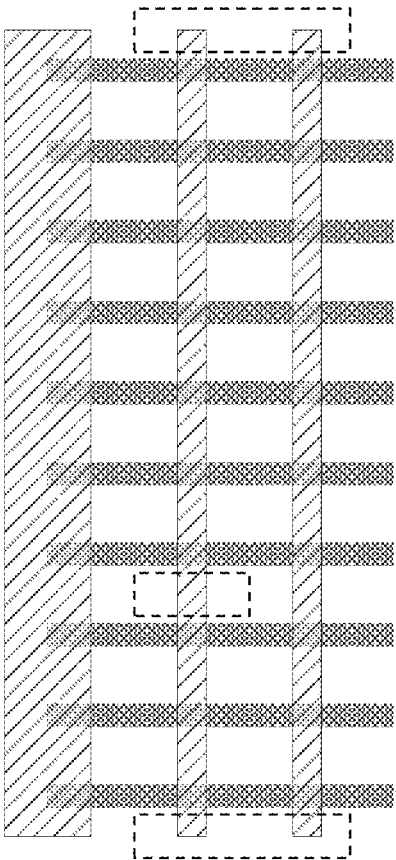


FIG. 19B

aoi222x1

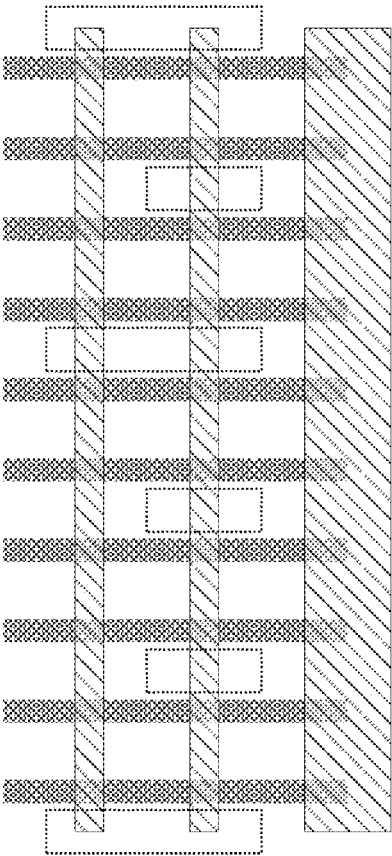


FIG. 19C

aoi222x1

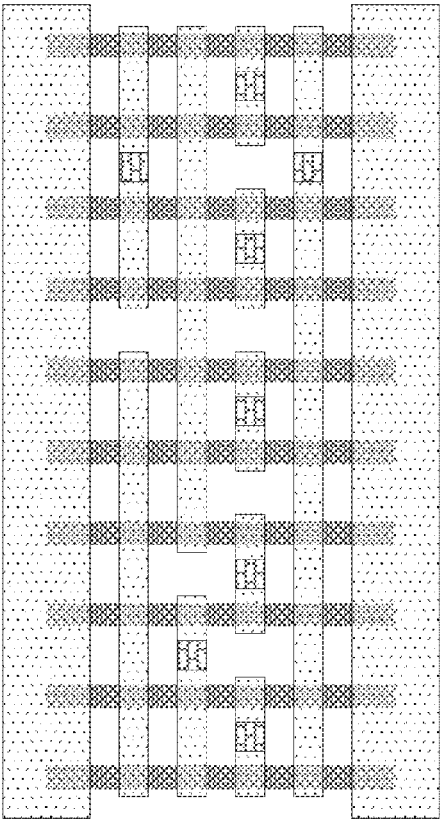


FIG. 19D

bufhx6

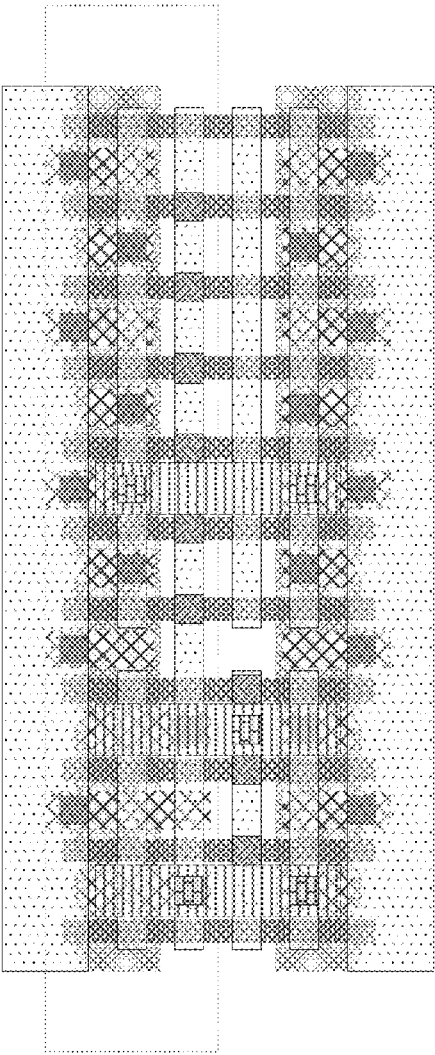


FIG. 20A

bufhx6

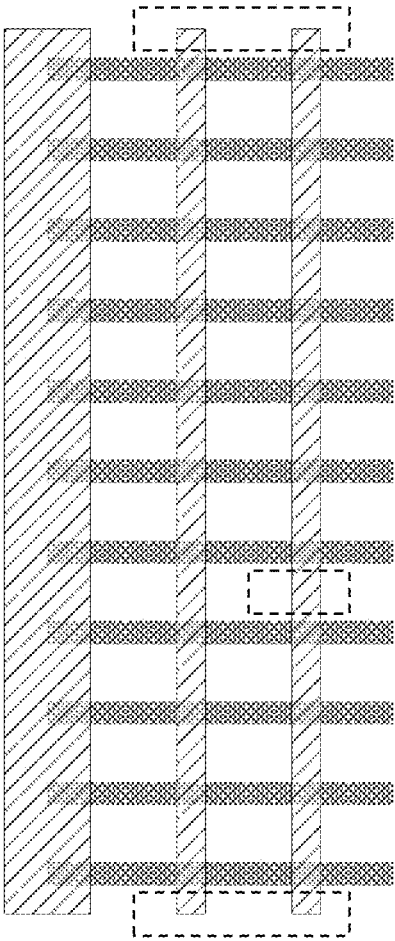


FIG. 20B

bufhx6

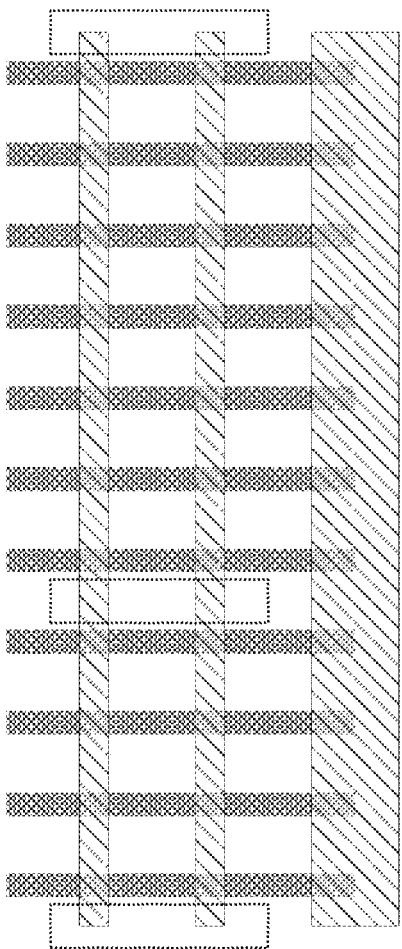


FIG. 20C

bufhx6

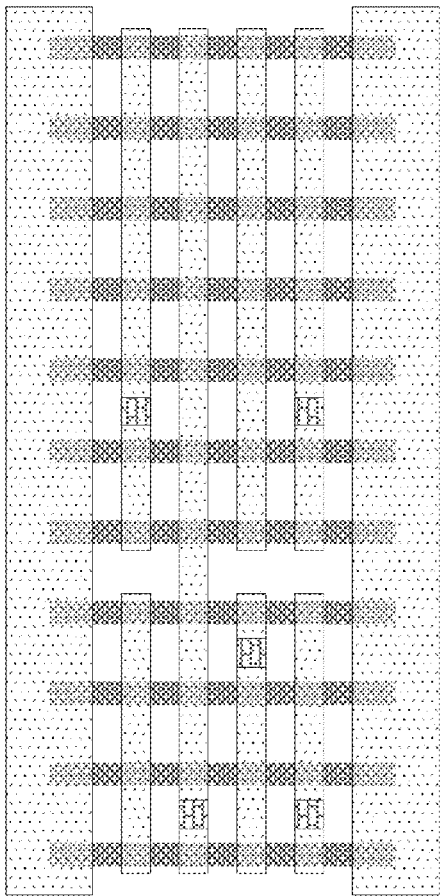


FIG. 20D

bufx1

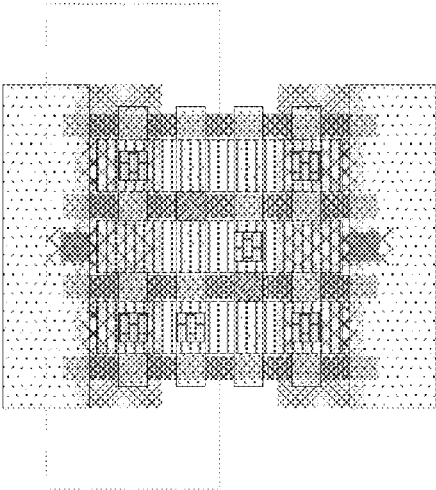


FIG. 21A

bufx1

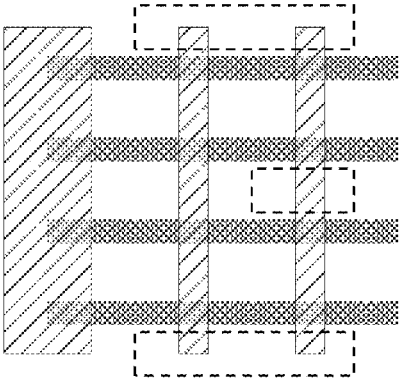


FIG. 21B

bufx1

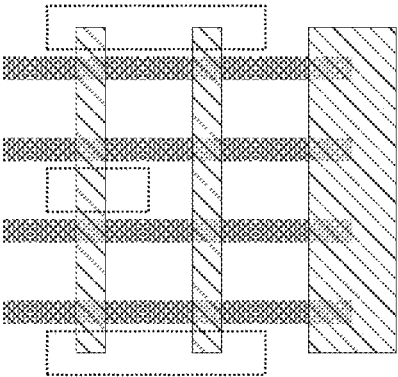


FIG. 21C

bufx1

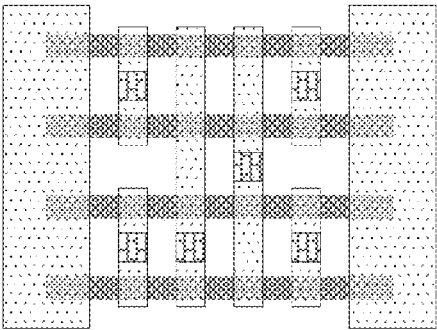


FIG. 21D

bufx2

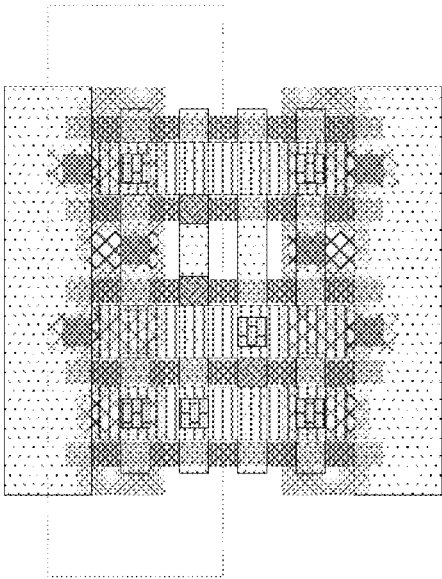


FIG. 22A

bufx2

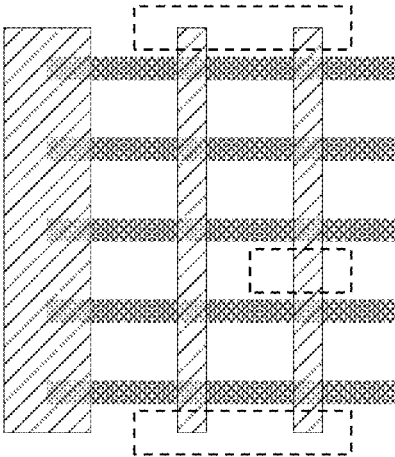


FIG. 22B

bufx2

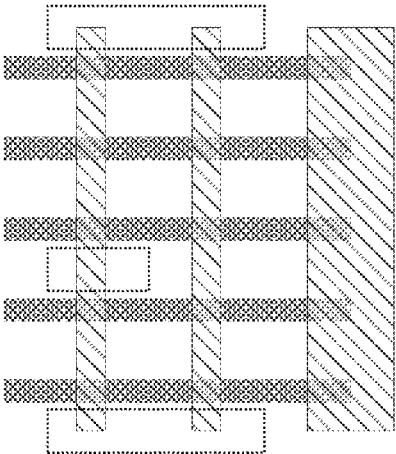


FIG. 22C

bufx2

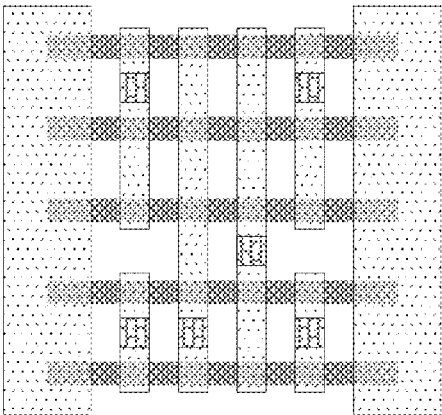


FIG. 22D

bufx3

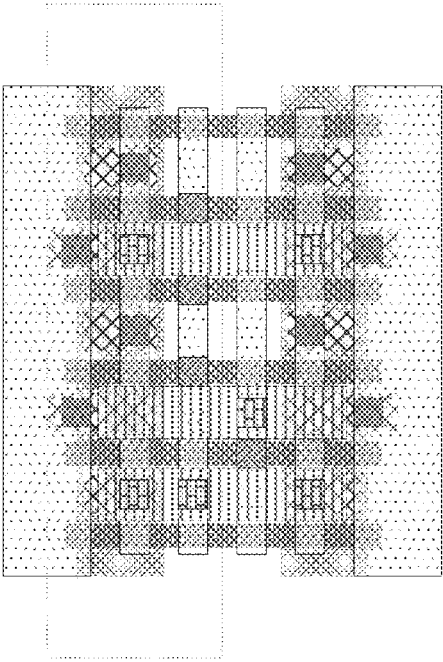


FIG. 23A

bufx3

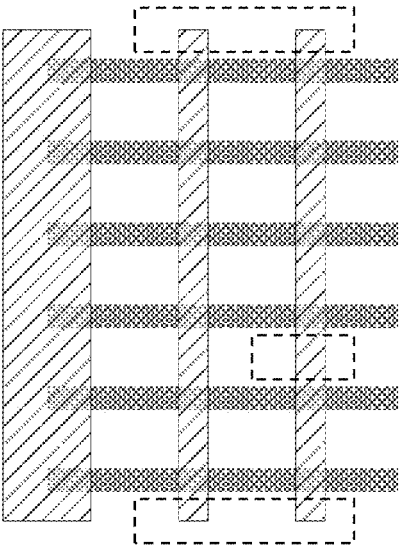


FIG. 23B

bufx3

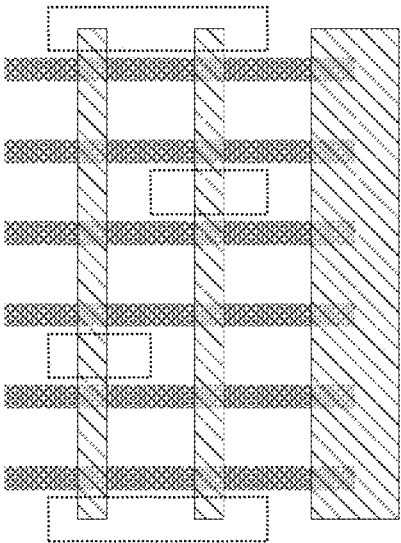


FIG. 23C

bufx3

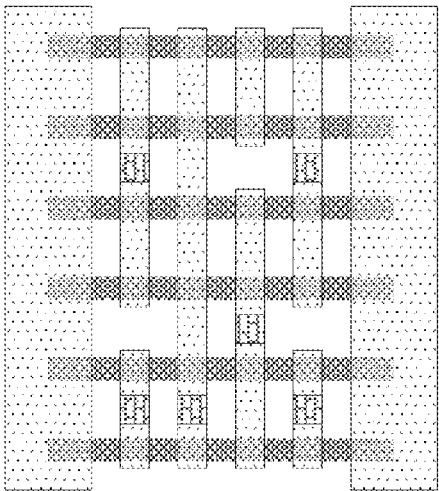


FIG. 23D

bufx4

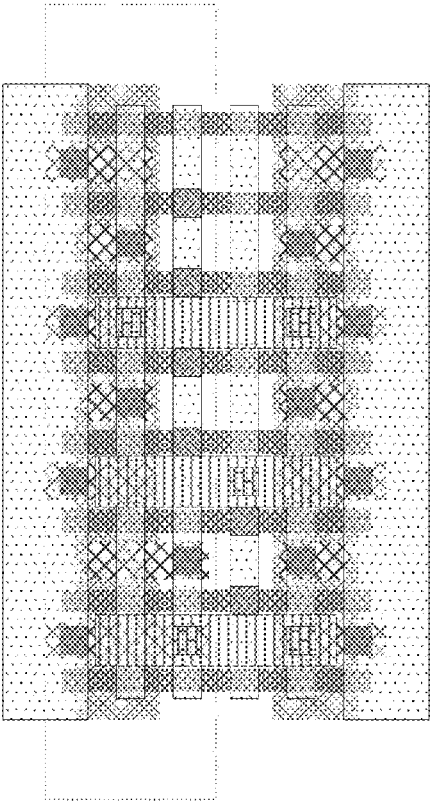


FIG. 24A

bufx4

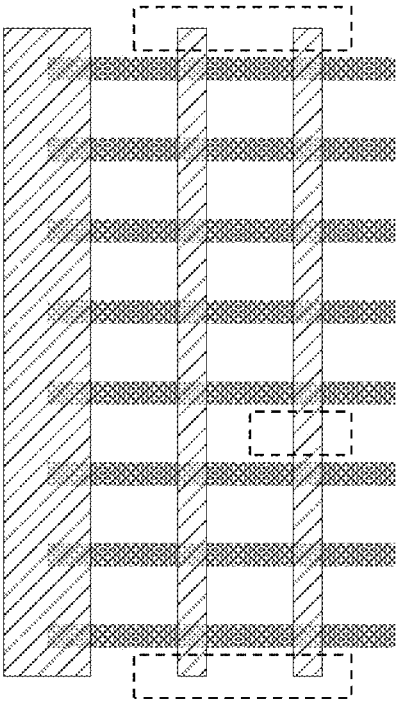


FIG. 24B

bufx4

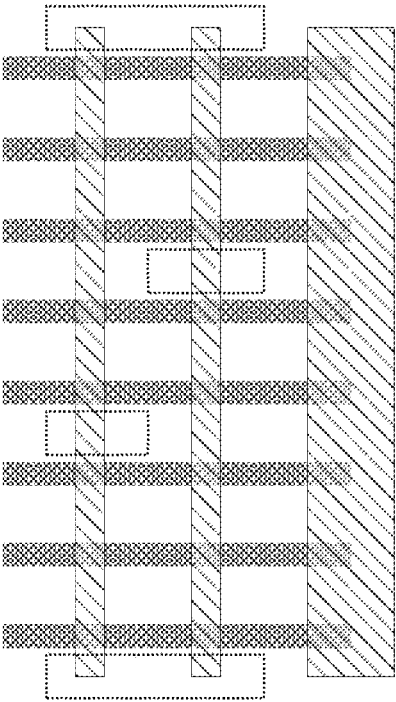


FIG. 24C

bufx4

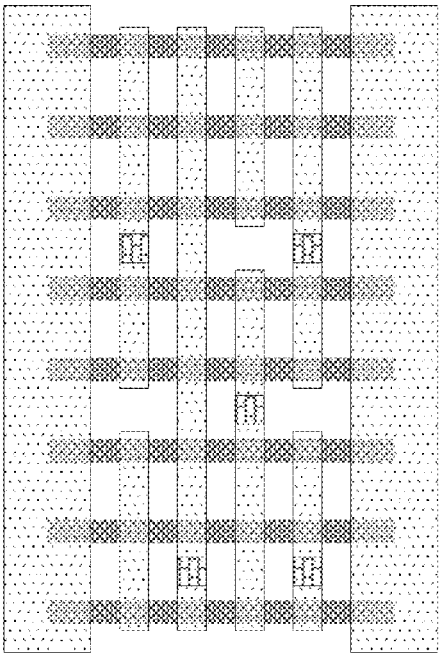


FIG. 24D

bufx6

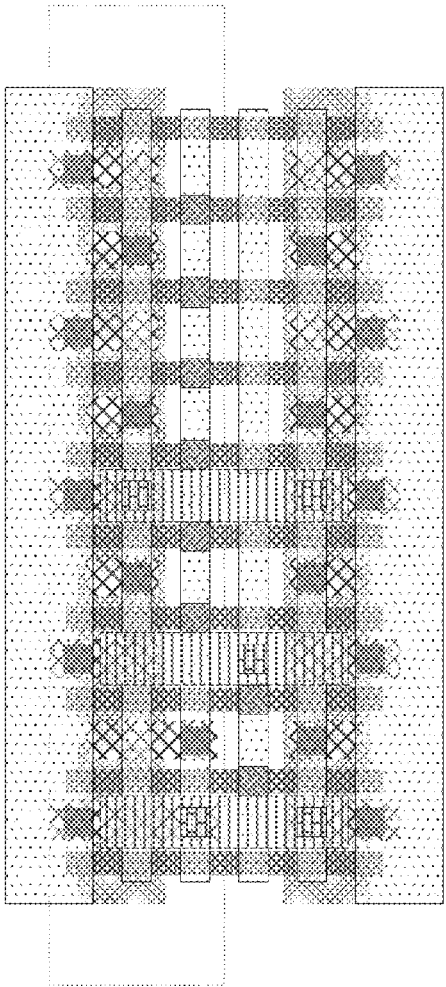


FIG. 25A

bufx6

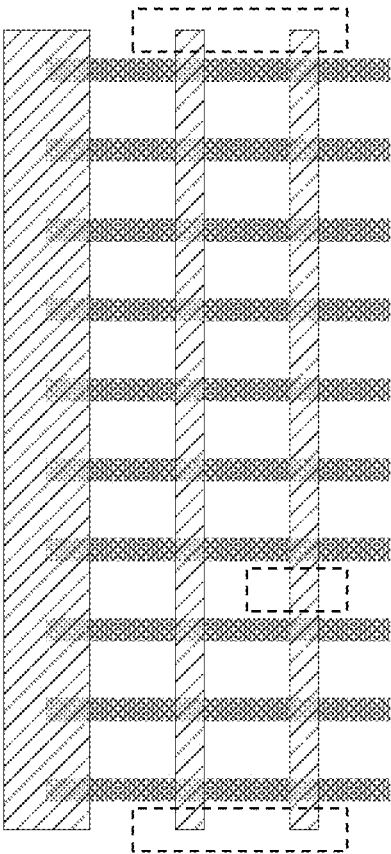


FIG. 25B

bufx6

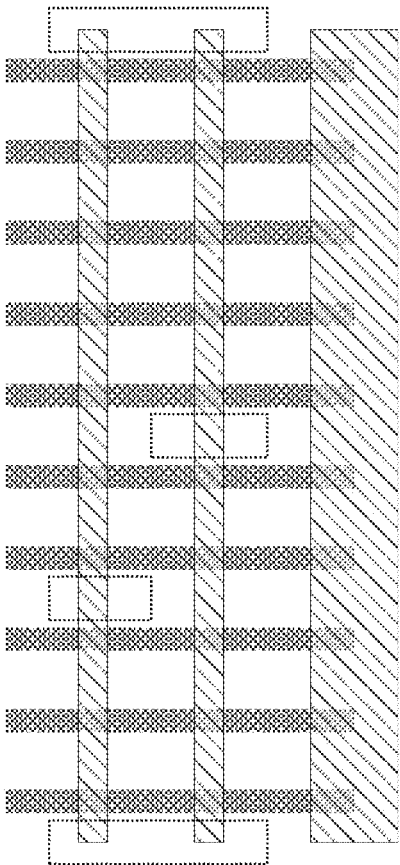


FIG. 25C

bufx6

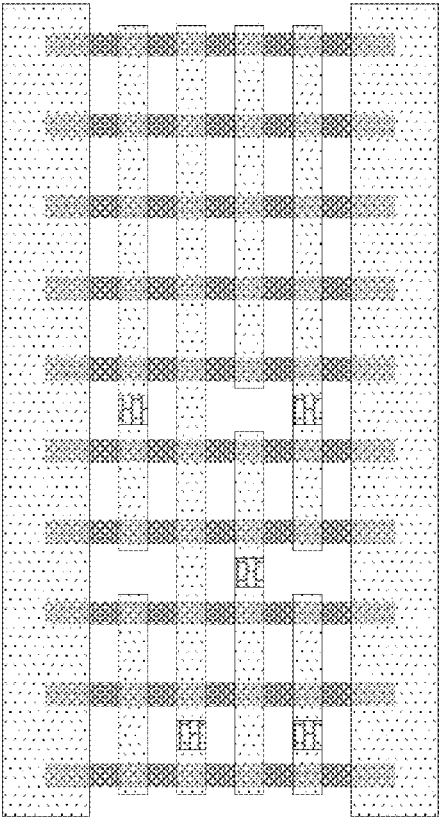


FIG. 25D

bufx8

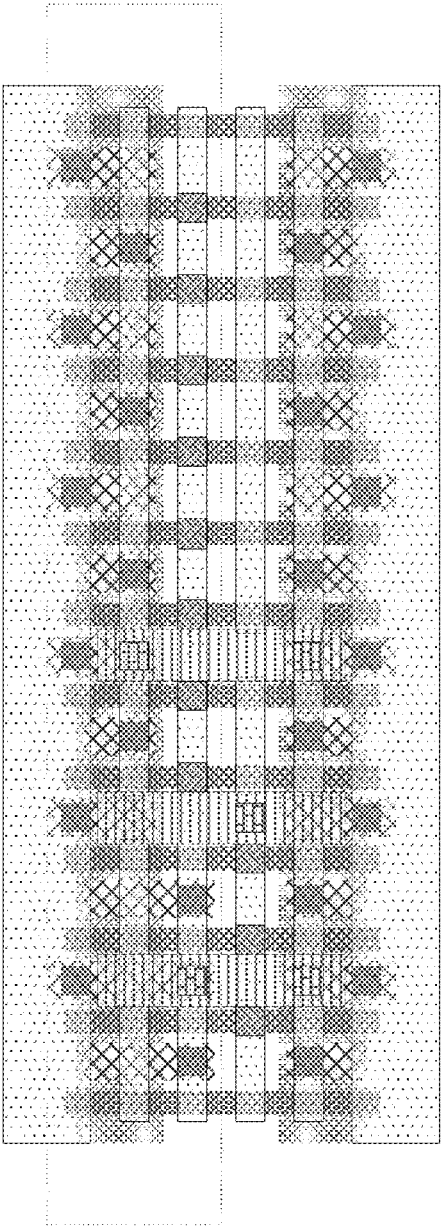


FIG. 26A

bufx8

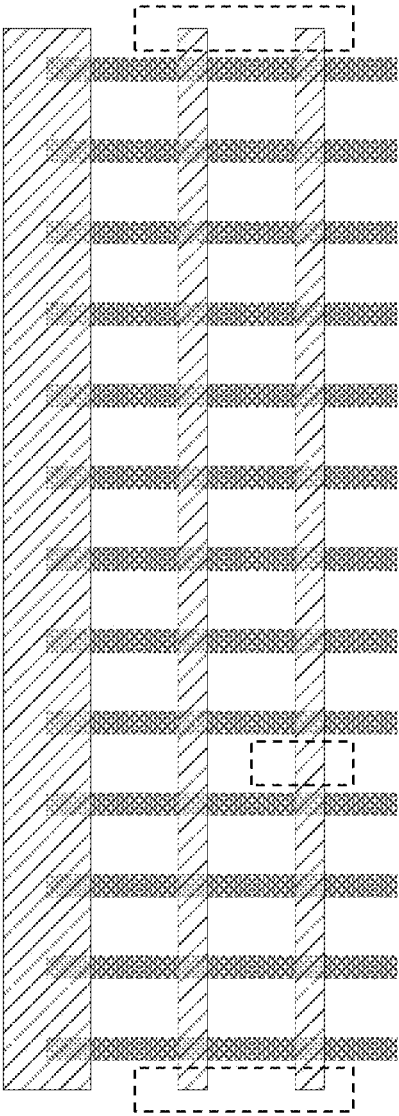


FIG. 26B

bufx8

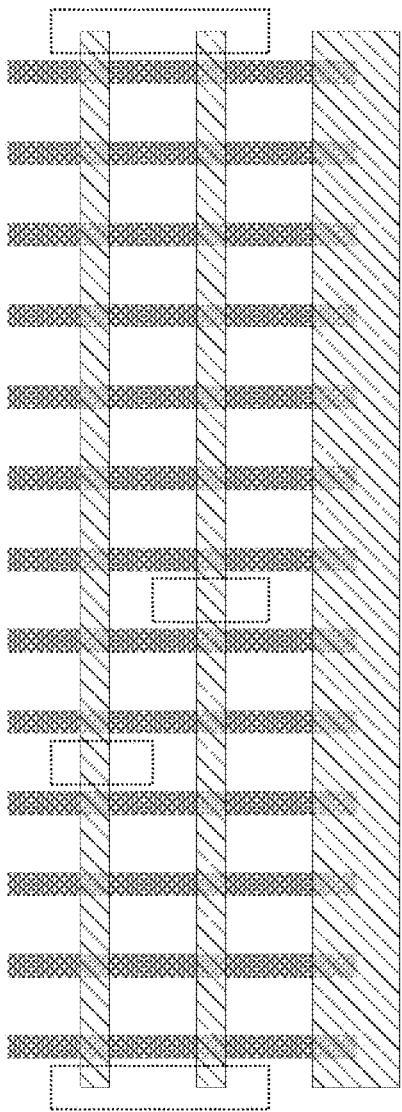


FIG. 26C

bufx8

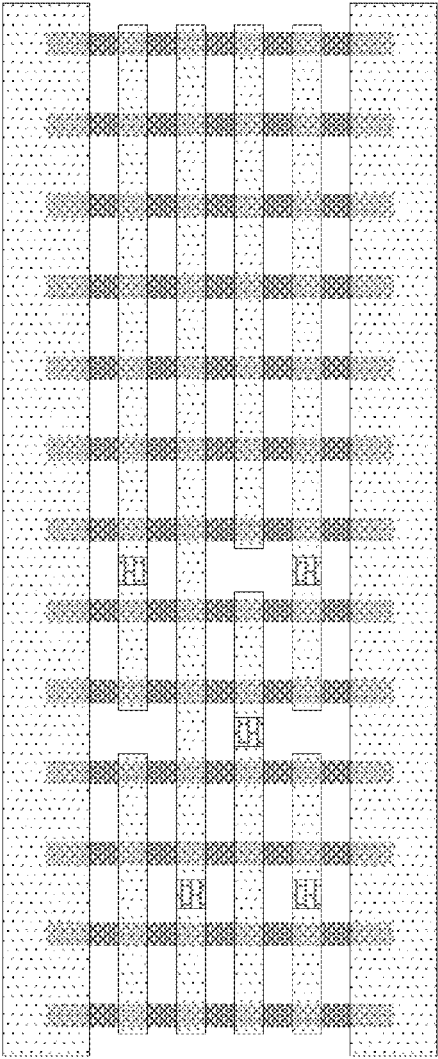


FIG. 26D

ckor2lban2x1

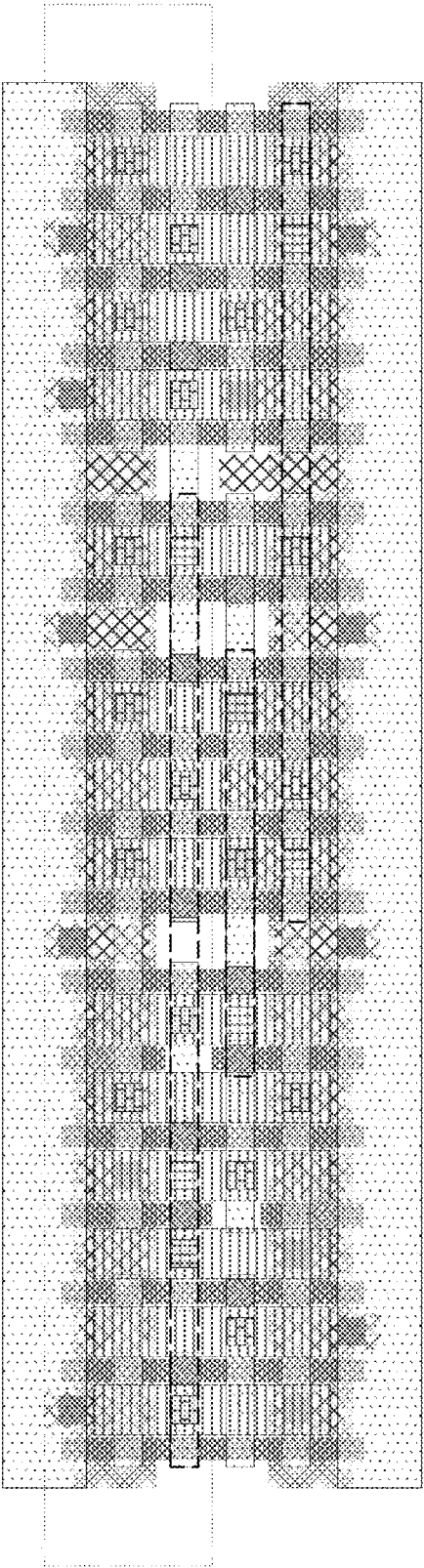


FIG. 27A

ckor2lban2x1

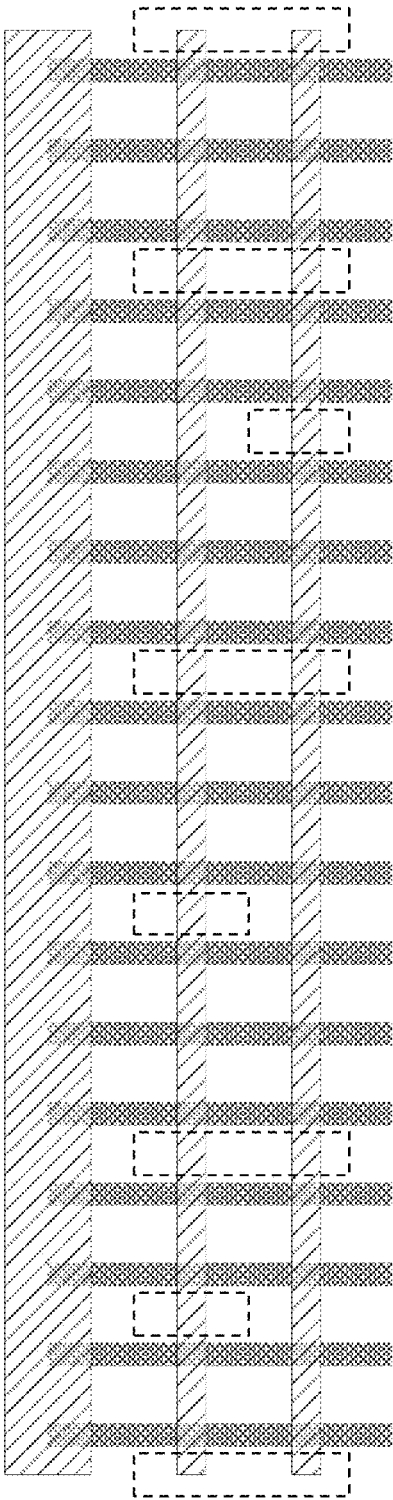


FIG. 27B

ckor2lban2x1

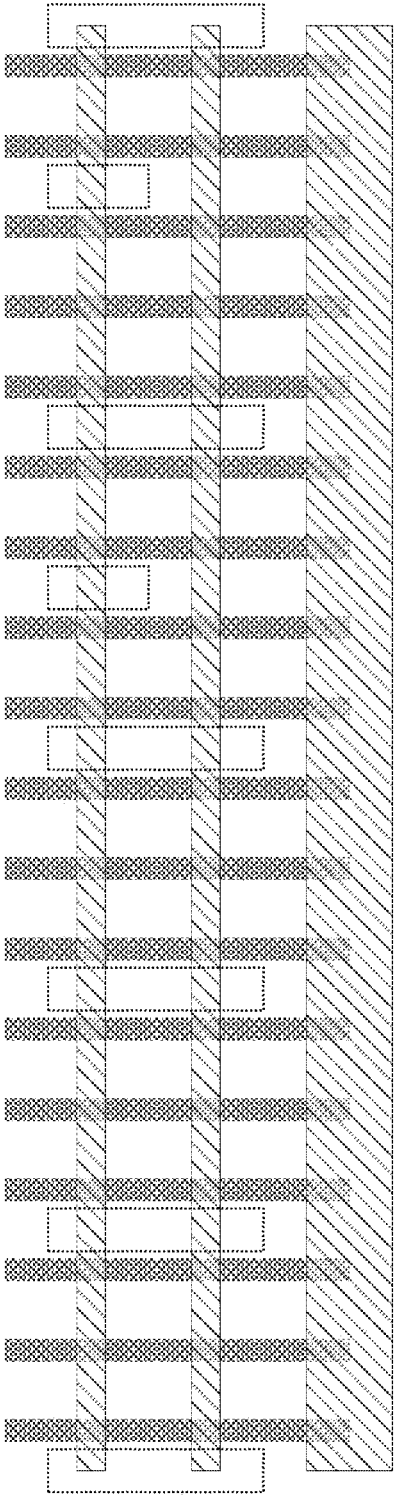


FIG. 27C

ckor2lban2x1

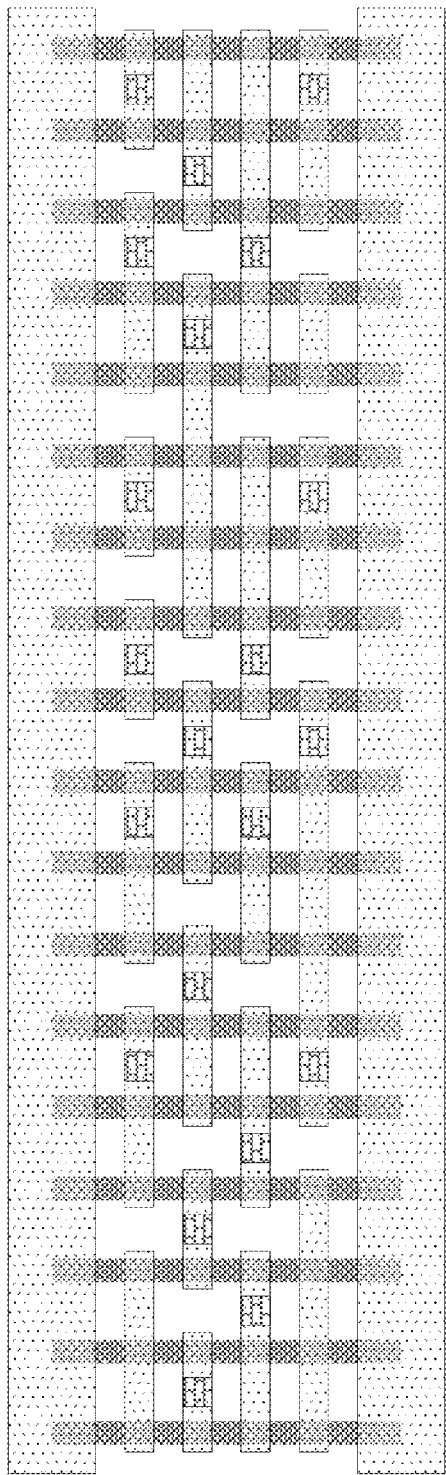


FIG. 27D

dlyx1

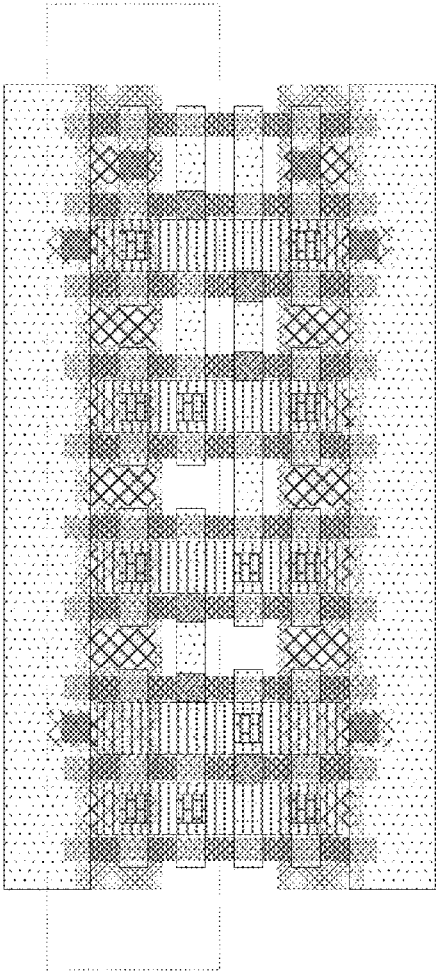


FIG. 28A

dlyx1

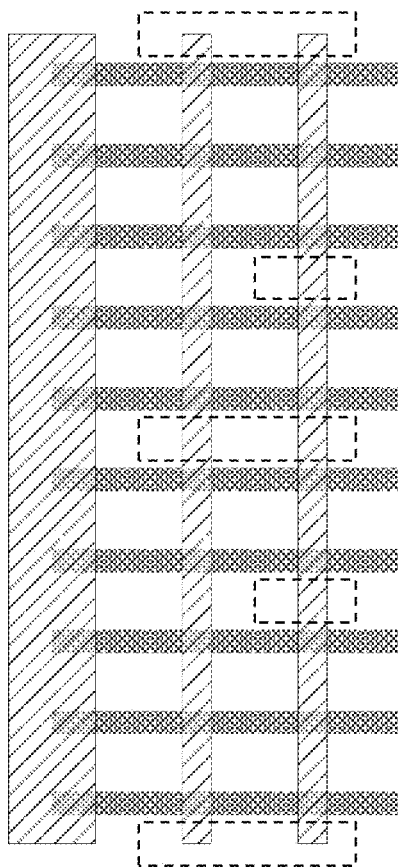


FIG. 28B

dlyx1

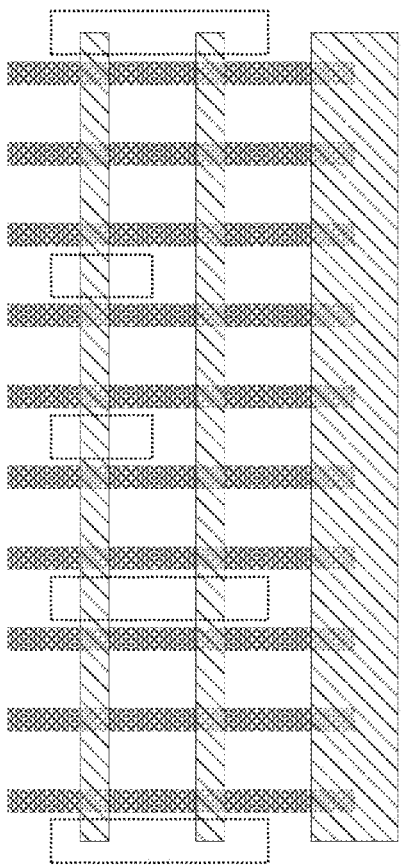


FIG. 28C

dlyx1

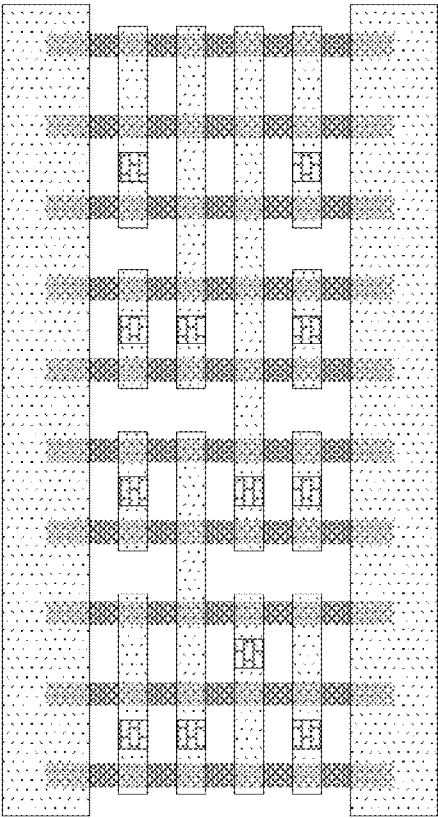


FIG. 28D

fax1

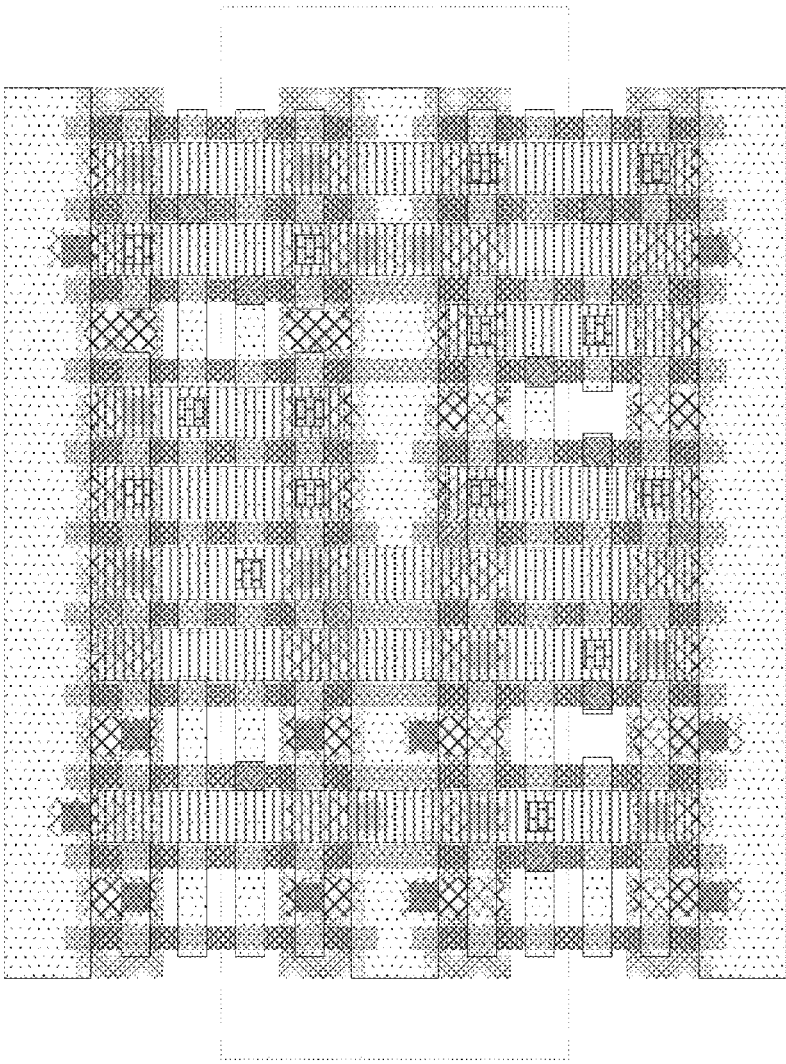


FIG. 29A

fax1

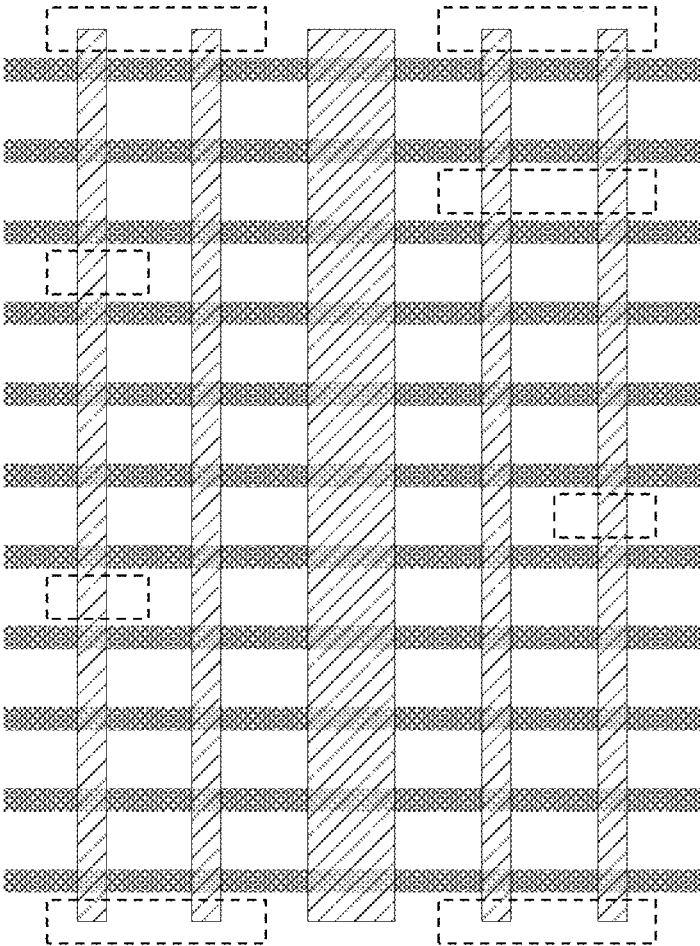


FIG. 29B

fax1

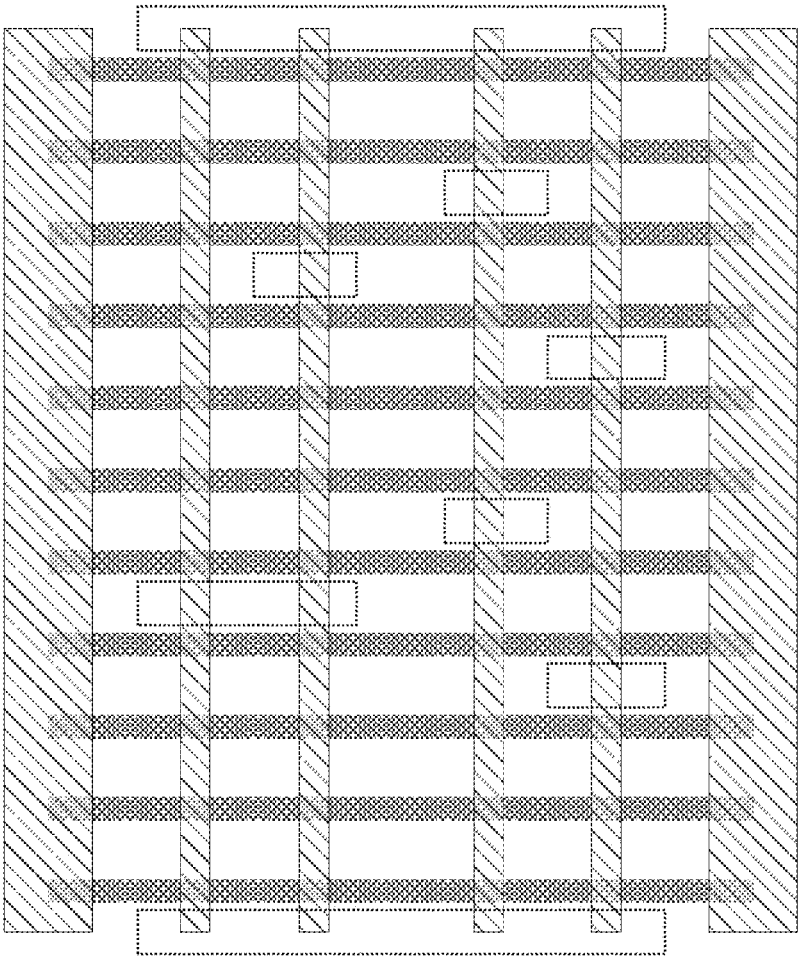


FIG. 29C

fax1

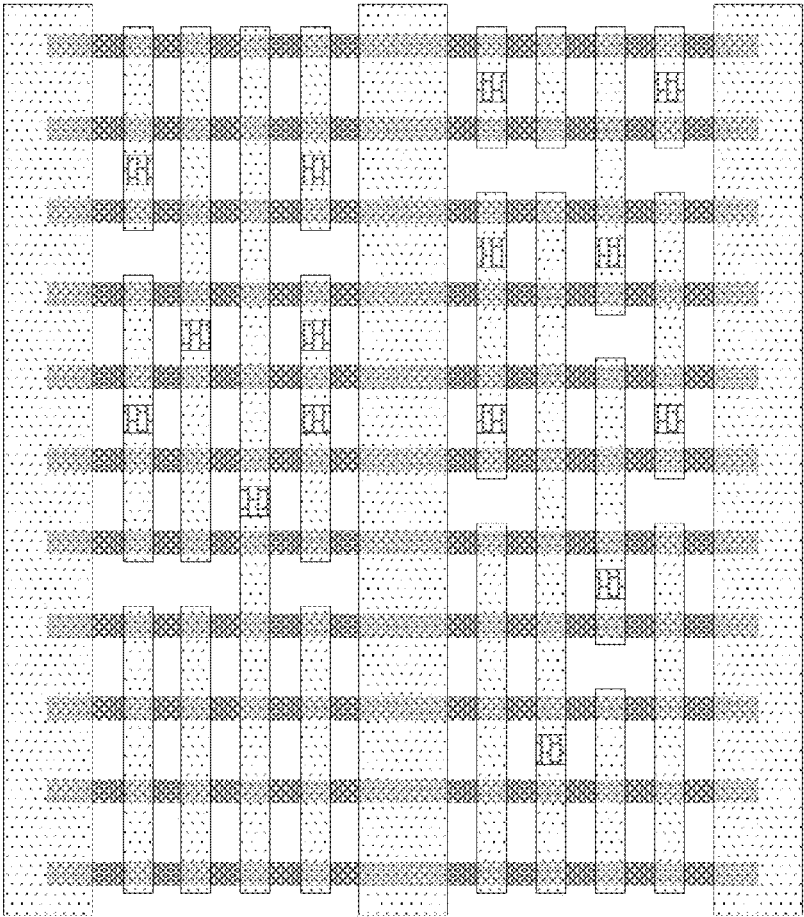


FIG. 29D

hax1

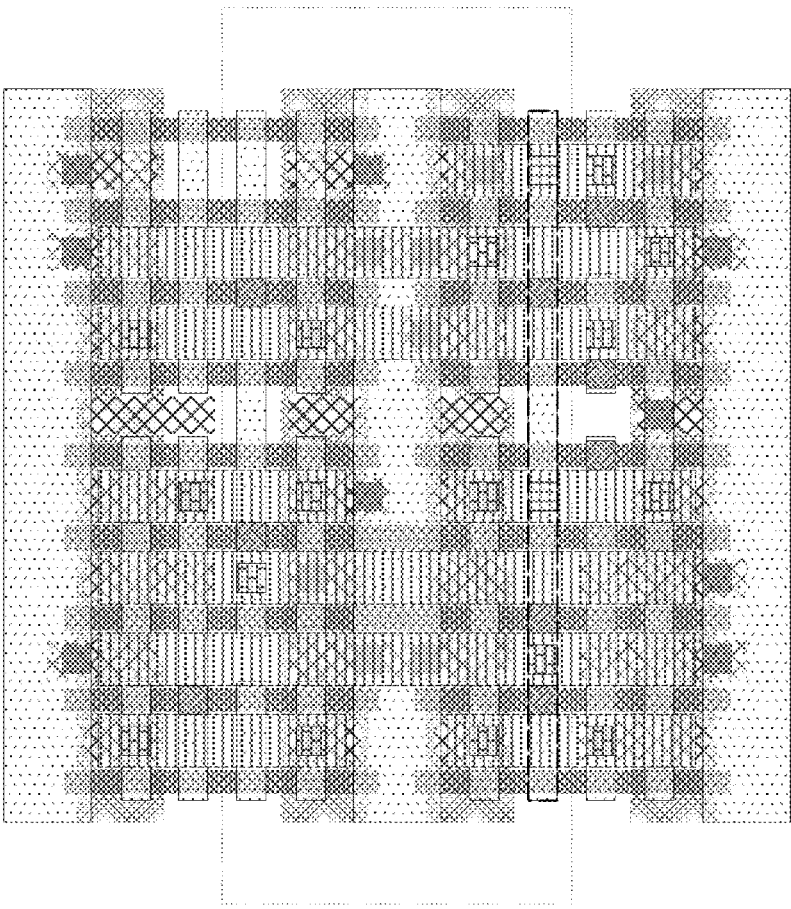


FIG. 30A

hax1

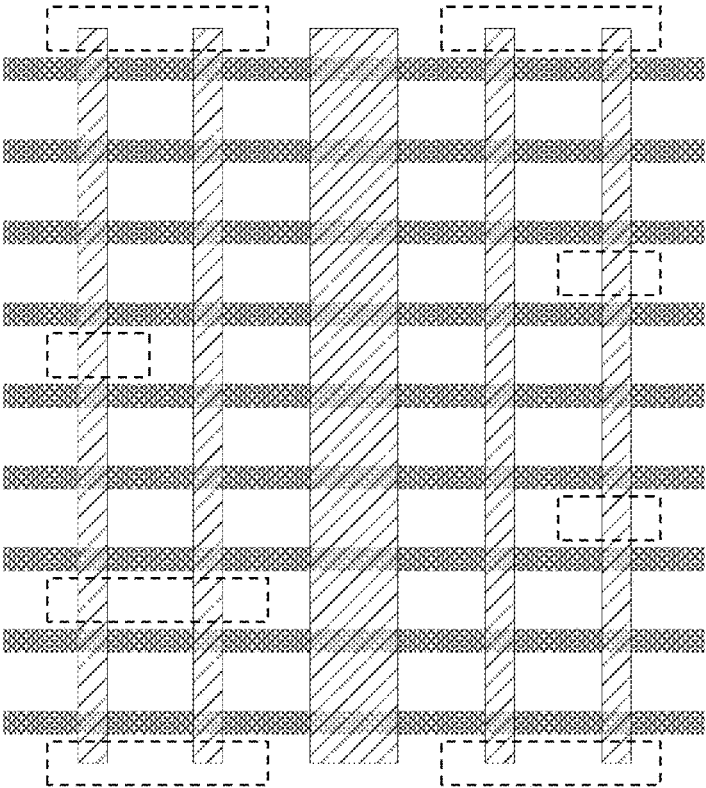


FIG. 30B

hax1

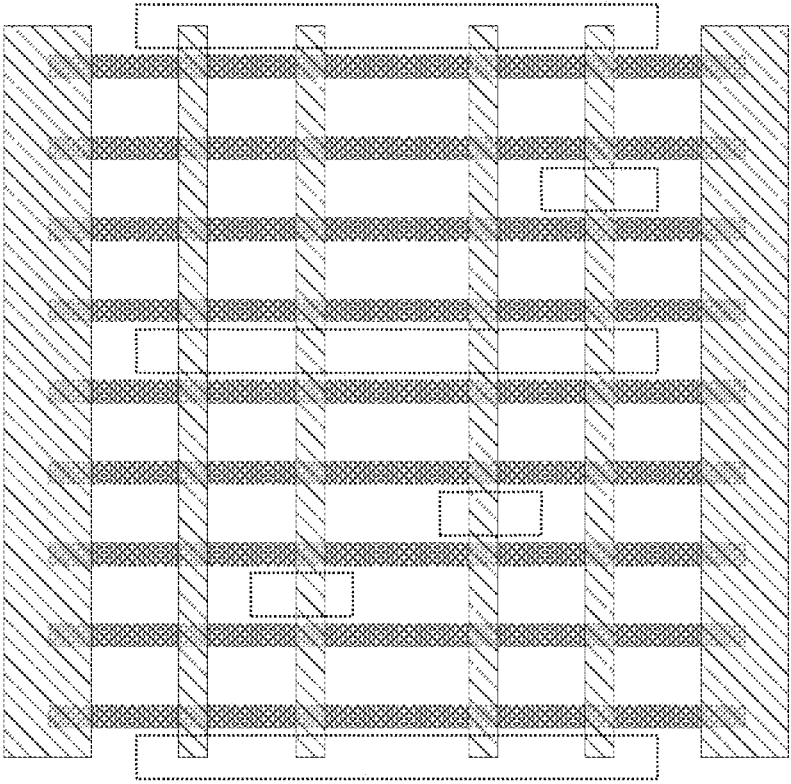


FIG. 30C

hax1

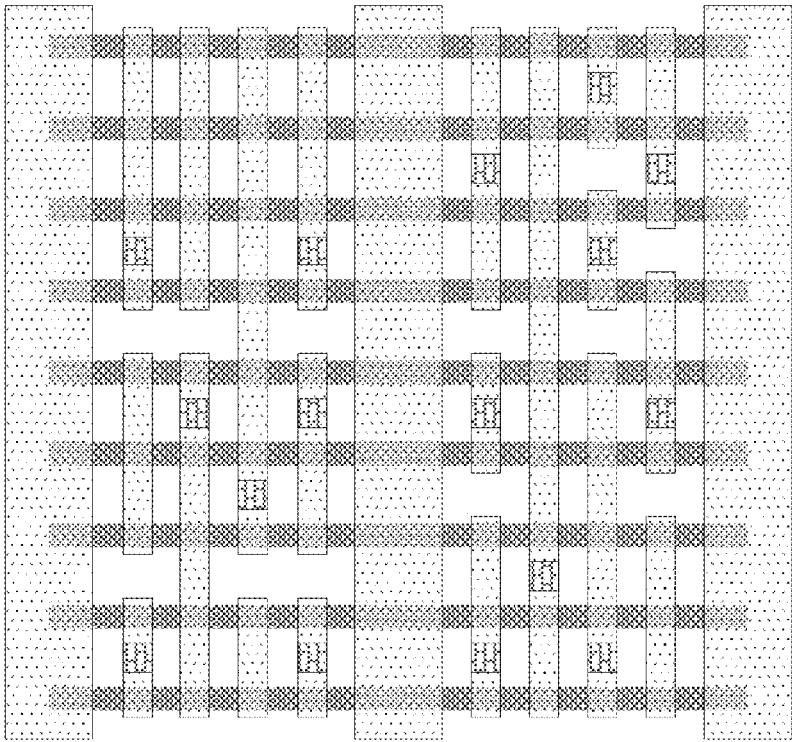


FIG. 30D

iaoi21x1

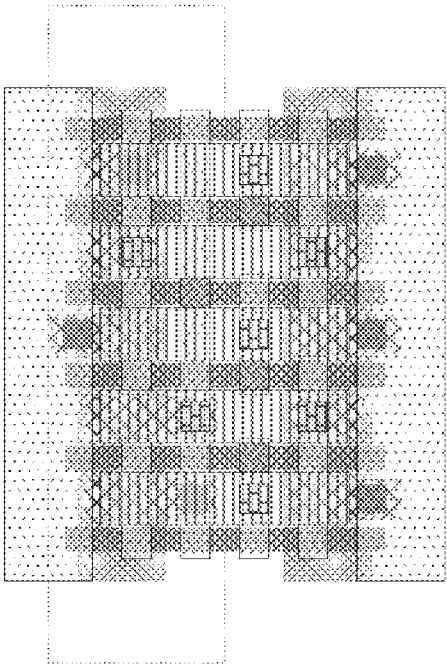


FIG. 31A

iaoi21x1

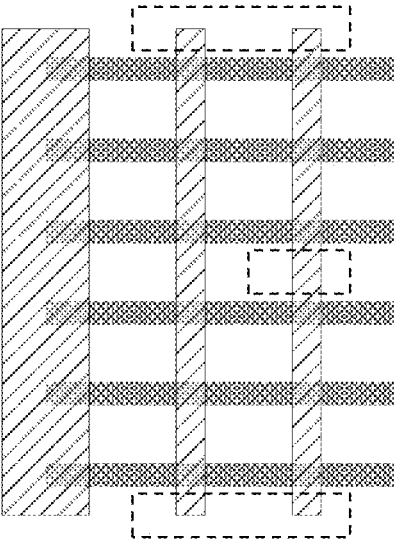


FIG. 31B

iaoi21x1

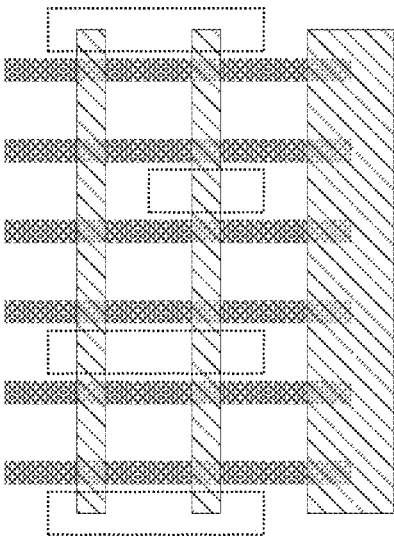


FIG. 31C

iaoi21x1

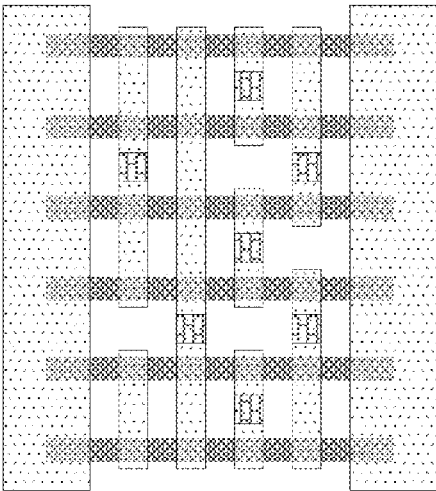


FIG. 31D

ind2x1

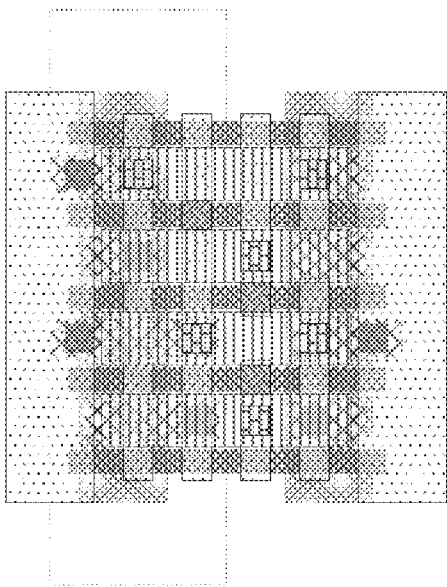


FIG. 32A

ind2x1

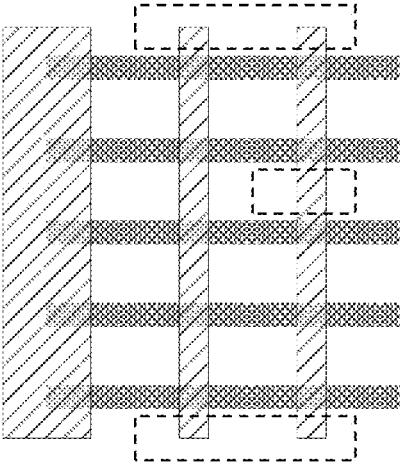


FIG. 32B

ind2x1

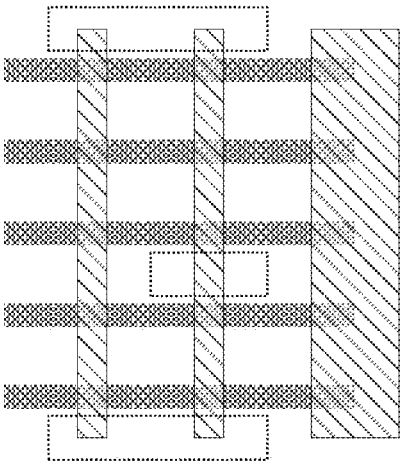


FIG. 32C

ind2x1

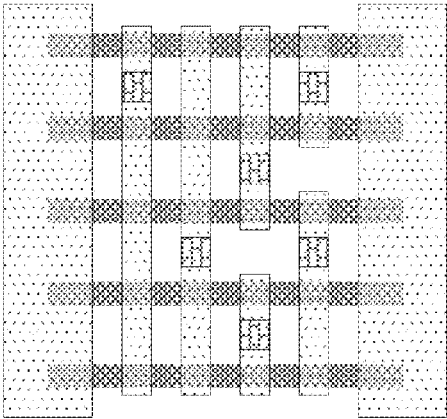


FIG. 32D

ind2x2

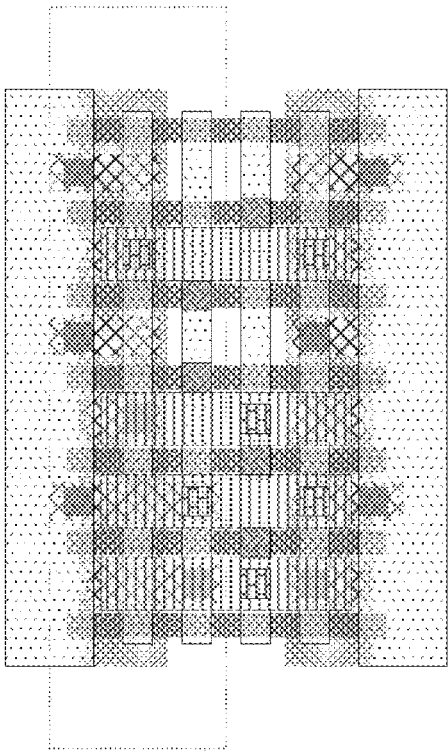


FIG. 33A

ind2x2

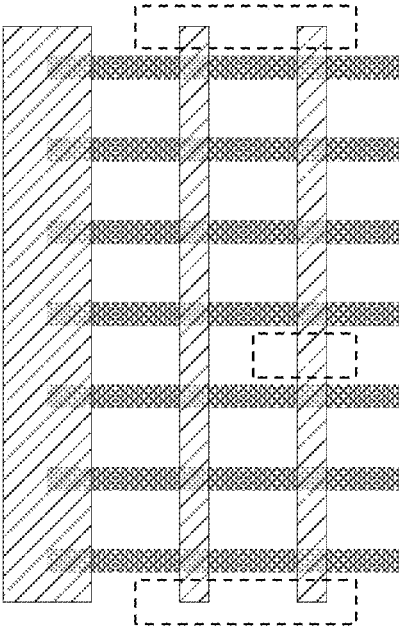


FIG. 33B

ind2x2

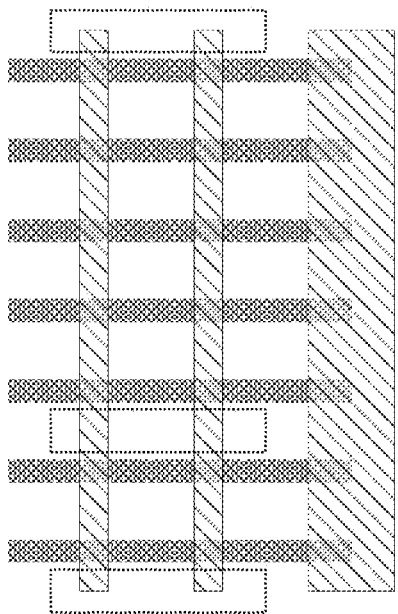


FIG. 33C

ind2x2

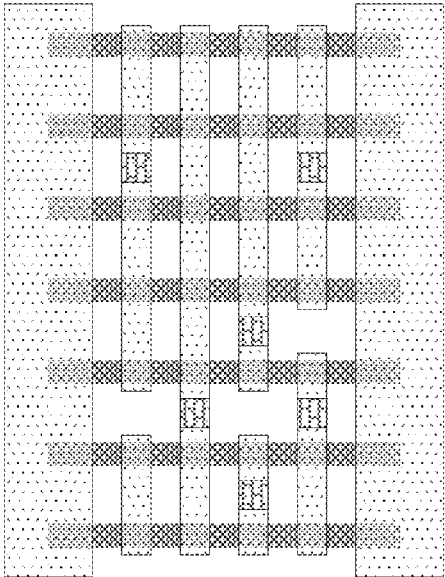


FIG. 33D

ind3x1

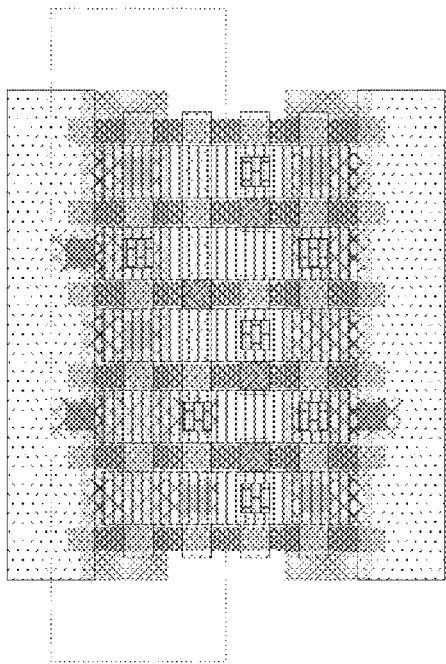


FIG. 34A

ind3x1

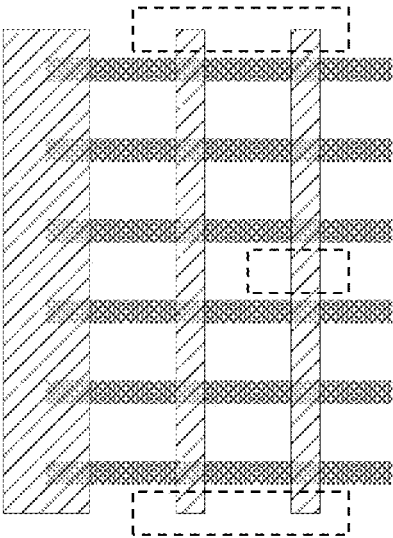


FIG. 34B

ind3x1

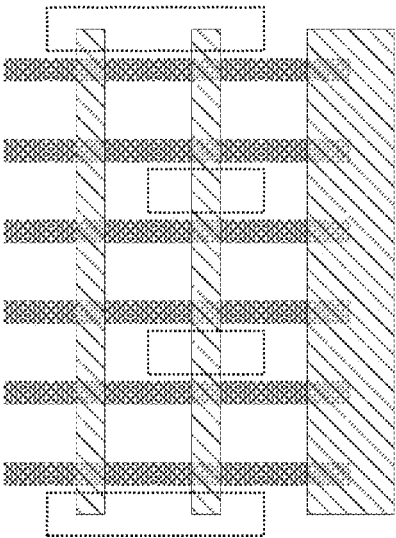


FIG. 34C

ind3x1

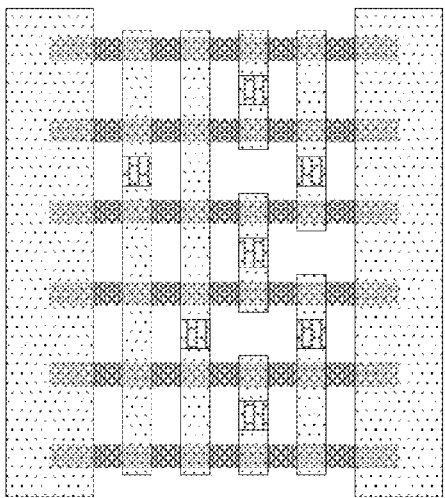


FIG. 34D

ind3x2

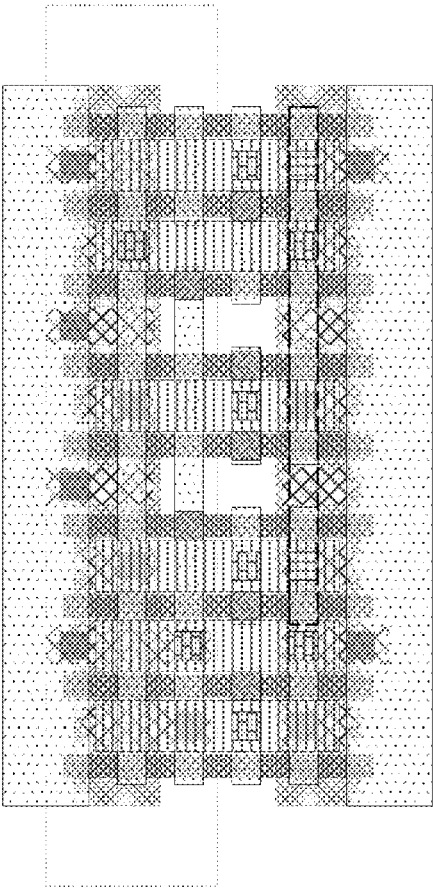


FIG. 35A

ind3x2

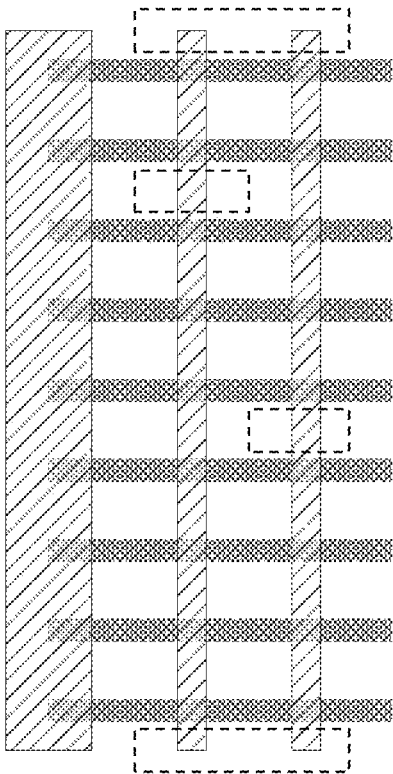


FIG. 35B

ind3x2

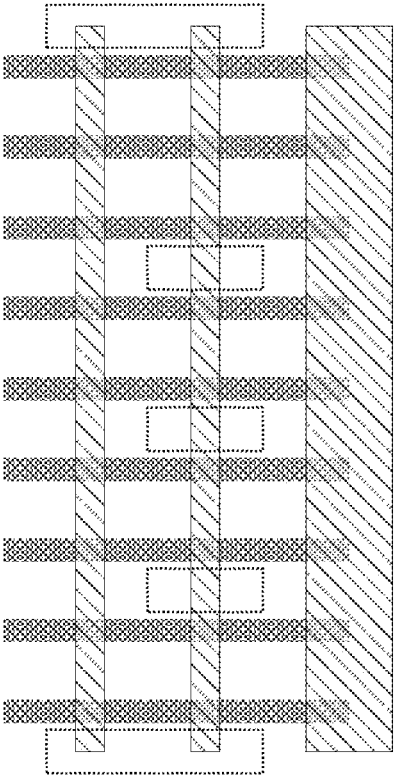


FIG. 35C

ind3x2

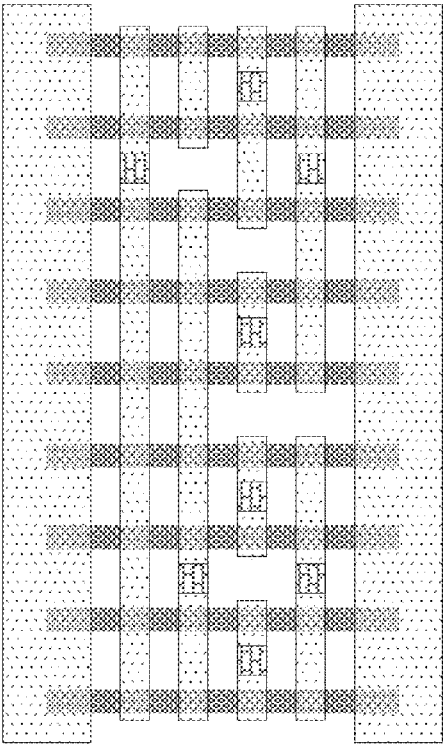


FIG. 35D

inr2x1

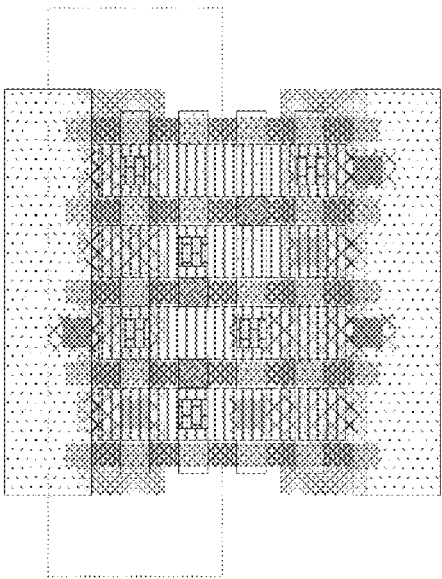


FIG. 36A

inr2x1

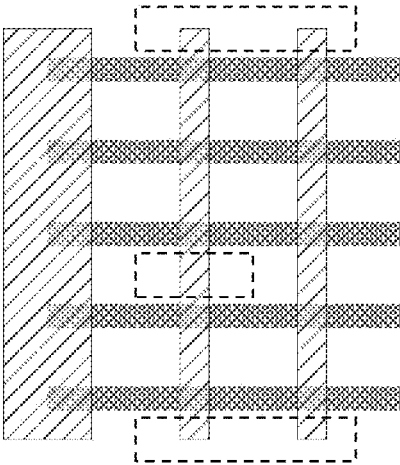


FIG. 36B

inr2x1

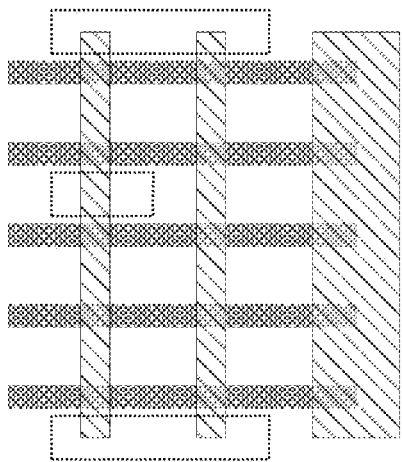


FIG. 36C

inr2x1

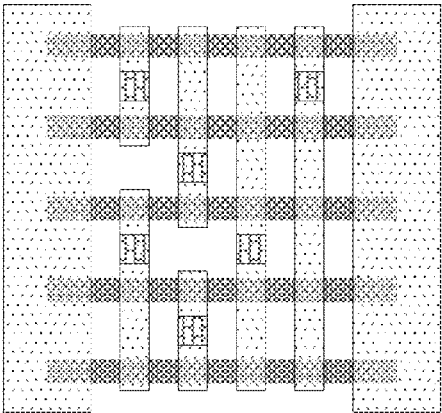


FIG. 36D

inr2x2

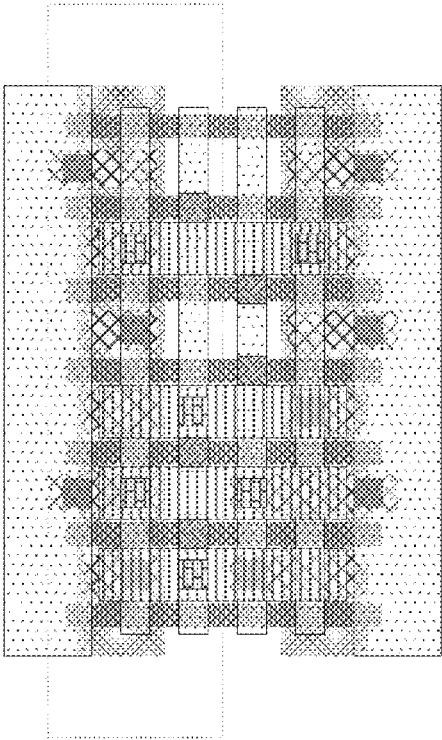


FIG. 37A

inr2x2

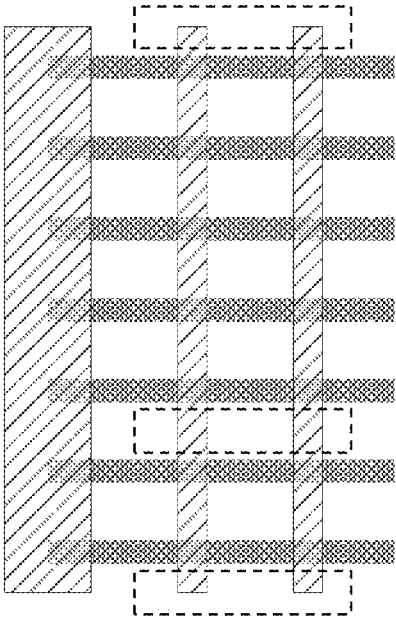


FIG. 37B

inr2x2

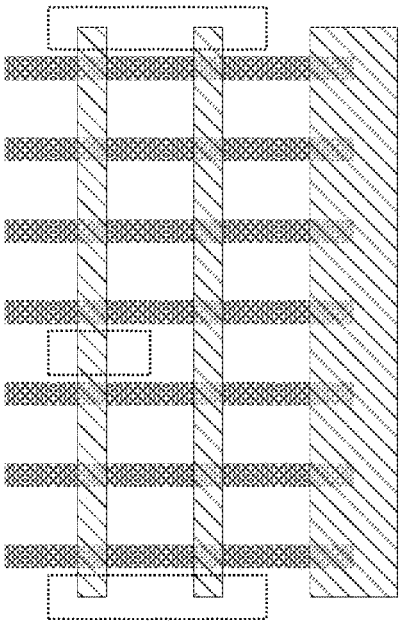


FIG. 37C

inr2x2

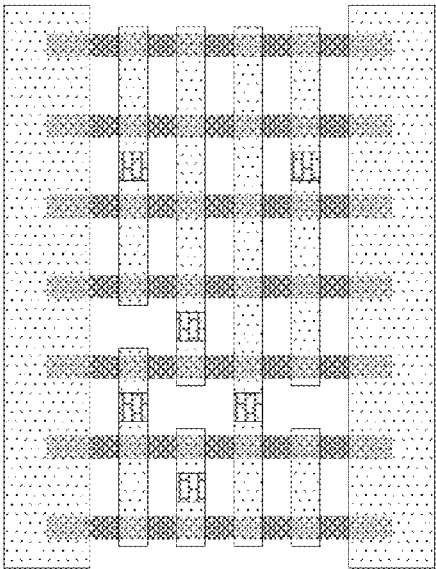


FIG. 37D

inr3x1

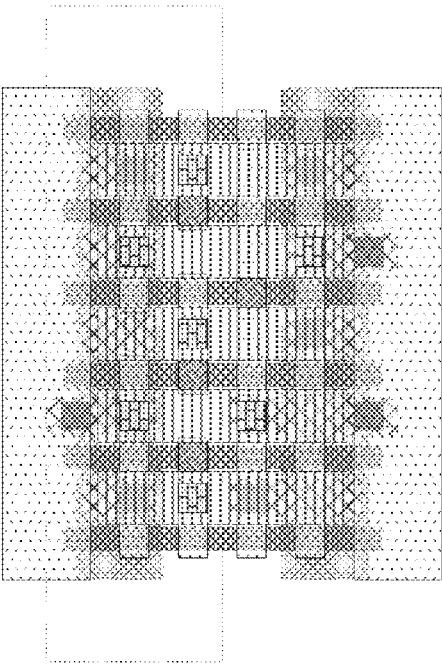


FIG. 38A

inr3x1

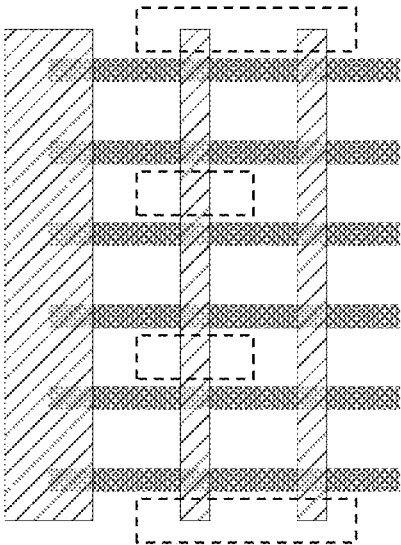


FIG. 38B

inr3x1

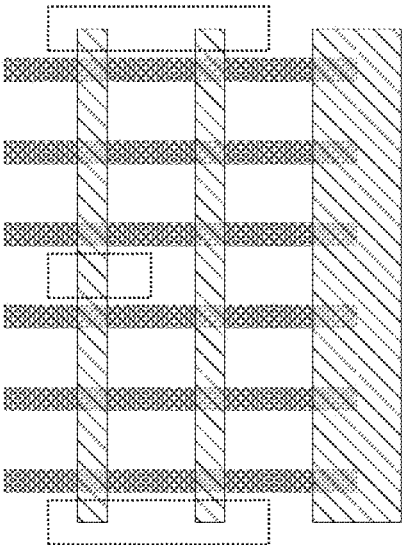


FIG. 38C

inr3x1

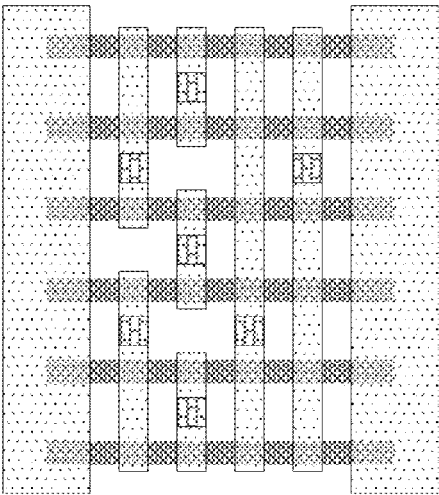


FIG. 38D

inr3x2

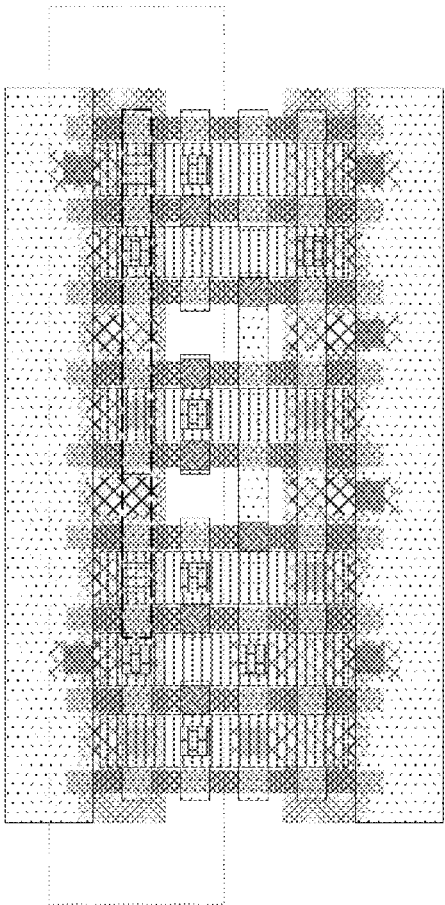


FIG. 39A

inr3x2

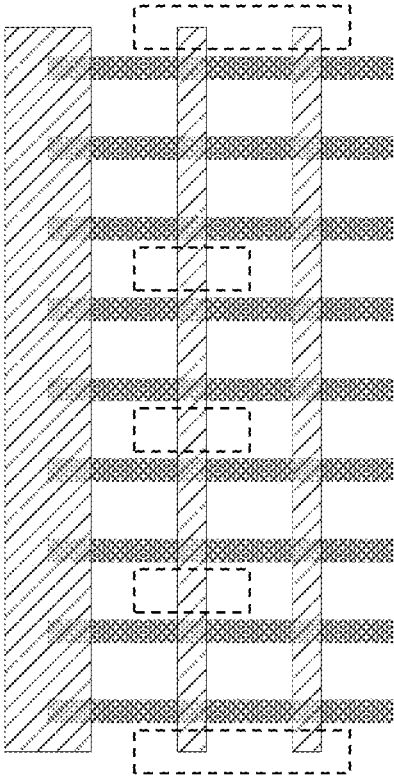


FIG. 39B

inr3x2

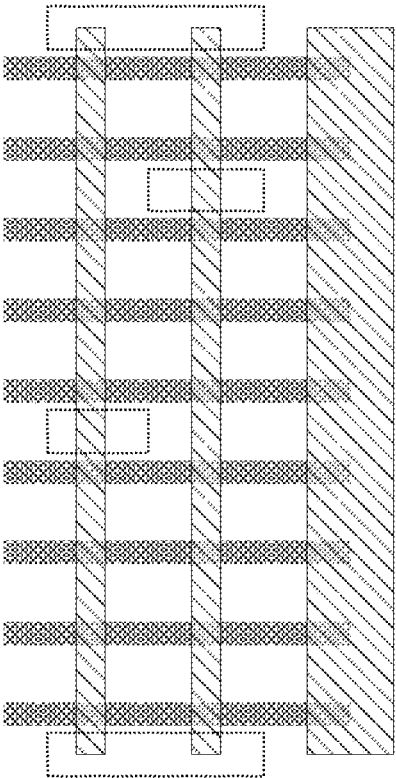


FIG. 39C

inr3x2

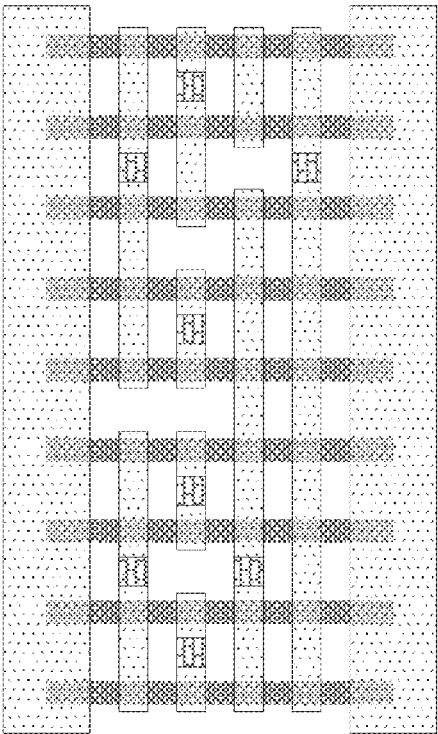


FIG. 39D

invx1

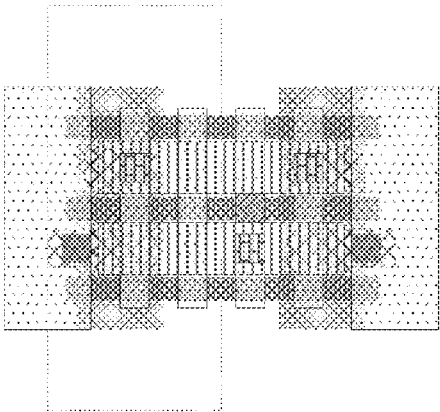


FIG. 40A

invx1

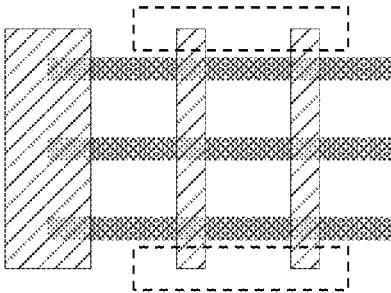


FIG. 40B

invx1

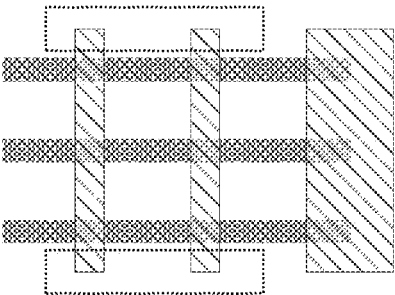


FIG. 40C

invx1

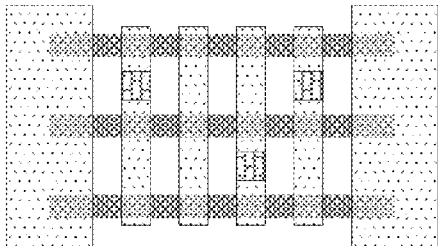


FIG. 40D

invx2

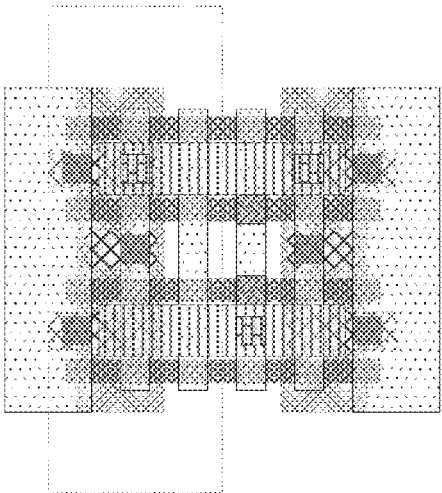


FIG. 41A

invx2

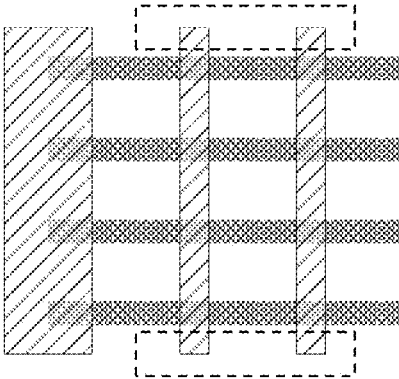


FIG. 41B

invx2

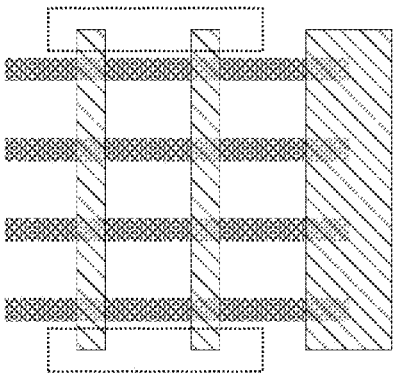


FIG. 41C

invx2

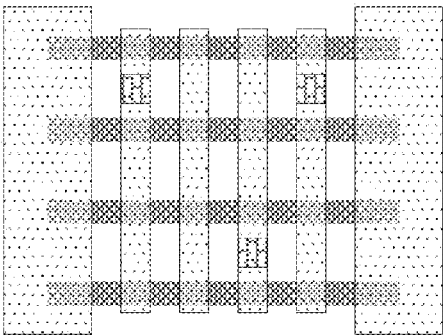


FIG. 41D

invx4

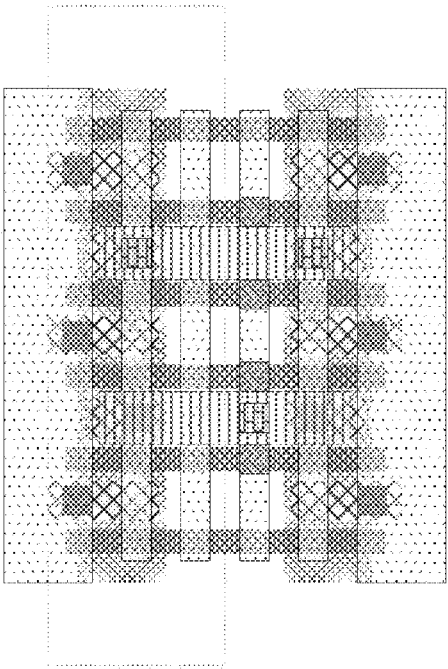


FIG. 42A

invx4

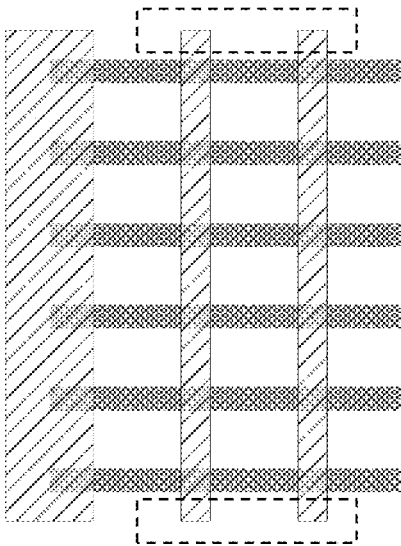


FIG. 42B

invx4

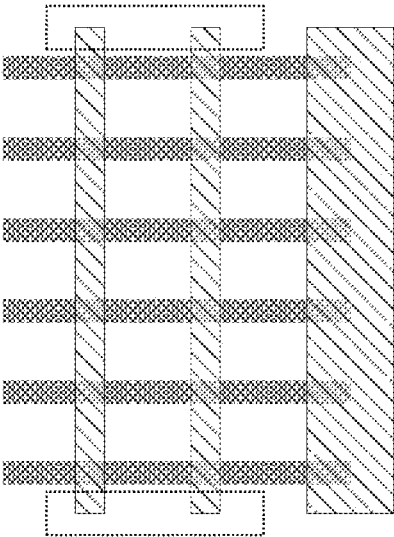


FIG. 42C

invx4

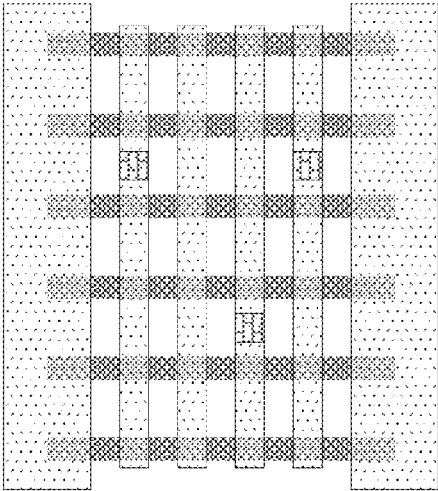


FIG. 42D

invx6

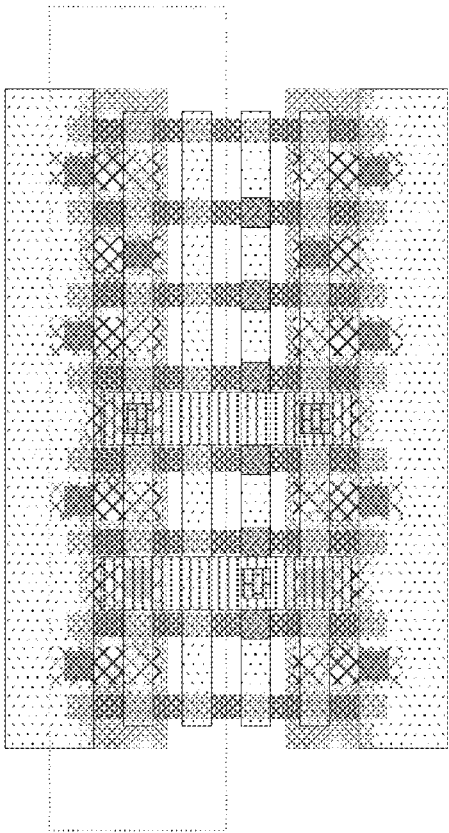


FIG. 43A

invx6

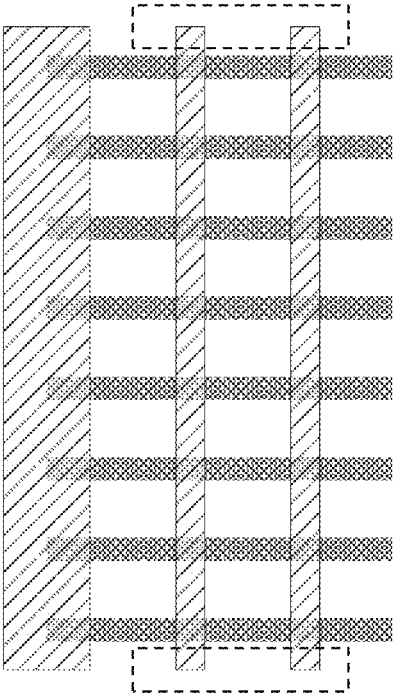


FIG. 43B

invx6

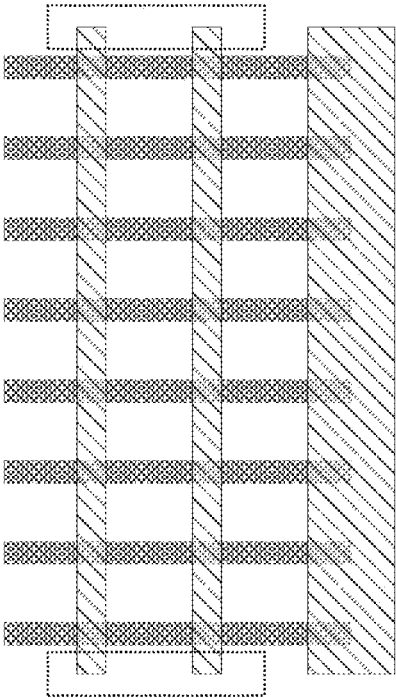


FIG. 43C

invx6

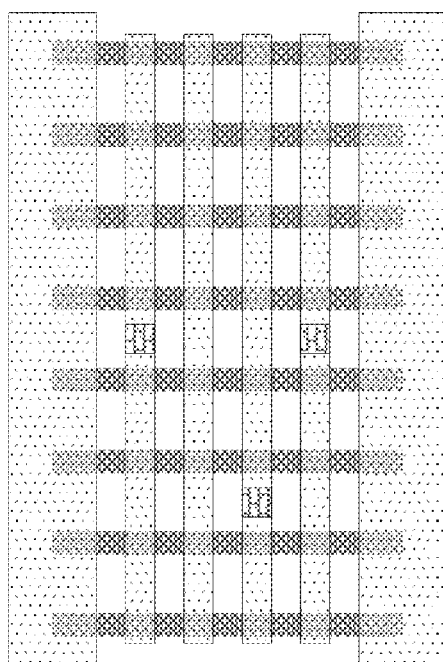


FIG. 43D

invx8

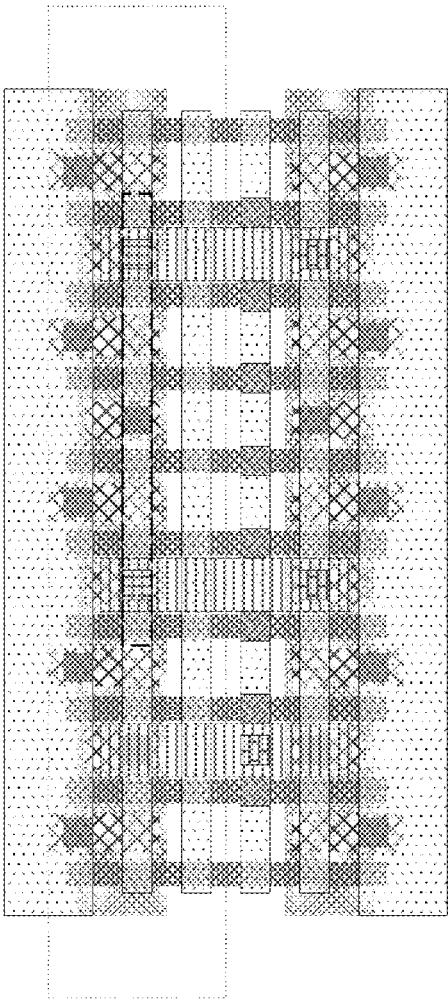


FIG. 44A

invx8

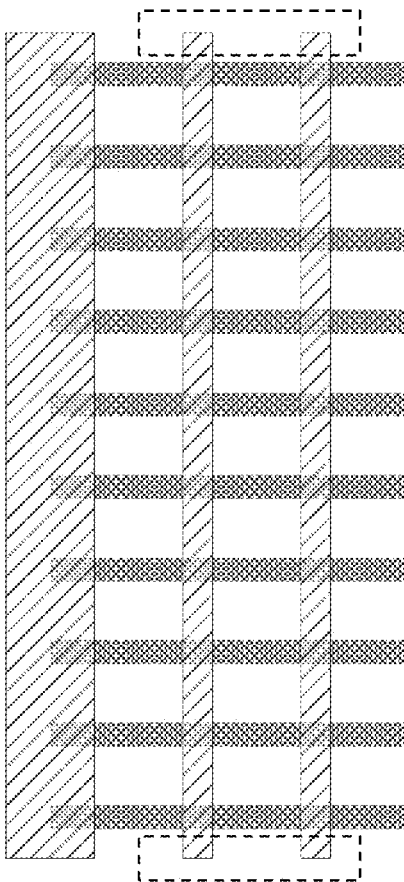


FIG. 44B

invx8

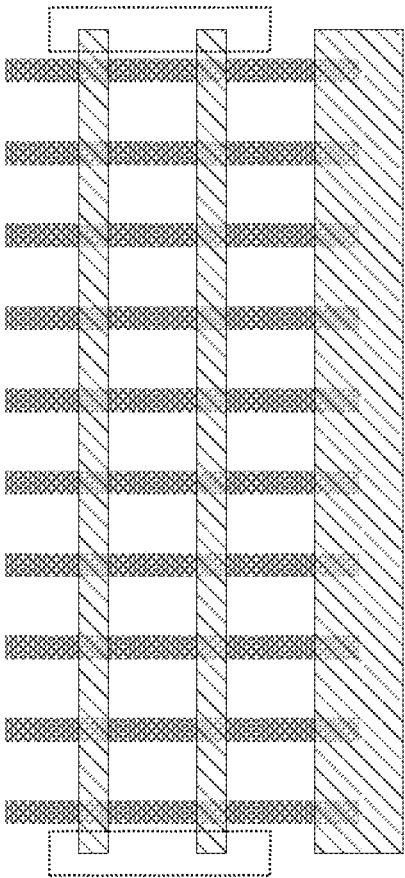


FIG. 44C

invx8

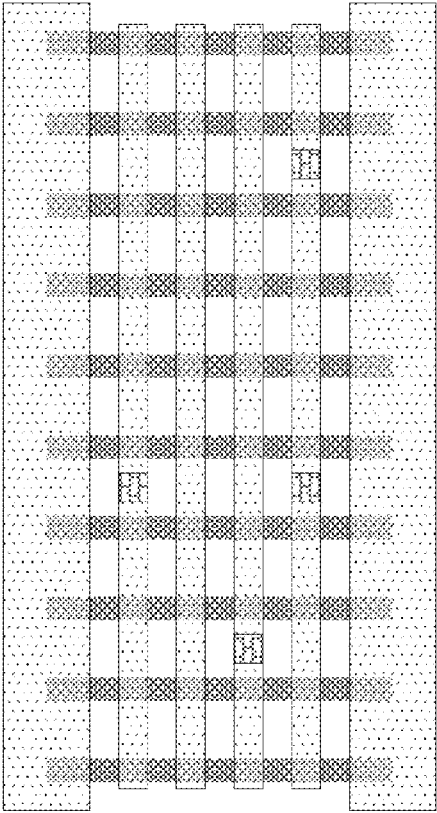


FIG. 44D

ioai21x1

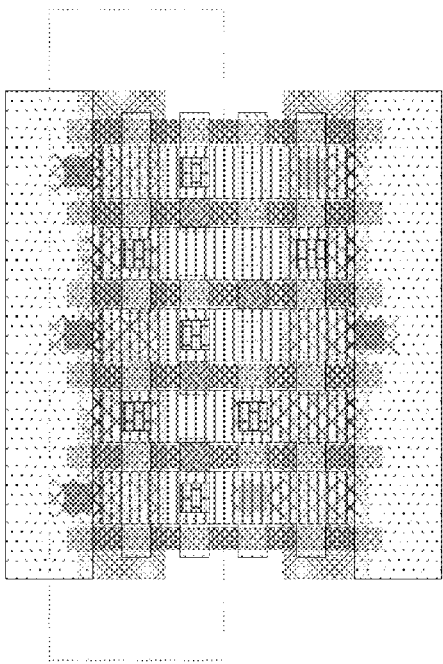


FIG. 45A

ioai21x1

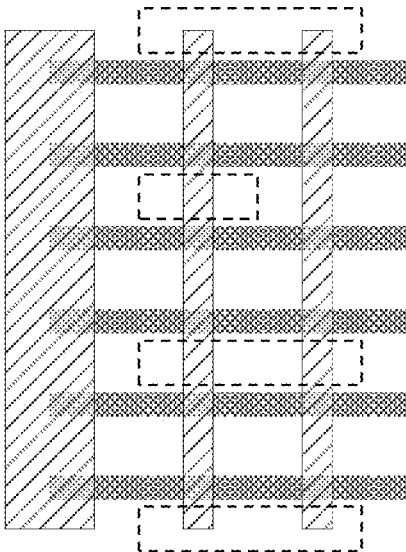


FIG. 45B

ioai21x1

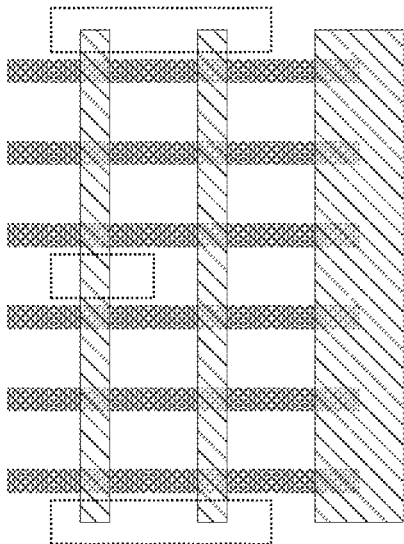


FIG. 45C

ioai21x1

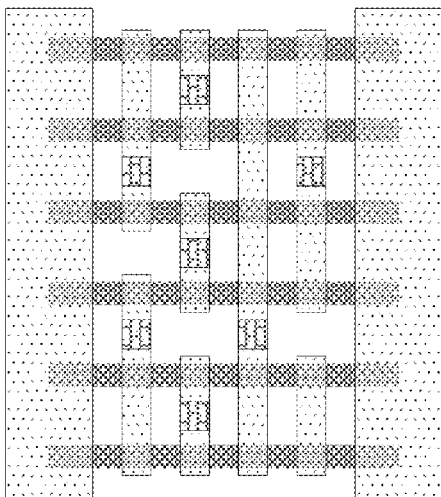


FIG. 45D

latq_x1

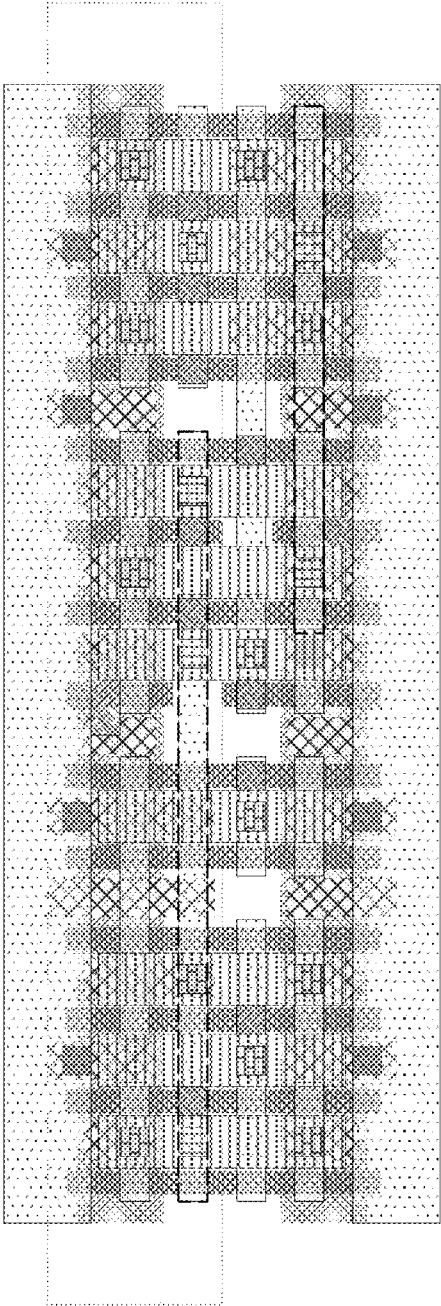


FIG. 46A

latq_x1

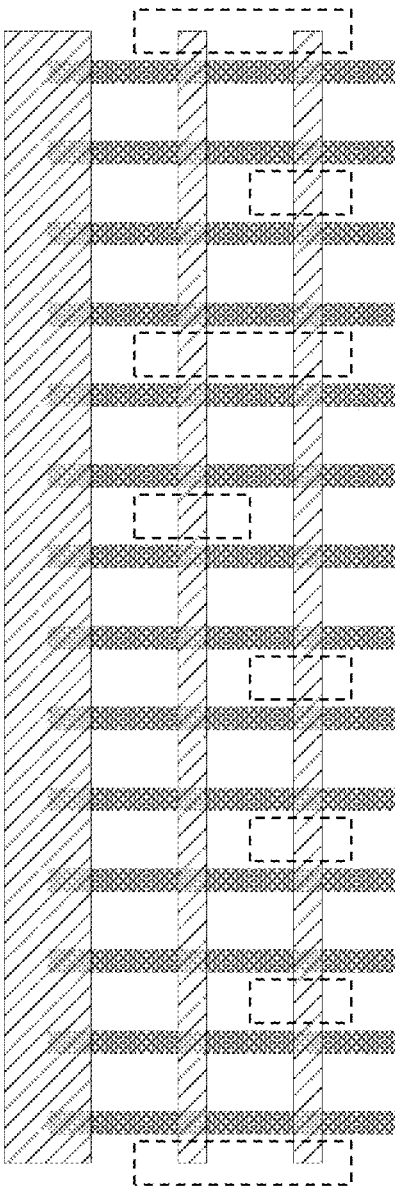


FIG. 46B

latqvx1

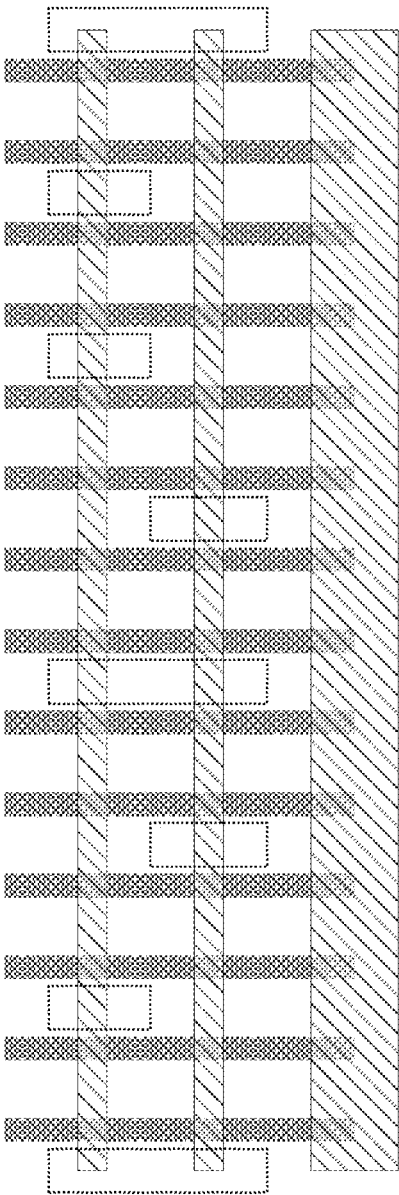


FIG. 46C

latq_x1

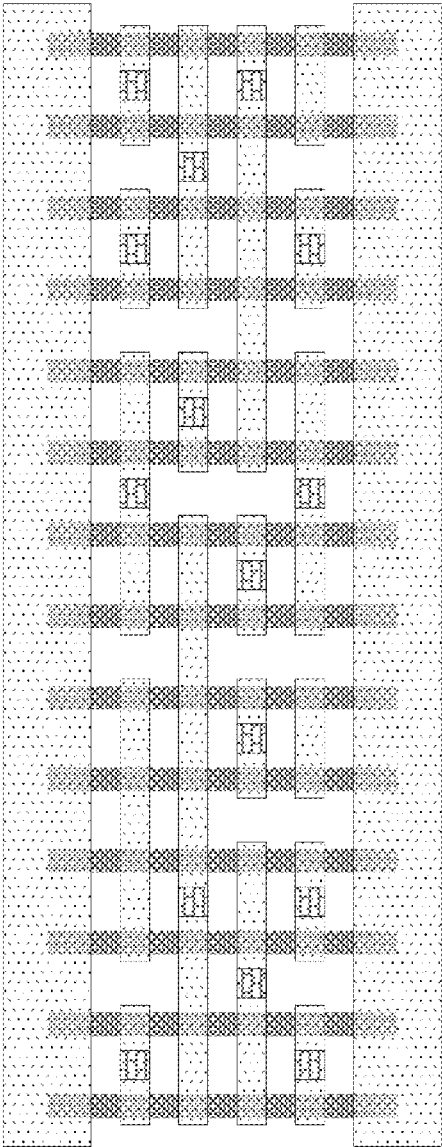


FIG. 46D

mux2x1

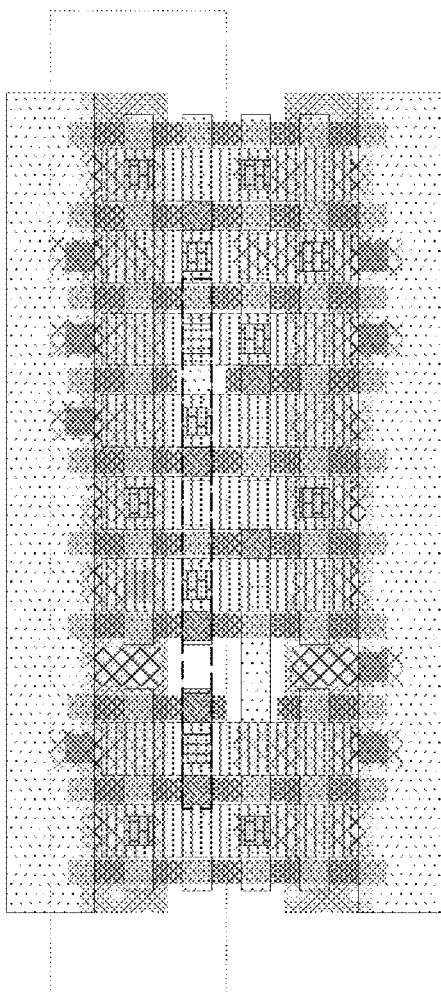


FIG. 47A

mux2x1

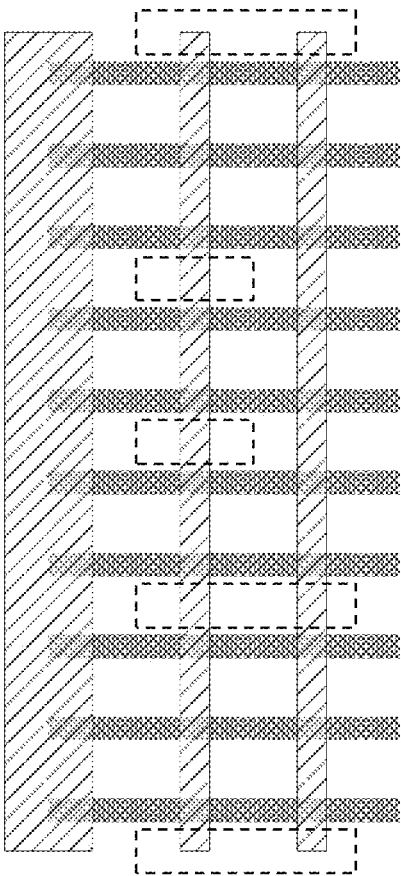


FIG. 47B

mux2x1

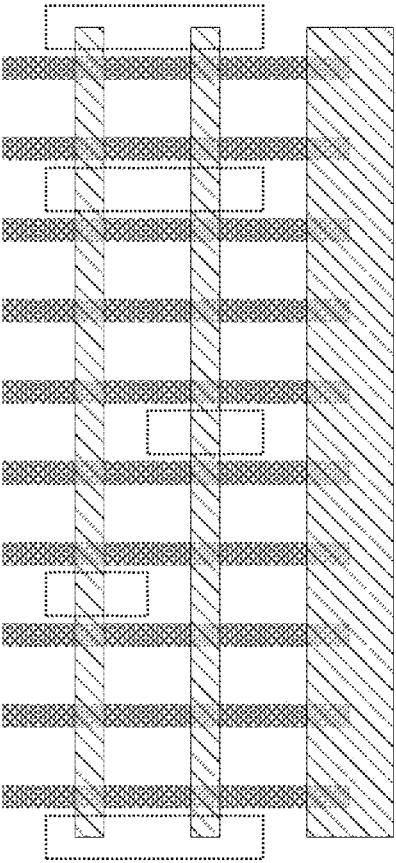


FIG. 47C

mux2x1

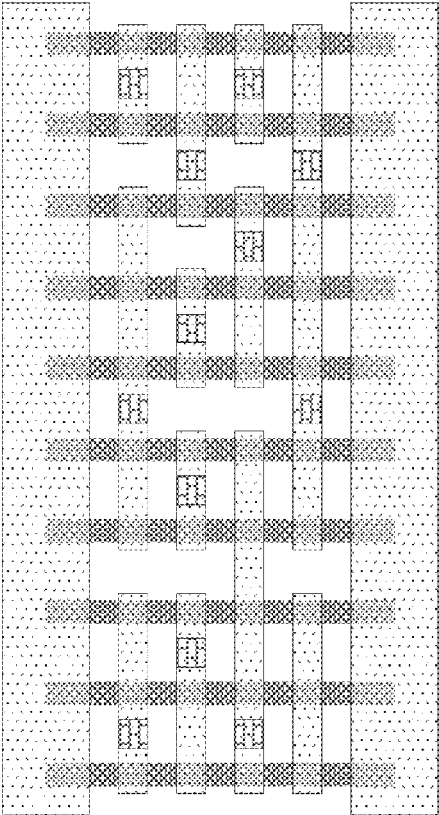


FIG. 47D

mux2x2

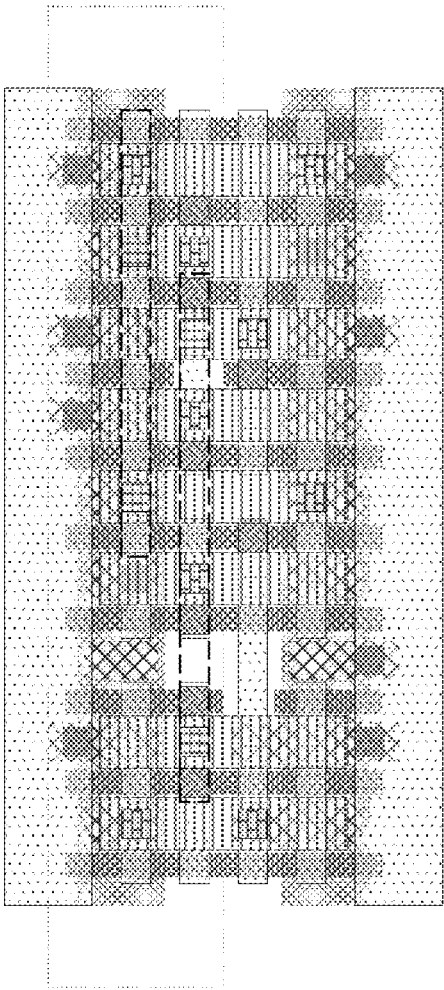


FIG. 48A

mux2x2

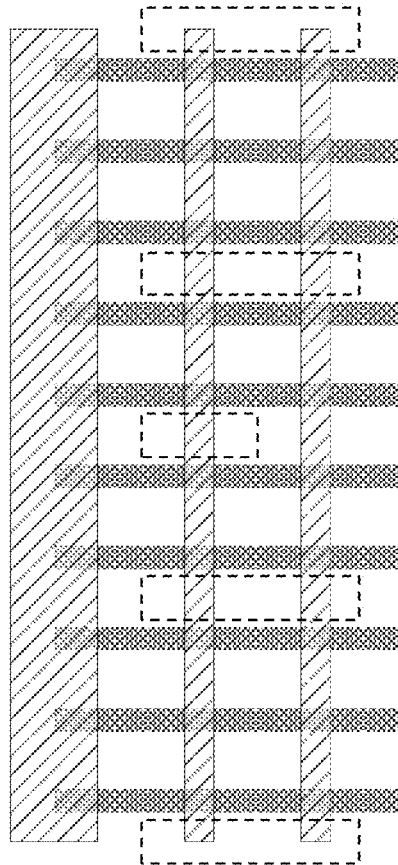


FIG. 48B

mux2x2

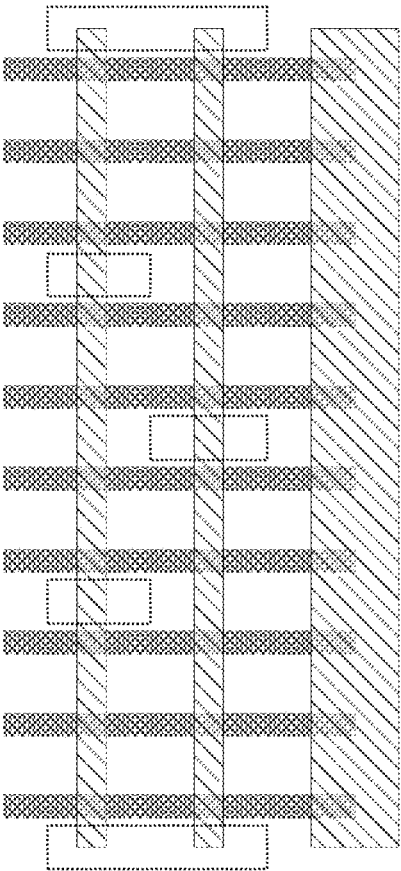


FIG. 48C

mux2x2

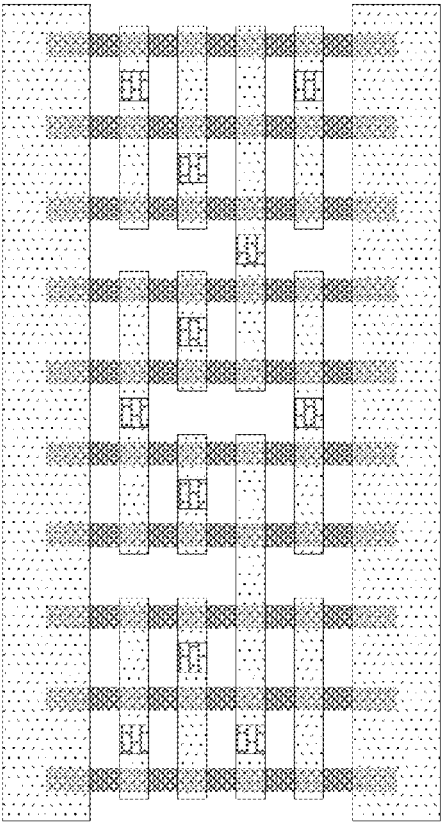


FIG. 48D

muxi2x1

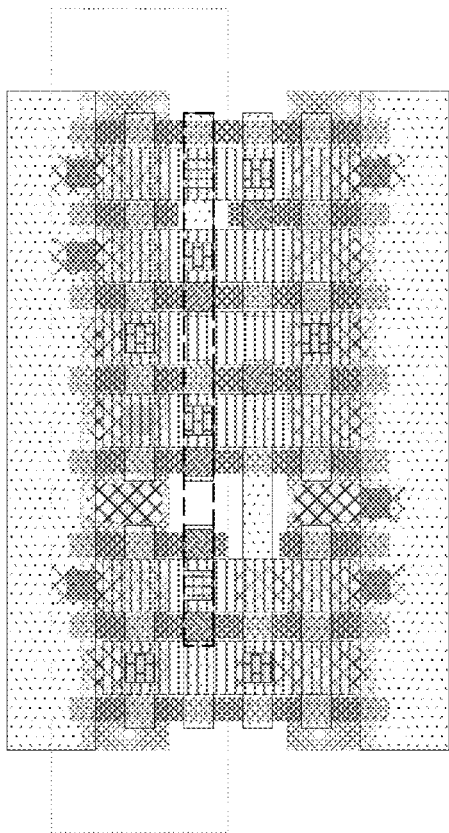


FIG. 49A

muxi2x1

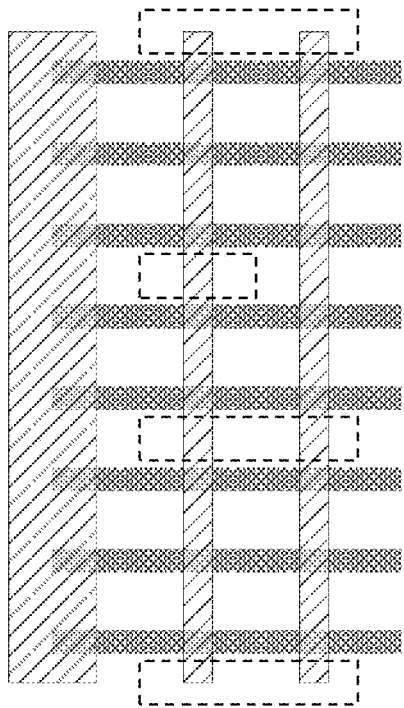


FIG. 49B

muxi2x1

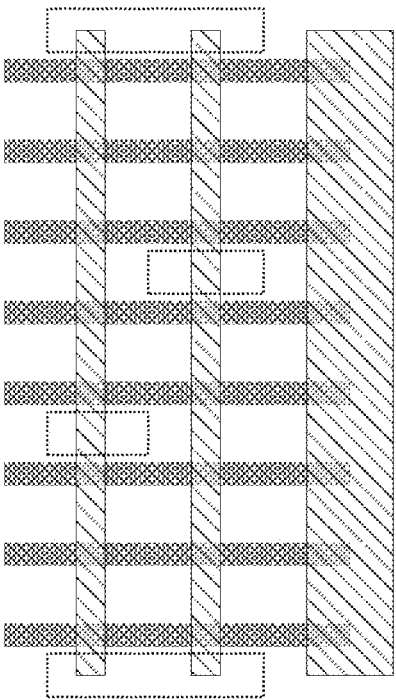


FIG. 49C

muxi2x1

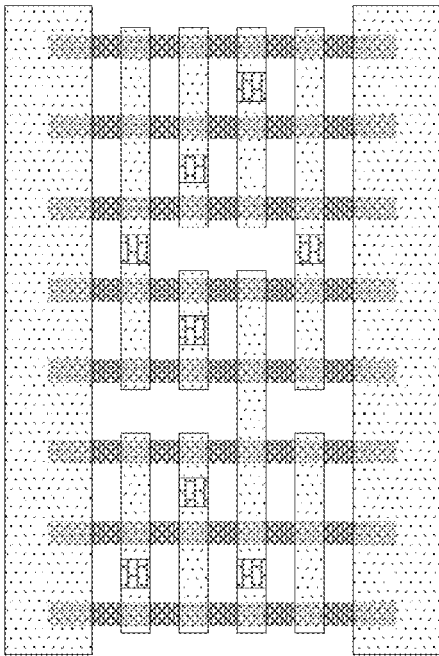


FIG. 49D

nd2x1

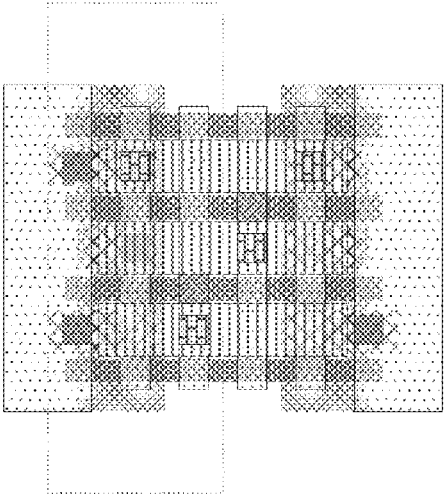


FIG. 50A

nd2x1

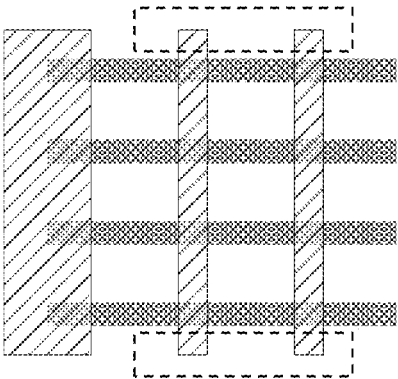


FIG. 50B

nd2x1

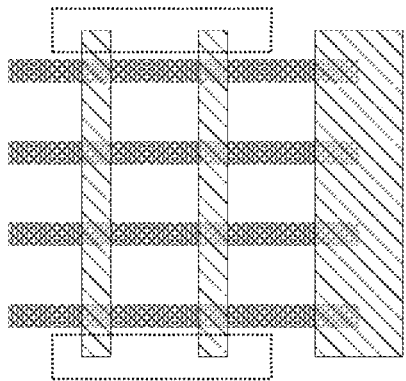


FIG. 50C

nd2x1

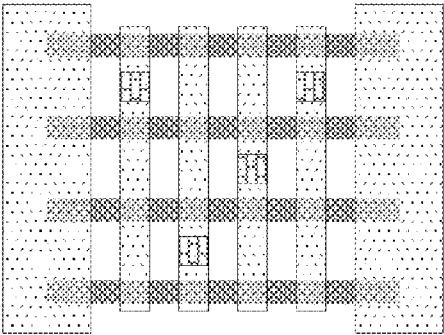


FIG. 50D

nd2x2

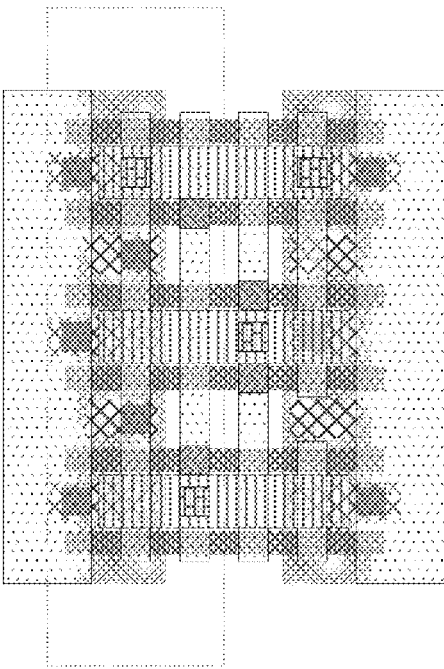


FIG. 51A

nd2x2

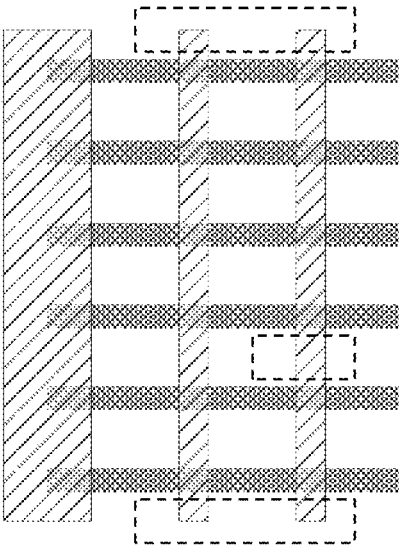


FIG. 51B

nd2x2

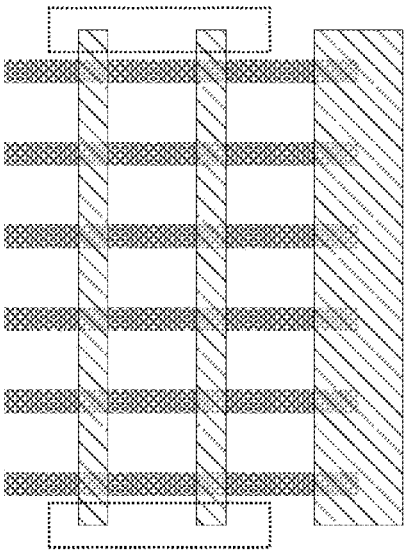


FIG. 51C

nd2x2

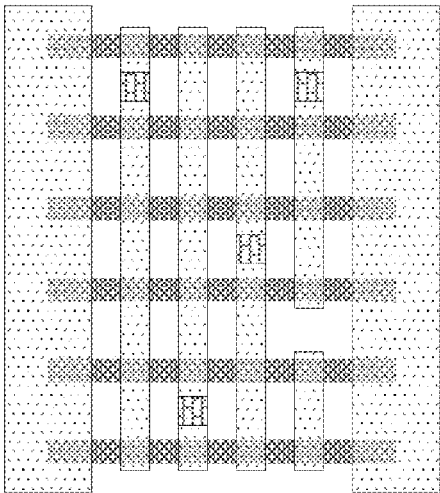


FIG. 51D

nd2x3

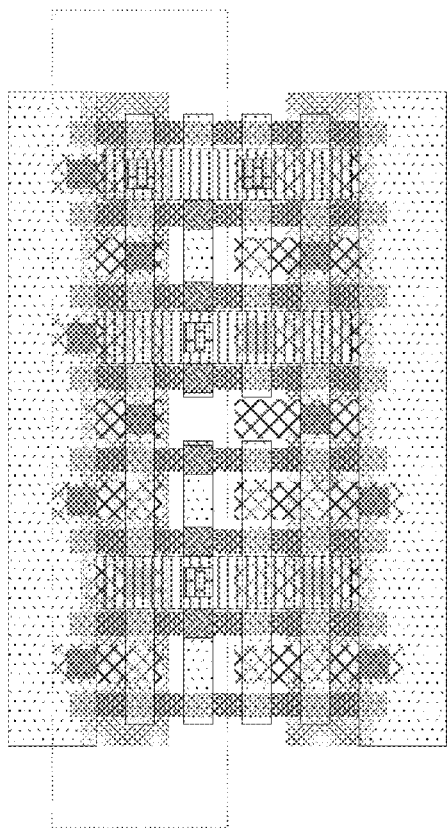


FIG. 52A

nd2x3

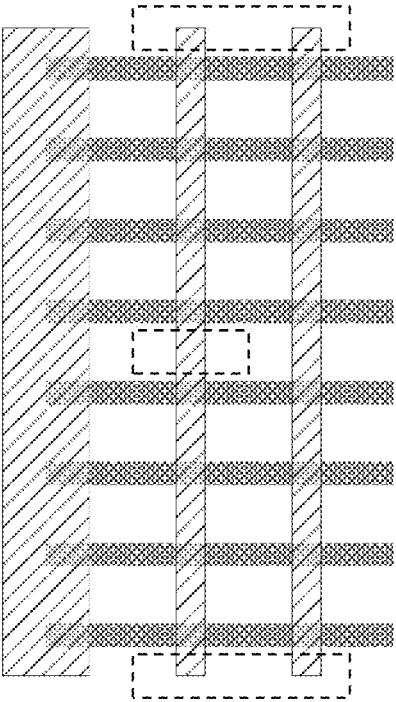


FIG. 52B

nd2x3

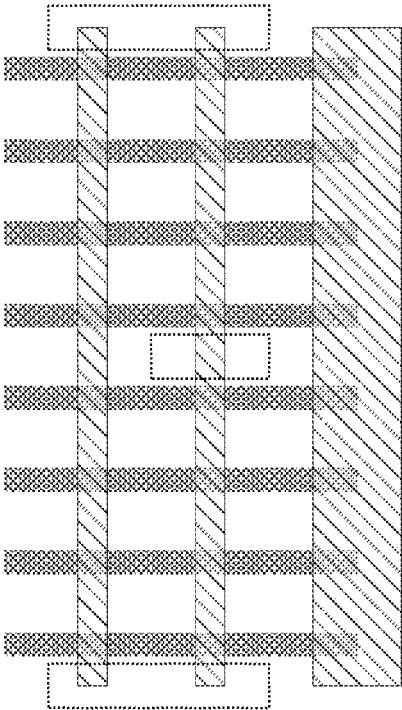


FIG. 52C

nd2x3

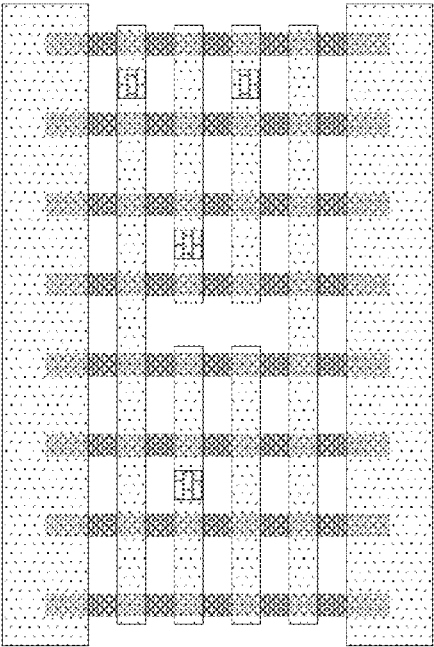


FIG. 52D

nd2x4

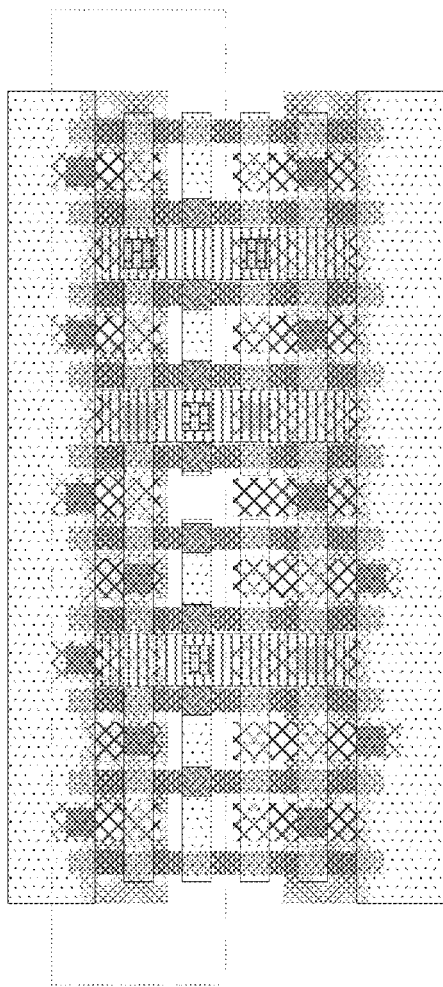


FIG. 53A

nd2x4

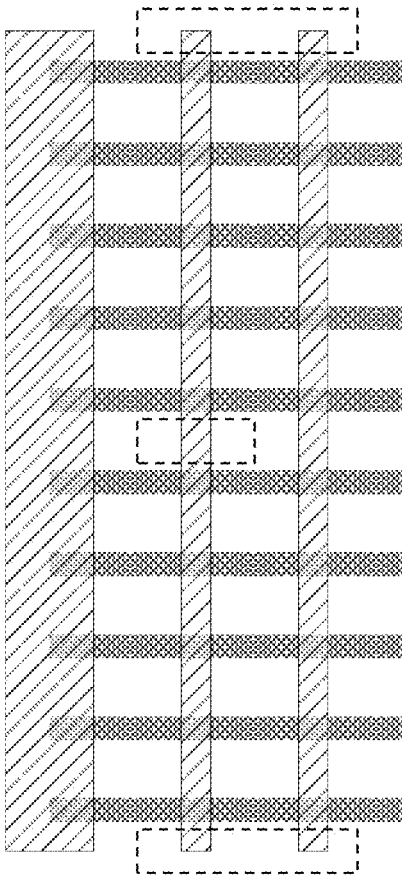


FIG. 53B

nd2x4

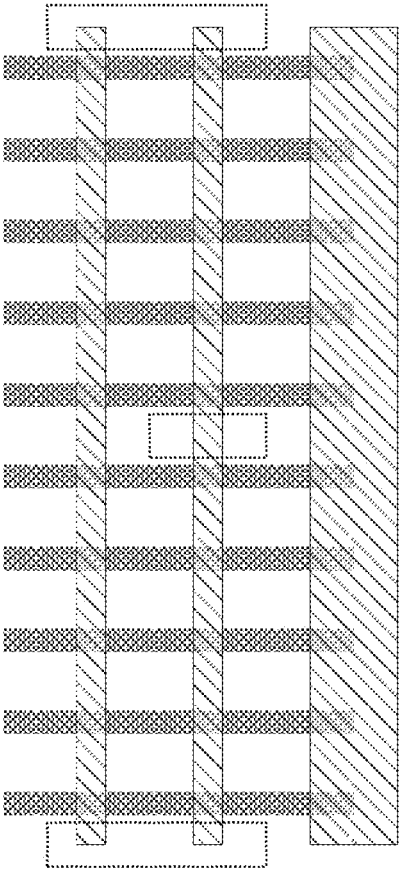


FIG. 53C

nd2x4

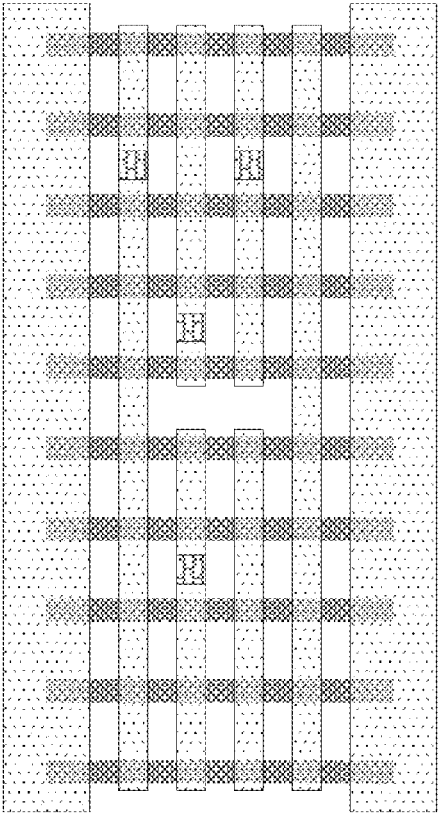


FIG. 53D

nd3x1

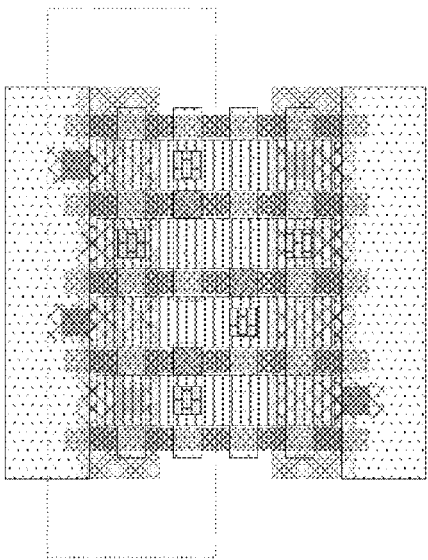


FIG. 54A

nd3x1

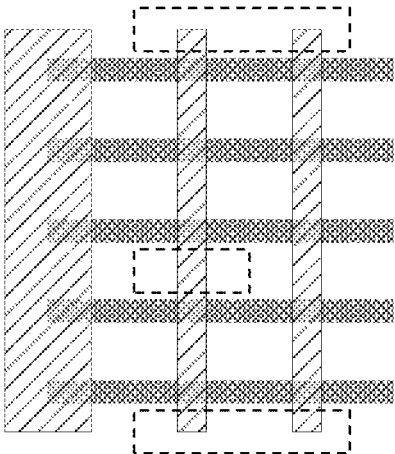


FIG. 54B

nd3x1

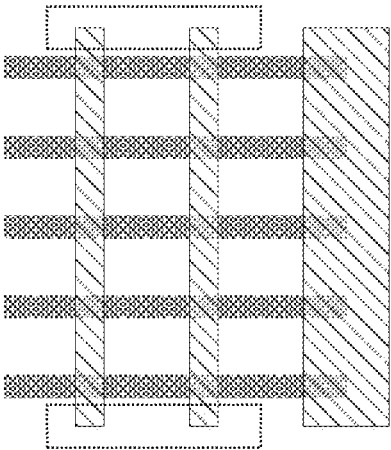


FIG. 54C

nd3x1

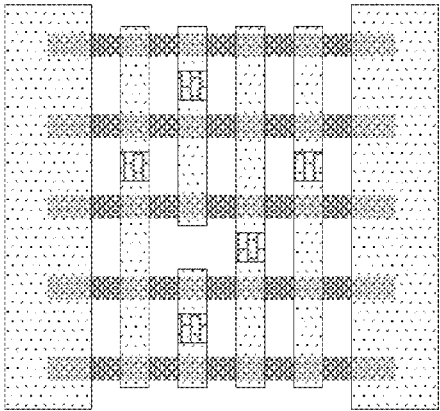


FIG. 54D

nd3x2

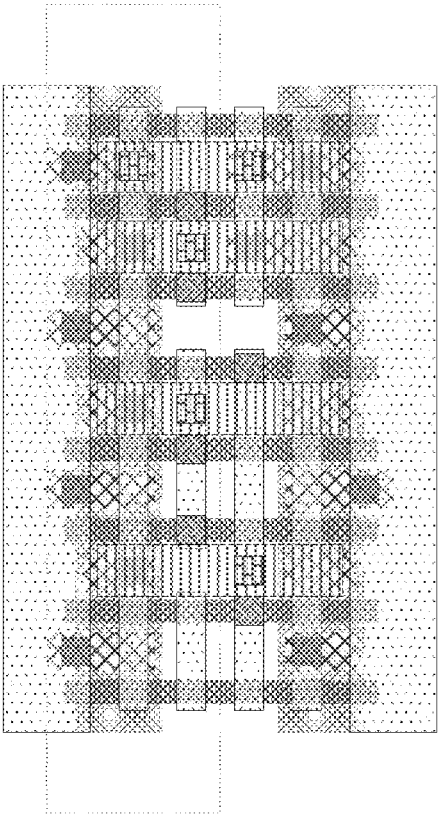


FIG. 55A

nd3x2

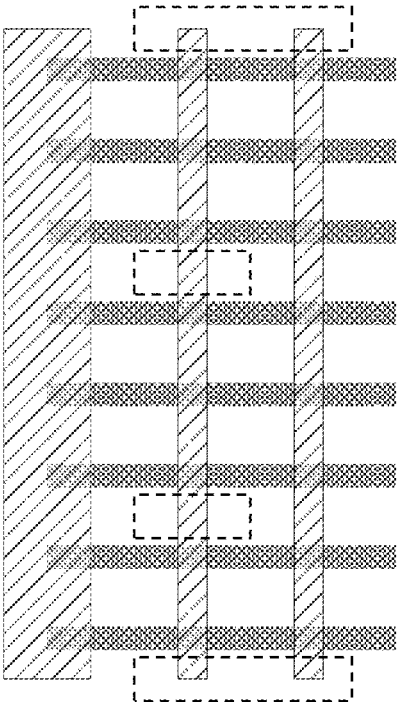


FIG. 55B

nd3x2

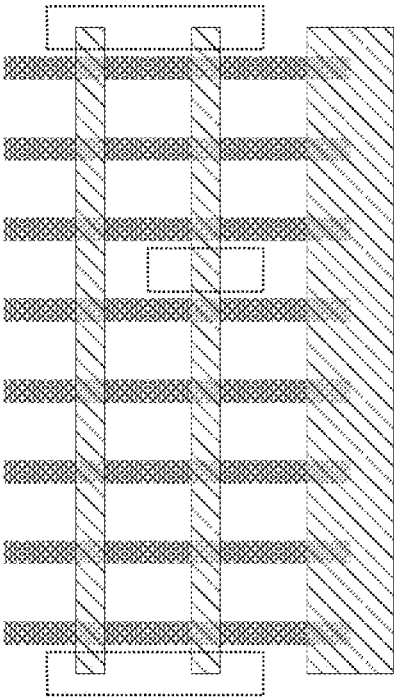


FIG. 55C

nd3x2

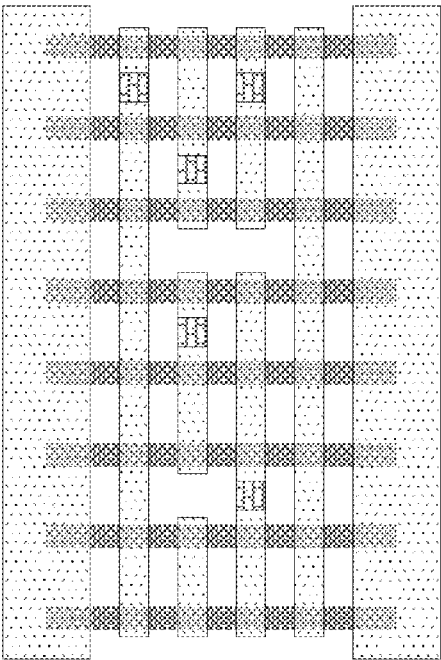


FIG. 55D

nd3x3

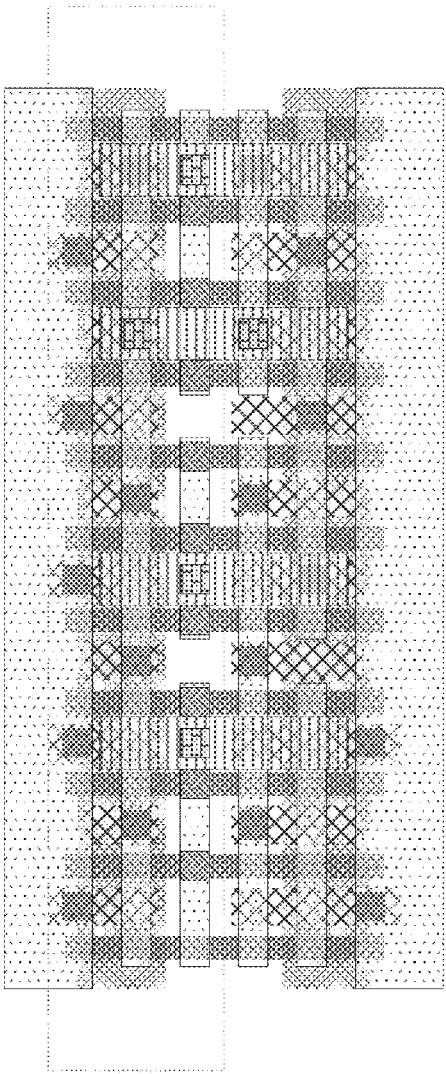


FIG. 56A

nd3x3

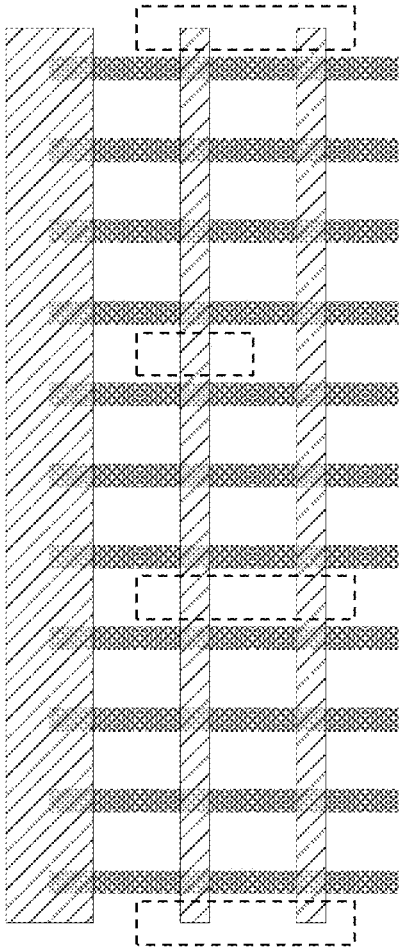


FIG. 56B

nd3x3

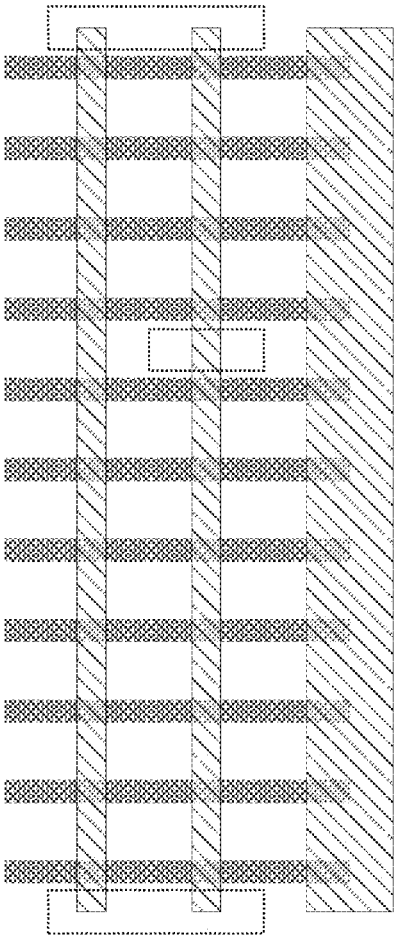


FIG. 56C

nd3x3

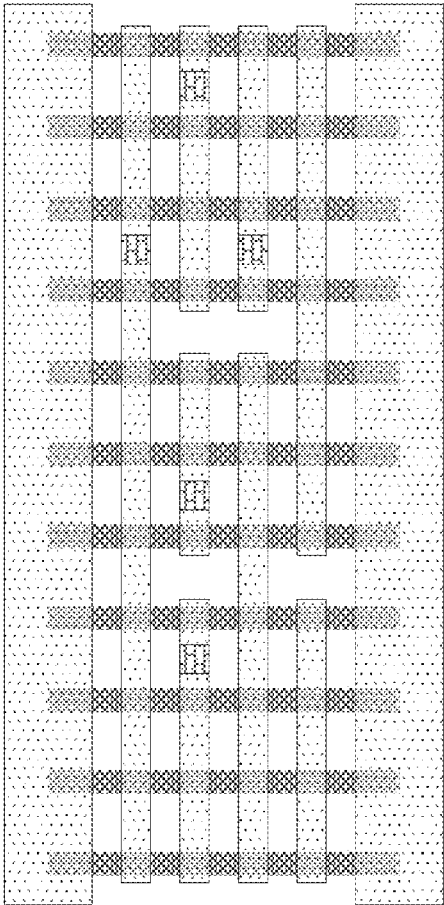


FIG. 56D

nd3x4

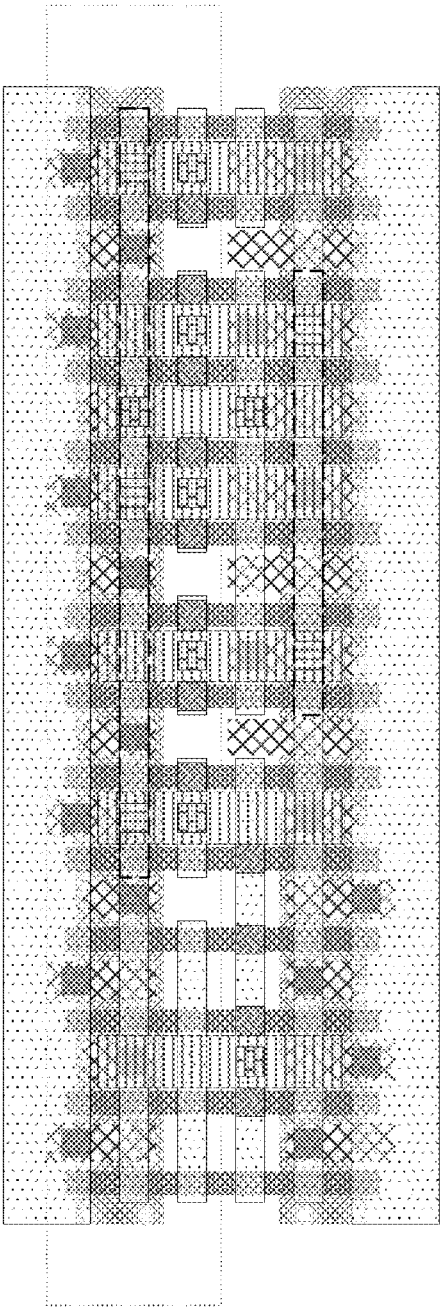


FIG. 57A

nd3x4

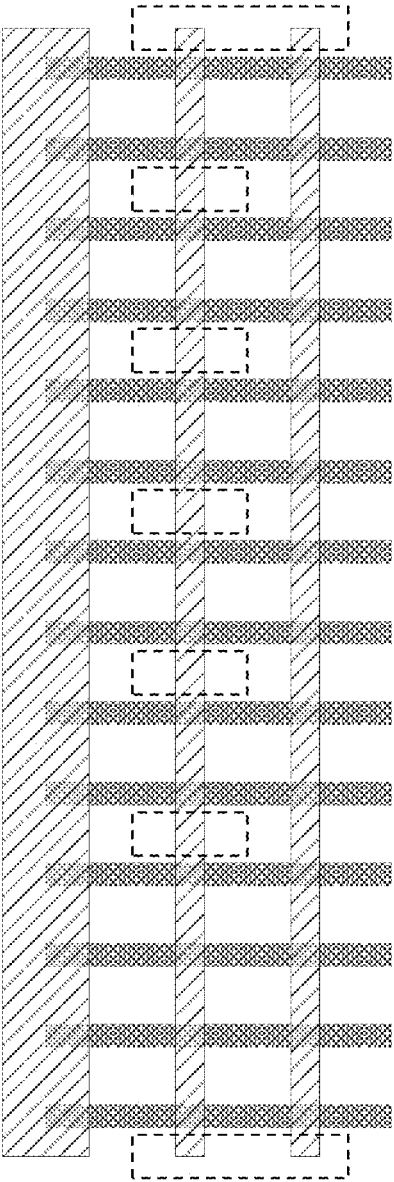


FIG. 57B

nd3x4

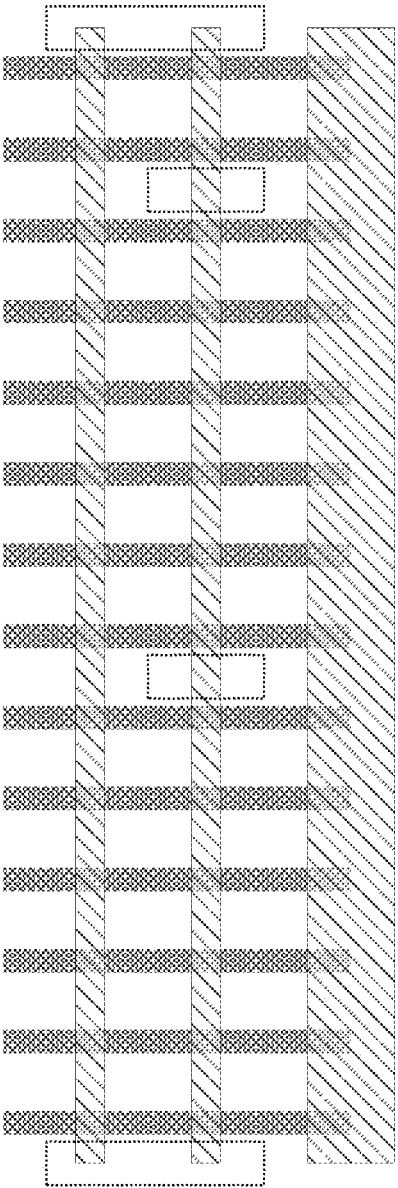


FIG. 57C

nd3x4

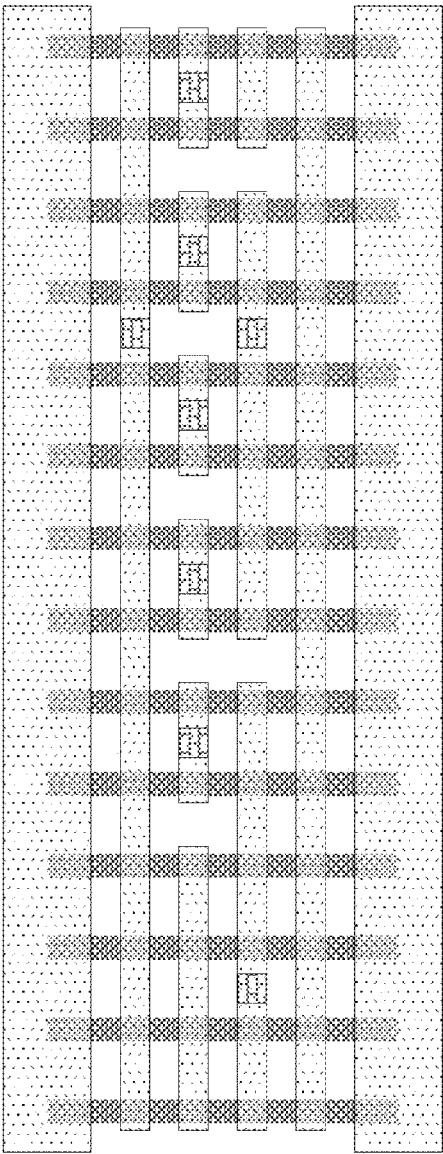


FIG. 57D

nd4x1

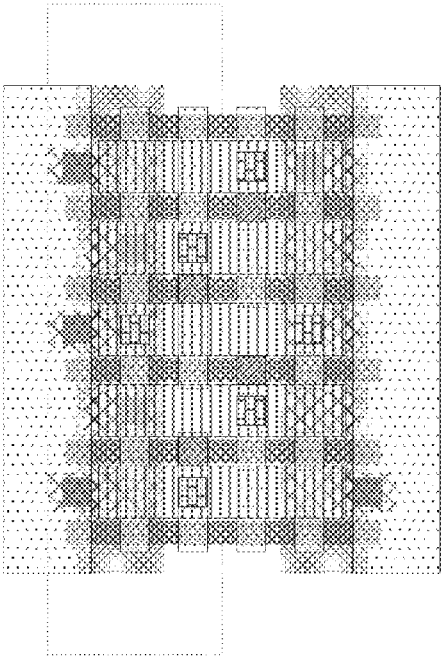


FIG. 58A

nd4x1

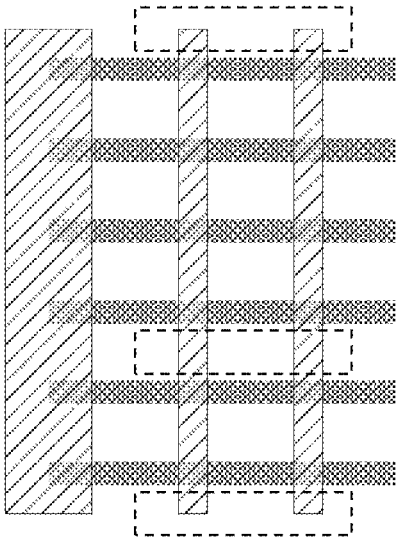


FIG. 58B

nd4x1

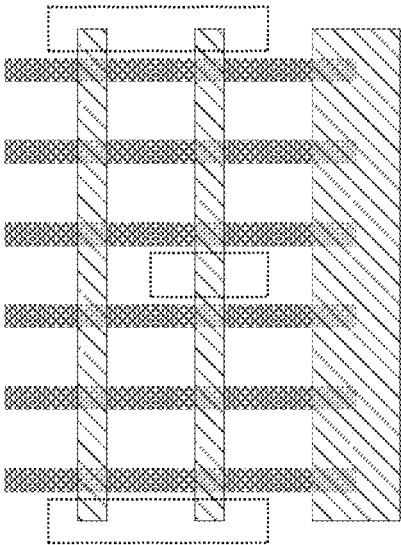


FIG. 58C

nd4x1

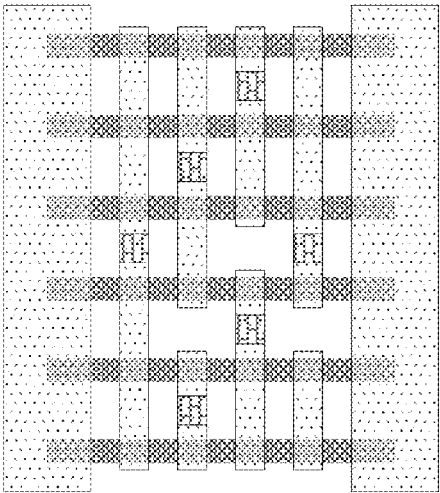


FIG. 58D

nd4x2

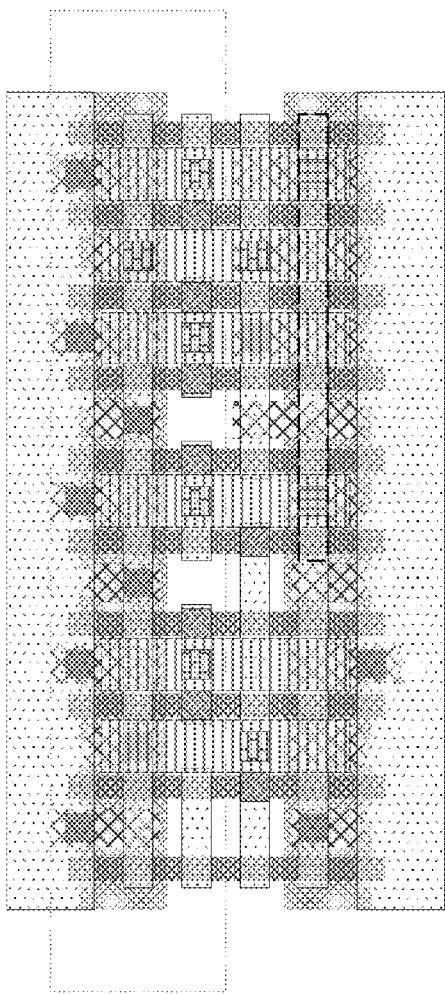


FIG. 59A

nd4x2

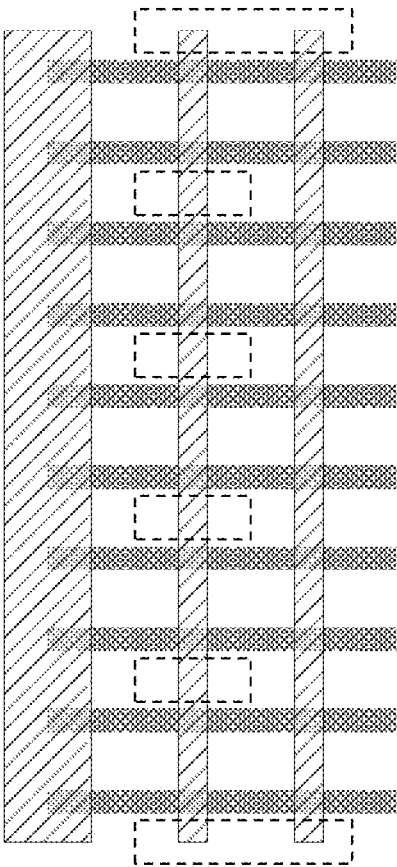


FIG. 59B

nd4x2

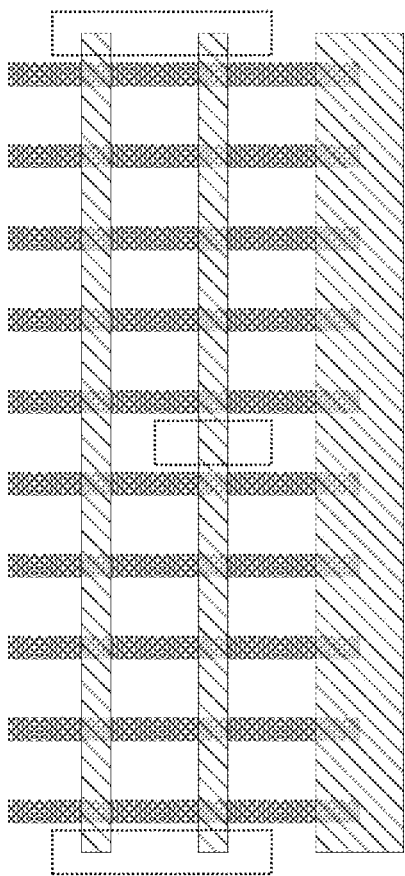


FIG. 59C

nd4x2

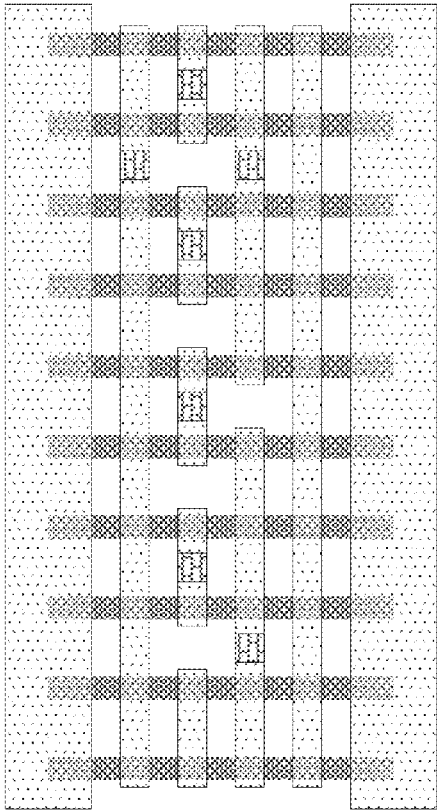


FIG. 59D

nr2x1

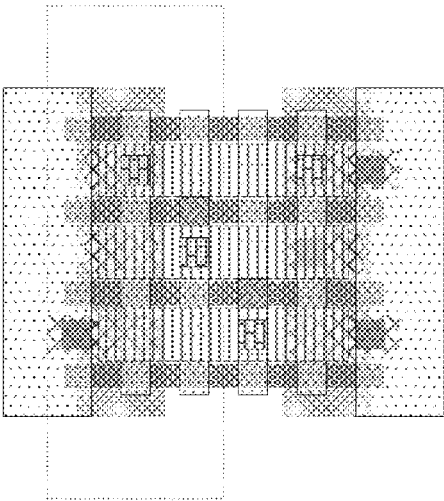


FIG. 60A

nr2x1

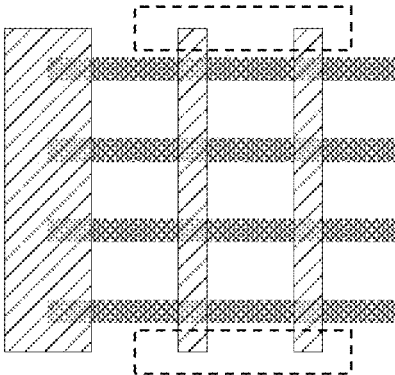


FIG. 60B

nr2x1

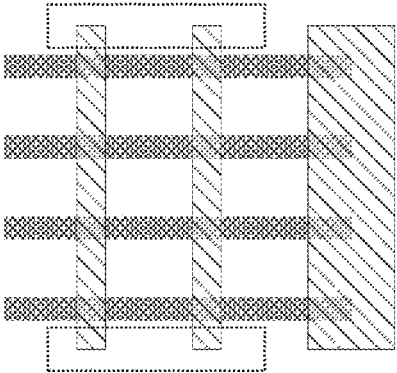


FIG. 60C

nr2x1

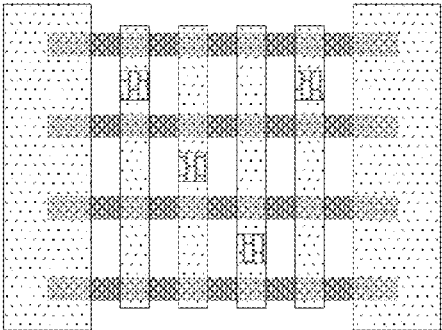


FIG. 60D

nr2x2

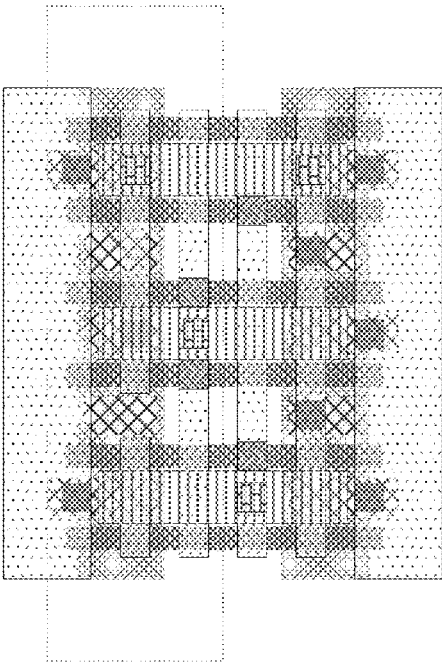


FIG. 61A

nr2x2

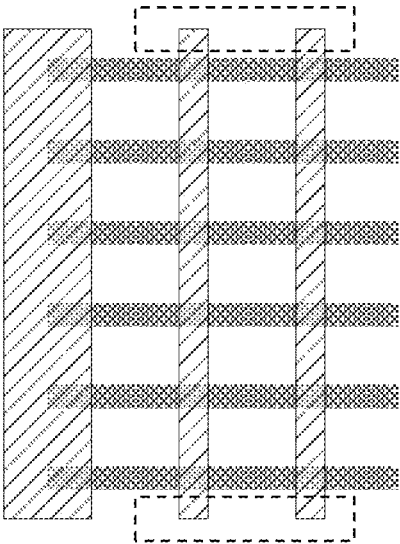


FIG. 61B

nr2x2

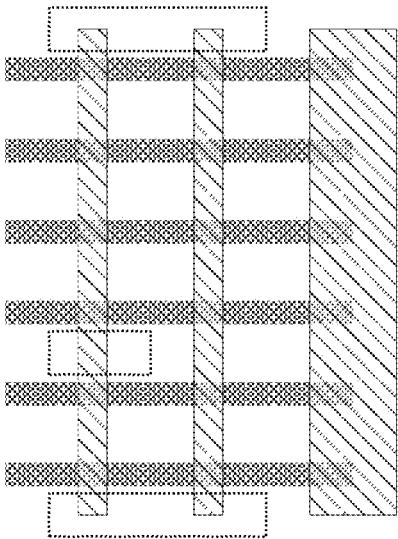


FIG. 61C

nr2x2

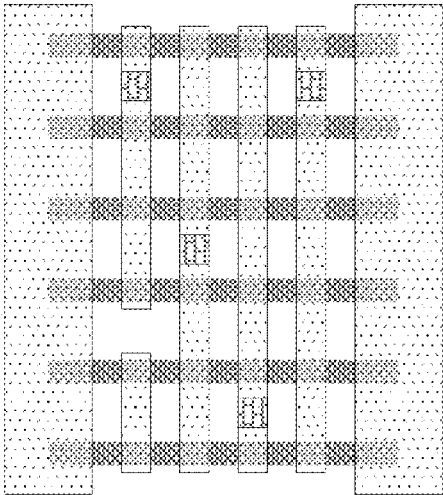


FIG. 61D

nr2x3

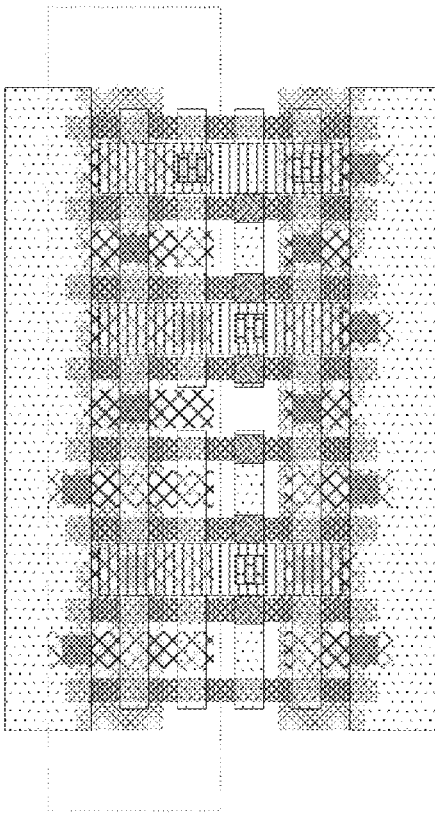


FIG. 61.1A

nr2x3

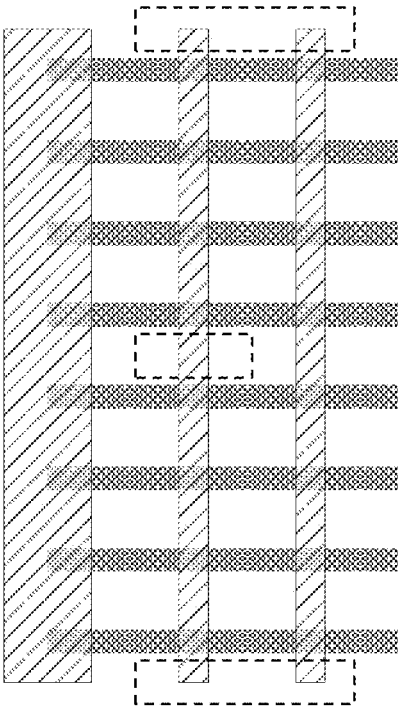


FIG. 61.1B

nr2x3

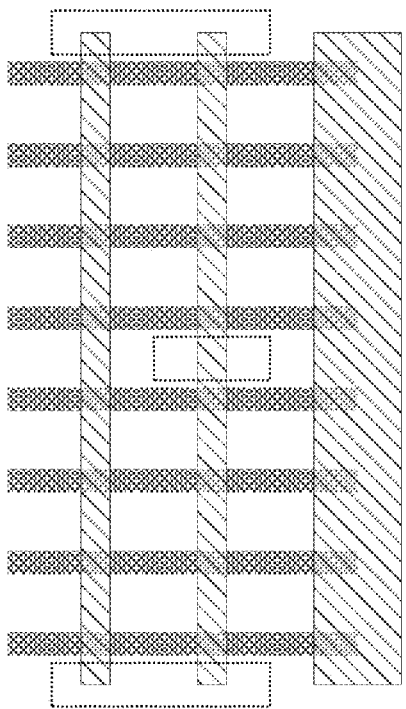


FIG. 61.1C

nr2x3

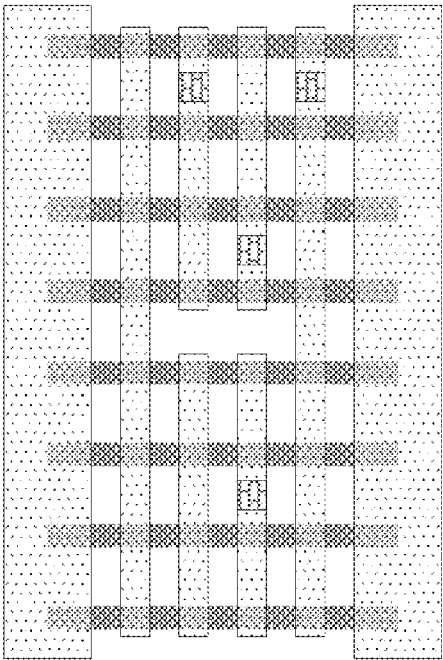


FIG. 61.1D

nr2x4

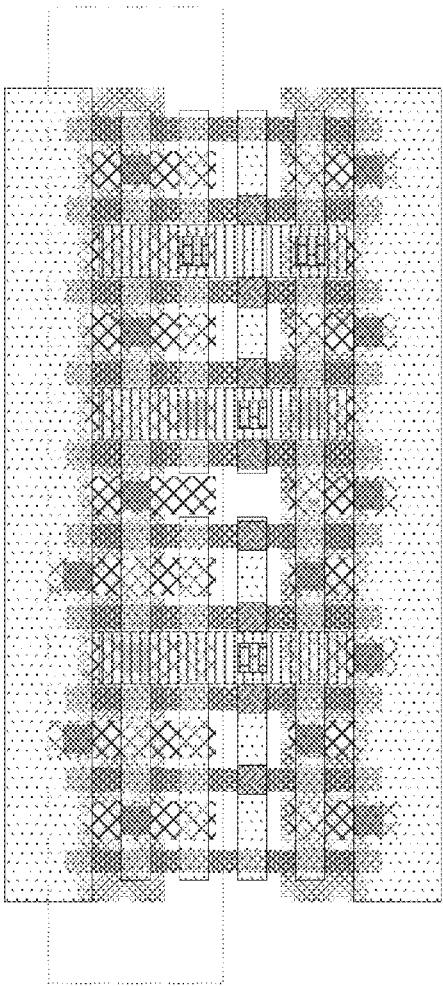


FIG. 62A

nr2x4

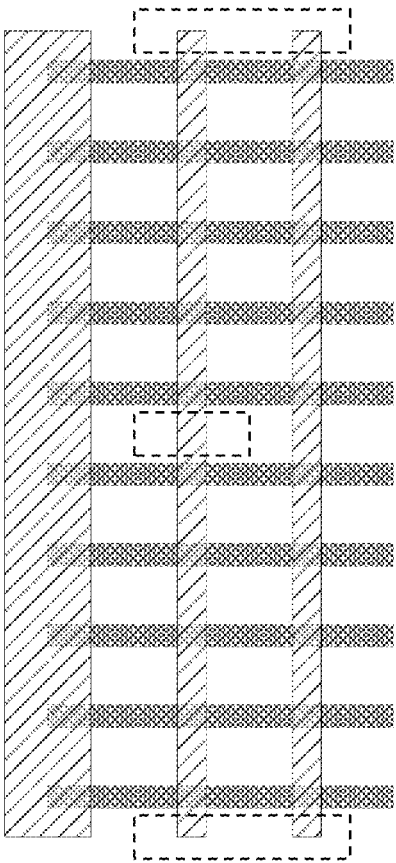


FIG. 62B

nr2x4

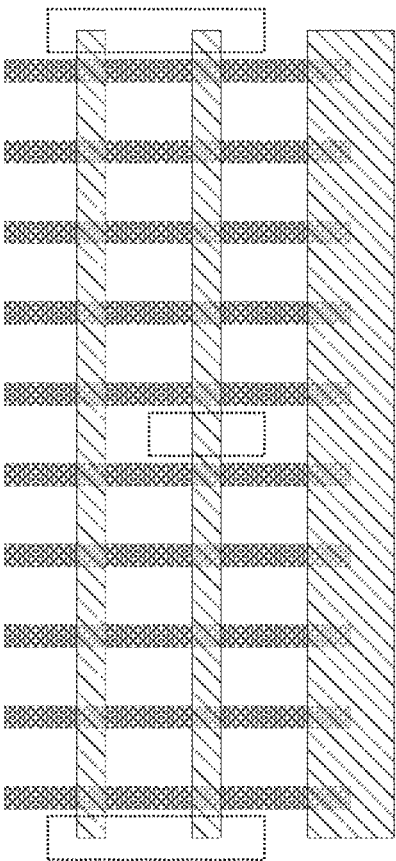


FIG. 62C

nr2x4

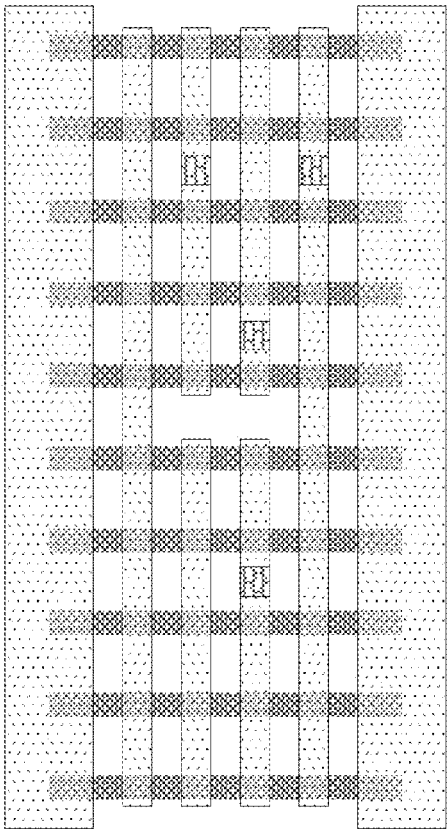


FIG. 62D

nr3x1

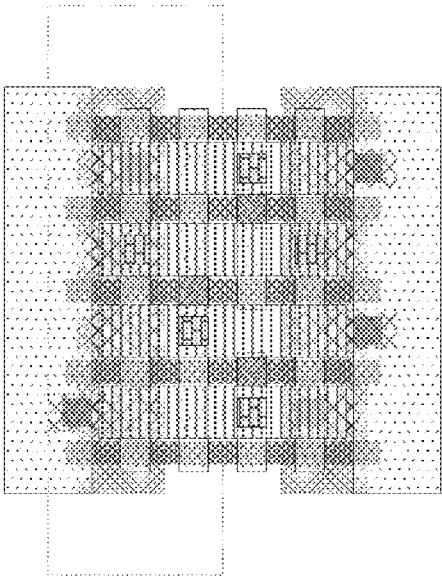


FIG. 63A

nr3x1

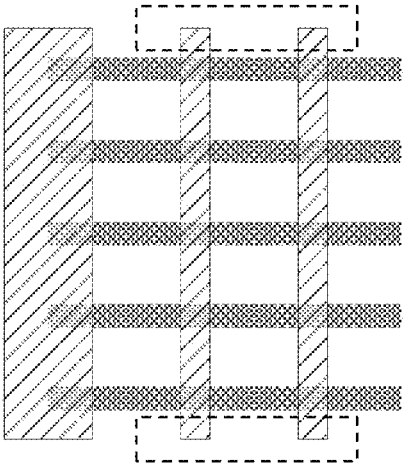


FIG. 63B

nr3x1

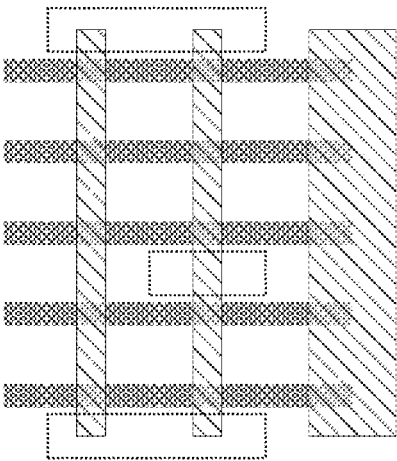


FIG. 63C

nr3x1

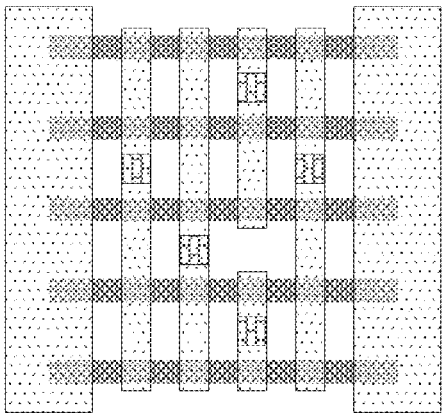


FIG. 63D

nr3x2

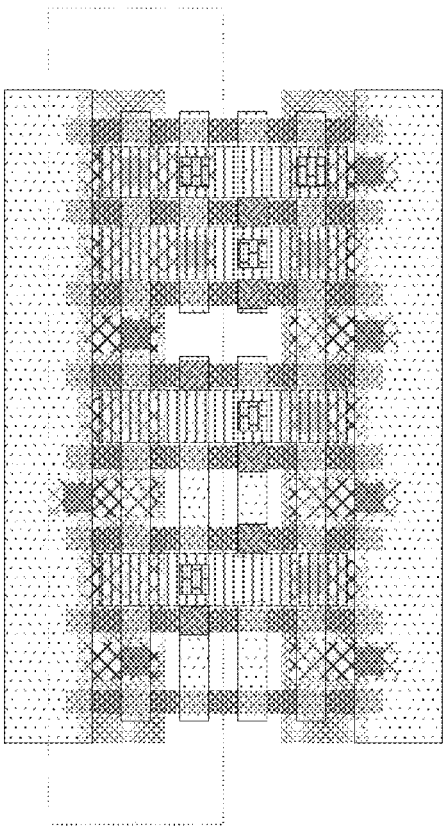


FIG. 64A

nr3x2

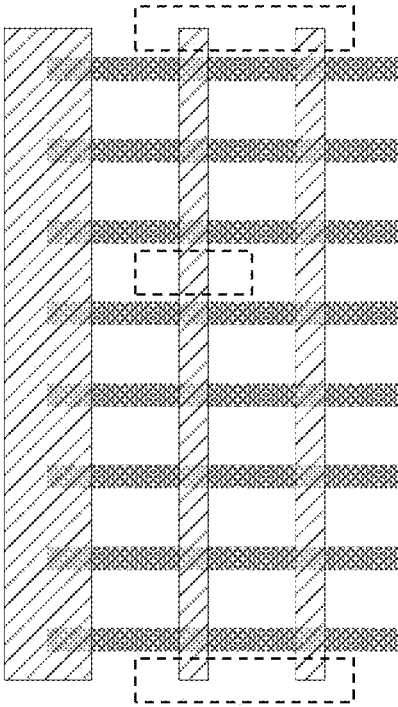


FIG. 64B

nr3x2

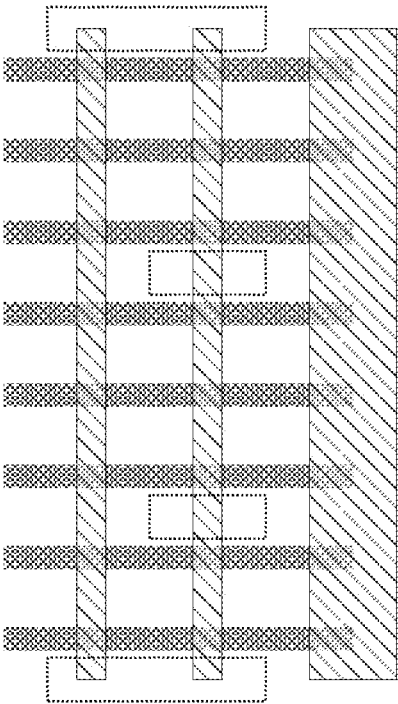


FIG. 64C

nr3x2

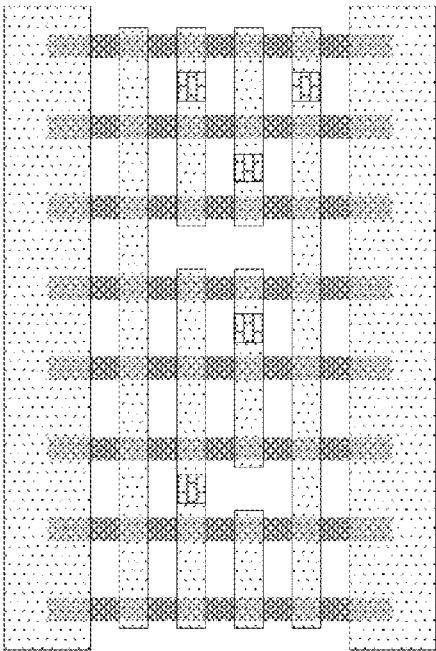


FIG. 64D

nr3x3

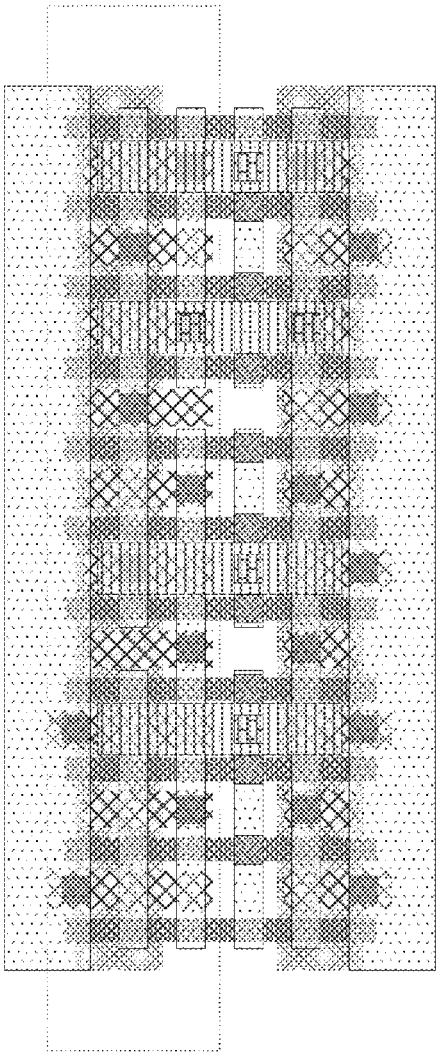


FIG. 65A

nr3x3

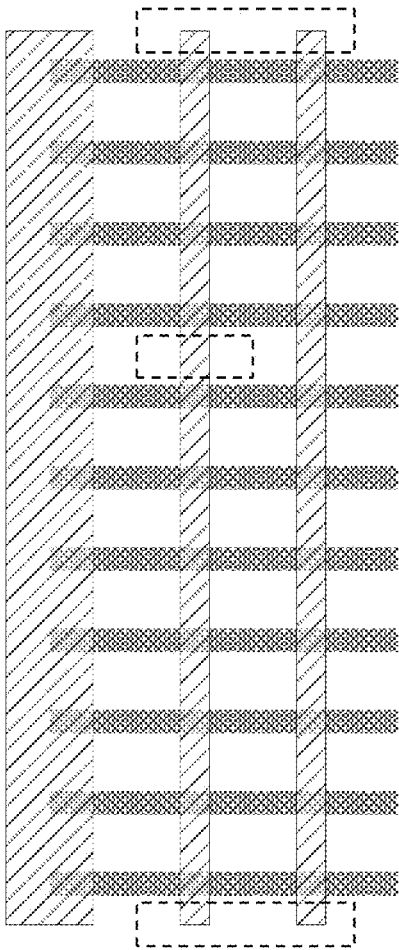


FIG. 65B

nr3x3

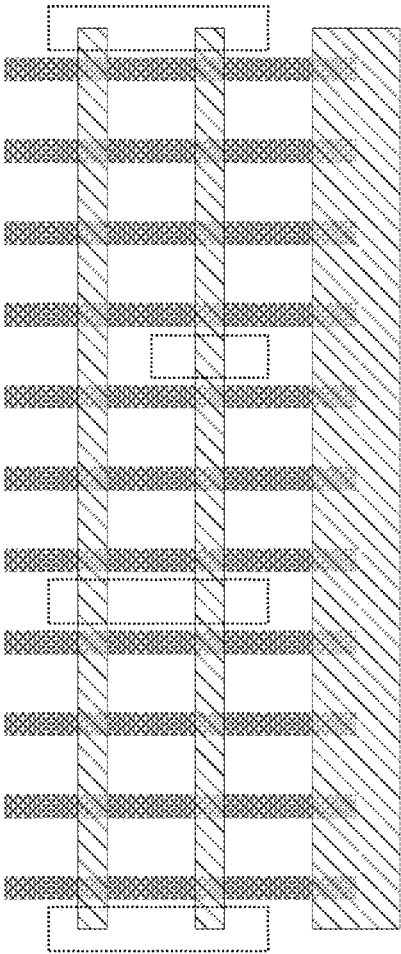


FIG. 65C

nr3x3

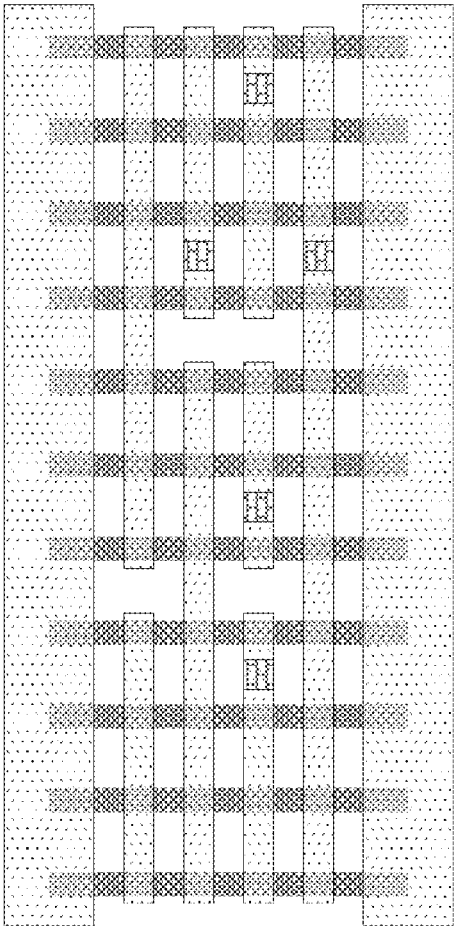


FIG. 65D

nr3x4

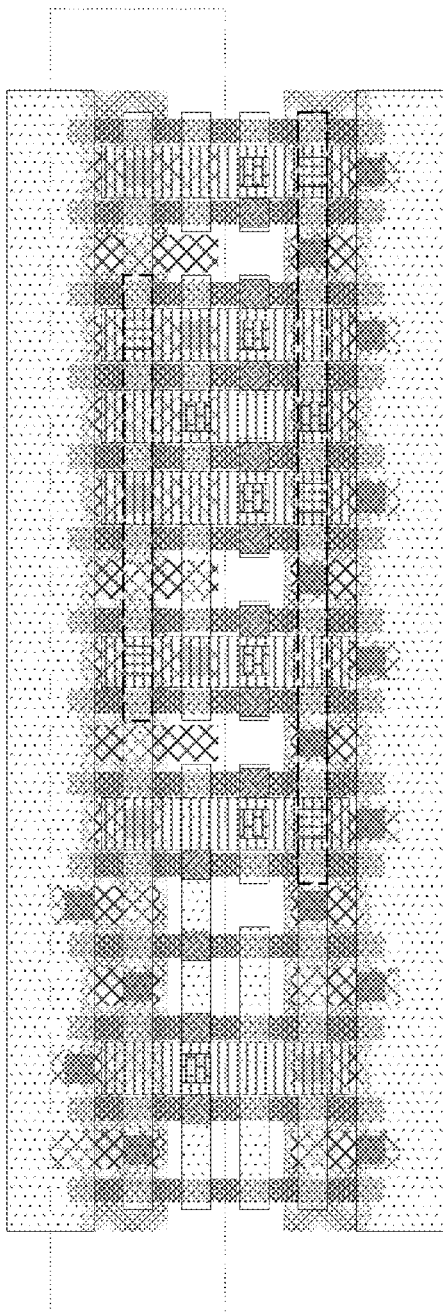


FIG. 66A

nr3x4

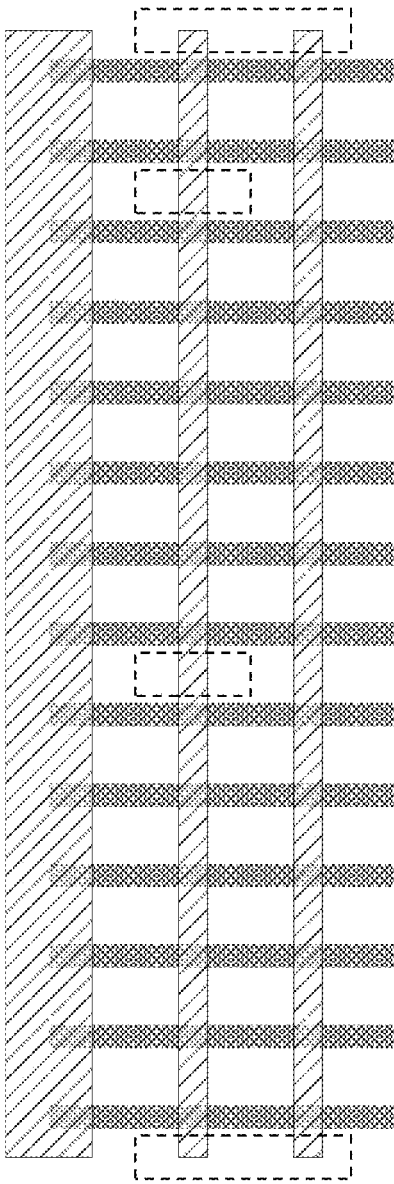


FIG. 66B

nr3x4

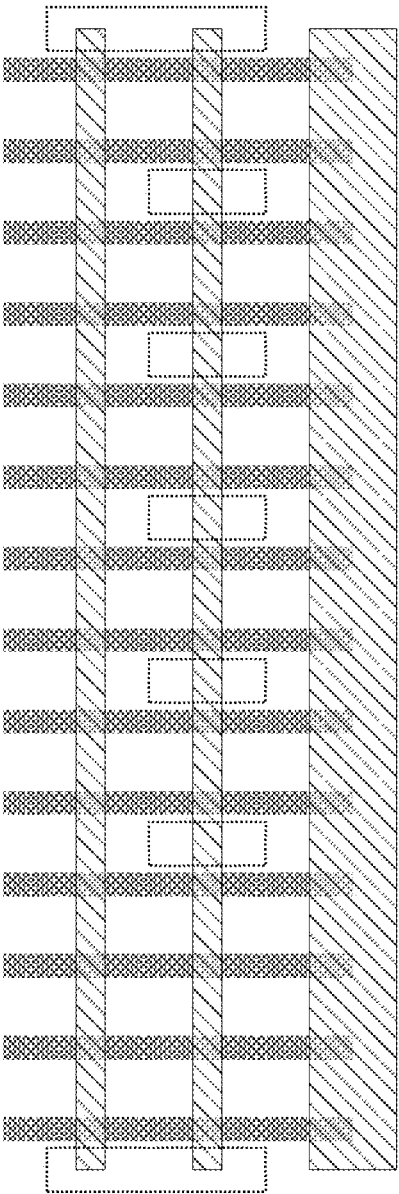


FIG. 66C

nr3x4

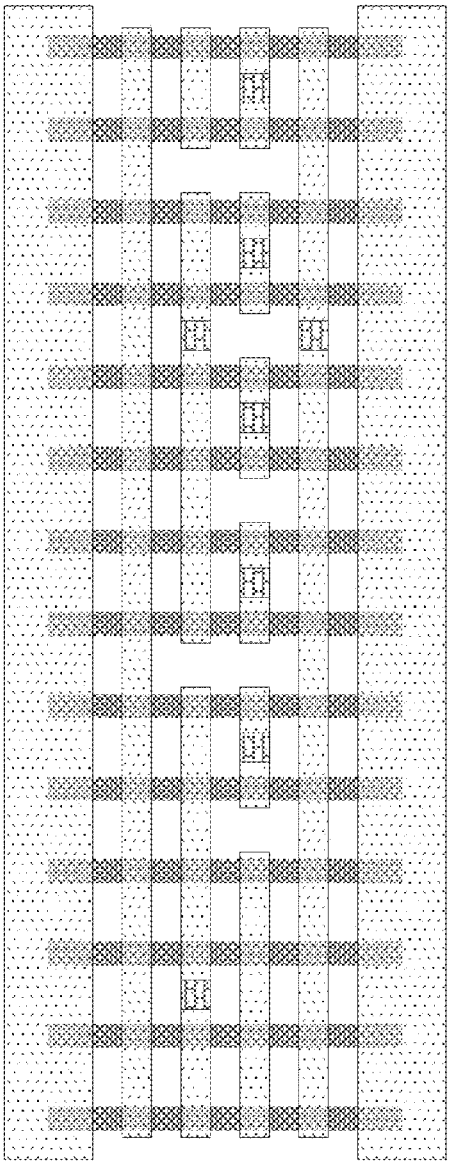


FIG. 66D

nr4x1

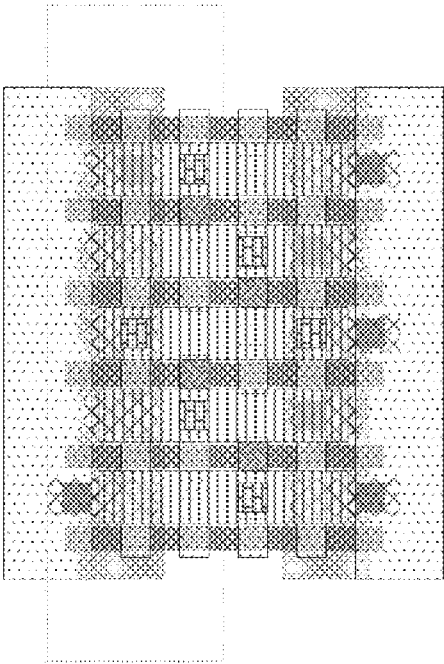


FIG. 67A

nr4x1

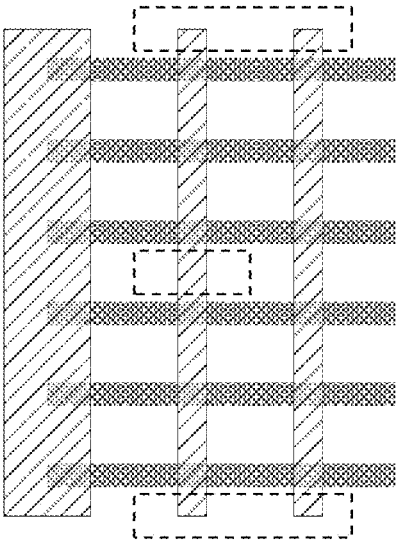


FIG. 67B

nr4x1

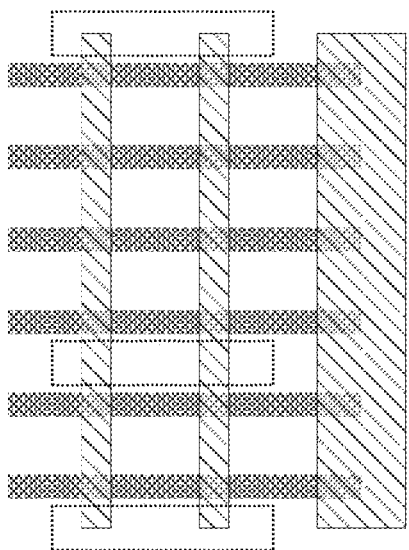


FIG. 67C

nr4x1

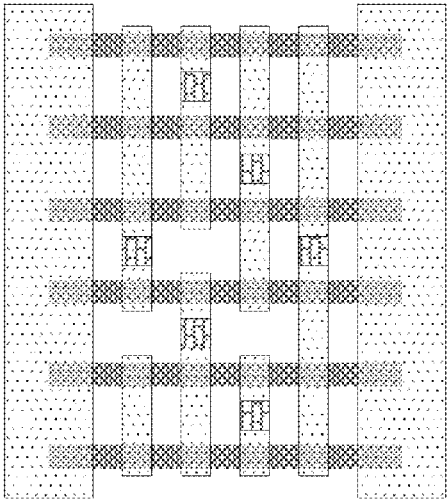


FIG. 67D

nr4x2

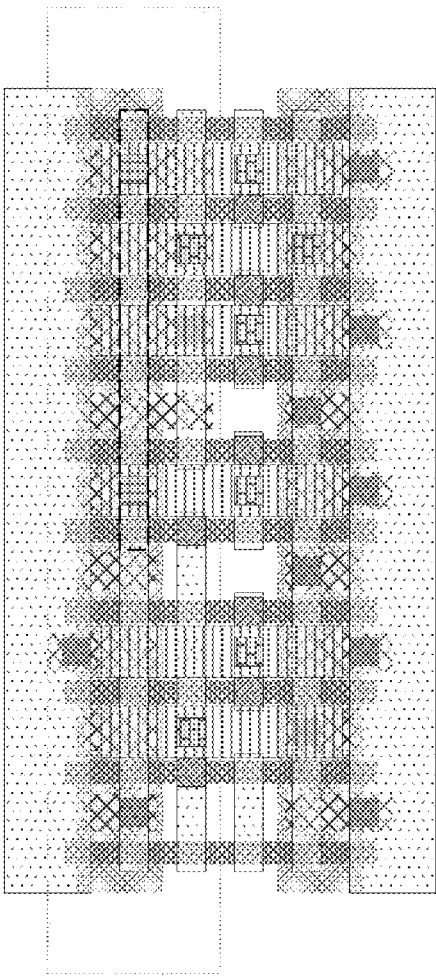


FIG. 68A

nr4x2

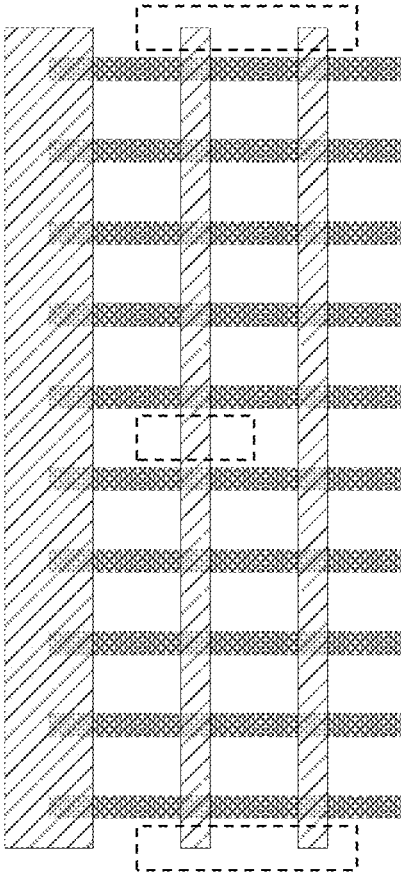


FIG. 68B

nr4x2

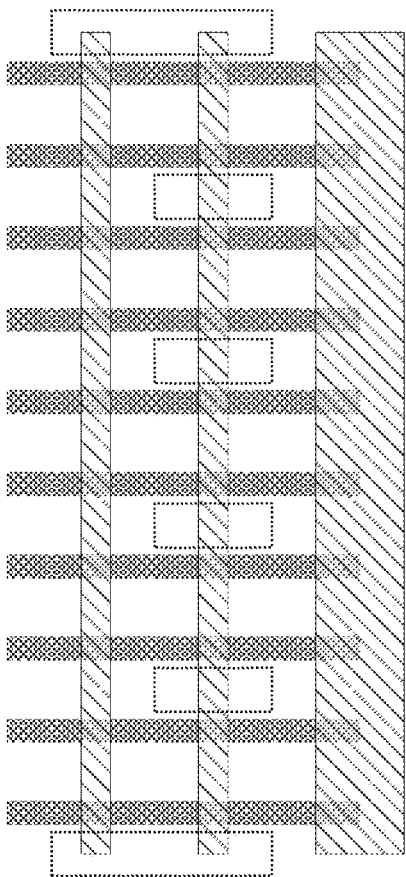


FIG. 68C

nr4x2

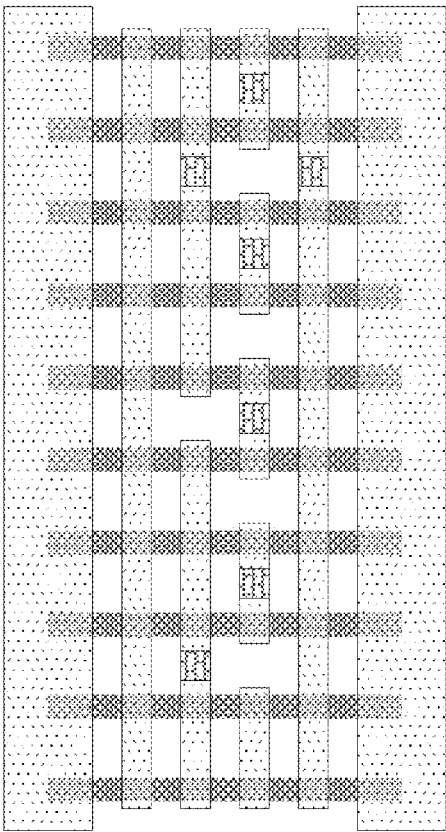


FIG. 68D

oa21x1

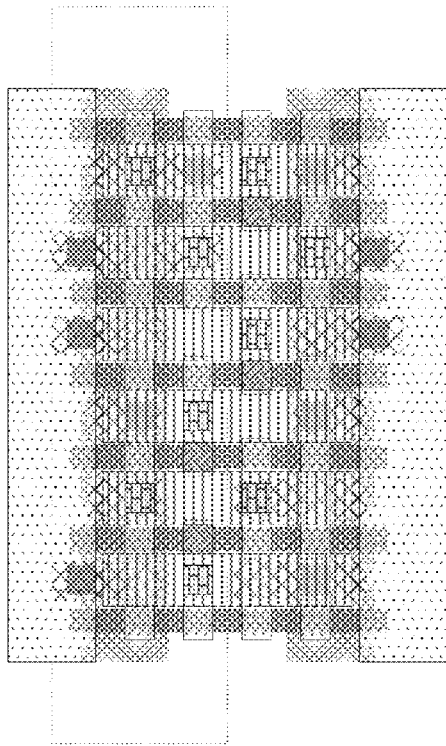


FIG. 69A

oa21x1

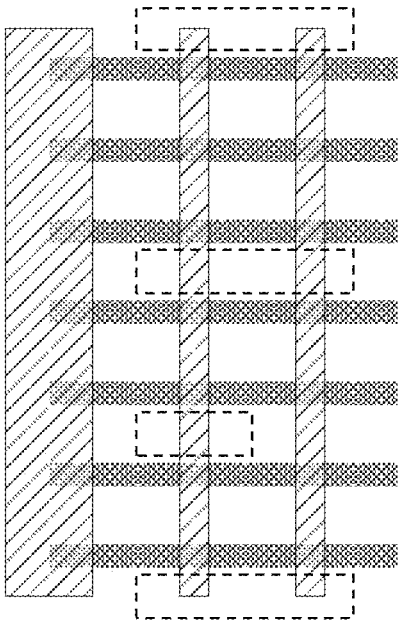


FIG. 69B

oa21x1

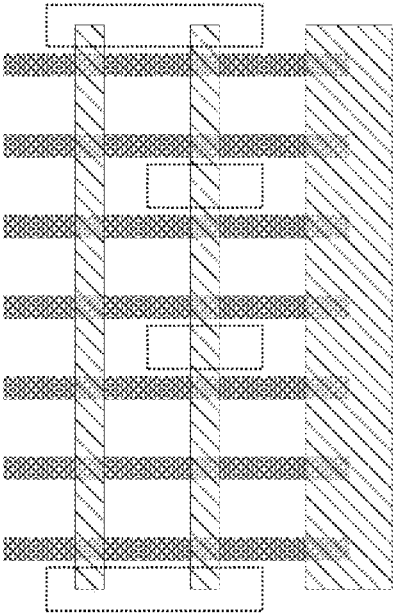


FIG. 69C

oa21x1

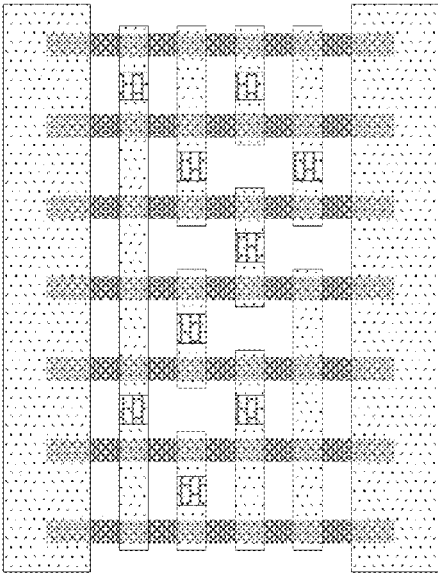


FIG. 69D

oa31x1

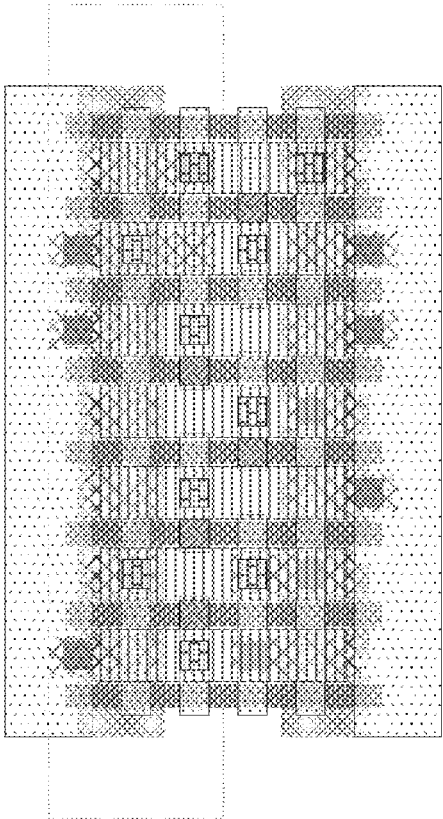


FIG. 70A

oa31x1

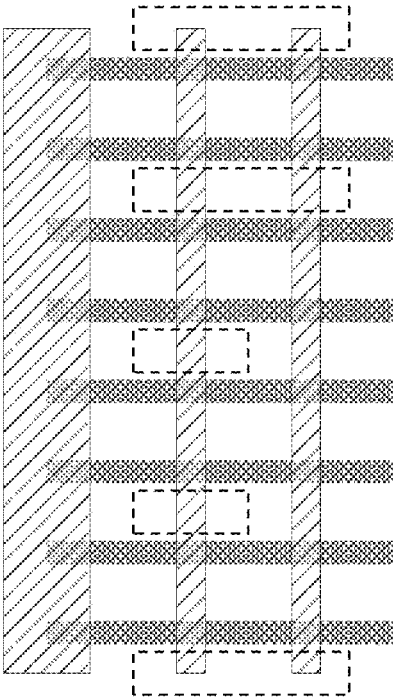


FIG. 70B

oa31x1

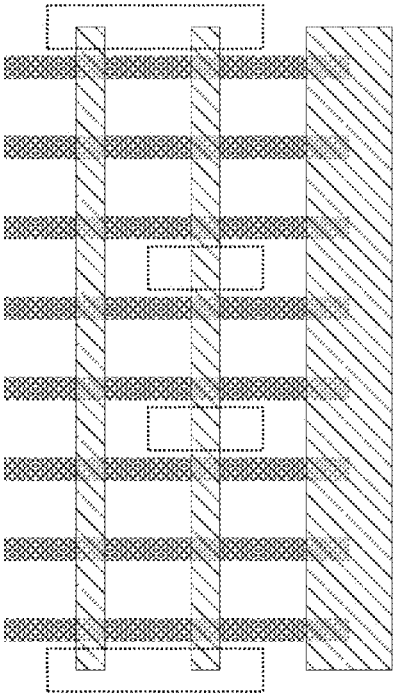


FIG. 70C

oa31x1

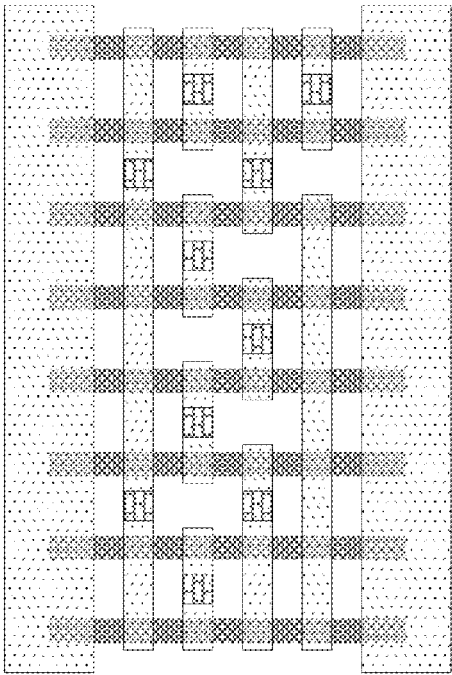


FIG. 70D

oa211x1

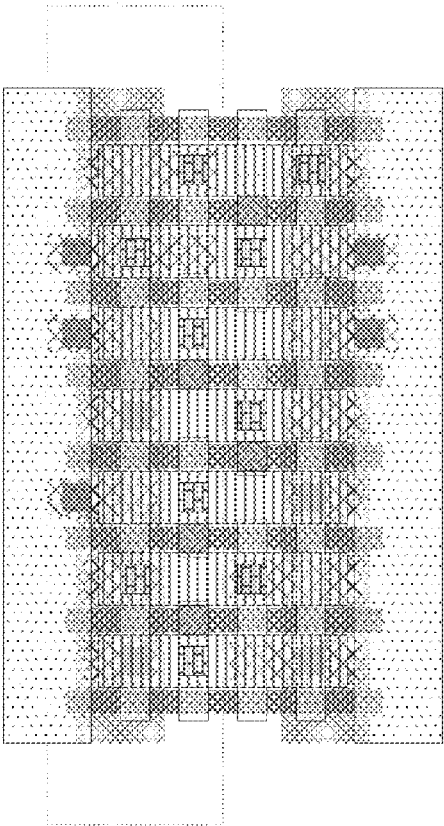


FIG. 71A

oa211x1

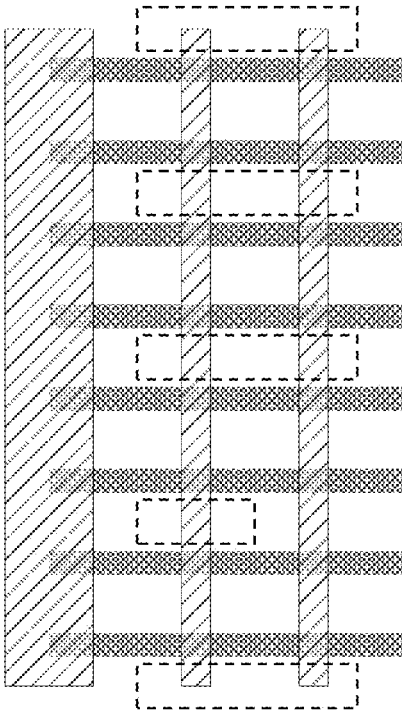


FIG. 71B

oa211x1

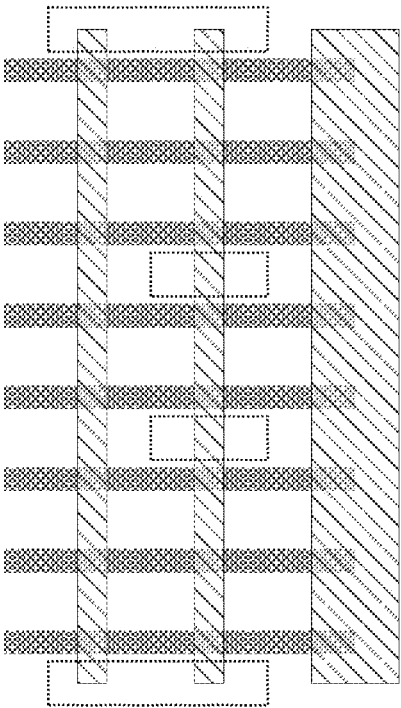


FIG. 71C

oa211x1

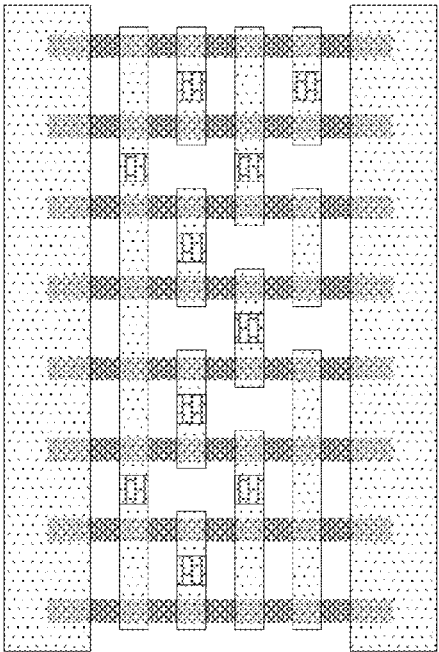


FIG. 71D

oai21x1

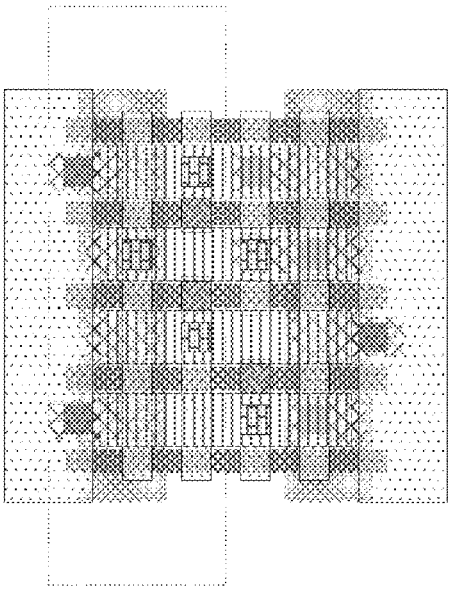


FIG. 72A

oai21x1

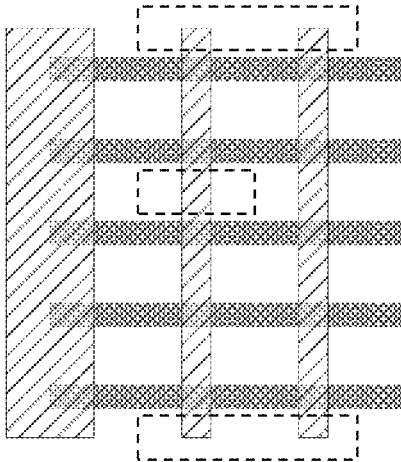


FIG. 72B

oai21x1

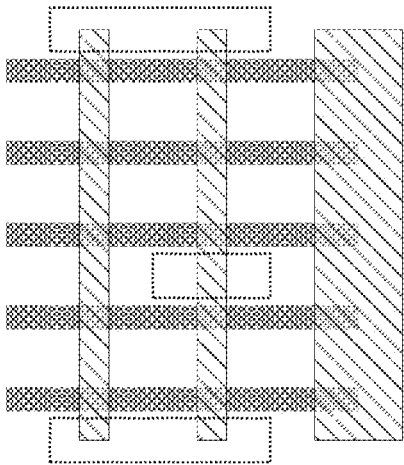


FIG. 72C

oai21x1

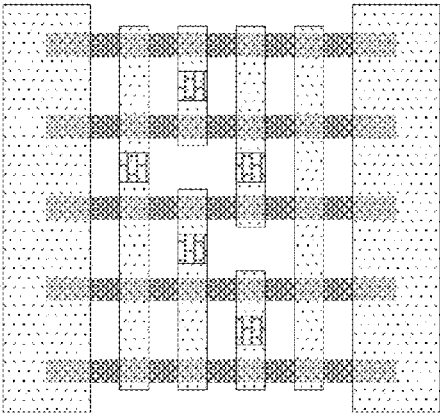


FIG. 72D

oai21x2

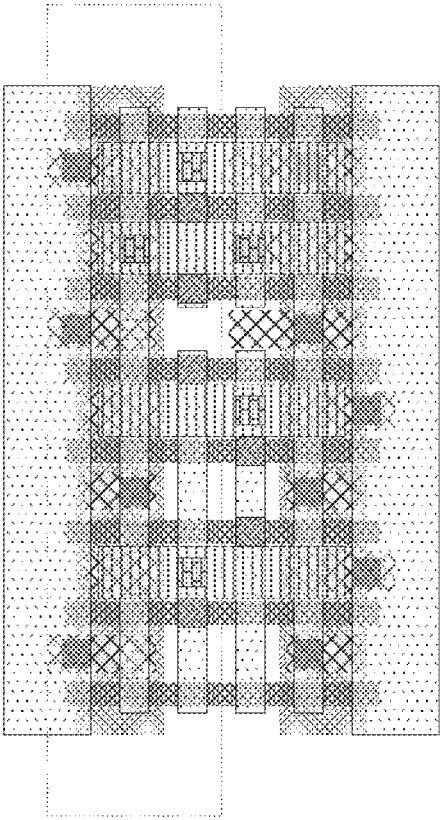


FIG. 73A

oai21x2

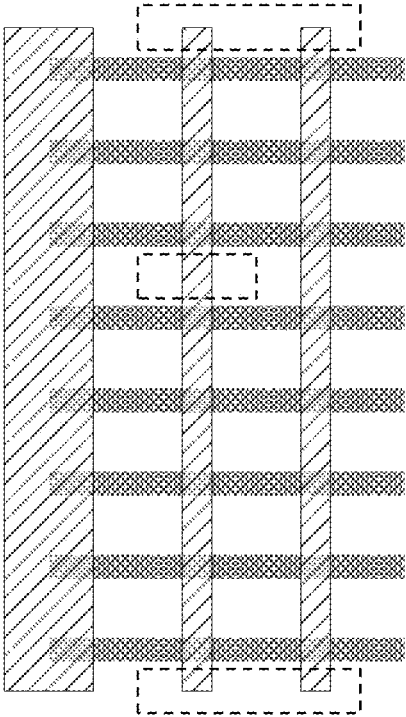


FIG. 73B

oai21x2

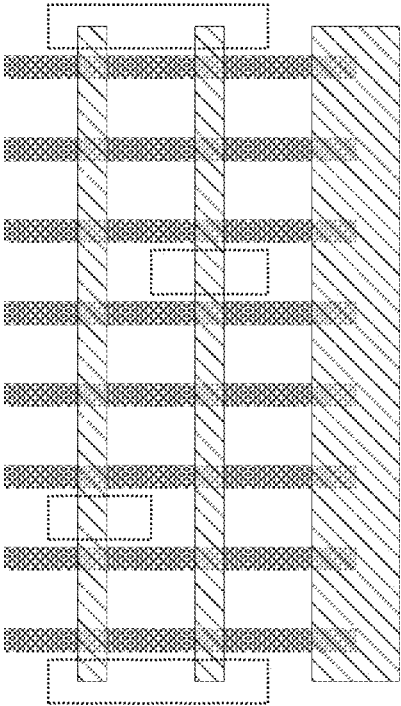


FIG. 73C

oai21x2

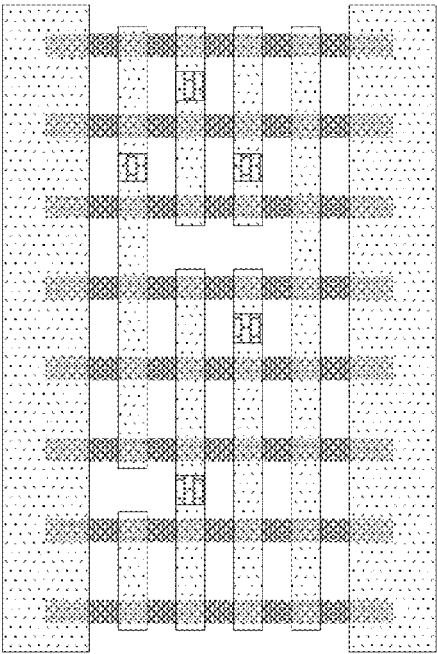


FIG. 73D

oai22x1

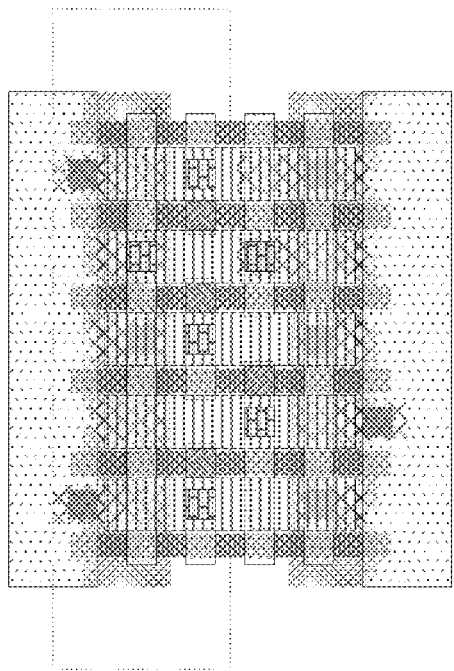


FIG. 74A

oai22x1

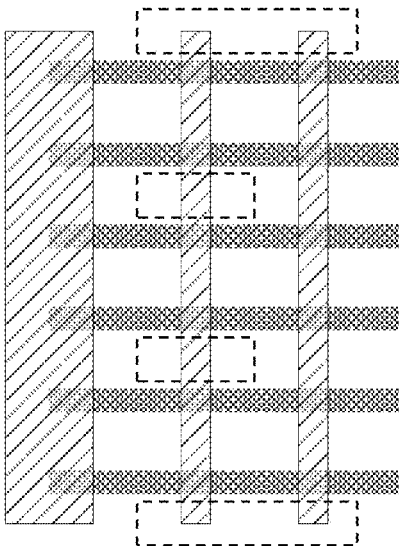


FIG. 74B

oai22x1

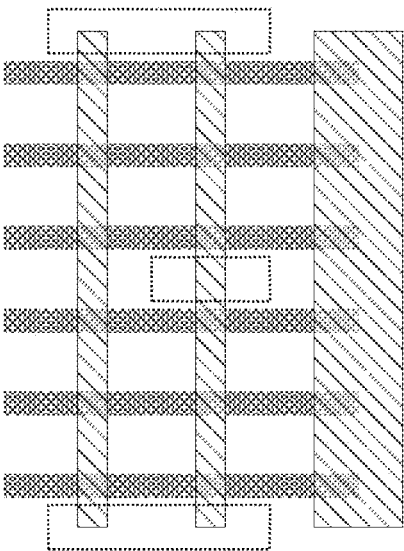


FIG. 74C

oai22x1

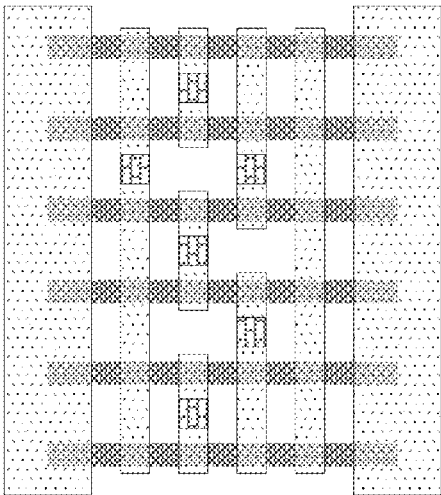


FIG. 74D

oai22x2

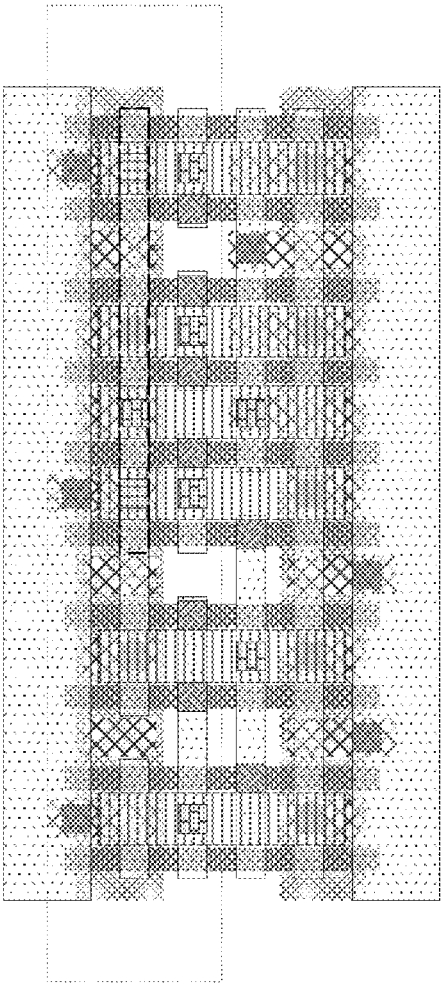


FIG. 75A

oai22x2

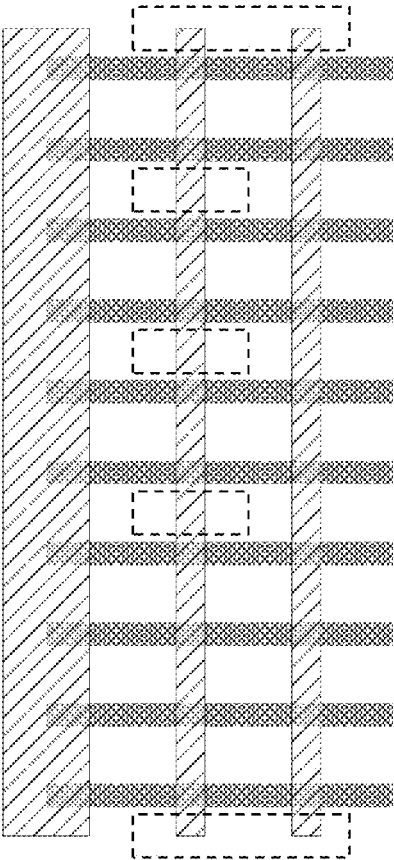


FIG. 75B

oai22x2

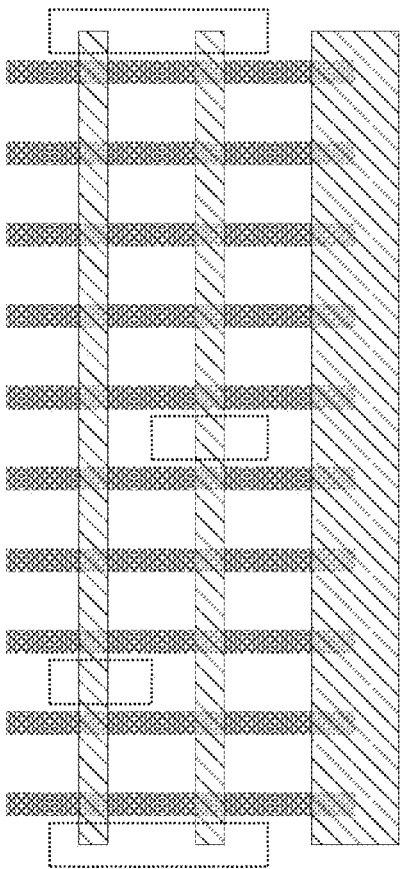


FIG. 75C

oai22x2

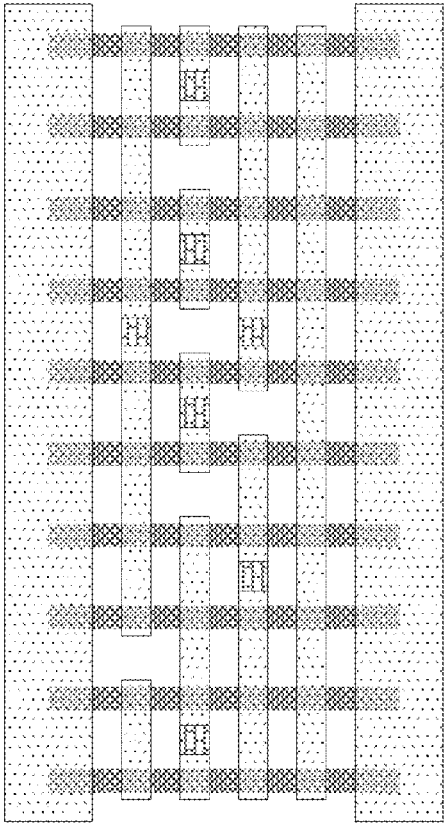


FIG. 75D

oai31x1

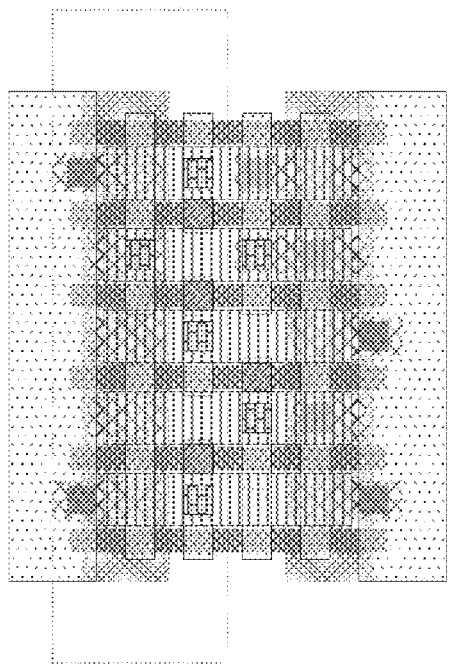


FIG. 76A

oai31x1

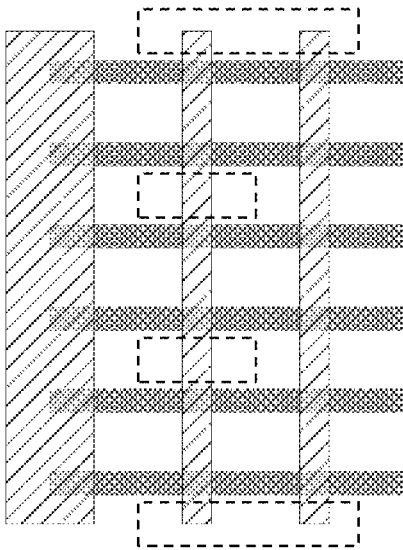


FIG. 76B

oai31x1

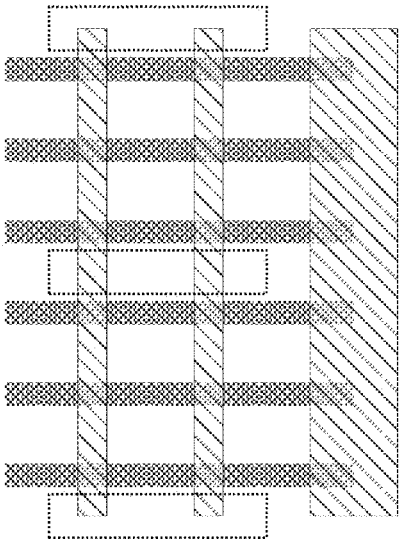


FIG. 76C

oai31x1

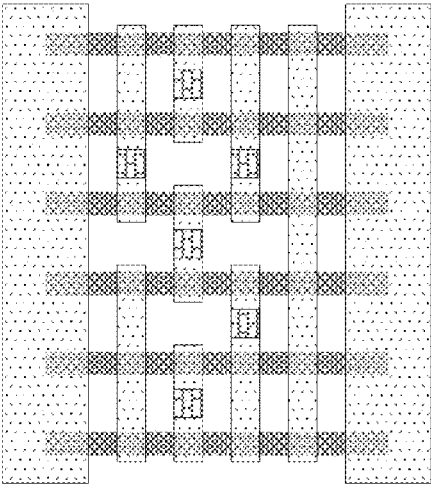


FIG. 76D

oai31x2

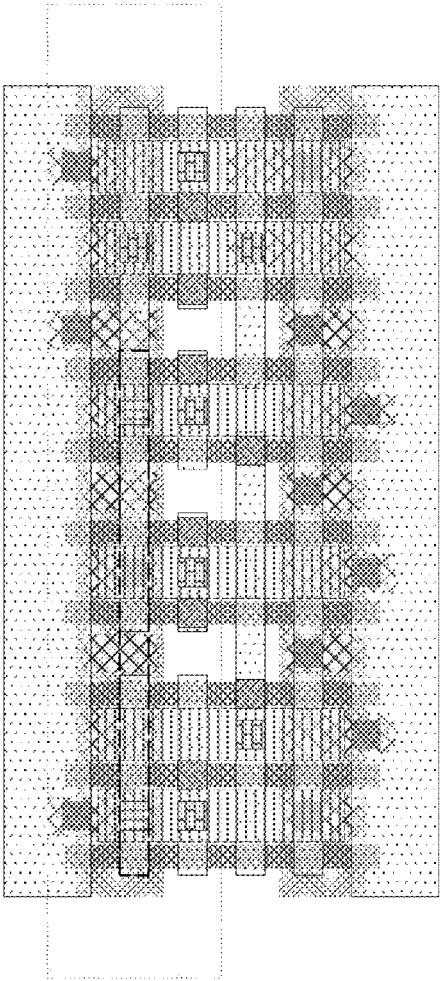


FIG. 77A

oai31x2

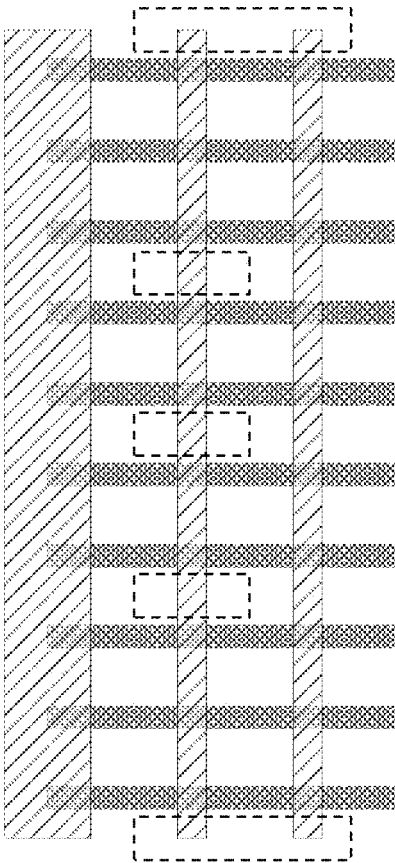


FIG. 77B

oai31x2

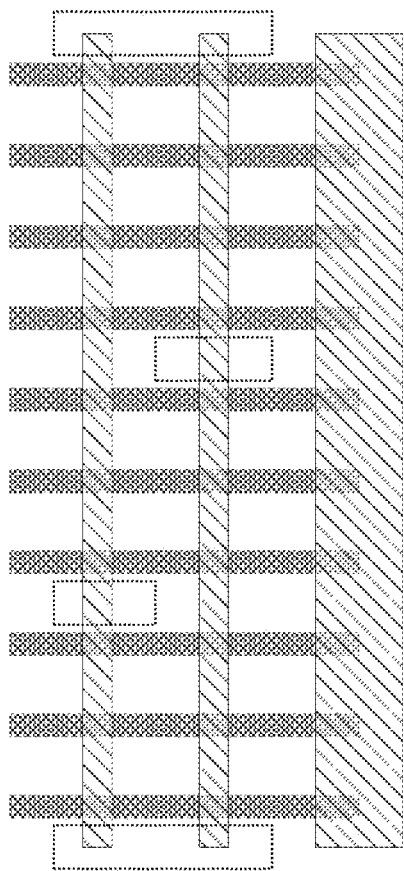


FIG. 77C

oai31x2

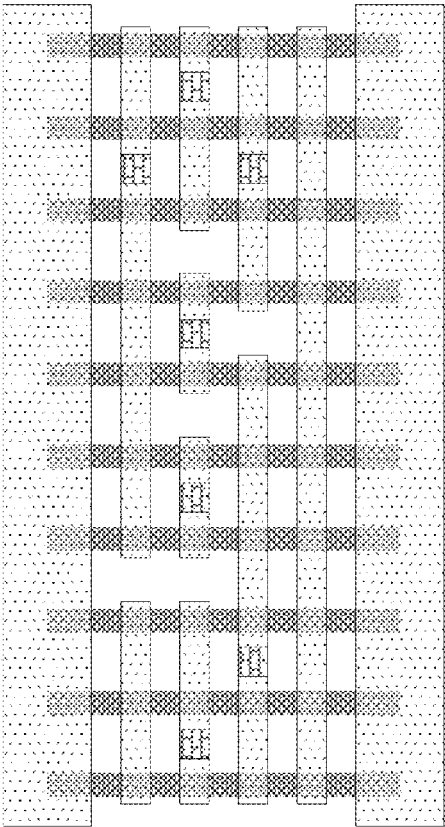


FIG. 77D

oai211x1

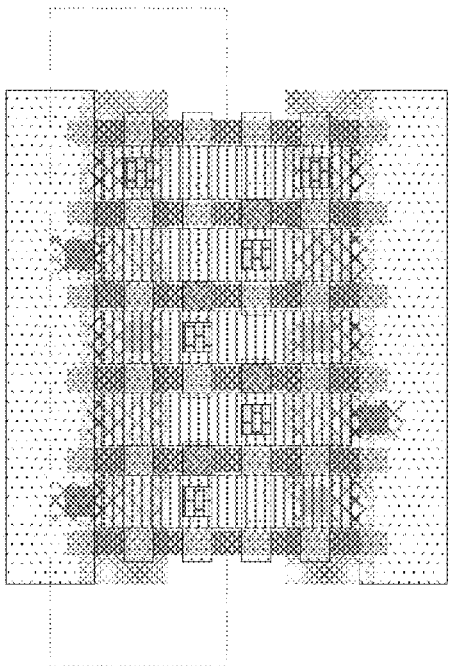


FIG. 78A

oai211x1

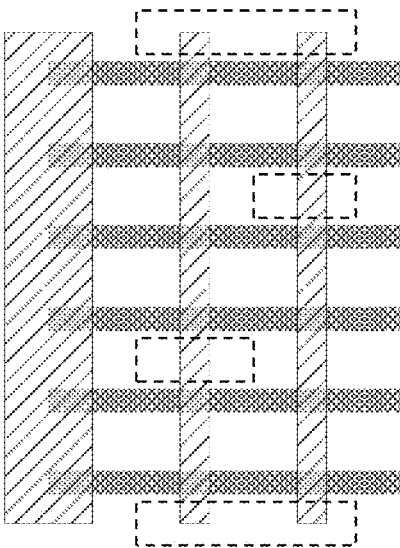


FIG. 78B

oai211x1

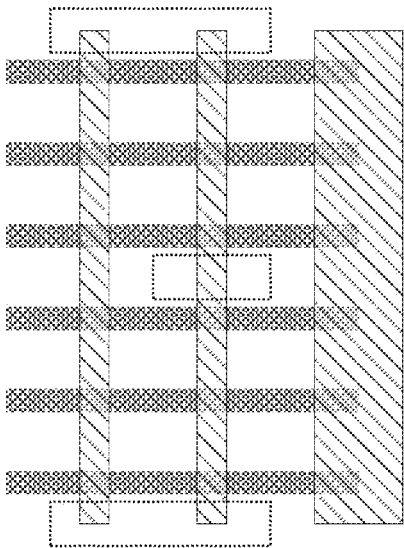


FIG. 78C

oai211x1

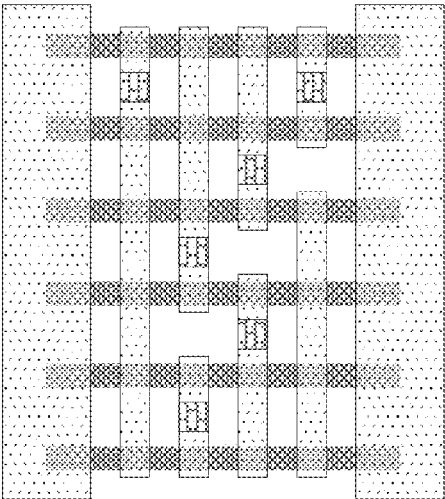


FIG. 78D

oai222x1

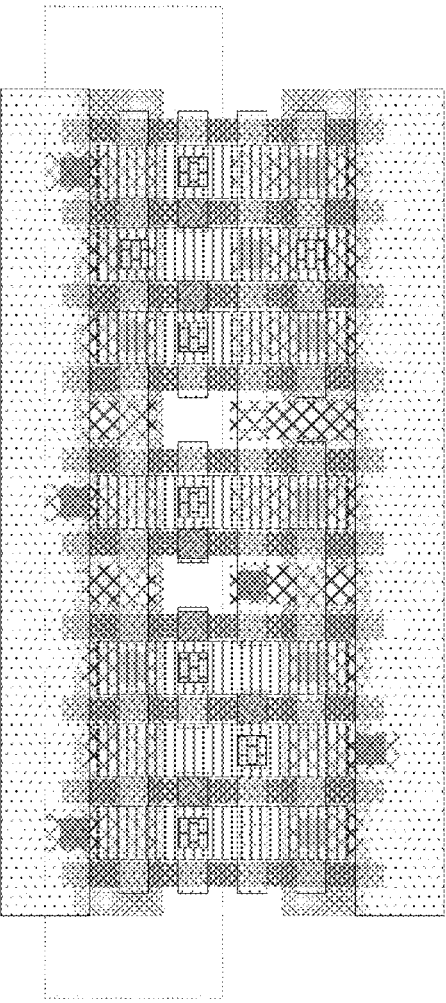


FIG. 79A

oai222x1

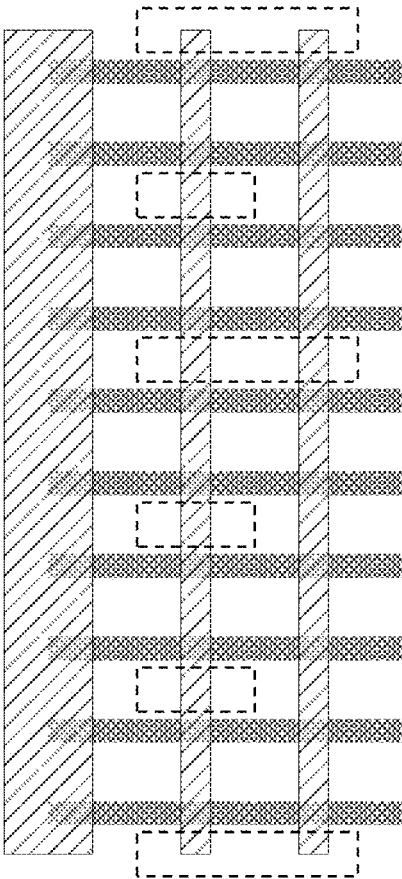


FIG. 79B

oai222x1

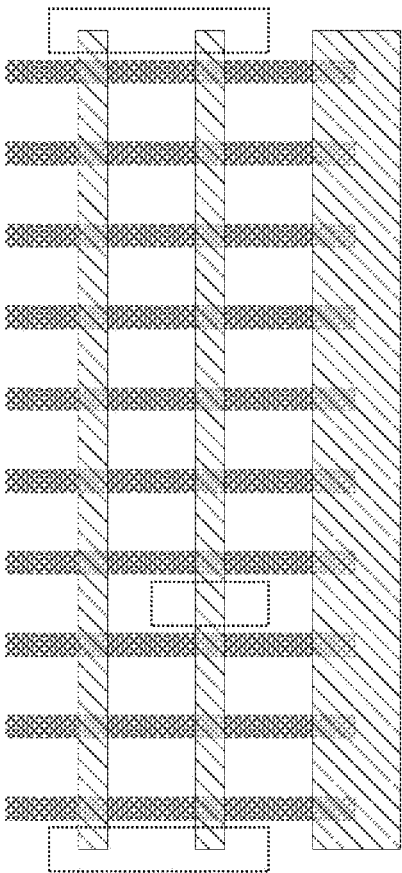


FIG. 79C

oai222x1

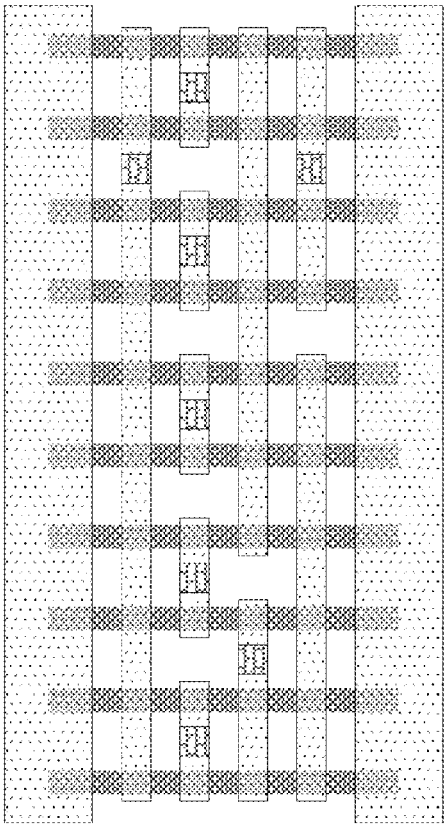


FIG. 79D

or2x1

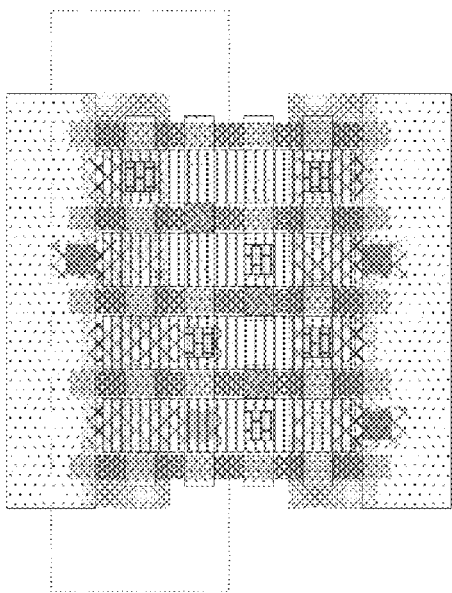


FIG. 80A

or2x1

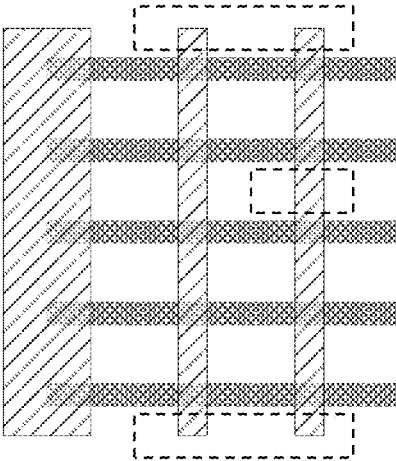


FIG. 80B

or2x1

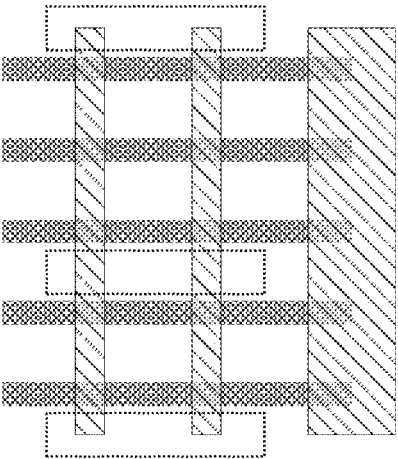


FIG. 80C

or 2x1

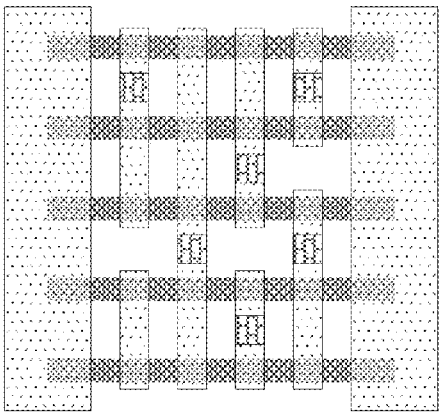


FIG. 80D

or2x2

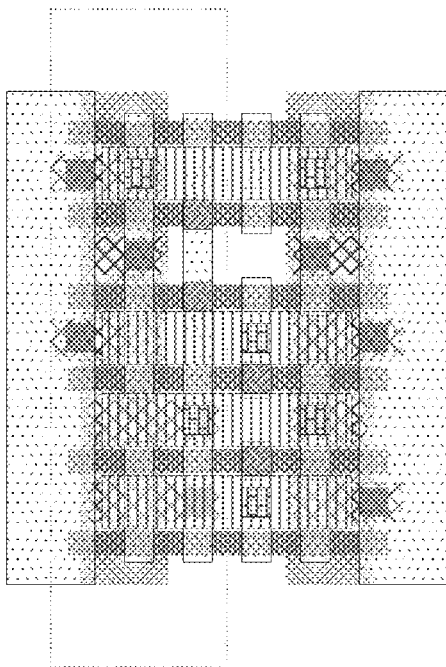


FIG. 81A

or2x2

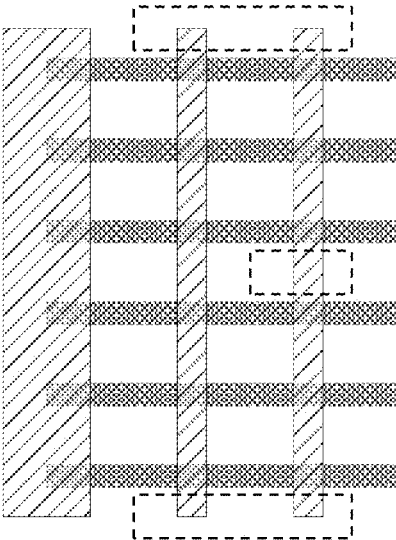


FIG. 81B

or2x2

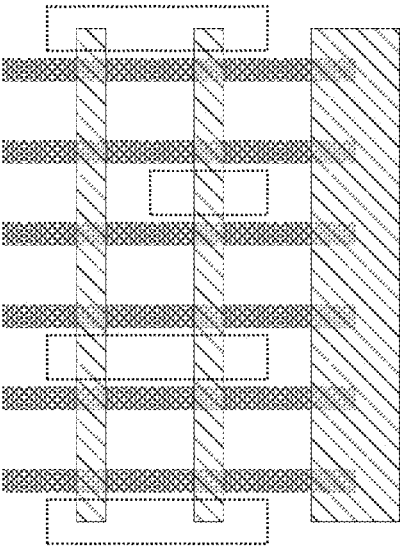


FIG. 81C

or 2x2

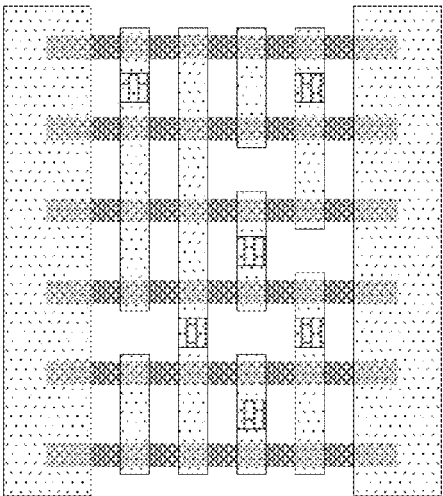


FIG. 81D

or3x1

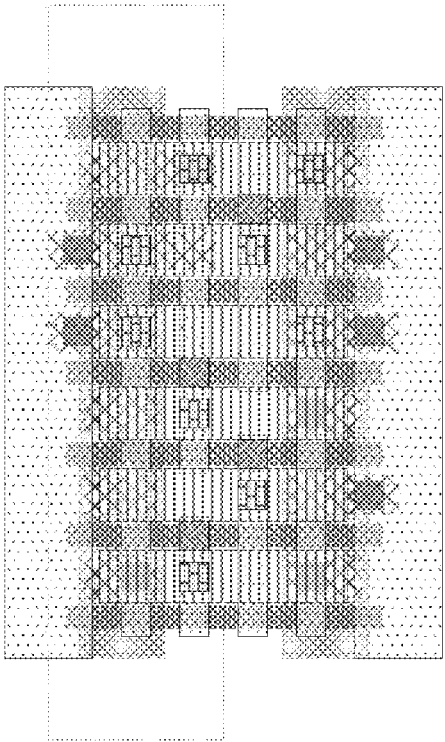


FIG. 82A

or3x1

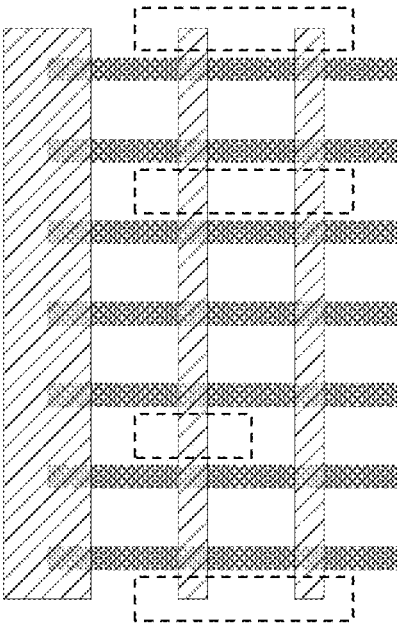


FIG. 82B

or3x1

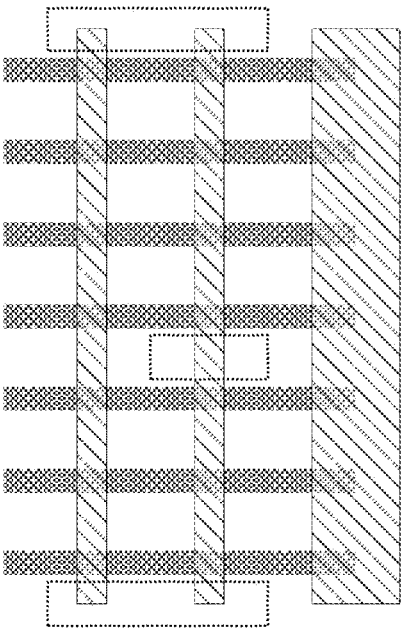


FIG. 82C

or3x1

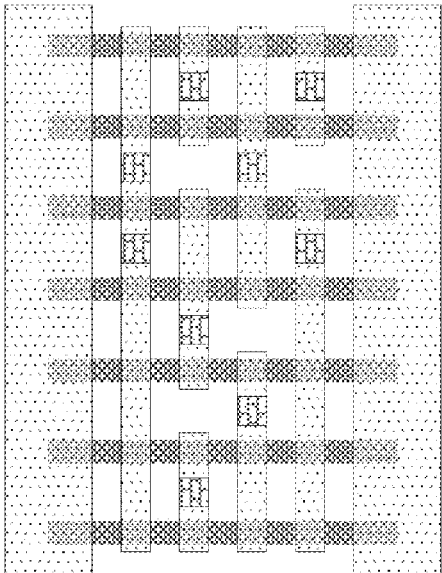


FIG. 82D

or3x2

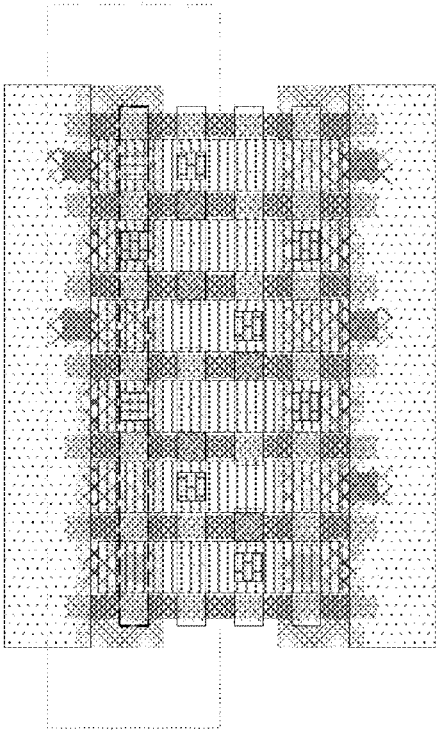


FIG. 83A

or3x2

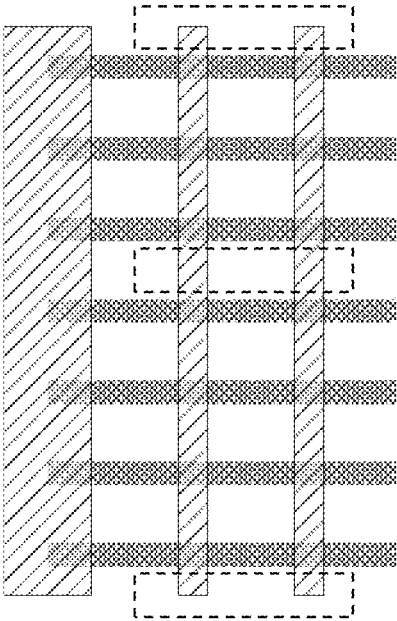


FIG. 83B

or3x2

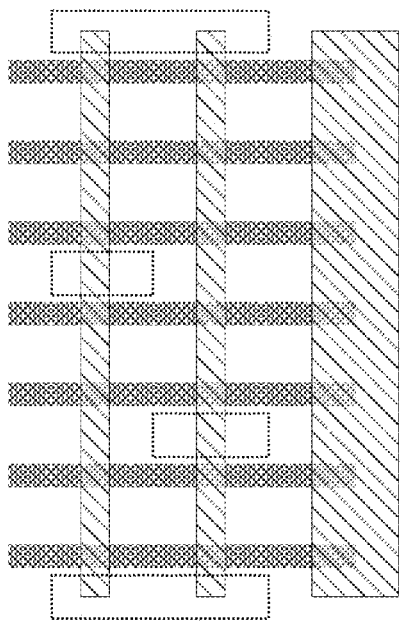


FIG. 83C

or3x2

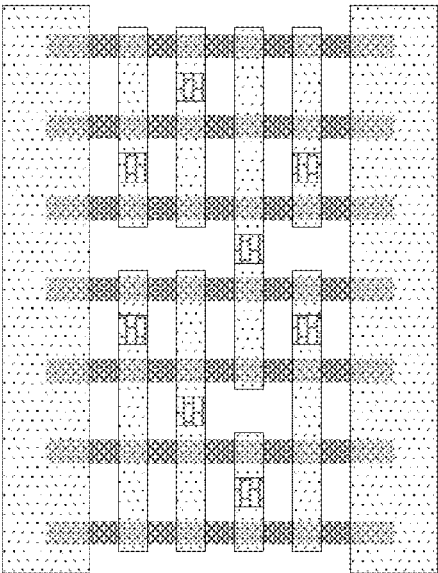


FIG. 83D

or4x1

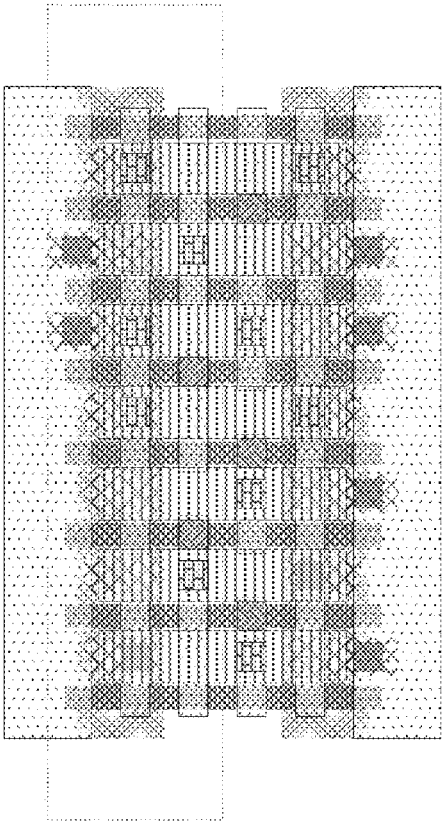


FIG. 84A

or 4x1

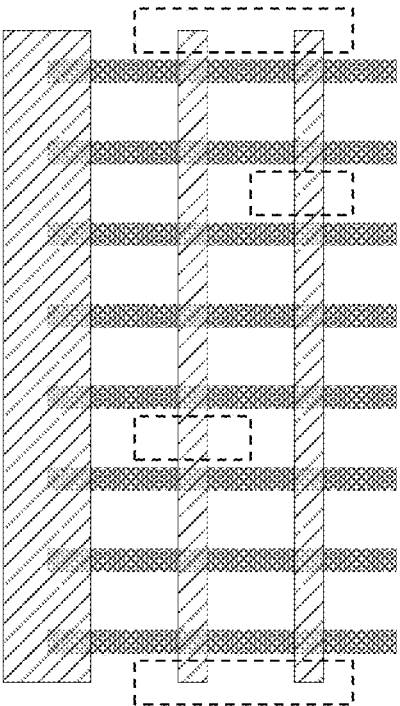


FIG. 84B

or 4x1

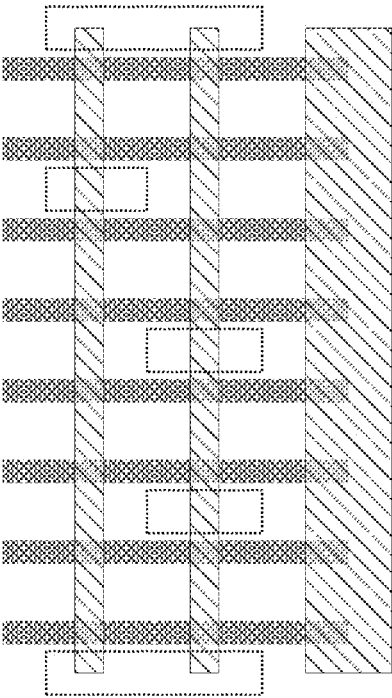


FIG. 84C

or4x1

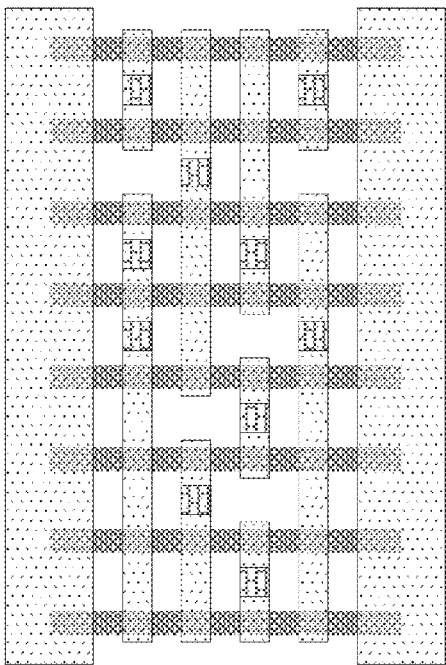


FIG. 84D

or 4x2

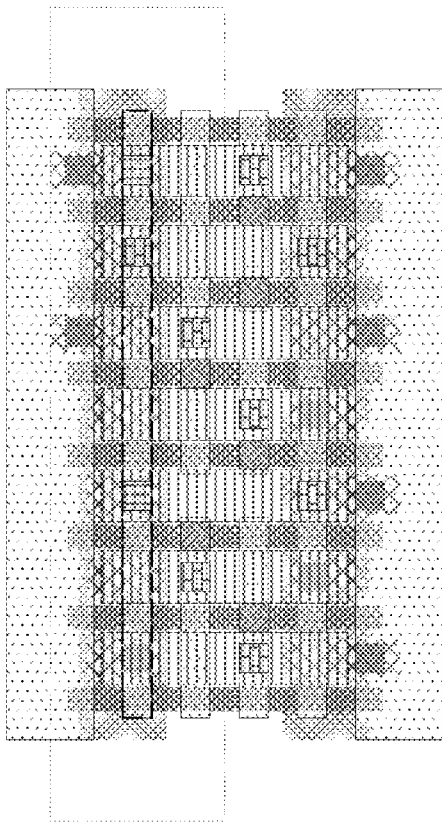


FIG. 85A

or4x2

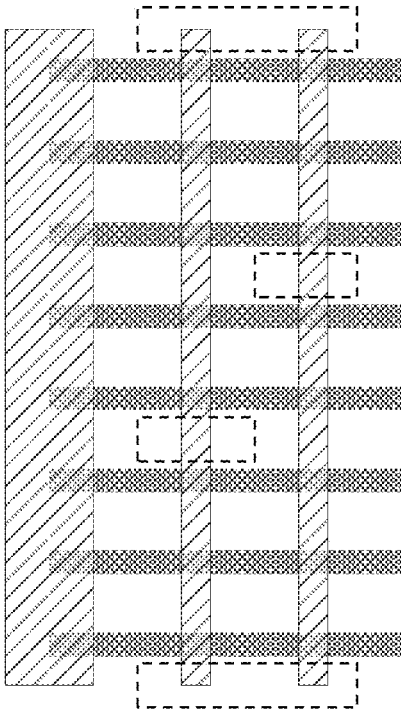


FIG. 85B

or4x2

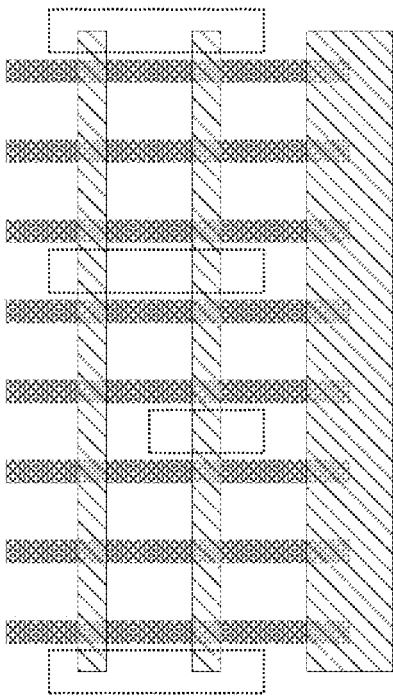


FIG. 85C

or 4x2

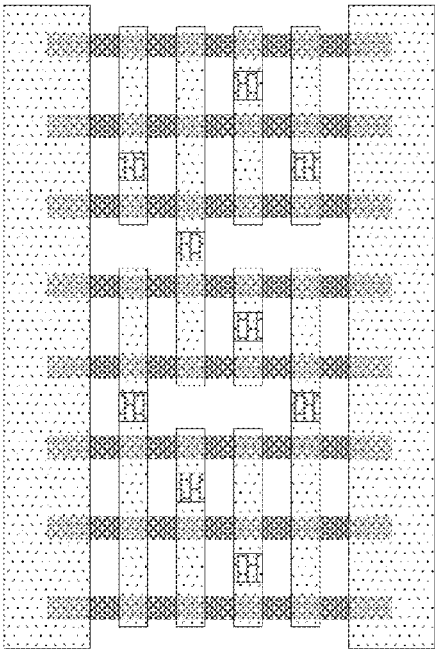


FIG. 85D

sdffqx1

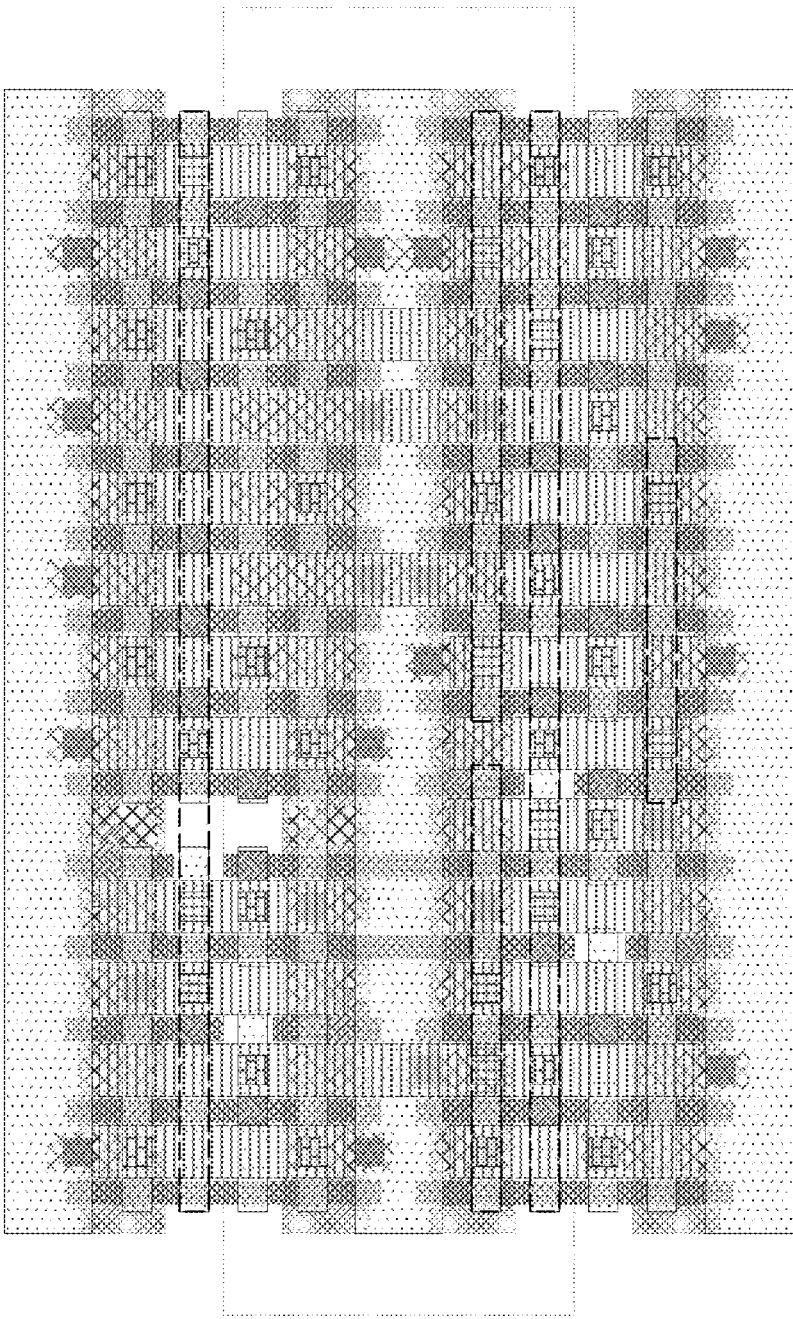


FIG. 86A

sdffqx1

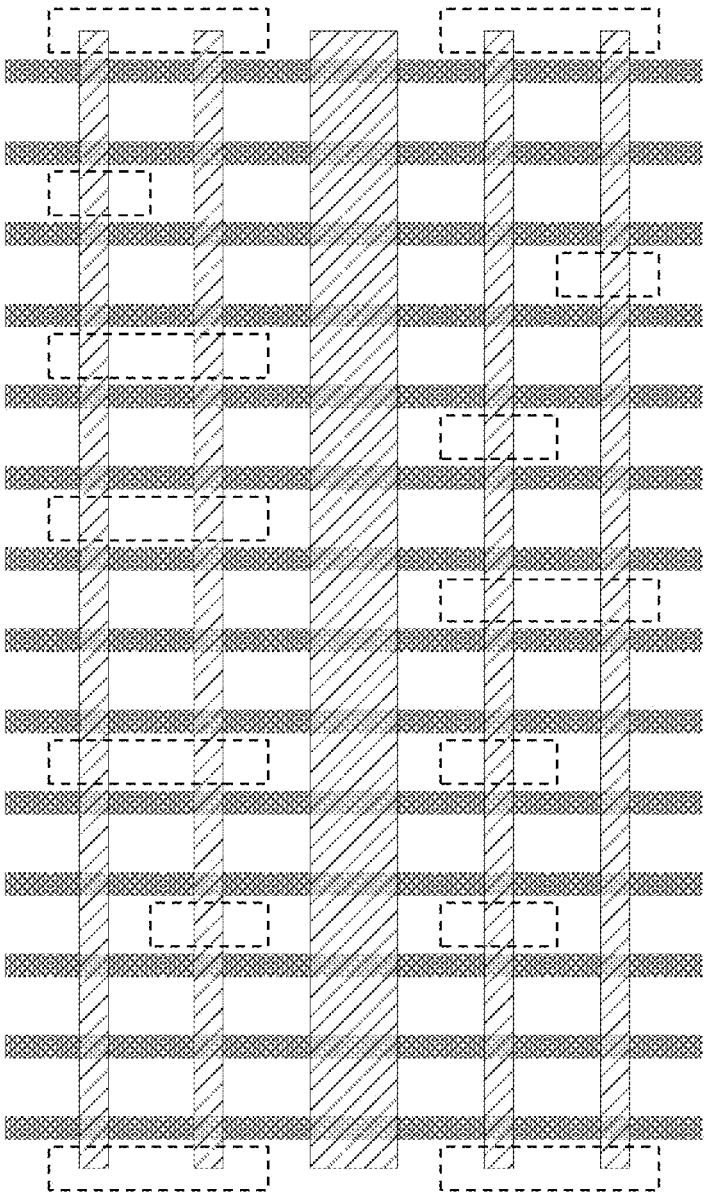


FIG. 86B

sdffqx1

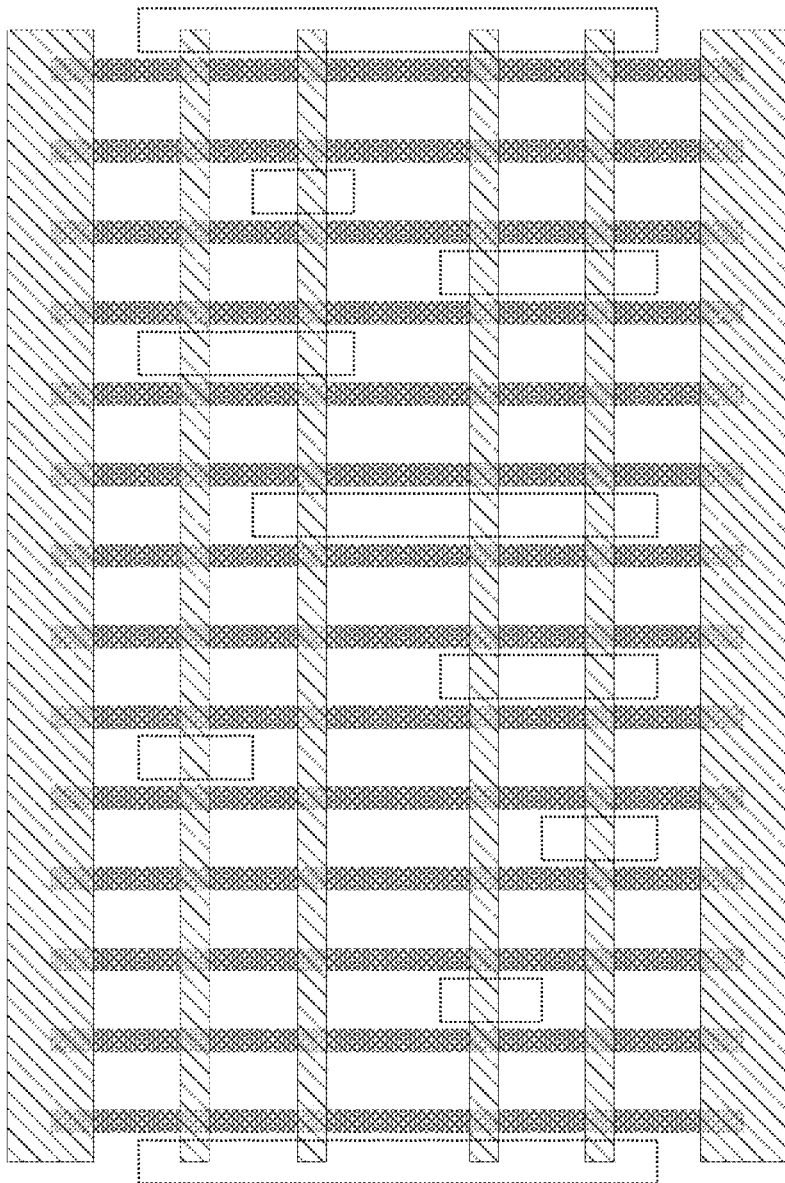


FIG. 86C

sdffqx1

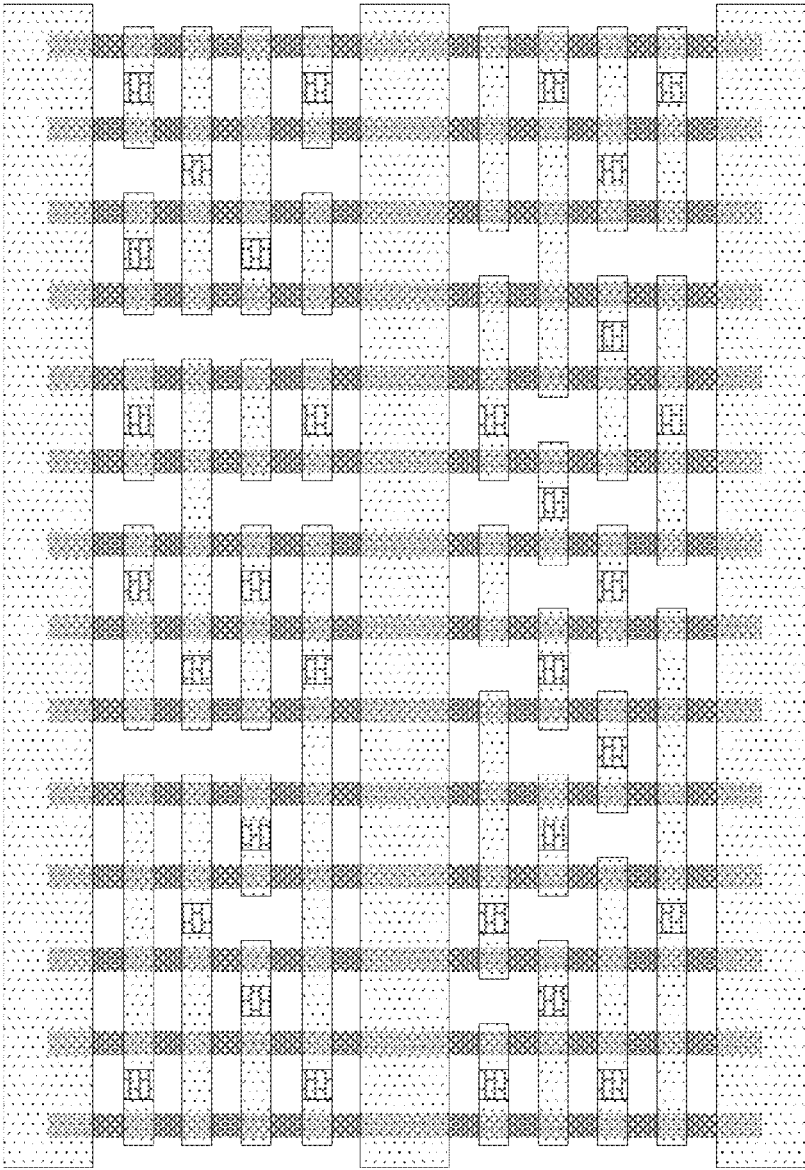


FIG. 86D

sdffrsqx1

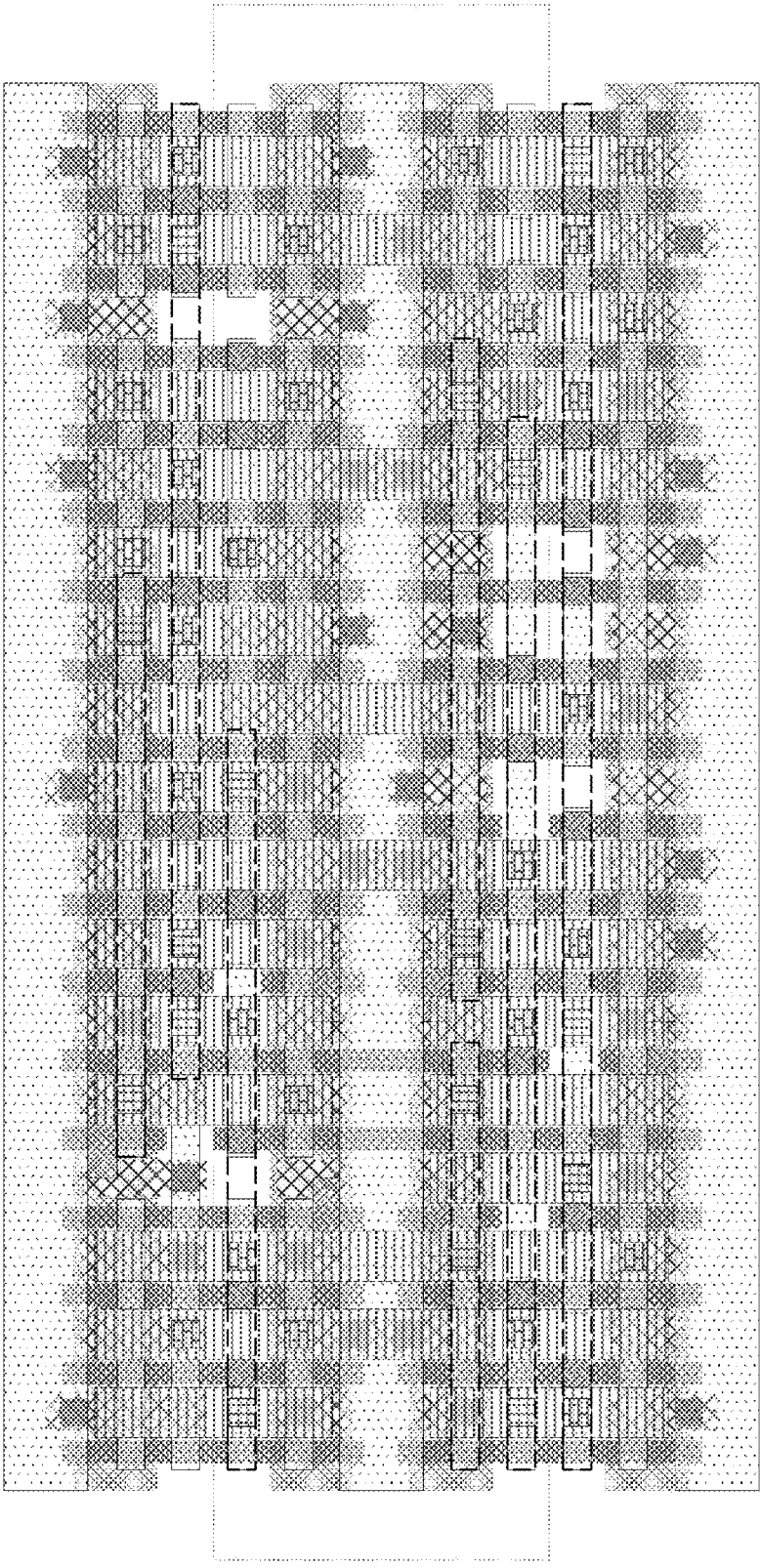


FIG. 87A

sdffrsqx1

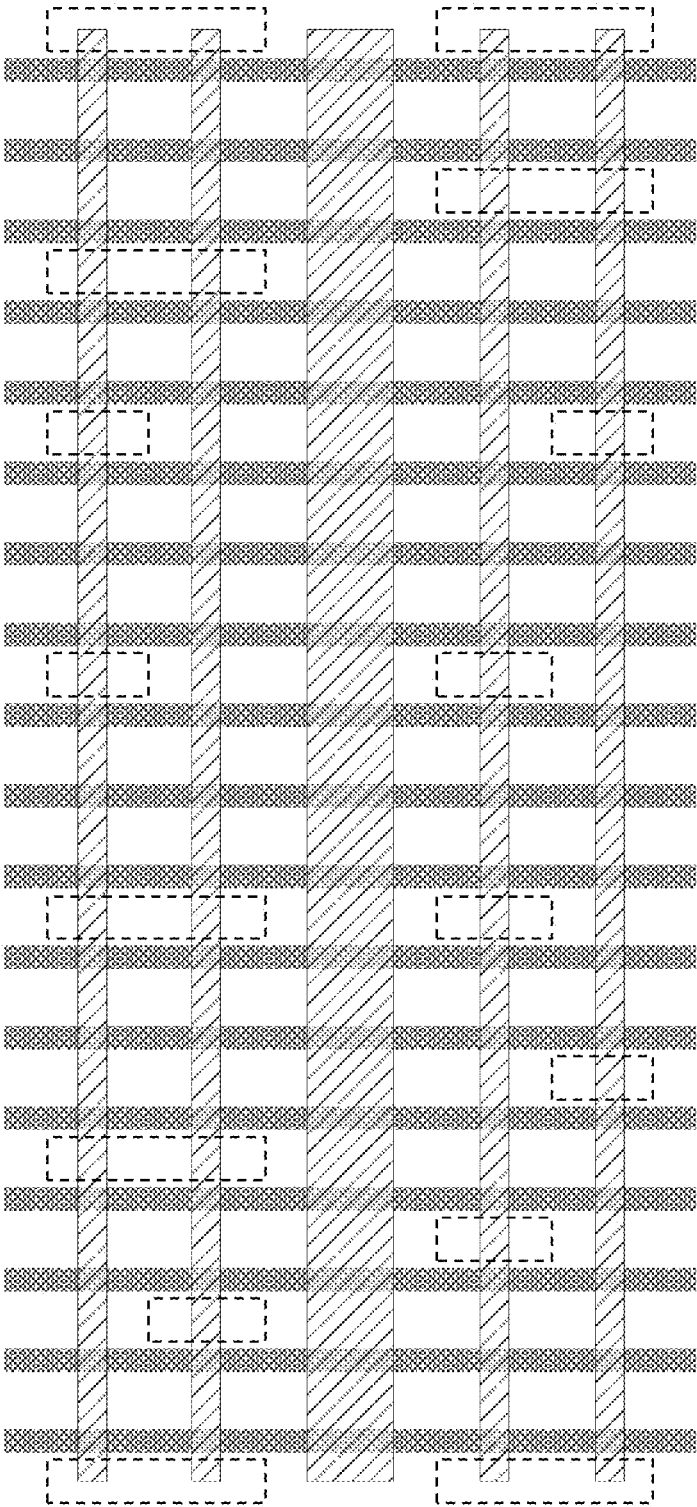


FIG. 87B

sdffrsqx1

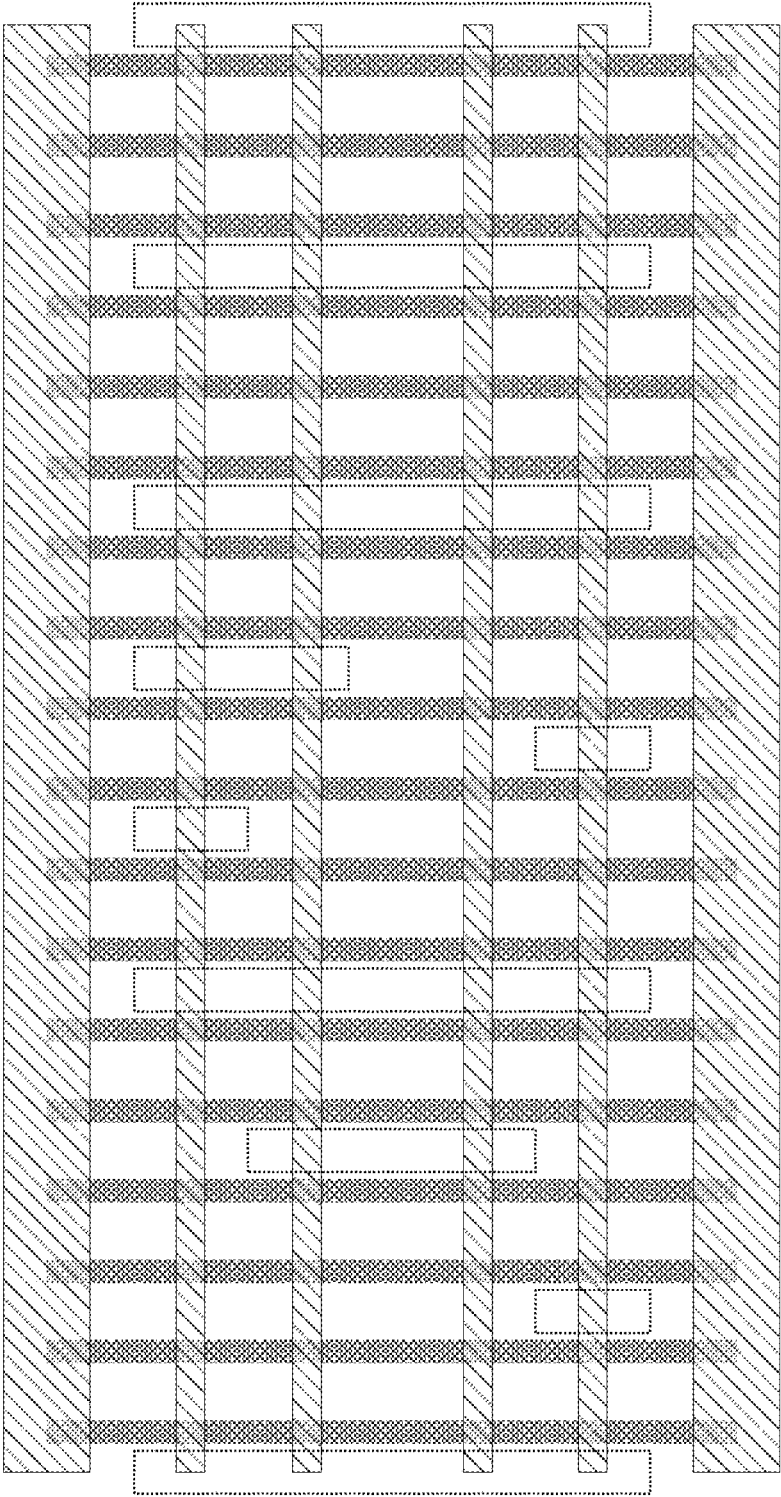


FIG. 87C

sdffrsqx1

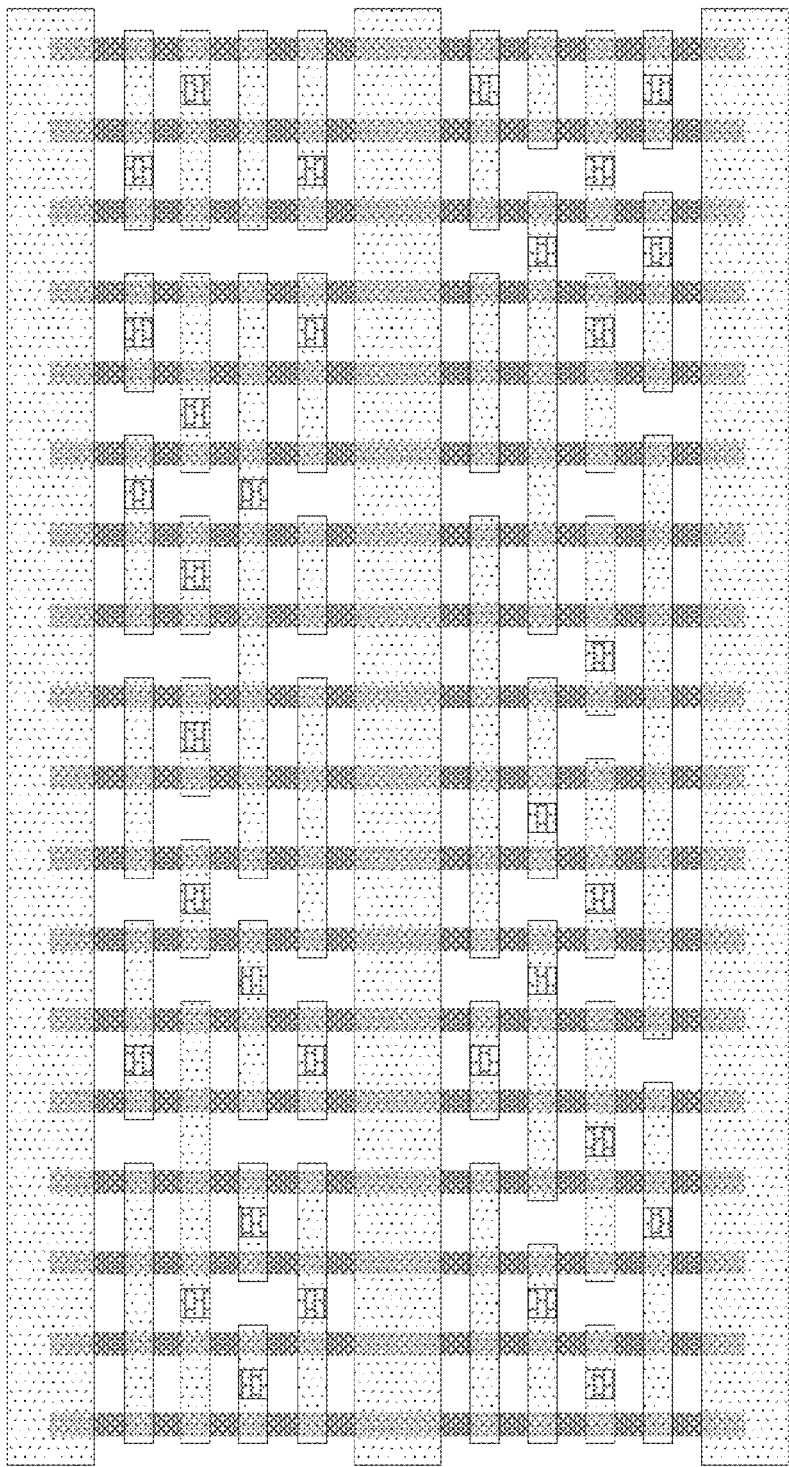


FIG. 87D

tiehix1

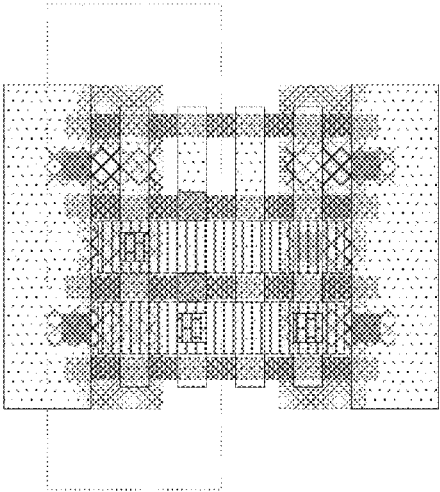


FIG. 88A

tiehix1

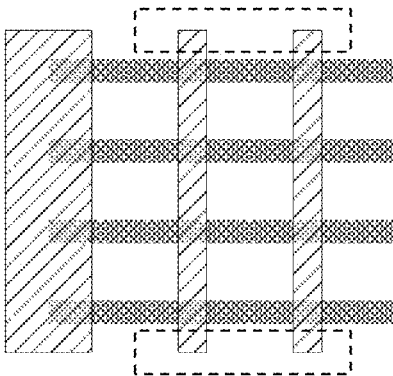


FIG. 88B

tiehix1

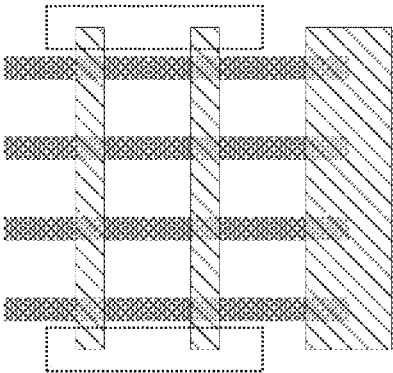


FIG. 88C

tiehix1

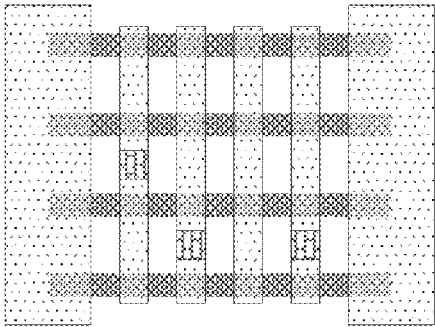


FIG. 88D

tielox1

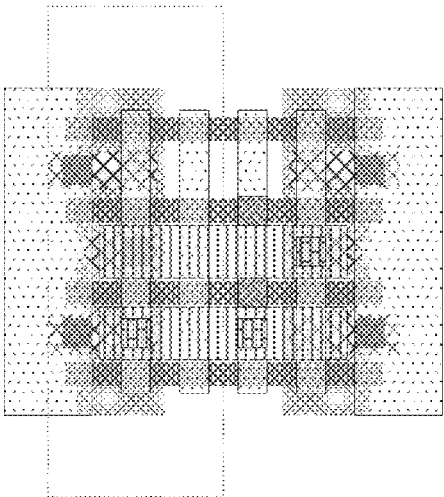


FIG. 89A

tielox1

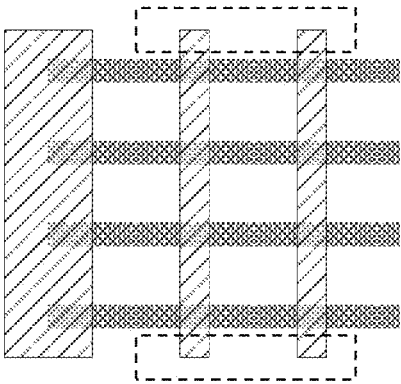


FIG. 89B

tielox1

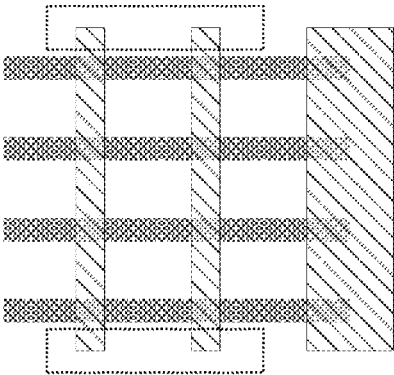


FIG. 89C

tielox1

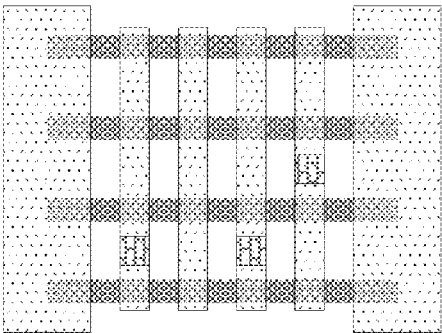


FIG. 89D

xnr2x1

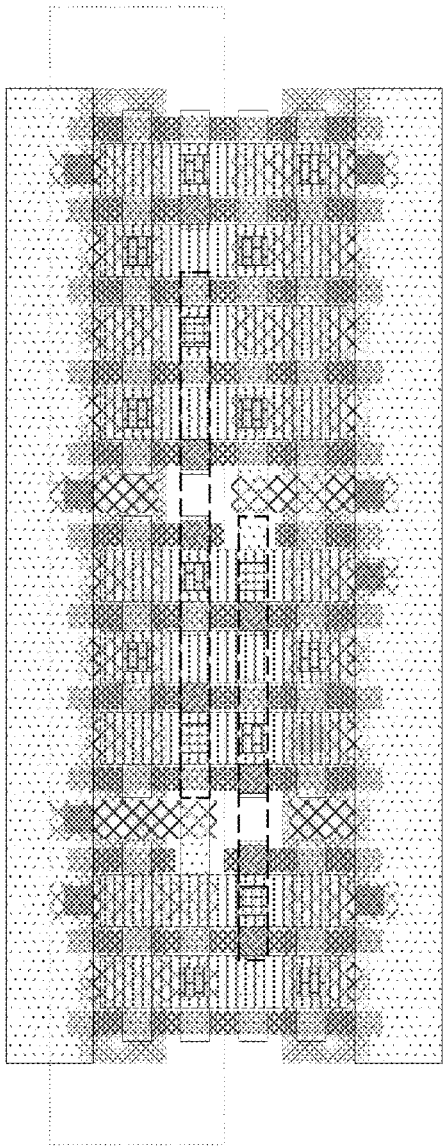


FIG. 90A

xnr2x1

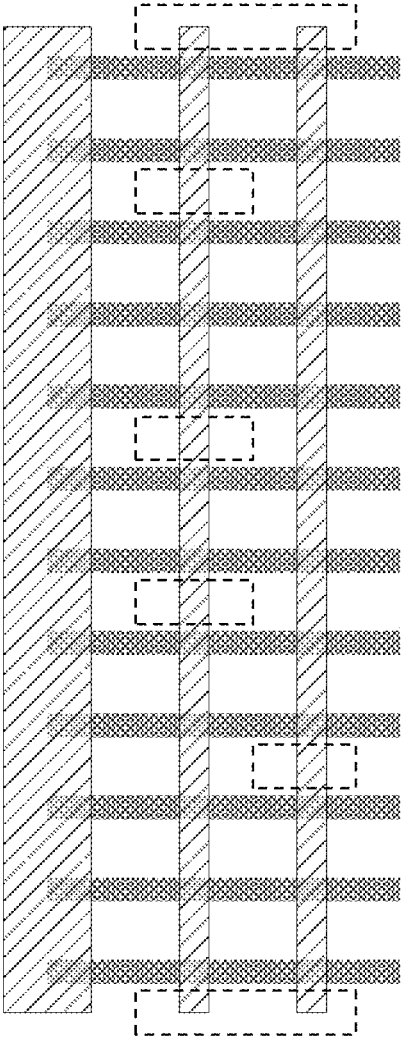


FIG. 90B

xnr2x1

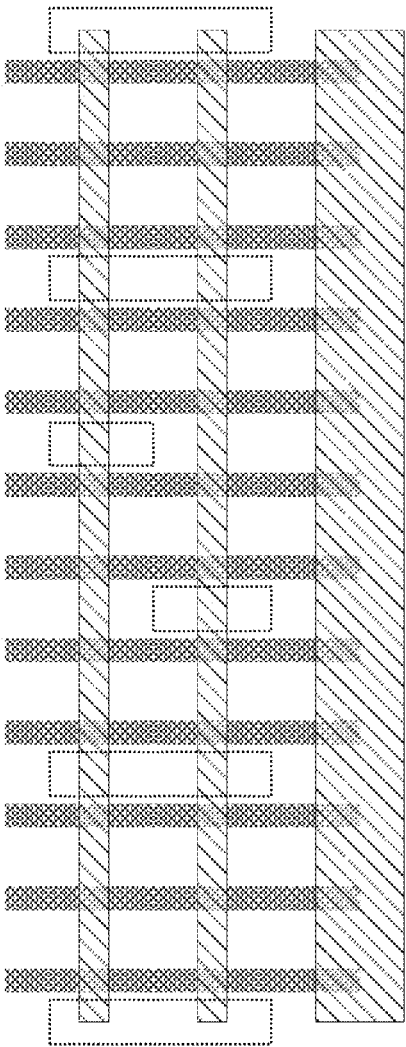


FIG. 90C

xnr2x1

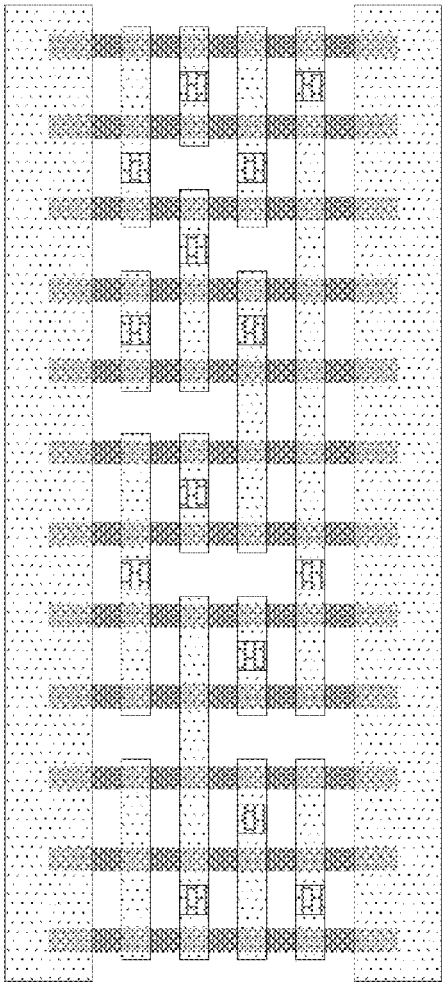


FIG. 90D

xor2x1

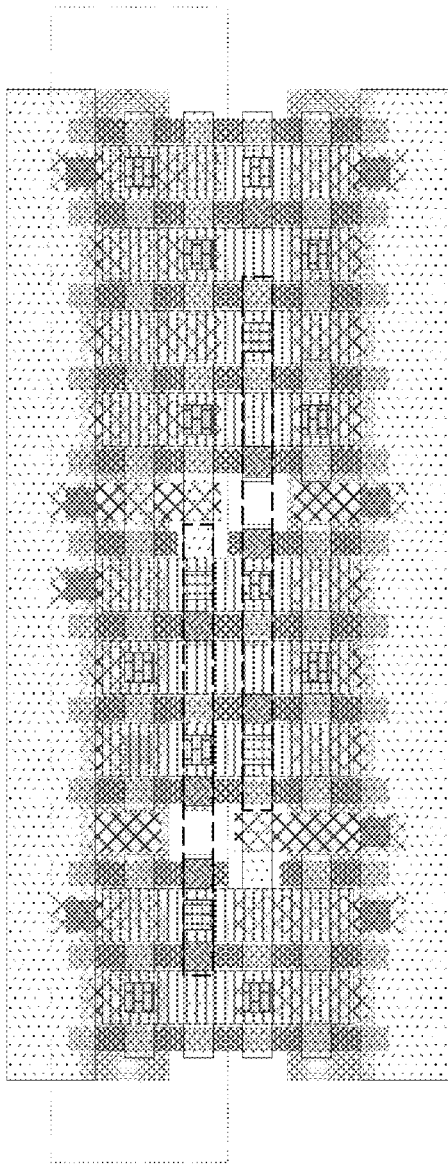


FIG. 91A

xor2x1

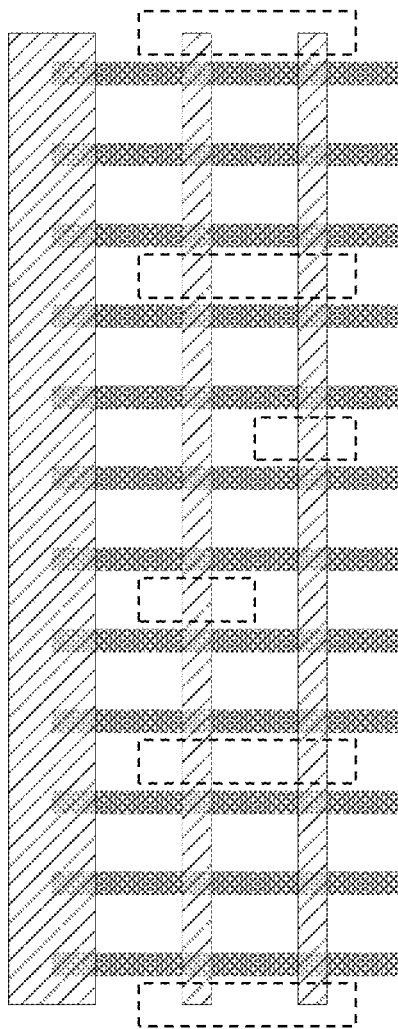


FIG. 91B

xor2x1

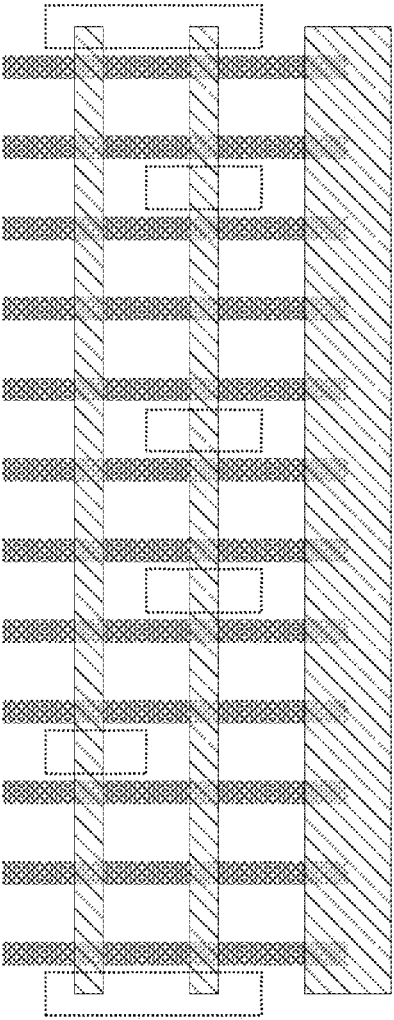


FIG. 91C

xor2x1

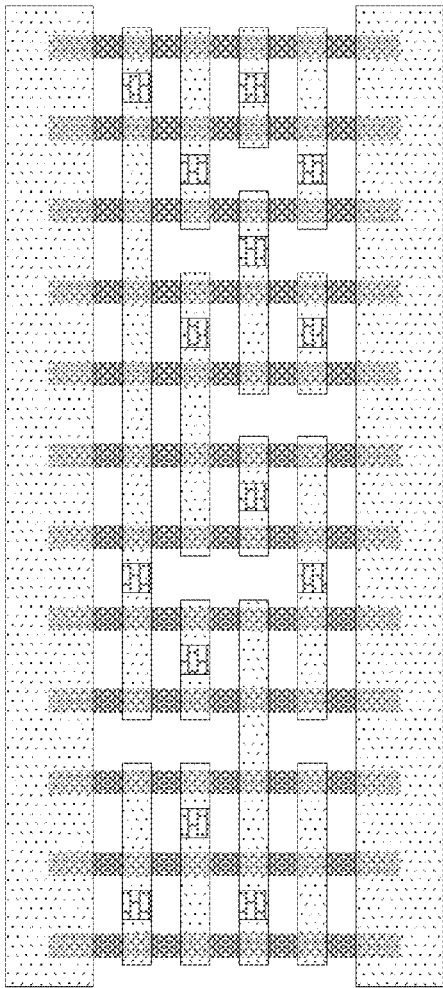


FIG. 91D

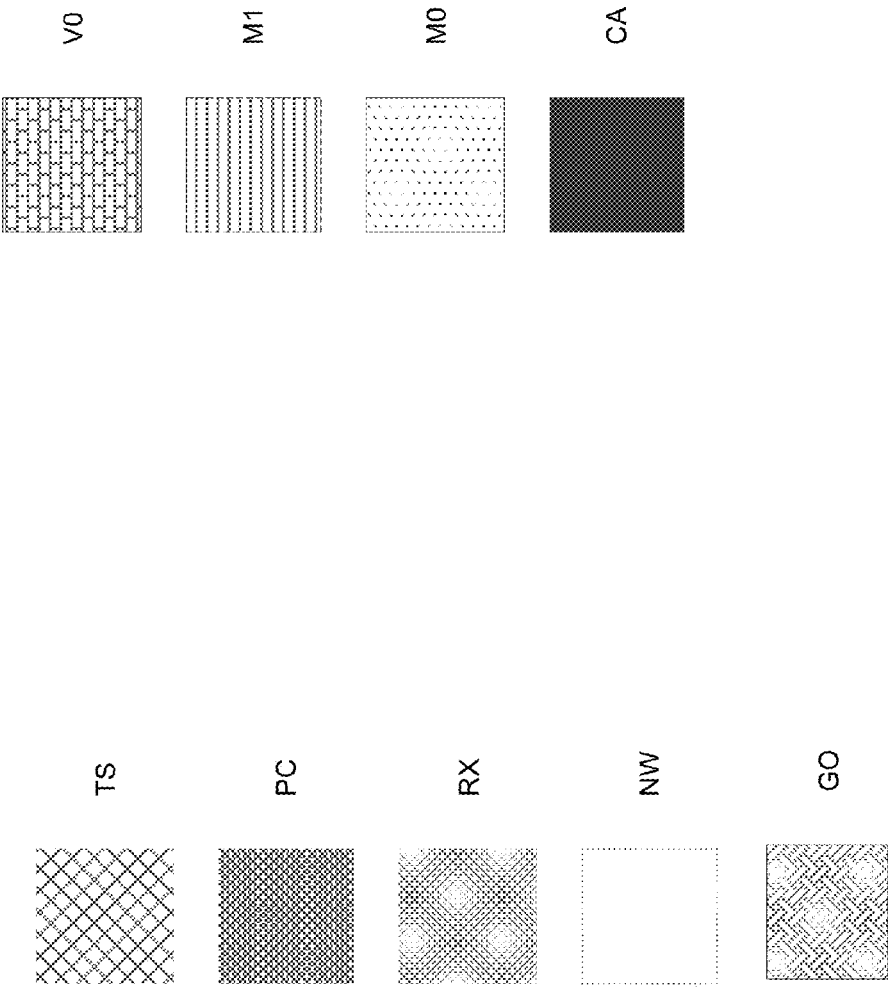


FIG. 92

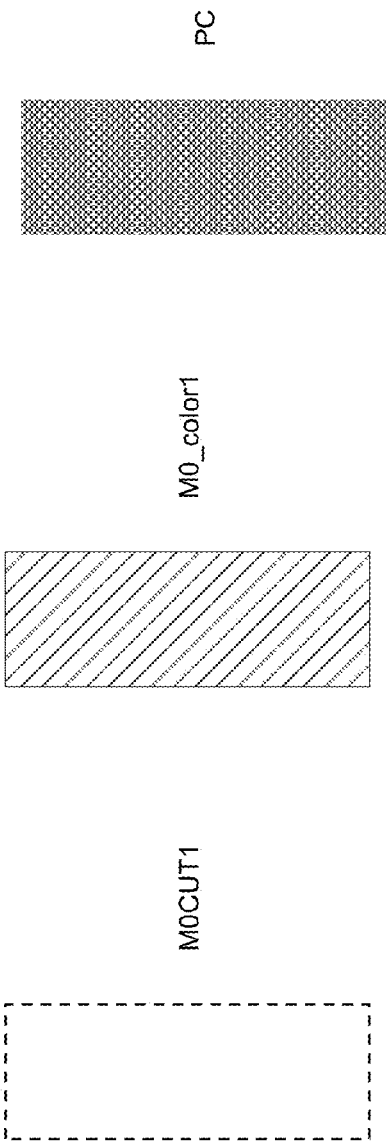


FIG. 93

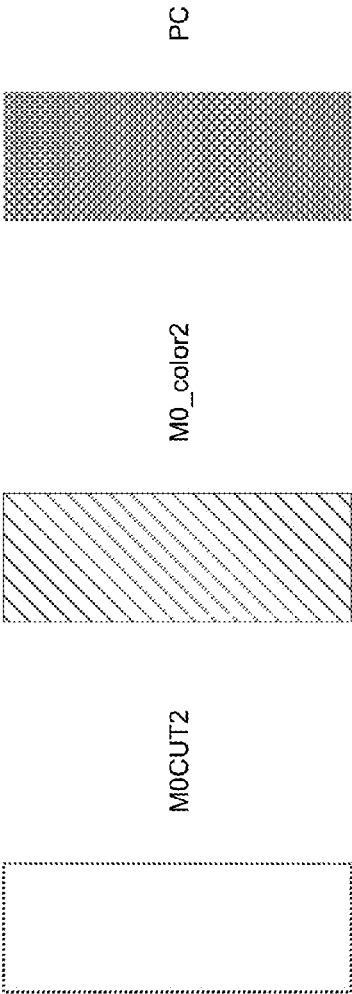


FIG. 94

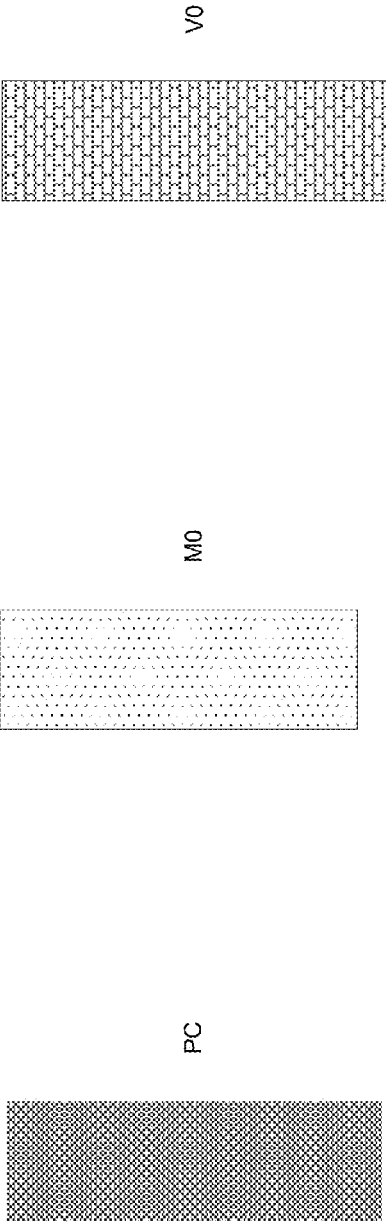


FIG. 95

1

STANDARD CELL LIBRARY WITH DFM-OPTIMIZED M0 CUTS AND V0 ADJACENCIES

CROSS-REFERENCE TO RELATED APPLICATION(S)

This application is a continuation-in-part of U.S. patent application Ser. No. 15/067,252, entitled "Standard Cell Library with DFM-Optimized M0 Cuts," filed Mar. 11, 2016, by the present applicant, which '252 application is incorporated by reference herein.

MASK WORK NOTICE

A portion of the disclosure of this patent document contains material which is subject to mask work protection, *M*, PDF Solutions, Inc. The mask work owner (PDF Solutions, Inc.) has no objection to the facsimile reproduction by anyone of the patent document or the patent disclosure, as it appears in the Patent and Trademark Office patent file or records, but otherwise reserves all mask work rights whatsoever.

FIELD OF THE INVENTION

This invention relates to design for manufacturability (DFM) of standard cells for advanced semiconductor processes (e.g., 10 nm, 7 nm), to libraries containing such cells, and to wafers/chips that contain instances of such cells.

BACKGROUND OF THE INVENTION

As semiconductor processes advance to render increasingly smaller features, the design of dense, high-yielding (manufacturable) cells becomes increasingly challenging. See, e.g., U.S. Pat. No. 9,202,820, "Flip-flop, latch, and mux cells for use in a standard cell library and integrated circuits made therefrom," to the inventor herein.

In the most advanced processes, patterning of critical layers is typically restricted to one direction (unidirectional) in each layer, delimited by cut masks, with the cut masks increasingly multi-patterned. In such technologies, careful attention to often non-obvious potential manufacturability problems is critical to successful implementation of a standard cell library. The invention, as described in detail below, provides an example of a DFM-optimized standard cell library for use in such advanced semiconductor processes.

SUMMARY OF THE INVENTION

One aspect of the invention relates to a library of DFM-improved standard cells, optimized for use in advanced semiconductor processes that include multi-patterned M0 cut masks.

Another aspect of the invention relates to wafers, chips, and systems that include such DFM-improved cells.

Applicant has discovered that, with very careful design, seemingly incompatible demands for cell density and avoidance of certain difficult-to-manufacture features can be simultaneously achieved. In particular, as exemplified by the depicted cells herein, the present invention provides a library of competitively dense logic cells with highly-optimized patterning in the first-level metal (M0) and/or via to interconnect (V0) layer(s). As described in greater detail below, such patterning avoids one or more of: (i) spacing M0 cuts so close to each other that they increase the risk of

2

manufacturing failure; (ii) spacing V0 vias so close to each other that they increase the risk of manufacturing failure; and/or (iii) spacing V0 vias and M0 cuts so close to each other that they increase the risk of manufacturing failure.

Accordingly, generally speaking, and without intending to be limiting, certain aspects of the invention relate to collections of standard logic cells, implementing a plurality of logic functions, wherein each standard cell comprises, for example, at least the following: two elongated supply rails, each formed in a first metal (M0) layer, each supply rail having a width at least twice a minimum permitted width for M0 features, and each supply rail extending horizontally across the entire width of the standard cell; at least three elongated gate stripes, each formed in a gate (PC) layer, and each extending vertically between at least two of the supply rails, with adjacent gate stripes spaced at a minimum contacted poly pitch (CPP); positioned vertically between the supply rails, at least two, first-exposure M0 tracks, each of the first-exposure M0 tracks having the minimum permitted width and extending horizontally across the cell, the first-exposure M0 tracks patterned, in part, by portion(s) of a first-exposure M0 mask (M0_color1) and, in part, by portion(s) of a first-exposure M0 cut mask (M0CUT1); positioned vertically between the supply rails, at least two, second-exposure M0 tracks, each of the second-exposure M0 tracks having the minimum permitted width and extending horizontally across the cell, the second-exposure M0 tracks patterned, in part, by portion(s) of a second-exposure M0 mask (M0_color2) and, in part, by portion(s) of a second-exposure M0 cut mask (M0CUT2); and additional patterned features, in NW (N-well), TS (trench silicide), RX (active), CA (contact to active), GO (gate open, a/k/a CB), V0 (via to interconnect), and M1 (first-level interconnect) layers, configured to realize a logical function or behavior of the standard cell; wherein within in the cell: all M0CUT1 features are rectangular in shape, with a left edge, right edge, top edge, and bottom edge, and as between any two first and second M0CUT1 features within the cell, there is at least 2xCPP of spacing between all points at which the left edge of the first M0CUT1 feature intersects an M0color1 feature and all points at which the left edge of the second M0CUT1 feature intersects an M0color1 feature, and there is at least 2xCPP of spacing between all points at which the right edge of the first M0CUT1 feature intersects an M0color1 feature and all points at which the right edge of the second M0CUT1 feature intersects an M0color1 feature; and all M0CUT2 features are rectangular in shape, with a left edge, right edge, top edge, and bottom edge, and as between any two first and second M0CUT2 features within the cell, there is at least 2xCPP of spacing between all points at which the left edge of the first M0CUT2 feature intersects an M0color2 feature and all points at which the left edge of the second M0CUT2 feature intersects an M0color2 feature, and there is at least 2xCPP of spacing between all points at which the right edge of the first M0CUT2 feature intersects an M0color2 feature and all points at which the right edge of the second M0CUT2 feature intersects an M0color2 feature. Such collections may be embodied on silicon wafers, chips, or systems, or as instructions for patterning such cells, where such instruction are contained in a non-transient, computer-readable mediums, in data formats such as GDSII. Such collections preferably include cells implementing at least four, six, eight, ten, twelve, fourteen, sixteen, eighteen, twenty or more logical functions selected from the following list, each of which may be provided in multiple drive strength variants:

3

1. the logic function of a 2-input AND;
2. the logic function of a 3-input AND;
3. the logic function of a 4-input AND;
4. the logic function $\text{OR}(\text{AND}(a,b),c)$;
5. the logic function $\text{OR}(\text{AND}(a,b),c,d)$;
6. the logic function $\text{OR}(\text{AND}(a,b),c,d)$;
7. the logic function $\text{NOT}(\text{OR}(\text{AND}(a,b),c,d))$;
8. the logic function $\text{NOT}(\text{OR}(\text{AND}(a,b),\text{AND}(c,d)))$;
9. the logic function $\text{NOT}(\text{OR}(\text{AND}(a,b,c),d))$;
10. the logic function $\text{NOT}(\text{OR}(\text{AND}(a,b),c,d))$;
11. the logic function $\text{NOT}(\text{OR}(\text{AND}(a,b),\text{AND}(c,d),\text{AND}(e,f)))$;
12. the logic function of a buffer;
13. the logic function of a clock-gating latch;
14. the logic function of a delay gate;
15. the logic function of a full adder;
16. the logic function of a half adder;
17. the logic function $\text{NOT}(\text{OR}(\text{AND}(a,b),c))$, with one of its inputs inverted;
18. the logic function of a 2-input NAND, with one of its inputs inverted;
19. the logic function of a 3-input NAND, with one of its inputs inverted;
20. the logic function of a 2-input NOR, with one of its inputs inverted;
21. the logic function of a 3-input NOR, with one of its inputs inverted;
22. the logic function of an inverter;
23. the logic function $\text{NOT}(\text{AND}(\text{OR}(a,b),c))$, with one of its inputs inverted;
24. the logic function of a latch;
25. the logic function of a 2-input MUX;
26. the logic function of a 2-input MUX, with one of its inputs inverted;
27. the logic function of a 2-input NAND;
28. the logic function of a 3-input NAND;
29. the logic function of a 4-input NAND;
30. the logic function of a 2-input NOR;
31. the logic function of a 3-input NOR;
32. the logic function of a 4-input NOR;
33. the logic function $\text{AND}(\text{OR}(a,b),c)$;
34. the logic function $\text{AND}(\text{OR}(a,b,c),d)$;
35. the logic function $\text{AND}(\text{OR}(a,b),c,d)$;
36. the logic function $\text{NOT}(\text{AND}(\text{OR}(a,b),c))$;
37. the logic function $\text{NOT}(\text{AND}(\text{OR}(a,b),\text{OR}(c,d)))$;
38. the logic function $\text{NOT}(\text{AND}(\text{OR}(a,b,c),d))$;
39. the logic function $\text{NOT}(\text{AND}(\text{OR}(a,b),c,d))$;
40. the logic function $\text{NOT}(\text{AND}(\text{OR}(a,b),\text{OR}(c,d),\text{OR}(e,f)))$;
41. the logic function of a 2-input OR;
42. the logic function of a 3-input OR;
43. the logic function of a 4-input OR;
44. the logic function of a scan-enabled D flip-flop;
45. the logic function of a scan-enabled D flip-flop, with set and reset;
46. the logic function 1;
47. the logic function 0;
48. the logic function of a 2-input XNOR; and,
49. the logic function of a 2-input XOR.

Again, generally speaking, and without intending to be limiting, other aspects of the invention relate to collections of standard logic cells, implementing a plurality of logic functions, wherein each standard cell comprises, for example, at least the following: at least two elongated supply rails, extending horizontally across the standard cell; at least three elongated gate stripes, each extending vertically between at least two of said supply rails, adjacent gate

4

stripes spaced at a minimum contacted poly pitch (CPP); positioned vertically between the supply rails, one or more first-exposure M0 tracks, each of the first-exposure M0 tracks having a minimum permitted width for M0 patterning and extending horizontally across the cell, the first-exposure M0 tracks patterned, in part, by feature(s) of a first-exposure M0 mask (M0_color1) and, in part, by feature(s) of a first-exposure M0 cut mask (M0CUT1); positioned vertically between the supply rails, one or more second-exposure M0 tracks, each of the second-exposure M0 tracks having the minimum permitted width and extending horizontally across the cell, the second-exposure M0 tracks patterned, in part, by feature(s) of a second-exposure M0 mask (M0_color2) and, in part, by feature(s) of a second-exposure M0 cut mask (M0CUT2); and means, including additional patterned features in NW (N-well), TS (trench silicide), RX (active), CA (contact to active), GO (gate open), V0 (via to interconnect), and M1 (first-level interconnect) layers, configured to realize a logical function or behavior of the standard cell; and wherein within in the cell: all M0CUT1 features are rectangular in shape, with a left edge, right edge, top edge, and bottom edge, and as between any two first and second M0CUT1 features within the cell, there is at least 2xCPP of spacing between all points at which the left edge of the first M0CUT1 feature intersects an M0color1 feature and all points at which the left edge of the second M0CUT1 feature intersects an M0color1 feature, and there is at least 2xCPP of spacing between all points at which the right edge of the first M0CUT1 feature intersects an M0color1 feature and all points at which the right edge of the second M0CUT1 feature intersects an M0color1 feature; and all M0CUT2 features are rectangular in shape, with a left edge, right edge, top edge, and bottom edge, and as between any two first and second M0CUT2 features within the cell, there is at least 2xCPP of spacing between all points at which the left edge of the first M0CUT2 feature intersects an M0color2 feature and all points at which the left edge of the second M0CUT2 feature intersects an M0color2 feature, and there is at least 2xCPP of spacing between all points at which the right edge of the first M0CUT2 feature intersects an M0color2 feature and all points at which the right edge of the second M0CUT2 feature intersects an M0color2 feature.

Again, generally speaking, and without intending to be limiting, another aspect of the invention relates to collections of standard logic cells, implementing a plurality of logic functions, wherein each standard cell comprises, for example, at least the following: two elongated supply rails, each formed in a first metal (M0) layer, each supply rail having a width at least twice a minimum permitted width for M0 features, each supply rail extending horizontally across the entire width of the standard cell; at least three elongated gate stripes, each formed in a gate (PC) layer, and each extending vertically between at least two of the supply rails, adjacent gate stripes spaced at a minimum contacted poly pitch (CPP); positioned vertically between the supply rails, at least two, first-exposure M0 tracks, each of the first-exposure M0 tracks having the minimum permitted width and extending horizontally across the cell, the first-exposure M0 tracks patterned, in part, by portion(s) of a first-exposure M0 mask (M0_color1) and, in part, by portion(s) of a first-exposure M0 cut mask (M0CUT1); positioned vertically between the supply rails, at least two, second-exposure M0 tracks, each of the second-exposure M0 tracks having the minimum permitted width and extending horizontally across the cell, the second-exposure M0 tracks patterned, in part, by portion(s) of a second-exposure M0 mask (M0_color2) and, in part, by portion(s) of a second-exposure

M0 cut mask (M0CUT2); a plurality of vias, patterned in a V0 (via to interconnect) layer, each of the plurality of vias instantiated on an M0 track; additional patterned features, in NW (N-well), TS (trench silicide), RX (active), CA (contact to active), GO (gate open), and M1 (first-level interconnect) layers, configured to realize a logical function or behavior of the standard cell; wherein within the cell: all M0CUT1 features are rectangular in shape, with a left edge, right edge, top edge, and bottom edge, and as between any two first and second M0CUT1 features within the cell, there is at least 1.3 (or 1.4, 1.5, 1.6, 1.7, 1.8, 1.9 or 2.0)×CPP of spacing between all points at which the left edge of the first M0CUT1 feature intersects an M0color1 feature and all points at which the left edge of the second M0CUT1 feature intersects an M0color1 feature, and there is at least 1.3 (or 1.4, 1.5, 1.6, 1.7, 1.8, 1.9 or 2.0)×CPP of spacing between all points at which the right edge of the first M0CUT1 feature intersects an M0color1 feature and all points at which the right edge of the second M0CUT1 feature intersects an M0color1 feature; all M0CUT2 features are rectangular in shape, with a left edge, right edge, top edge, and bottom edge, and as between any two first and second M0CUT2 features within the cell, there is at least 1.3 (or 1.4, 1.5, 1.6, 1.7, 1.8, 1.9 or 2.0)×CPP of spacing between all points at which the left edge of the first M0CUT2 feature intersects an M0color2 feature and all points at which the left edge of the second M0CUT2 feature intersects an M0color2 feature, and there is at least 1.3 (or 1.4, 1.5, 1.6, 1.7, 1.8, 1.9 or 2.0)×CPP of spacing between all points at which the right edge of the first M0CUT2 feature intersects an M0color2 feature and all points at which the right edge of the second M0CUT2 feature intersects an M0color2 feature; and, among the plurality of vias, each is spaced from its nearest neighbor by more than the edge-to-edge distance between adjacent M0 tracks. In some embodiments, each of the plurality of vias is also spaced at least 0.7 (or 0.8, 0.9 or 1.0)×CPP from the nearest cut in the M0 track in which said via is instantiated, with the spacing measured as the horizontal distance between the center of the via and the center of the cut.

Again, generally speaking, and without intending to be limiting, another aspect of the invention relates to collections of at least five (or six, seven, eight, ten, twelve, fifteen or more) standard logic cells, each implementing a different logic function, wherein each standard cell comprises, for example, at least the following: at least two elongated supply rails, extending horizontally across the standard cell; at least three elongated gate stripes, each extending vertically between at least two of said supply rails, adjacent gate stripes spaced at a minimum contacted poly pitch (CPP); positioned vertically between the supply rails, a plurality of M0 tracks, including one or more first-exposure M0 tracks, each of the first-exposure M0 tracks having a minimum permitted width for M0 patterning and extending horizontally across the cell, and one or more second-exposure M0 tracks, each of the second-exposure M0 tracks having the minimum permitted width and extending horizontally across the cell; a plurality of vias, patterned in a V0 (via to interconnect) layer, each of the plurality of vias instantiated on an M0 track; and, means, including additional patterned features in NW (N-well), TS (trench silicide), RX (active), CA (contact to active), GO (gate open), and M1 (first-level interconnect) layers, configured to realize a logical function or behavior of the standard cell; wherein within the cell, among the plurality of vias, each is spaced from its nearest neighbor by more than the edge-to-edge distance between adjacent M0 tracks. In some embodiments, each of the

plurality of vias is spaced at least 0.8 (or 0.7, 0.9 or 1.0)×CPP from the nearest cut in the M0 track in which the via is instantiated, with the spacing measured as the horizontal distance between the center of the via and the center of the cut. In some embodiments, the first-exposure M0 tracks are patterned, in part, by feature(s) of a first-exposure M0 mask (M0_color1) and, in part, by feature(s) of a first-exposure M0 cut mask (M0CUT1); the second-exposure M0 tracks are patterned, in part, by feature(s) of a second-exposure M0 mask (M0_color2) and, in part, by feature(s) of a second-exposure M0 cut mask (M0CUT2); all M0CUT1 features are rectangular in shape, with a left edge, right edge, top edge, and bottom edge, and as between any two first and second M0CUT1 features within the cell, there is at least 1.3 (or 1.4, 1.5, 1.6, 1.7, 1.8, 1.9 or 2.0)×CPP of spacing between all points at which the left edge of the first M0CUT1 feature intersects an M0color1 feature and all points at which the left edge of the second M0CUT1 feature intersects an M0color1 feature, and there is at least 1.3 (or 1.4, 1.5, 1.6, 1.7, 1.8, 1.9 or 2.0)×CPP of spacing between all points at which the right edge of the first M0CUT1 feature intersects an M0color1 feature and all points at which the right edge of the second M0CUT1 feature intersects an M0color1 feature; and, all M0CUT2 features are rectangular in shape, with a left edge, right edge, top edge, and bottom edge, and as between any two first and second M0CUT2 features within the cell, there is at least 1.3 (or 1.4, 1.5, 1.6, 1.7, 1.8, 1.9 or 2.0)×CPP of spacing between all points at which the left edge of the first M0CUT2 feature intersects an M0color2 feature and all points at which the left edge of the second M0CUT2 feature intersects an M0color2 feature, and there is at least 1.3 (or 1.4, 1.5, 1.6, 1.7, 1.8, 1.9 or 2.0)×CPP of spacing between all points at which the right edge of the first M0CUT2 feature intersects an M0color2 feature and all points at which the right edge of the second M0CUT2 feature intersects an M0color2 feature.

BRIEF DESCRIPTION OF THE DRAWINGS

The above, as well as other, aspects, features and advantages of the present invention are illustrated in the accompanying set of figures, which are rendered to relative scale, and in which:

FIGS. 1A-D depict an sddfxq1_alt cell;
 FIGS. 2A-D depict a mux2x1_alt cell;
 FIGS. 3A-D depict an an2x1 cell;
 FIGS. 4A-D depict an an2x2 cell;
 FIGS. 5A-D depict an an3x1 cell;
 FIGS. 6A-D depict an an3x2 cell;
 FIGS. 7A-D depict an an4x1 cell;
 FIGS. 8A-D depict an an4x2 cell;
 FIGS. 9A-D depict an ao21x1 cell;
 FIGS. 10A-D depict an ao31x1 cell;
 FIGS. 11A-D depict an ao211x1 cell;
 FIGS. 12A-D depict an aoi21x1 cell;
 FIGS. 13A-D depict an aoi21x2 cell;
 FIGS. 14A-D depict an aoi22x1 cell;
 FIGS. 15A-D depict an aoi22x2 cell;
 FIGS. 16A-D depict an aoi31x1 cell;
 FIGS. 17A-D depict an aoi31x2 cell;
 FIGS. 18A-D depict an aoi211x1 cell;
 FIGS. 19A-D depict an aoi222x1 cell;
 FIGS. 20A-D depict an bufhx6 cell;
 FIGS. 21A-D depict an bufx1 cell;
 FIGS. 22A-D depict an bufx2 cell;
 FIGS. 23A-D depict an bufx3 cell;

FIGS. 24A-D depict an bufx4 cell;
 FIGS. 25A-D depict an bufx6 cell;
 FIGS. 26A-D depict an bufx8 cell;
 FIGS. 27A-D depict an ckor2lban2x1 cell;
 FIGS. 28A-D depict an dlyx1 cell;
 FIGS. 29A-D depict an fax1 cell;
 FIGS. 30A-D depict an hax1 cell;
 FIGS. 31A-D depict an iaai21x1 cell;
 FIGS. 32A-D depict an ind2x1 cell;
 FIGS. 33A-D depict an ind2x2 cell;
 FIGS. 34A-D depict an ind3x1 cell;
 FIGS. 35A-D depict an ind3x2 cell;
 FIGS. 36A-D depict an inr2x1 cell;
 FIGS. 37A-D depict an inr2x2 cell;
 FIGS. 38A-D depict an inr3x1 cell;
 FIGS. 39A-D depict an inr3x2 cell;
 FIGS. 40A-D depict an invx1 cell;
 FIGS. 41A-D depict an invx2 cell;
 FIGS. 42A-D depict an invx4 cell;
 FIGS. 43A-D depict an invx6 cell;
 FIGS. 44A-D depict an invx8 cell;
 FIGS. 45A-D depict an ioai21x1 cell;
 FIGS. 46A-D depict an latqx1 cell;
 FIGS. 47A-D depict an mux2x1 cell;
 FIGS. 48A-D depict an mux2x2 cell;
 FIGS. 49A-D depict an muxi2x1 cell;
 FIGS. 50A-D depict an nd2x1 cell;
 FIGS. 51A-D depict an nd2x2 cell;
 FIGS. 52A-D depict an nd2x3 cell;
 FIGS. 53A-D depict an nd2x4 cell;
 FIGS. 54A-D depict an nd3x1 cell;
 FIGS. 55A-D depict an nd3x2 cell;
 FIGS. 56A-D depict an nd3x3 cell;
 FIGS. 57A-D depict an nd3x4 cell;
 FIGS. 58A-D depict an nd4x1 cell;
 FIGS. 59A-D depict an nd4x2 cell;
 FIGS. 60A-D depict an nr2x1 cell;
 FIGS. 61A-D depict an nr2x2 cell;
 FIGS. 61.1A-D depict an nr2x3 cell;
 FIGS. 62A-D depict an nr2x4 cell;
 FIGS. 63A-D depict an nr3x1 cell;
 FIGS. 64A-D depict an nr3x2 cell;
 FIGS. 65A-D depict an nr3x3 cell;
 FIGS. 66A-D depict an nr3x4 cell;
 FIGS. 67A-D depict an nr4x1 cell;
 FIGS. 68A-D depict an nr4x2 cell;
 FIGS. 69A-D depict an oa21x1 cell;
 FIGS. 70A-D depict an oa31x1 cell;
 FIGS. 71A-D depict an oa211x1 cell;
 FIGS. 72A-D depict an oai21x1 cell;
 FIGS. 73A-D depict an oai21x2 cell;
 FIGS. 74A-D depict an oai22x1 cell;
 FIGS. 75A-D depict an oai22x2 cell;
 FIGS. 76A-D depict an oai31x1 cell;
 FIGS. 77A-D depict an oai31x2 cell;
 FIGS. 78A-D depict an oai211x1 cell;
 FIGS. 79A-D depict an oai222x1 cell;
 FIGS. 80A-D depict an or2x1 cell;
 FIGS. 81A-D depict an or2x2 cell;
 FIGS. 82A-D depict an or3x1 cell;
 FIGS. 83A-D depict an or3x2 cell;
 FIGS. 84A-D depict an or4x1 cell;
 FIGS. 85A-D depict an or4x2 cell;
 FIGS. 86A-D depict an sddfxq1 cell;
 FIGS. 87A-D depict an sddfrsqx1 cell;
 FIGS. 88A-D depict an tiehix1 cell;
 FIGS. 89A-D depict an tielox1 cell;

FIGS. 90A-D depict an xnr2x1 cell;
 FIGS. 91A-D depict an xor2x1 cell;
 FIG. 92 contains a layer legend for the A-labeled (i.e., 1A, 2A, 3A, etc.) figures;
 FIG. 93 contains a layer legend the B-labeled figures;
 FIG. 94 contains a layer legend for the C-labeled figures;
 and,
 FIG. 95 contains a layer legend for the D-labeled figures.

DESCRIPTION OF EXEMPLARY EMBODIMENT(S)

FIGS. 92-95 show layer maps for the respective A-labeled, B-labeled, C-labeled, and D-labeled figures that follow. With reference to FIG. 92, the full set of depicted layers includes: M0 (first metal), NW (N-well), TS (trench silicide), RX (active), CA (contact to active), PC (gate, a/k/a polysilicon or poly—although the gate material in advanced processes is typically metallic), GO (gate open, a/k/a CB), V0 (via to interconnect), and M1 (first-level interconnect). Persons skilled in the art will appreciate that any of these layers may be created through multiple exposure (e.g., double, triple or quadruple patterned) processes, and/or through use of cut masks, which themselves may be multi-patterned. The A-labeled figures in this application are intended to show the resulting complete cells as clearly as possible; thus, the details of multi-patterning and cut-masking have been eliminated from these figures.

Referring now to FIGS. 93 and 94, these show the layer maps for the B-labeled and C-labeled figures, which depict the multi-patterning, cut-masked details of M0 patterning in the inventive cells. In particular, in the exemplary embodiment herein, M0 is patterned in two exposures (M0_color1 and M0_color2), each of which is patterned by its own cut mask (M0CUT1 and M0CUT2, respectively). PC is shown in both the A-labeled and B-labeled figures as a measurement reference. Persons skilled in the art will understand that variations on the M0 process are possible. For example, M0 may be triple patterned, with a separate cut mask for each exposure, and/or an additional cut mask may be provided that cuts both (or all) exposures of M0.

Referring now to FIG. 95, which shows a layer map for the D-labeled figures, these figures depict the V0 patterning details of the cells, with M0 and PC layers shown for reference. Persons skilled in the art will understand that variations on the V0 process are possible. For example, V0 may be double or triple patterned, with a separate cut mask for each exposure, and/or an additional cut mask may be provided that cuts all exposures.

Reference is now made to FIGS. 1A-D, which depict an sddfx1_alt cell. This cell implements the logic function of a scan-enabled, D flip-flop, in drive strength 1. This cell is an example of a state-of-the-art layout that, nevertheless, does not meet the objects of the present invention. Referring first to FIG. 1B, one can see that CPP (contacted poly pitch) can be equivalently measured as the left-edge-to-left-edge distance, center-to-center distance, or right-edge-to-right-edge distance between adjacent gate stripes. As further depicted in FIG. 1B, this cell contains several undesirable configurations in the first-exposure M0 layer: two instances of left-edge-to-left-edge first-exposure M0 cuts with spacing (1 and 3) of less than 2×CPP; and an instance of right-edge-to-right-edge first-exposure M0 cuts with a spacing (2) of less than 2×CPP. (Note, there may be additional violations on this layout, and others that follow in FIGS. 1C and 2B-C. The flagged examples are intended to be exemplary, not exhaustive.) Referring now to FIG. 1C, additional undesir-

able configurations in the second-exposure M0 layer are flagged: an instance of left-edge-to-left-edge second-exposure M0 cuts with a spacing (4) of less than 2×CPP; and an instance of right-edge-to-right-edge second-exposure M0 cuts with a spacing (5) of less than 2×CPP. Referring now to FIG. 1D, this cell also contains several undesirable configurations in the V0 layer: (i) four instances (11-14) of adjacent V0 vias in adjacent M0 tracks (i.e., V0 vias with a spacing less than or equal to the minimum spacing between adjacent M0 tracks); and (ii) two instances (17-18) of V0 vias in the same M0 track, separated by an M0 cut of less than one CPP.

Reference is now made to FIGS. 2A-D, which depict a mux2x1_alt cell. This cell implements the logic function of a 2-input MUX, in drive strength 1. This cell is another example of a state-of-the-art layout that, nevertheless, does not meet the DFM objects of the present invention. As flagged in FIGS. 2B and 2C, this cell contains undesirable spacings between cuts in the first-exposure M0 layer (see 7 on FIG. 2B) and between cuts in the second-exposure M0 layer (see 8 and 9 in FIG. 2C). Referring now to FIG. 2D, this cell also contains several undesirable configurations in the V0 layer: (i) one instance (15) of adjacent V0 vias in adjacent M0 tracks; and (ii) three instances (19-21) of V0 vias in the same M0 track, separated by an M0 cut of less than one CPP.

FIGS. 3A-D, et seq., as described below, contain examples of cells that meet the DFM objects of the present invention, and collectively comprise the exemplary, inventive library herein.

Reference is now made to FIGS. 3A-D, which depict an an2x1 cell. This cell implements the logic function of a 2-input AND, in drive strength 1. This cell is 4 CPP wide.

Reference is now made to FIGS. 4A-D, which depict an an2x2 cell. This cell implements the logic function of a 2-input AND, in drive strength 2. This cell is 5 CPP wide.

Reference is now made to FIGS. 5A-D, which depict an an3x1 cell. This cell implements the logic function of a 3-input AND, in drive strength 1. This cell is 6 CPP wide.

Reference is now made to FIGS. 6A-D, which depict an an3x2 cell. This cell implements the logic function of a 3-input AND, in drive strength 2. This cell is 7 CPP wide.

Reference is now made to FIGS. 7A-D, which depict an an4x1 cell. This cell implements the logic function of a 4-input AND, in drive strength 1. This cell is 7 CPP wide.

Reference is now made to FIGS. 8A-D, which depict an an4x2 cell. This cell implements the logic function of a 4-input AND, in drive strength 2. This cell is 8 CPP wide.

Reference is now made to FIGS. 9A-D, which depict an ao21x1 cell. This cell implements the logic function $\text{OR}(\text{AND}(a,b),c)$, in drive strength 1. This cell is 6 CPP wide.

Reference is now made to FIGS. 10A-D, which depict an ao31x1 cell. This cell implements the logic function $\text{OR}(\text{AND}(a,b,c),d)$, in drive strength 1. This cell is 7 CPP wide.

Reference is now made to FIGS. 11A-D, which depict an ao211x1 cell. This cell implements the logic function $\text{OR}(\text{AND}(a,b),c,d)$, in drive strength 1. This cell is 7 CPP wide.

Reference is now made to FIGS. 12A-D, which depict an ao121x1 cell. This cell implements the logic function $\text{NOT}(\text{OR}(\text{AND}(a,b),c))$, in drive strength 1. This cell is 4 CPP wide.

Reference is now made to FIGS. 13A-D, which depict an ao121x2 cell. This cell implements the logic function $\text{NOT}(\text{OR}(\text{AND}(a,b),c))$, in drive strength 2. This cell is 7 CPP wide.

Reference is now made to FIGS. 14A-D, which depict an ao122x1 cell. This cell implements the logic function $\text{NOT}(\text{OR}(\text{AND}(a,b),\text{AND}(c,d)))$, in drive strength 1. This cell is 5 CPP wide.

Reference is now made to FIGS. 15A-D, which depict an ao122x2 cell. This cell implements the logic function $\text{NOT}(\text{OR}(\text{AND}(a,b),\text{AND}(c,d)))$, in drive strength 2. This cell is 9 CPP wide.

Reference is now made to FIGS. 16A-D, which depict an ao131x1 cell. This cell implements the logic function $\text{NOT}(\text{OR}(\text{AND}(a,b,c),d))$, in drive strength 1. This cell is 5 CPP wide.

Reference is now made to FIGS. 17A-D, which depict an ao131x2 cell. This cell implements the logic function $\text{NOT}(\text{OR}(\text{AND}(a,b,c),d))$, in drive strength 2. This cell is 9 CPP wide.

Reference is now made to FIGS. 18A-D, which depict an ao1211x1 cell. This cell implements the logic function $\text{NOT}(\text{OR}(\text{AND}(a,b),c,d))$, in drive strength 1. This cell is 5 CPP wide.

Reference is now made to FIGS. 19A-D, which depict an ao1222x1 cell. This cell implements the logic function $\text{NOT}(\text{OR}(\text{AND}(a,b),\text{AND}(c,d),\text{AND}(e,f)))$, in drive strength 1. This cell is 9 CPP wide.

Reference is now made to FIGS. 20A-D, which depict an bufhx6 cell. This cell implements the logic function of a buffer, in drive strength 6. This cell is 10 CPP wide.

Reference is now made to FIGS. 21A-D, which depict an bufx1 cell. This cell implements the logic function of a buffer, in drive strength 1. This cell is 3 CPP wide.

Reference is now made to FIGS. 22A-D, which depict an bufx2 cell. This cell implements the logic function of a buffer, in drive strength 2. This cell is 4 CPP wide.

Reference is now made to FIGS. 23A-D, which depict an bufx3 cell. This cell implements the logic function of a buffer, in drive strength 3. This cell is 5 CPP wide.

Reference is now made to FIGS. 24A-D, which depict an bufx4 cell. This cell implements the logic function of a buffer, in drive strength 4. This cell is 7 CPP wide.

Reference is now made to FIGS. 25A-D, which depict an bufx6 cell. This cell implements the logic function of a buffer, in drive strength 6. This cell is 9 CPP wide.

Reference is now made to FIGS. 26A-D, which depict an bufx8 cell. This cell implements the logic function of a buffer, in drive strength 8. This cell is 12 CPP wide.

Reference is now made to FIGS. 27A-D, which depict an ckor2lban2x1 cell. This cell implements the logic function of a clock-gating latch, in drive strength 1. This cell is 17 CPP wide.

Reference is now made to FIGS. 28A-D, which depict an dlyx1 cell. This cell implements the logic function of a delay gate, in drive strength 1. This cell is 9 CPP wide.

Reference is now made to FIGS. 29A-D, which depict an fax1 cell. This cell implements the logic function of a full adder, in drive strength 1. This double-height cell is 10 CPP wide.

Reference is now made to FIGS. 30A-D, which depict an hax1 cell. This cell implements the logic function of a half adder, in drive strength 1. This double-height cell is 8 CPP wide.

Reference is now made to FIGS. 31A-D, which depict an iaol21x1 cell. This cell implements the logic function $\text{NOT}(\text{OR}(\text{AND}(a,b),c))$, with one of the inputs inverted, in drive strength 1. This cell is 5 CPP wide.

Reference is now made to FIGS. 32A-D, which depict an ind2x1 cell. This cell implements the logic function of a

Reference is now made to FIGS. 50A-D, which depict an nd2x1 cell. This cell implements the logic function of a 2-input NAND, in drive strength 1. This cell is 3 CPP wide.

Reference is now made to FIGS. 71A-D, which depict an oa211x1 cell. This cell implements the logic function AND (OR(a,b).c.d), in drive strength 1. This cell is 7 CPP wide.

13

Reference is now made to FIGS. 72A-D, which depict an oai21x1 cell. This cell implements the logic function NOT (AND(OR(a,b),c)), in drive strength 1. This cell is 4 CPP wide.

Reference is now made to FIGS. 73A-D, which depict an oai21x2 cell. This cell implements the logic function NOT (AND(OR(a,b),c)), in drive strength 2. This cell is 7 CPP wide.

Reference is now made to FIGS. 74A-D, which depict an oai22x1 cell. This cell implements the logic function NOT (AND(OR(a,b),OR(c,d)), in drive strength 1. This cell is 5 CPP wide.

Reference is now made to FIGS. 75A-D, which depict an oai22x2 cell. This cell implements the logic function NOT (AND(OR(a,b),OR(c,d)), in drive strength 2. This cell is 9 CPP wide.

Reference is now made to FIGS. 76A-D, which depict an oai31x1 cell. This cell implements the logic function NOT (AND(OR(a,b,c),d)), in drive strength 1. This cell is 5 CPP wide.

Reference is now made to FIGS. 77A-D, which depict an oai31x2 cell. This cell implements the logic function NOT (AND(OR(a,b,c),d)), in drive strength 2. This cell is 9 CPP wide.

Reference is now made to FIGS. 78A-D, which depict an oai211x1 cell. This cell implements the logic function NOT (AND(OR(a,b),c,d)), in drive strength 1. This cell is 5 CPP wide.

Reference is now made to FIGS. 79A-D, which depict an oai222x1 cell. This cell implements the logic function NOT(AND(OR(a,b),OR(c,d),OR(e,f))), in drive strength 1. This cell is 9 CPP wide.

Reference is now made to FIGS. 80A-D, which depict an or2x1 cell. This cell implements the logic function of a 2-input OR, in drive strength 1. This cell is 4 CPP wide.

Reference is now made to FIGS. 81A-D, which depict an or2x2 cell. This cell implements the logic function of a 2-input OR, in drive strength 2. This cell is 5 CPP wide.

Reference is now made to FIGS. 82A-D, which depict an or3x1 cell. This cell implements the logic function of a 3-input OR, in drive strength 1. This cell is 6 CPP wide.

Reference is now made to FIGS. 83A-D, which depict an or3x2 cell. This cell implements the logic function of a 3-input OR, in drive strength 2. This cell is 7 CPP wide.

Reference is now made to FIGS. 84A-D, which depict an or4x1 cell. This cell implements the logic function of a 4-input OR, in drive strength 1. This cell is 7 CPP wide.

Reference is now made to FIGS. 85A-D, which depict an or4x2 cell. This cell implements the logic function of a 4-input OR, in drive strength 2. This cell is 8 CPP wide.

Reference is now made to FIGS. 86A-D, which depict an sdfdqx1 cell. This cell implements the logic function of a scan-enabled D flip-flop, in drive strength 1. This double-height cell is 13 CPP wide.

Reference is now made to FIGS. 87A-D, which depict an sdfsrqx1 cell. This cell implements the logic function of a scan-enabled D flip-flop, with set and reset, in drive strength 1. This double-height cell is 17 CPP wide.

Reference is now made to FIGS. 88A-D, which depict an tiehix1 cell. This cell implements the logic function 1, in drive strength 1. This cell is 3 CPP wide.

Reference is now made to FIGS. 89A-D, which depict an tielox1 cell. This cell implements the logic function 0, in drive strength 1. This cell is 3 CPP wide.

Reference is now made to FIGS. 90A-D, which depict an xnr2x1 cell. This cell implements the logic function of a 2-input XNOR, in drive strength 1. This cell is 11 CPP wide.

14

Reference is now made to FIGS. 91A-D, which depict an xor2x1 cell. This cell implements the logic function of a 2-input XOR, in drive strength 1. This cell is 11 CPP wide. What is claimed in this application is:

1. A collection of standard logic cells, implementing a plurality of logic functions, wherein each standard cell comprises at least:

two elongated supply rails, each formed in a first metal (M0) layer, each supply rail having a width at least twice a minimum permitted width for M0 features, each supply rail extending horizontally across the entire width of the standard cell;

at least three elongated gate stripes, each formed in a gate (PC) layer, and each extending vertically between at least two of said supply rails, adjacent gate stripes spaced at a minimum contacted poly pitch (CPP);

positioned vertically between said supply rails, at least two, first-exposure M0 tracks, each of said first-exposure M0 tracks having the minimum permitted width and extending horizontally across the cell, said first-exposure M0 tracks patterned, in part, by portion(s) of a first-exposure M0 mask (M0_color1) and, in part, by portion(s) of a first-exposure M0 cut mask (M0CUT1); positioned vertically between said supply rails, at least two, second-exposure M0 tracks, each of said second-exposure M0 tracks having the minimum permitted width and extending horizontally across the cell, said second-exposure M0 tracks patterned, in part, by portion(s) of a second-exposure M0 mask (M0_color2) and, in part, by portion(s) of a second-exposure M0 cut mask (M0CUT2);

a plurality of vias, patterned in a V0 (via to interconnect) layer, each of said plurality of vias instantiated on an M0 track;

additional patterned features, in NW (N-well), TS (trench silicide), RX (active), CA (contact to active), GO (gate open), and M1 (first-level interconnect) layers, configured to realize a logical function or behavior of the standard cell;

wherein within the cell:

all M0CUT1 features are rectangular in shape, with a left edge, right edge, top edge, and bottom edge, and as between any two first and second M0CUT1 features within the cell, there is at least 1.6×CPP of spacing between all points at which the left edge of the first M0CUT1 feature intersects an M0color1 feature and all points at which the left edge of the second M0CUT1 feature intersects an M0color1 feature, and there is at least 1.6×CPP of spacing between all points at which the right edge of the first M0CUT1 feature intersects an M0color1 feature and all points at which the right edge of the second M0CUT1 feature intersects an M0color1 feature;

all M0CUT2 features are rectangular in shape, with a left edge, right edge, top edge, and bottom edge, and as between any two first and second M0CUT2 features within the cell, there is at least 1.6×CPP of spacing between all points at which the left edge of the first M0CUT2 feature intersects an M0color2 feature and all points at which the left edge of the second M0CUT2 feature intersects an M0color2 feature, and there is at least 1.6×CPP of spacing between all points at which the right edge of the first M0CUT2 feature intersects an M0color2 feature and all points at which the right edge of the second M0CUT2 feature intersects an M0color2 feature; and,

15

among said plurality of vias, each is spaced from its nearest neighbor by more than the edge-to-edge distance between adjacent M0 tracks.

2. The collection of standard logic cells, as defined in claim 1, wherein within each cell:

each of said plurality of vias is spaced at least 0.8×CPP from the nearest cut in the M0 track in which said via is instantiated, where said spacing is measured as the horizontal distance between the center of the via and the center of the cut.

3. The collection of standard logic cells, as defined in claim 2, wherein within each cell:

each of said plurality of vias is spaced at least 1.0×CPP from the nearest cut in the M0 track in which said via is instantiated, where said spacing is measured as the horizontal distance between the center of the via and the center of the cut.

4. The collection of standard logic cells, as defined in claim 3, wherein said instructions are contained in a non-transient, computer-readable medium in GDSII format.

5. The collection of standard logic cells, as defined in claim 1, wherein said cells are instantiated on a single silicon chip.

6. The collection of standard logic cells, as defined in claim 1, wherein said cells are instantiated as instructions for patterning features on a silicon wafer.

7. The collection of standard logic cells, as defined in claim 1, wherein the collection includes cells implementing at least four functions selected from the following list:

the logic function of a 2-input AND;
the logic function of a 3-input AND;
the logic function of a 4-input AND;
the logic function OR(AND(a,b),c);
the logic function OR(AND(a,b,c),d);
the logic function OR(AND(a,b),c,d);
the logic function NOT(OR(AND(a,b),c));
the logic function NOT(OR(AND(a,b),AND(c,d)));
the logic function NOT(OR(AND(a,b,c),d));
the logic function NOT(OR(AND(a,b),c,d));
the logic function NOT(OR(AND(a,b),AND(c,d),AND(e,f)));
the logic function of a buffer;
the logic function of a clock-gating latch;
the logic function of a delay gate;
the logic function of a full adder;
the logic function of a half adder;
the logic function NOT(OR(AND(a,b),c)), with one of its inputs inverted;
the logic function of a 2-input NAND, with one of its inputs inverted;
the logic function of a 3-input NAND, with one of its inputs inverted;
the logic function of a 2-input NOR, with one of its inputs inverted;
the logic function of a 3-input NOR, with one of its inputs inverted;
the logic function of an inverter;
the logic function NOT(AND(OR(a,b),c)), with one of its inputs inverted;
the logic function of a latch;
the logic function of a 2-input MUX;
the logic function of a 2-input MUX, with one of its inputs inverted;
the logic function of a 2-input NAND;
the logic function of a 3-input NAND;
the logic function of a 4-input NAND;
the logic function of a 2-input NOR;

16

the logic function of a 3-input NOR;

the logic function of a 4-input NOR;

the logic function AND(OR(a,b),c);

the logic function AND(OR(a,b,c),d);

the logic function AND(OR(a,b),c,d);

the logic function NOT(AND(OR(a,b),c));

the logic function NOT(AND(OR(a,b),OR(c,d)));

the logic function NOT(AND(OR(a,b,c),d));

the logic function NOT(AND(OR(a,b),c,d));

the logic function NOT(AND(OR(a,b),OR(c,d),OR(e,f)));

the logic function of a 2-input OR;

the logic function of a 3-input OR;

the logic function of a 4-input OR;

the logic function of a scan-enabled D flip-flop;

the logic function of a scan-enabled D flip-flop, with set and reset;

the logic function 1;

the logic function 0;

the logic function of a 2-input XNOR; and,

the logic function of a 2-input XOR.

8. The collection of standard logic cells, as defined in claim 7, wherein the collection includes cells implementing at least eight functions selected from the following list:

the logic function of a 2-input AND;

the logic function of a 3-input AND;

the logic function of a 4-input AND;

the logic function OR(AND(a,b),c);

the logic function OR(AND(a,b,c),d);

the logic function OR(AND(a,b),c,d);

the logic function NOT(OR(AND(a,b),c));

the logic function NOT(OR(AND(a,b),AND(c,d)));

the logic function NOT(OR(AND(a,b,c),d));

the logic function NOT(OR(AND(a,b),c,d));

the logic function NOT(OR(AND(a,b),AND(c,d),AND(e,f)));

the logic function of a buffer;

the logic function of a clock-gating latch;

the logic function of a delay gate;

the logic function of a full adder;

the logic function of a half adder;

the logic function NOT(OR(AND(a,b),c)), with one of its inputs inverted;

the logic function of a 2-input NAND, with one of its inputs inverted;

the logic function of a 3-input NAND, with one of its inputs inverted;

the logic function of a 2-input NOR, with one of its inputs inverted;

the logic function of a 3-input NOR, with one of its inputs inverted;

the logic function of an inverter;

the logic function NOT(AND(OR(a,b),c)), with one of its inputs inverted;

the logic function of a latch;

the logic function of a 2-input MUX;

the logic function of a 2-input MUX, with one of its inputs inverted;

the logic function of a 2-input NAND;

the logic function of a 3-input NAND;

the logic function of a 4-input NAND;

the logic function of a 2-input NOR;

the logic function of a 3-input NOR;

the logic function of a 4-input NOR;

the logic function AND(OR(a,b),c);

the logic function AND(OR(a,b,c),d);

the logic function AND(OR(a,b),c,d);

17

the logic function NOT(AND(OR(a,b),c));
 the logic function NOT(AND(OR(a,b),OR(c,d)));
 the logic function NOT(AND(OR(a,b,c),d));
 the logic function NOT(AND(OR(a,b),c,d));
 the logic function NOT(AND(OR(a,b),OR(c,d),OR(e, 5
 f)));
 the logic function of a 2-input OR;
 the logic function of a 3-input OR;
 the logic function of a 4-input OR;
 the logic function of a scan-enabled D flip-flop;
 the logic function of a scan-enabled D flip-flop, with set
 and reset;
 the logic function 1;
 the logic function 0;
 the logic function of a 2-input XNOR; and,
 the logic function of a 2-input XOR.
 9. The collection of standard logic cells, as defined in
 claim 8, wherein the collection includes cells implementing
 at least twelve functions selected from the following list: 20
 the logic function of a 2-input AND;
 the logic function of a 3-input AND;
 the logic function of a 4-input AND;
 the logic function OR(AND(a,b),c);
 the logic function OR(AND(a,b,c),d);
 the logic function OR(AND(a,b),c,d);
 the logic function NOT(OR(AND(a,b),c));
 the logic function NOT(OR(AND(a,b),AND(c,d)));
 the logic function NOT(OR(AND(a,b,c),d));
 the logic function NOT(OR(AND(a,b),c,d));
 the logic function NOT(OR(AND(a,b),AND(c,d),AND
 (e,f)));
 the logic function of a buffer;
 the logic function of a clock-gating latch;
 the logic function of a delay gate;
 the logic function of a full adder;
 the logic function of a half adder;
 the logic function NOT(OR(AND(a,b),c)), with one of its
 inputs inverted;
 the logic function of a 2-input NAND, with one of its 40
 inputs inverted;
 the logic function of a 3-input NAND, with one of its
 inputs inverted;
 the logic function of a 2-input NOR, with one of its inputs
 inverted;
 the logic function of a 3-input NOR, with one of its inputs
 inverted;
 the logic function of an inverter;
 the logic function NOT(AND(OR(a,b),c)), with one of its
 inputs inverted;
 the logic function of a latch;
 the logic function of a 2-input MUX;
 the logic function of a 2-input MUX, with one of its inputs
 inverted;
 the logic function of a 2-input NAND;
 the logic function of a 3-input NAND;
 the logic function of a 4-input NAND;
 the logic function of a 2-input NOR;
 the logic function of a 3-input NOR;
 the logic function of a 4-input NOR;
 the logic function AND(OR(a,b),c);
 the logic function AND(OR(a,b,c),d);
 the logic function AND(OR(a,b),c,d);
 the logic function NOT(AND(OR(a,b),c));
 the logic function NOT(AND(OR(a,b),OR(c,d)));
 the logic function NOT(AND(OR(a,b,c),d));
 the logic function NOT(AND(OR(a,b),c,d));
 the logic function NOT(AND(OR(a,b),OR(c,d),OR(e,
 f)));

18

the logic function NOT(AND(OR(a,b),OR(c,d),OR(e,
 f)));
 the logic function of a 2-input OR;
 the logic function of a 3-input OR;
 the logic function of a 4-input OR;
 the logic function of a scan-enabled D flip-flop;
 the logic function of a scan-enabled D flip-flop, with set
 and reset;
 the logic function 1;
 the logic function 0;
 the logic function of a 2-input XNOR; and,
 the logic function of a 2-input XOR.
 10. The collection of standard logic cells, as defined in
 claim 9, wherein the collection includes cells implementing
 at least sixteen functions selected from the following list: 15
 the logic function of a 2-input AND;
 the logic function of a 3-input AND;
 the logic function of a 4-input AND;
 the logic function OR(AND(a,b),c);
 the logic function OR(AND(a,b,c),d);
 the logic function OR(AND(a,b),c,d);
 the logic function NOT(OR(AND(a,b),c));
 the logic function NOT(OR(AND(a,b),AND(c,d)));
 the logic function NOT(OR(AND(a,b,c),d));
 the logic function NOT(OR(AND(a,b),c,d)); 25
 the logic function NOT(OR(AND(a,b),AND(c,d),AND
 (e,f)));
 the logic function of a buffer;
 the logic function of a clock-gating latch;
 the logic function of a delay gate;
 the logic function of a full adder;
 the logic function of a half adder;
 the logic function NOT(OR(AND(a,b),c)), with one of its
 inputs inverted;
 the logic function of a 2-input NAND, with one of its 35
 inputs inverted;
 the logic function of a 3-input NAND, with one of its
 inputs inverted;
 the logic function of a 2-input NOR, with one of its inputs
 inverted;
 the logic function of a 3-input NOR, with one of its inputs
 inverted;
 the logic function of an inverter;
 the logic function NOT(AND(OR(a,b),c)), with one of its
 inputs inverted;
 the logic function of a latch;
 the logic function of a 2-input MUX;
 the logic function of a 2-input MUX, with one of its inputs
 inverted;
 the logic function of a 2-input NAND;
 the logic function of a 3-input NAND;
 the logic function of a 4-input NAND;
 the logic function of a 2-input NOR;
 the logic function of a 3-input NOR;
 the logic function of a 4-input NOR;
 the logic function AND(OR(a,b),c);
 the logic function AND(OR(a,b,c),d);
 the logic function AND(OR(a,b),c,d);
 the logic function NOT(AND(OR(a,b),c));
 the logic function NOT(AND(OR(a,b),OR(c,d)));
 the logic function NOT(AND(OR(a,b,c),d));
 the logic function NOT(AND(OR(a,b),c,d));
 the logic function NOT(AND(OR(a,b),OR(c,d),OR(e,
 f)));
 the logic function of a 2-input OR;
 the logic function of a 3-input OR;
 the logic function of a 4-input OR;

19

the logic function of a scan-enabled D flip-flop;
 the logic function of a scan-enabled D flip-flop, with set
 and reset;
 the logic function 1;
 the logic function 0;
 the logic function of a 2-input XNOR; and,
 the logic function of a 2-input XOR.

11. A collection of at least five standard logic cells, each
 implementing a different logic function, wherein each stan-
 dard cell comprises at least:

at least two elongated supply rails, extending horizontally
 across the standard cell;

at least three elongated gate stripes, each extending ver-
 tically between at least two of said supply rails, adja-
 cent gate stripes spaced at a minimum contacted poly
 pitch (CPP);

positioned vertically between said supply rails, a plurality
 of M0 tracks, including one or more first-exposure M0
 tracks, each of said first-exposure M0 tracks having a
 minimum permitted width for M0 patterning and
 extending horizontally across the cell, and one or more
 second-exposure M0 tracks, each of said second-expo-
 sure M0 tracks having the minimum permitted width
 and extending horizontally across the cell;

a plurality of vias, patterned in a V0 (via to interconnect)
 layer, each of said plurality of vias instantiated on an
 M0 track; and,

means, including additional patterned features in NW
 (N-well), TS (trench silicide), RX (active), CA (contact
 to active), GO (gate open), and M1 (first-level inter-
 connect) layers, configured to realize a logical function
 or behavior of the standard cell;

wherein within the cell:

among said plurality of vias, each is spaced from its
 nearest neighbor by more than the edge-to-edge
 distance between adjacent M0 tracks.

12. The collection of standard logic cells, as defined in
 claim 11, wherein within each cell:

each of said plurality of vias is spaced at least 0.8×CPP
 from the nearest cut in the M0 track in which said via
 is instantiated, where said spacing is measured as the
 horizontal distance between the center of the via and
 the center of the cut.

13. The collection of standard logic cells, as defined in
 claim 12, wherein within each cell:

each of said plurality of vias is spaced at least 1.0×CPP
 from the nearest cut in the M0 track in which said via
 is instantiated, where said spacing is measured as the
 horizontal distance between the center of the via and
 the center of the cut.

14. The collection of standard logic cells, as defined in
 claim 12, wherein said cells are instantiated on a single
 silicon chip.

15. The collection of standard logic cells, as defined in
 claim 12, wherein said cells are instantiated as instructions
 for patterning features on a silicon wafer.

16. The collection of standard logic cells, as defined in
 claim 15, wherein said instructions are contained in a
 non-transient, computer-readable medium in GDSII format.

17. The collection of standard logic cells, as defined in
 claim 12, wherein the collection includes cells implementing
 at least six functions selected from the following list:

the logic function of a 2-input AND;
 the logic function of a 3-input AND;
 the logic function of a 4-input AND;
 the logic function OR(AND(a,b),c);
 the logic function OR(AND(a,b,c),d);

20

the logic function OR(AND(a,b),c,d);
 the logic function NOT(OR(AND(a,b),c));
 the logic function NOT(OR(AND(a,b),AND(c,d)));
 the logic function NOT(OR(AND(a,b,c),d));
 the logic function NOT(OR(AND(a,b),c,d));
 the logic function NOT(OR(AND(a,b),AND(c,d),AND
 (e,f)));

the logic function of a buffer;

the logic function of a clock-gating latch;

the logic function of a delay gate;

the logic function of a full adder;

the logic function of a half adder;

the logic function NOT(OR(AND(a,b),c)), with one of its
 inputs inverted;

the logic function of a 2-input NAND, with one of its
 inputs inverted;

the logic function of a 3-input NAND, with one of its
 inputs inverted;

the logic function of a 2-input NOR, with one of its inputs
 inverted;

the logic function of a 3-input NOR, with one of its inputs
 inverted;

the logic function of an inverter;

the logic function NOT(AND(OR(a,b),c)), with one of its
 inputs inverted;

the logic function of a latch;

the logic function of a 2-input MUX;

the logic function of a 2-input MUX, with one of its inputs
 inverted;

the logic function of a 2-input NAND;

the logic function of a 3-input NAND;

the logic function of a 4-input NAND;

the logic function of a 2-input NOR;

the logic function of a 3-input NOR;

the logic function of a 4-input NOR;

the logic function AND(OR(a,b),c);

the logic function AND(OR(a,b,c),d);

the logic function AND(OR(a,b,c),d);

the logic function NOT(AND(OR(a,b),c));

the logic function NOT(AND(OR(a,b),OR(c,d)));

the logic function NOT(AND(OR(a,b,c),d));

the logic function NOT(AND(OR(a,b),c,d));

the logic function NOT(AND(OR(a,b),OR(c,d),OR(e,
 f)));

the logic function of a 2-input OR;

the logic function of a 3-input OR;

the logic function of a 4-input OR;

the logic function of a scan-enabled D flip-flop;

the logic function of a scan-enabled D flip-flop, with set
 and reset;

the logic function 1;

the logic function 0;

the logic function of a 2-input XNOR; and,

the logic function of a 2-input XOR.

18. The collection of standard logic cells, as defined in
 claim 17, wherein the collection includes cells implementing
 at least ten functions selected from the following list:

the logic function of a 2-input AND;

the logic function of a 3-input AND;

the logic function of a 4-input AND;

the logic function OR(AND(a,b),c);

the logic function OR(AND(a,b,c),d);

the logic function OR(AND(a,b),c,d);

the logic function NOT(OR(AND(a,b),c));

the logic function NOT(OR(AND(a,b),AND(c,d)));

the logic function NOT(OR(AND(a,b,c),d));

the logic function NOT(OR(AND(a,b),c,d));

21

the logic function NOT(OR(AND(a,b),AND(c,d),AND(e,f)));
the logic function of a buffer;
the logic function of a clock-gating latch;
the logic function of a delay gate;
the logic function of a full adder;
the logic function of a half adder;
the logic function NOT(OR(AND(a,b),c)), with one of its inputs inverted;
the logic function of a 2-input NAND, with one of its inputs inverted;
the logic function of a 3-input NAND, with one of its inputs inverted;
the logic function of a 2-input NOR, with one of its inputs inverted;
the logic function of a 3-input NOR, with one of its inputs inverted;
the logic function of an inverter;
the logic function NOT(AND(OR(a,b),c)), with one of its inputs inverted;
the logic function of a latch;
the logic function of a 2-input MUX;
the logic function of a 2-input MUX, with one of its inputs inverted;
the logic function of a 2-input NAND;
the logic function of a 3-input NAND;
the logic function of a 4-input NAND;
the logic function of a 2-input NOR;
the logic function of a 3-input NOR;
the logic function of a 4-input NOR;
the logic function AND(OR(a,b),c);
the logic function AND(OR(a,b,c),d);
the logic function AND(OR(a,b),c,d);
the logic function NOT(AND(OR(a,b),c));
the logic function NOT(AND(OR(a,b),OR(c,d)));
the logic function NOT(AND(OR(a,b,c),d));
the logic function NOT(AND(OR(a,b),c,d));
the logic function NOT(AND(OR(a,b),OR(c,d),OR(e,f)));
the logic function of a 2-input OR;
the logic function of a 3-input OR;
the logic function of a 4-input OR;
the logic function of a scan-enabled D flip-flop;
the logic function of a scan-enabled D flip-flop, with set and reset;
the logic function 1;
the logic function 0;
the logic function of a 2-input XNOR; and,
the logic function of a 2-input XOR.

19. The collection of standard logic cells, as defined in claim 18, wherein the collection includes cells implementing at least fourteen functions selected from the following list:

the logic function of a 2-input AND;
the logic function of a 3-input AND;
the logic function of a 4-input AND;
the logic function OR(AND(a,b),c);
the logic function OR(AND(a,b,c),d);
the logic function OR(AND(a,b),c,d);
the logic function NOT(OR(AND(a,b),c));
the logic function NOT(OR(AND(a,b),AND(c,d)));
the logic function NOT(OR(AND(a,b,c),d));
the logic function NOT(OR(AND(a,b),c,d));
the logic function NOT(OR(AND(a,b),AND(c,d),AND(e,f)));
the logic function of a buffer;
the logic function of a clock-gating latch;
the logic function of a delay gate;

22

the logic function of a full adder;
the logic function of a half adder;
the logic function NOT(OR(AND(a,b),c)), with one of its inputs inverted;
the logic function of a 2-input NAND, with one of its inputs inverted;
the logic function of a 3-input NAND, with one of its inputs inverted;
the logic function of a 2-input NOR, with one of its inputs inverted;
the logic function of a 3-input NOR, with one of its inputs inverted;
the logic function of an inverter;
the logic function NOT(AND(OR(a,b),c)), with one of its inputs inverted;
the logic function of a latch;
the logic function of a 2-input MUX;
the logic function of a 2-input MUX, with one of its inputs inverted;
the logic function of a 2-input NAND;
the logic function of a 3-input NAND;
the logic function of a 4-input NAND;
the logic function of a 2-input NOR;
the logic function of a 3-input NOR;
the logic function of a 4-input NOR;
the logic function AND(OR(a,b),c);
the logic function AND(OR(a,b,c),d);
the logic function AND(OR(a,b),c,d);
the logic function NOT(AND(OR(a,b),c));
the logic function NOT(AND(OR(a,b),OR(c,d)));
the logic function NOT(AND(OR(a,b,c),d));
the logic function NOT(AND(OR(a,b),c,d));
the logic function NOT(AND(OR(a,b),OR(c,d),OR(e,f)));
the logic function of a 2-input OR;
the logic function of a 3-input OR;
the logic function of a 4-input OR;
the logic function of a scan-enabled D flip-flop;
the logic function of a scan-enabled D flip-flop, with set and reset;
the logic function 1;
the logic function 0;
the logic function of a 2-input XNOR; and,
the logic function of a 2-input XOR.

20. The collection of standard logic cells, as defined in claim 19, wherein the collection includes cells implementing at least twenty functions selected from the following list:

the logic function of a 2-input AND;
the logic function of a 3-input AND;
the logic function of a 4-input AND;
the logic function OR(AND(a,b),c);
the logic function OR(AND(a,b,c),d);
the logic function OR(AND(a,b),c,d);
the logic function NOT(OR(AND(a,b),c));
the logic function NOT(OR(AND(a,b),AND(c,d)));
the logic function NOT(OR(AND(a,b,c),d));
the logic function NOT(OR(AND(a,b),c,d));
the logic function NOT(OR(AND(a,b),AND(c,d),AND(e,f)));
the logic function of a buffer;
the logic function of a clock-gating latch;
the logic function of a delay gate;
the logic function of a full adder;
the logic function of a half adder;
the logic function NOT(OR(AND(a,b),c)), with one of its inputs inverted;

23

the logic function of a 2-input NAND, with one of its inputs inverted;
 the logic function of a 3-input NAND, with one of its inputs inverted;
 the logic function of a 2-input NOR, with one of its inputs inverted;
 the logic function of a 3-input NOR, with one of its inputs inverted;
 the logic function of an inverter;
 the logic function NOT(AND(OR(a,b),c)), with one of its inputs inverted;
 the logic function of a latch;
 the logic function of a 2-input MUX;
 the logic function of a 2-input MUX, with one of its inputs inverted;
 the logic function of a 2-input NAND;
 the logic function of a 3-input NAND;
 the logic function of a 4-input NAND;
 the logic function of a 2-input NOR;
 the logic function of a 3-input NOR;
 the logic function of a 4-input NOR;
 the logic function AND(OR(a,b),c);
 the logic function AND(OR(a,b,c),d);
 the logic function AND(OR(a,b),c,d);
 the logic function NOT(AND(OR(a,b),c));
 the logic function NOT(AND(OR(a,b),OR(c,d)));
 the logic function NOT(AND(OR(a,b,c),d));
 the logic function NOT(AND(OR(a,b),c,d));
 the logic function NOT(AND(OR(a,b),OR(c,d),OR(e,f)));
 the logic function of a 2-input OR;
 the logic function of a 3-input OR;
 the logic function of a 4-input OR;
 the logic function of a scan-enabled D flip-flop;
 the logic function of a scan-enabled D flip-flop, with set and reset;
 the logic function 1;
 the logic function 0;
 the logic function of a 2-input XNOR; and,
 the logic function of a 2-input XOR.

21. The collection of standard logic cells, as defined in claim 12, wherein said collection includes at least three logic cells that are implemented in at least two different drive strengths.

22. The collection of standard logic cells, as defined in claim 12, wherein said collection includes at least two logic cells that are implemented in at least three different drive strengths.

24

23. The collection of standard logic cells, as defined in claim 11, wherein within each cell:

said first-exposure M0 tracks patterned, in part, by feature(s) of a first-exposure M0 mask (M0_color1) and, in part, by feature(s) of a first-exposure M0 cut mask (M0CUT1);

said second-exposure M0 tracks patterned, in part, by feature(s) of a second-exposure M0 mask (M0_color2) and, in part, by feature(s) of a second-exposure M0 cut mask (M0CUT2);

all M0CUT1 features are rectangular in shape, with a left edge, right edge, top edge, and bottom edge, and as between any two first and second M0CUT1 features within the cell, there is at least 2×CPP of spacing between all points at which the left edge of the first M0CUT1 feature intersects an M0color1 feature and all points at which the left edge of the second M0CUT1 feature intersects an M0color1 feature, and there is at least 2×CPP of spacing between all points at which the right edge of the first M0CUT1 feature intersects an M0color1 feature and all points at which the right edge of the second M0CUT1 feature intersects an M0color1 feature; and,

all M0CUT2 features are rectangular in shape, with a left edge, right edge, top edge, and bottom edge, and as between any two first and second M0CUT2 features within the cell, there is at least 2×CPP of spacing between all points at which the left edge of the first M0CUT2 feature intersects an M0color2 feature and all points at which the left edge of the second M0CUT2 feature intersects an M0color2 feature, and there is at least 2×CPP of spacing between all points at which the right edge of the first M0CUT2 feature intersects an M0color2 feature and all points at which the right edge of the second M0CUT2 feature intersects an M0color2 feature.

24. The collection of standard logic cells, as defined in claim 23, wherein said collection includes at least three logic cells that are implemented in at least two different drive strengths.

25. The collection of standard logic cells, as defined in claim 23, wherein said collection includes at least two logic cells that are implemented in at least three different drive strengths.

* * * * *